

# **SiMetrix**

## **SiMetrix Simulator Reference Manual**

**Version 8**

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# SIMetrix Simulator Reference Manual

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# Chapter 1

## Introduction

### 1.1 Overview

This manual provides full reference documentation for the SIMetrix simulator. Essentially the simulator receives a netlist as its input and creates a binary data file and list file as its output. The netlist defines the circuit topology and also specifies the analyses to be performed by the simulator. The netlist may directly include any device models required or these may be automatically imported from a device model library.

The simulator may be operated in GUI mode or non-GUI mode. GUI mode is the normal method of operation and requires the SIMetrix front end. In non-GUI mode the simulator runs stand alone in a non-interactive fashion and may be set to run at low priority in the background.

### 1.2 The SIMetrix Simulator - What is it?

The SIMetrix simulator core comprises a direct matrix analog simulator closely coupled with an event driven gate-level digital simulator. This combination is often described as *mixed-mode* or *mixed-signal* and has the ability to efficiently simulate both analog and digital circuits together.

The core algorithms employed by the SIMetrix analog simulator are based on the SPICE program developed by the CAD/IC group at the department of Electrical Engineering and Computer Sciences, University of California at Berkeley. The digital event driven simulator is derived from XSPICE developed by the Computer Science and Information Technology Laboratory, Georgia Tech. Research Institute, Georgia Institute of Technology.

### 1.3 What is in This Manual

This reference manual contains detailed descriptions of all simulator analysis modes and supported devices.

## Chapter 2

# Running the Simulator

### 2.1 Using the Simulator with the Schematic Editor

Full documentation on using the SIMetrix schematic editor for simulation is described in the SIMetrix User's manual. However, just a few features of the schematic editor are of particular importance for running the simulator and for convenience their description is repeated here.

#### 2.1.1 Adding Extra Netlist Lines

The analysis mode selected using the schematic editor's **Simulator | Choose Analysis...** menu is stored in text form in the schematic's simulator command window. If you wish, it is possible to edit this directly. Sometimes this is quicker and easier than using the GUI especially for users who are familiar with the command syntax.

Note that the text entered in the simulator command window and the Choose Analysis dialog settings remain synchronised so you can freely switch between the two methods.

To open the simulator command window, select the schematic then press the F11 key. It has a toggle action, pressing it again will hide it. If you have already selected an analysis mode using the Choose Analysis dialog, you will see the simulator statements already present.

The window has a popup menu selected with the right key. The top item **Edit file at cursor** will open a text editor with the file name pointed to by the cursor or selected text item if there is one.

The simulator command window can be resized using the splitter bar between it and the schematic drawing area.

You can add anything you like to this window not just simulator commands. The contents are simply appended to the netlist before being presented to the simulator. So, you can place .PARAM statements, device models, inductor coupling specifications, .OPTION statements or simply comments. The Choose Analysis dialog will parse and possibly modify analysis statements and some .OPTIONS settings but will leave everything else intact.

#### 2.1.2 Displaying Net and Pin Names

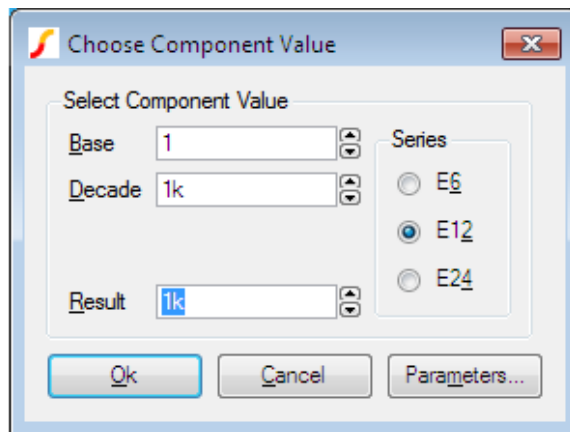
It is sometimes necessary to know the name used for a particular net on the schematic to be referenced in a simulator statement (such as .NOISE) or for an arbitrary source input. There are two approaches:



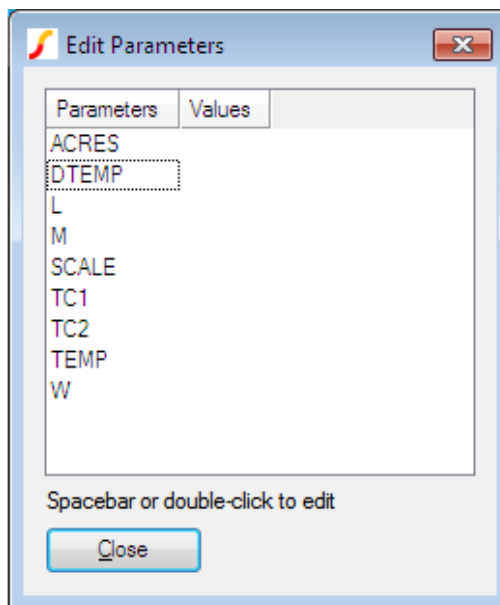
- Find out the default name generated by the schematic editor’s netlist generator. To do this, move the mouse cursor over the net of interest then observe the netname in the status bar in the form “NET=???”.
- Force a net name of your choice. For this, use a terminal or small terminal symbol. These can be found under the **Place | Connectors** menu. After placing on the schematic, select it then press F7 to edit its name. This name will be used to name the net to which it is connected.

### 2.1.3 Editing Device Parameters

To use any of the additional parameters in a schematic, use the *Parameters* button in the dialog box opened by F7 or the equivalent menu. For example you see this box when editing a resistor:



Pressing the Parameters button will open another dialog from which you can edit parameter values:



You can also bring up this box directly using the right click menu **Edit Additional Parameters...**

### 2.1.4 Editing Literal Values - Using shift-F7

The above method is not infallible as it requires the schematic editor to know about the device being edited. In some circumstances, this will require special properties to be present on the symbol and these may have not been defined (for example something to tell the schematic what level a MOSFET is).

Another situation where the usual device editing methods may be unsuitable is when you need to define a parameter as an expression.

In these situations you can use shift-F7. This will edit the device's literal value including any model names exactly as it will be placed in the netlist. shift-F7 bypasses all smart algorithms and presents you with the raw values and you must also supply raw values. For example, here is what you might enter for a MOSFET referencing a model called N1

```
N1 L={LL-2*EDGE} W={WW-2*EDGE}
```

Note the model name must be included.

## 2.2 Running in non-GUI Mode

### 2.2.1 Overview

The simulator can be run in a non-interactive non-GUI mode independently of the front end. This is useful for running simulation 'batches' controlled by a proprietary script or language or DOS batch files.

Under Windows, the simulator will run as a 'console mode' application and no GUI elements will be created.

When run in this mode, the simulator will read in the specified netlist, run the simulation then close and return control to the calling program. It will generate a binary data file and a list file.

### 2.2.2 Important Licensing Information

Non-GUI mode is only possible if you are using network licensing. This feature is not available if you are using a portable (i.e. dongled) license. Please contact support if you have a non-network license and wish to use non-GUI simulation mode.

This mode of operation is 'counted' for licensing purposes. This means you can only run one non-GUI simulation process for each license issued even if all are run by a single user on a single machine. By contrast, regular simulation initiated manually through the GUI are not counted and any number of runs may be initiated on the same machine by the same user for this purpose.

These restrictions have been made to limit exploitation of multiple core machines for simulations run from non-SIMetrix environments.

### 2.2.3 Syntax

The command syntax is as follows:

```
SIM [/config "config_location"] [/gui mode] [/check] [/an "analysis_line"]
    [/list list_filename] [/options "options"] [/nolist] [/lowPriority]
    [/nodata] [/k] [/extraline extra_line] netlist_file [data_file]
```

*config\_location* Location of file holding configuration settings. Configuration settings include global options and global model library locations. The value must be of the form:

PATH;pathname

*pathname* may use system symbolic path values such as %EXEPATH%. See *User's Manual/Sundry Topics/Symbolic Path Names* for details.

If not specified, the configuration settings will be taken from the Base.sxprj file. See the *User's Manual/Sundry Topics/Configuration Settings/Default Configuration Location* for details on where this file is located.

Alternatively, you can specify the location using a setting in the startup.ini file. Add a value called SimConfig to the [Startup] section and give it a value of:

PATH;pathname

The startup.ini file must be located in the same directory as the SIMetrix executable binary. (SIMetrix.exe on Windows). See *User's Manual/Sundry Topics/SIMetrix Command Line Parameters/Using startup.ini* for more information on the startup.ini file.

Note that the /config switch if present must always appear before the first argument to the command.

*mode* Mode of operation. Default = -1. Valid values are -1, 0, 1 and 2 but only -1 and 1 are meaningful for stand-alone operation. 0 and 2 are used when starting the simulator process from the front end. -1 (same as omitting /gui) runs the simulator in console mode with all messages output to the console or terminal window. 1 enables GUI mode where the simulator runs in a stand-alone mode but displays a graphical status box showing messages and simulator progress. This mode is used by the 'asynchronous' menus in the front end.

*analysis\_line* If /an switch is specified, *analysis\_line* specifies the analysis to be performed and overrides all analysis lines specified in the netlist.

*list\_filename* Name of list file. Default is main netlist file name with extension .OUT. Enclose path name in quotes if it contains spaces.

*options* List of options valid for .OPTIONS statement.

*netlist\_file* File name of netlist.

*data\_file* File to receive binary data output.

/check If specified, the netlist will be read in and parsed but no simulation will be run. Used to check syntax

/nolist If specified, no list file will be created

/lowPriority If specified, the simulator will be run as a low priority process, i.e. in the background. Recommended for long runs.

/nodata Only vectors explicitly specified using .KEEP or .PRINT will be output to the binary file. Equivalent to '.KEEP /nov /noi /nodig' in the netlist.

<code>/k</code>	If specified, the program will not finally terminate until the user has pressed enter and a message to that effect will be displayed. Under Windows, if the program is not called from the DOS prompt but from another program, a console will be created for receiving messages. The console will close when the program exits sometimes before the user has had a chance to read the messages. This switch delays the exit of the program and hence the destruction of the console.
<code>extra_line</code>	An additional line that will be appended to the netlist. This permits simple customisation of the netlist. This should be enclosed in double quotation marks if the line has spaces.

## 2.2.4 Aborting

Press `cntrl-C` - you will be asked to confirm. The simulation will be paused while waiting for your response and will continue if you enter 'No'. This is an effective means of pausing the run if you need CPU cycles for another task, or you wish to copy the data file. See [“Reading Data” on page 6](#).

## 2.2.5 Reading Data

A data file will be created for the simulation results as normal (see [“The Binary Data File” on page 12](#)). You can read this file after the simulation is complete use the SIMetrix menu **File | Data | Load...** . You may also read this data file while the simulation is running but you must pause the simulation first using `cntrl-C`.

Important: if you read the data file before the simulation is complete or aborted, the file entries that provide the size of each vector will not have been filled. This means that the waveform viewer will have to scan the whole file in order to establish the size of the vectors. This could take a considerable time if the data file is large.

## 2.3 Configuration Settings

Configuration settings consist of a number of persistent global options as well as the locations for installed model libraries.

When the simulator is run in GUI mode, its configuration settings are controlled by the front end and stored wherever the front end's settings are stored. See the *User's Manual* for more details.

The settings when run in non-GUI mode are stored in a configuration file which in fact defaults to the same location as the default location for the front end's settings. You can change this location using the `/config` switch detailed in [“Running in non-GUI Mode” on page 4](#).

The format of the configuration file is:

```
[Options]
option_settings

[Models]
model_libraries
```

Where:

<code>option_settings</code>	These are of the form <i>name=value</i> and specify a number of global settings. Boolean values are of the form <i>name=</i> without a value. If the entry is present it is TRUE if absent it is FALSE. Available global settings are detailed below.
------------------------------	---

`model_libraries` A list of entries specifying search locations for model libraries. These are of the form `name=value` where `name` is a string and `value` is a search location. The string used for `name` is arbitrary but must be unique. Entries are sorted alphabetically according to the name and used to determine the search order. `value` is a path name and may contain wildcards (i.e. ‘\*’ and ‘?’).

### 2.3.1 Global Settings

Name	Type	Default	Description
<code>NoStopOnUnknownParam</code>	String	WARN	Specifies action to be taken in the event of an unknown parameter being encountered in a <code>.MODEL</code> statement. Choices are:  TRUE: No action taken, simulation continues normally FALSE: An error will be raised and the simulation will abort WARN: A warning will be displayed but the simulation will continue  This will be overridden by a <code>.OPTIONS</code> setting of the same name. See the “ <a href="#">List of Simulator Options</a> ” on page 216.
<code>MaxVectorBufferSize</code>	Numeric	32760	See “ <a href="#">Data Buffering</a> ” on page 7.
<code>TotalVectorBufferSize</code>	Numeric	Available RAM/10	See “ <a href="#">Data Buffering</a> ” on page 7.
<code>TempDataDir</code>	String	%STARTDIR%	Location of temporary binary data file if <code>data_file</code> is not specified on command line
<code>LibraryDiagnostics</code>	String	Full	Controls output of messages relating to model library search. Specify None to disable

### 2.3.2 Data Buffering

The simulator buffers data before writing it to disk. By doing so the binary data file can be organised more efficiently allowing data to be recovered from it quickly.

By default, the simulator won’t allocate more than 10% of your system RAM to vector buffers. Clearly if you are running a large circuit and saving many vectors, the buffer sizes could reduce to levels that would make data retrieval very slow. In this case you may wish to consider increasing the memory that is allowed for these buffers. Two configuration settings control the vector buffering. These are:

- `MaxVectorBufferSize`. This sets the maximum size that will be used for any individual vector. The default is 32768 bytes. If you have a high performance SCSI disk system, you may benefit from increasing this value
- `TotalVectorBufferSize`. This sets the maximum amount of memory in bytes used for all buffers. It defaults to a value equal to 10% of your system RAM. This is usually sufficient for most applications but if you are simulating a very large circuit and have sufficient RAM you may like to increase this value

The disk will not be written to until the buffers are full. With an all analog circuit all the buffers reach their full state at the same time so they all get written to disk at the same time. If you have 2G of RAM and are simulating a large circuit, approximately 200M of data will be written to the disk at regular intervals. This will result in a pause in the simulation coupled with a great deal of disk activity.

Note that both `MaxVectorBufferSize` and `TotalVectorBufferSize` may be set from the front end using the `Set` command. See *User's Manual/Sundry Topics/Using the Set and Unset Commands* for details.

## 2.4 Netlist Format

The SIMetrix netlist format follows the general format used for all SPICE and SPICE compatible simulators. However, with so many SPICE derivatives and with two significantly different versions of SPICE itself (SPICE 2 and SPICE 3) it is not possible to define a standard SPICE format. SIMetrix has been developed to be as compatible as possible with model libraries that can be obtained from external sources. For discrete devices, models are usually SPICE 2 compatible but some use extensions originally developed for PSpice®. IC designers usually receive model files from fabrication companies and these are available for a variety of simulators usually including Hspice®. SIMetrix is compatible with all of these but simultaneous compatibility with all formats is not technically possible due to a small number of syntax details - such as the character used for in line comments. To overcome these minor difficulties, a language declaration can be placed at the top of the netlist and any file included using `.INC` or the Hspice® variant of `.LIB`. This is described in the following sections.

### 2.4.1 File Format

A complete netlist consists of:

- A title line
- Optional language declaration
- Device lines
- Statement lines
- Comment lines

The title line must be the first line of the file and may be empty. The remaining lines - with some exceptions - may be placed in any order

All other lines are defined by their first non-whitespace character as follows.

- Statement lines begin with a period: `'`
- Comment lines begin with an asterix: `'*`
- Device lines begin with a letter

A line is usually terminated with a new line character but may be continued using the ‘+’ continuation character. So if the first non-whitespace character is a ‘+’ the line will be considered to be an extension of the previous line. SPICE requires the ‘+’ to be the first character, SIMetrix allows whitespace (space or tab) to precede it.

### 2.4.2 Language Declaration

SIMetrix is able to read PSpice®, Hspice® and native SIMetrix netlists, but in some cases needs to be instructed what format netlist it is reading. Currently there are three areas where simultaneous compatibility has not been possible. These are:

- Inline comment character.
- Unlabelled device parameters
- The meaning of LOG() and PWR() functions

SIMetrix can be instructed to use any of the three languages by using the language declaration. This is one of:

```
*#SIMETRIX *#HSPICE *#PSPICE
```

The language declaration must be placed at the top of the file immediately below the title line. It can also be placed in files referenced using .INC or the HSPICE® version of .LIB in which case it will apply only to that file and any others that it calls. A language declaration placed anywhere else in a file will be ignored.

For details see [“Language Differences” on page 34](#).

The `*#SIMETRIX` language declaration can also be supplied with a parameter to specify the separator letter used for devices. See [“Device Lines” on page 9](#) section for details.

### 2.4.3 Comments

Any line other than a language declaration beginning with a ‘\*’ is defined as a comment and will be ignored. Also anything between a semi-colon ‘;’ (‘\$’ in HSPICE mode) and the end of the line will be treated as comment and will also be ignored. Some SPICE simulators require the ‘\*’ character to be the first character of the line. SIMetrix allows it to be preceded by white space (spaces and tabs).

### 2.4.4 Device Lines

Device lines usually follow the following basic form but each type of device tends to have its own nuances:

```
Name nodelist value [parameters]
```

*value* may be an actual number e.g. in the case of passive components such as resistors, or it may be a model name in the case of semiconductor devices such as bipolar transistors. Models are defined using a .MODEL statement line.

*nodelist* is a list of netnames. The number and order of these is device dependent. The netname itself may consist of any collection of non-control ASCII characters except whitespace and ‘?’. All other ASCII characters are accepted although it is suggested that the following characters are avoided if possible:

```
\ " \% \& + - * / ^ < > [ ] ' @ { }
```

If any of these characters are used in a netname, a special syntax will be needed to plot any signal voltage on that net. This is explained in “[Output Data Names](#)” on page 12. In addition the characters ‘[’, ‘]’, ‘%’, ‘!’ and ‘ ’ have a special meaning when used with XSPICE devices and therefore should be avoided at all times.

The *name* is the circuit reference of the device. The first letter of this name determines the type of device as shown in the table below.

The Pin Names column in the following table is relevant to the vector name used for values of device pin current. See “[Output Data Names](#)” on page 12.

Letter	Number pins	Device	Pin Names
A	Any	XSPICE devices	depends on device
B	2	Arbitrary source	P, N
C	2	Capacitor	P, N
D	2	Diode	P, N
E	4	Voltage controlled voltage source	P, N, CP, CN
F	2	Current controlled current source	P, N
G	4	Voltage controlled current source	P, N, CP, CN
H	2	Current controlled voltage source	P, N
I	2	Fixed current source	P, N
J	3	JFET	D, G, S
K	0	Coupling for inductors	
L	2	Inductor	P, N
M	4	MOSFET	D, G, S, B
N	-	Not used	
O	4	Lossy transmission line	P1, N1, P2, N2
P	-	Not used	
Q	3-5	Bipolar transistor	C, B, E, S, DT
R	2	Resistor	P, N
S	4	Voltage controlled switch	P, N, CP, CN
T	4	Lossless transmission line	P1, N1, P2, N2
U	Any	VSXA devices (Verilog-HDL interface), Verilog-A devices, AC Table device	
V	2	Voltage source	P, N
W	-	Not used	
X	Any	Subcircuit	
Y	-	Not used	
Z	3	GaAs FET	D, G, S
		IGBT	C, G, E

To remove the naming restriction that this system imposes, SIMetrix supports an extension to the above to allow the user to use any name for all devices. If the device letter is followed by a dollar ‘\$’ symbol (by default but can be changed - see below), the remainder of the name following the



'\$' will be used as the device name. E.g.:

```
Q$TR23
```

will define a bipolar transistor with the name TR23. All output generated by the simulator will refer to TR23 not Q\$TR23.

The above mechanism can be disabled and also the character can be changed by adding a parameter to the language declaration (see [“Language Declaration” on page 9](#)). To disable, add this to the top of the netlist:

```
*#SIMETRIX sep=none
```

To change the character use:

```
*#SIMETRIX sep=character
```

*character* must be a single letter, anything else will be ignored. Although any character will be accepted it should clearly not be alpha-numeric.

The above mechanism will also be disabled if HSPICE or PSPICE languages are specified.

### 2.4.5 Simulator Statements

Instructions to the simulator other than device definitions and comments are referred to as *statements* and always begin with a period ':'.

Full documentation for SIMetrix statements see [“Command Reference” on page 187](#).

## 2.5 Simulator Output

### 2.5.1 The List File

SIMetrix produces a list file by default. This receives all text output except for the Monte Carlo log. This includes operating point results, model parameters, noise analysis results, sensitivity analysis results, pole-zero analysis results and tabulated vectors specified by .PRINT.

The list file is generated in the same directory as the netlist. It has the same name as the netlist but with the extension .OUT.

There are a number of options that control the list file output.

Option name	Description
PARAMLOG	Valid values: Full All instance and model parameter values reported Given All user specified model parameters and parameterised instance parameters Brief Parameterised model and instance parameters None None Default = Given
EXPAND	Flag. If specified, the netlist with all sub-circuits expanded will be output to the list file

Option name	Description
EXPANDFILE	String. If specified the expand netlist will be output to the specified file rather than the list file
NOMOD	Same as PARAMLOG=none. Model parameters will not be output
WIDTH	Page width in number of characters. (The list file is formatted assuming that it will be read or printed using a fixed width font such as Courier.) The default is 80 but any value may be used not just 80 and 132 as in SPICE 2.
OPINFO	If set DC operating point info file <i>is</i> created for all analyses (except .SENS). Normally it is created only for .OP analyses

## 2.5.2 The Binary Data File

The simulation data is stored in a binary data file. The format is proprietary to SIMetrix and is not compatible with SPICE ‘raw’ files.

The name and location of the binary file depends on configuration settings and in what mode the simulator is run. Usually, the file is located in the directory specified by the TEMPDATADIR configuration setting (see “[Configuration Settings](#)” on page 6) and is named according to the analysis type and appended with the extension .sxdat. E.g. tran1.sxdat, ac2.sxdat, dc3.sxdat etc. The name and location can be overridden at the program command line if operated in non-GUI mode or at the front end Run command line if run in GUI mode.

Only the SIMetrix front end can read the simulator’s binary data file. When run in GUI mode, the file is automatically loaded and in fact it is not usually necessary to know anything about it except perhaps when it grows very large and fills up your disk. If the simulator is run in non-GUI mode, it becomes necessary to explicitly load the data into the front end when the run is complete. This can be done with the command shell menu **File | Data | Load....** After the data is loaded, the results can be plotted in the usual manner. See *User’s Manual/Graphs, Probes and Data Analysis/Saving Data/Restoring Simulation Data* for further details.

## 2.5.3 Output Data Names

For transient, DC and AC analyses, SIMetrix calculates and stores the circuit’s node voltages and device pin currents and these are all given unique names. If using probing techniques with the front end’s schematic editor you don’t usually need to know anything about the names used. However there are situations where it is necessary or helpful to know how these names are derived. An example is when compiling an expression relating voltages and currents to be used in a .PRINT statement. Another is when plotting results created by simulating a netlist that was not generated using the schematic editor. The names used are documented in the following notes.

### Top Level Node Voltages

The vector names used for node voltages at the top level (i.e. not in a subcircuit) are simply the name of the node used in the netlist.

### Subcircuit Node Voltages

For nodes within a subcircuit, the name is prefixed with the subcircuit reference and a ':'. For example:

```
X1 N1 N2 N3 SubName
X2 N4 N5 N6 SubName

.SUBCKT 1 2 3 SubName
X3 N1 2 N3 SubName2
R1 VIN 0 1k
...
.ENDS

.SUBCKT 1 2 3 SubName2
V1 VCC 0 5
...
.ENDS
```

The internal node VIN in definition SubName referenced by X1 would be called X1.VIN. The same node referenced by X2 would be called X2.VIN. The node VCC defined in subcircuit SubName2 would be named X1.X3.VCC and X2.X3.VCC for X1 and X2 respectively.

### Nodes with Non-standard Names

A non-standard node name is one that begins with a digit or which contains one or more of the characters:

```
\ " \% \& + - * / ^ < > [ ] ' @ { }
```

These are legal but introduce problems when accessing the voltage data that they carry. The above characters can be used in arithmetic expressions so cause a conflict if used as a node name. In order to access the voltage data on a node so named, use the Vec() function:

```
Vec('node_name')
```

Example with .PRINT and node called V+

```
.PRINT TRAN {Vec('V+')}
```

A similar syntax is required when using the front end plotting commands.

### Device Pin Currents

Device pin currents are named in the following form:

```
device_name#pin_name
```

For primitive devices (i.e. not sub-circuits) pin\_name must comply with the table in [“Device Lines” on page 9](#). For example the current into the collector of Q23 would be Q23#c.

The pin names for sub-circuits depend on whether the *pinnames:* specifier (see [“Subcircuit Instance” on page 105](#)) is included in the netlist entry for the device. If it is the pin current name will be the name listed after *pinnames:*. If it isn't then they are numbered in sequence starting from 1. The order is the same as the order they appear in the netlist device line. For example, if the subcircuit line is:

```
X$U10 N1 N2 N3 N4 N5 LM324 pinnames: VINP VINN VP VN VOUT
```

The current into the last pin (connected to N5) would be U10#VOUT

(Note that ‘X\$’ is stripped off as explained above in [“Device Lines” on page 9](#)).

If the netlist line is:

```
X$U10 N1 N2 N3 N4 N5 LM324
```

The same current would be U10#5

### Internal Device Values

Some devices have internal nodes or sources and the voltages or currents associated with these may be output by the simulator. These are named in a similar manner to pin currents i.e.

```
device_name#internal_name
```

The *internal\_name* depends on the device. For example, bipolar transistors create an internal node for each terminal that specifies a corresponding resistance parameter. So if the RE parameter is specified an internal node will be created called emitter.

Note that internal device values are only output if explicitly enabled using the `“KEEP /INTERNAL”` statement. See [“KEEP” on page 203](#).

## 2.6 Data Handling - Controlling Data Saved

As explained in [“The Binary Data File” on page 12](#), all data is saved to a binary disk file. By default, all signals visible in a schematic are saved. That is all signals at the top level of a hierarchy and in all child schematics are saved. Signals inside subcircuits that were not generated by a hierarchical schematic are *not* saved.

SIMetrix has comprehensive features for changing exactly what data is saved. Some simulations can generate huge amounts of data and with multi-core multi-step simulations, the rate at which the data is created can exceed the performance of the disk system. It is therefore desirable in some cases to reduce the amount of data saved.

For simulations run from the user interface, some of the data handling features are available through the GUI. See *User’s Manual/Analysis Modes/Data Handling and Keeps*.

More comprehensive features are available using `.KEEP` and `.OPTIONS`. See [“KEEP” on page 203](#) for full details.

# Chapter 3

## Simulator Devices

### 3.1 Overview

This chapter is an introduction to the [“Analog Device reference” on page 41](#) and the [“Digital/Mixed Signal Device Reference” on page 132](#).

The device reference chapters describe all simulator devices at the netlist level. The netlist consists of a list of component definitions, along with simulator commands, which the simulator can understand. Simple components, such as resistors just need a value to define them. Other more complicated devices such as transistors need a number of parameters to describe their characteristics.

The device references includes details of all device and model parameters. Using the schematic editor and model library you may not often need to read this section. Some of the devices, however, have advanced options not directly supported by the user interface. For example, many devices allow a local temperature to be specified. This requires the component value to be appended with `TEMP=...`. This device parameter and others are documented here.

Note that many parts either supplied with SIMetrix or available from component manufacturers are implemented as subcircuits. These are circuit designs to simulate the behaviour of high level devices such as opamps. SIMetrix (and all other SPICE simulators) do not have an opamp device built in but use these *macro models* instead. Full documentation for these devices is beyond the scope of this manual but can sometimes be obtained from their suppliers.

### 3.2 Using XSPICE Devices

Some devices are implemented as part of the XSPICE ‘code modelling’ framework. This framework introduces some new features at the netlist level not supported by standard SPICE devices. These new features are described in this section.

All but one of these devices that use this framework are digital or mixed signal devices and the reference for these can be found at [“Digital/Mixed Signal Device Reference” on page 132](#).

The exception is the [“S-domain Transfer Function Block” on page 98](#) which is a pure analog part.

#### 3.2.1 Vector Connections

Some models feature an arbitrary number of inputs or/and outputs. For example, an AND gate can have any number of inputs. It would be inflexible to have a separate model for every configuration of AND gate so a method of grouping connections together has been devised. These are known as

*vector connections.* Vector connections are enclosed in square brackets. E.g. the netlist entry for an AND gate is:

```
Axxxx [ in_0 in_1 .. in_n ] out model_name
```

The pins `in_0` `in_1` to `in_n` form a single vector connection. Any number of pins may be placed inside the square brackets, in fact the same model may be used for devices with different numbers of inputs.

Some devices have a minimum and/or maximum number of pins that may be used in a vector connection. This is known as *vector bounds* and if they apply will be listed in the vector bounds column of the Connection Details table provided with every device definition.

### 3.2.2 Connection Types

In the device references that follow, each has a table titled Connection Details. Each table has a “Type” column and some have an “Allowed types” column. The type referred to here is the type of electrical connection e.g. voltage, current, differential or single-ended. Some devices allow some or all of their connections to be specified with a range of types. For example, the [analog-digital converter](#) has a single ended voltage input by default. However, using a simple modification to the netlist entry, an ADC can be specified with a differential voltage input or even a differential current. Changing the type of connection involves no changes to the .MODEL statement, only to the netlist entry.

The following table lists all the available types. The modifier is the text used to alter a connection type at the netlist level. This is explained below

Description	Modifier
Single ended voltage	%v
Single ended current	%i
Differential voltage	%vd
Differential current	%id
Digital	%d
Grounded conductance (voltage input current output)	%g
Grounded resistance (current input, voltage output)	%h
Differential conductance (voltage input current output)	%gd
Differential resistance (voltage input current output)	%hd

With the models supplied with SIMetrix, only the first four in the above table are ever offered as options. The others are used but are always compulsory, and an understanding of their meaning is not necessary to make full use the system.

As well as type, all connections also have a *flow* referring to the direction of the signal flow. This can be *in*, *out* or *inout*. Voltage, current and digital connections may be in or out while the conductance and resistance connections may only be *inout*. Voltage inputs are always open circuit, current inputs are always short circuit, voltage outputs always have zero output impedance and current outputs always have infinite output impedance.

The conductance connections are a combined voltage input and current output connected in parallel. If the output is made to be proportional to the input, the connection would be a conductor with a constant of proportionality equal to its conductance, hence the name.

Similarly, the resistance connections are a combined current input and voltage output connected

in series. If the output is made to be proportional to the input, the connection would be a resistor with a constant of proportionality equal to its resistance.

### Changing Connection Type

If a model allows one or more of its connections to be given a different type, this can be done by preceding the connection entry with the appropriate modifier listed in the table above. For example if you wish to specify a 4 bit ADC with a differential voltage input, the netlist entry would be something like:

```
A1 %vd ANALOG_INP ANALOG_INN CLOCK_IN [ DATA_OUT_0 DATA_OUT_1 DATA_OUT_2
DATA_OUT_3 ] DATA_VALID ADC_4
```

## 3.3 Using Expressions

### 3.3.1 Overview

Expressions consist of arithmetic operators, functions, variables and constants and may be employed in the following locations:

- As device parameters
- As model parameters
- To define a variable (see [“.PARAM” on page 232](#)) which can itself be used in an expression.
- As the governing expression used for [arbitrary sources](#).

They have a wide range of uses. For example:

- To define a number of device or model parameters that depend on some common characteristic. This could be a circuit specification such as the cut-off frequency of a filter or maybe a physical characteristic to define a device model.
- To define tolerances used in Monte Carlo analyses.
- Used with an arbitrary source, to define a non-linear device.

### 3.3.2 Using Expressions for Device Parameters

Device or instance parameters are placed on the device line. For example the length parameter of a MOSFET, L, is a device parameter. A MOSFET line with constant parameters might be:

```
M1 1 2 3 4 MOS1 L=1u W=2u
```

L and W could be replaced by expressions. For example:

```
M1 1 2 3 4 MOS1 L={LL-2*EDGE} W={WW-2*EDGE}
```

Device parameter expressions must usually be enclosed with either single quotation marks ( ' ) double quotation marks ( " ) or braces ( { and } ). The expression need not be so enclosed if it consists of a single variable. For example:

```
.PARAM LL=2u WW=1u
M1 1 2 3 4 MOS1 L=LL W=WW
```

### 3.3.3 Using Expressions for Model Parameters

The rules for using expressions for device parameters also apply to model parameters. E.g.

```
.MODEL N1 NPN IS=is BF={beta*1.3}
```

### 3.3.4 Expression Syntax

Expressions generally comprise the following elements:

- Circuit variables
- Parameters
- Constants.
- Operators
- Functions
- Look up tables

These are described in the following sections.

#### Circuit Variables

Circuit variables may only be used in expressions used to define “arbitrary sources” on page 42 and to define variables that themselves are accessed only in arbitrary source expressions.

Circuit variables allow an expression to reference voltages and currents in any part of the circuit being simulated.

Voltages are of the form:

```
V(node_name1)
```

OR

```
V(node_name1, node_name2)
```

Where *node\_name1* and *node\_name2* are the name of the node carrying the voltage of interest. The second form above returns the difference between the voltages on *node\_name1* and *node\_name2*. If using the schematic editor nodenames are normally allocated by the netlist generator. For information on how to display and edit the schematic’s node names, refer to “[Displaying Net and Pin Names](#)” on page 2.

Currents are of the form:

```
I(source_name)
```

Where *source\_name* is the name of a voltage source carrying the current of interest. The source may be a fixed voltage source, a current controlled voltage source, a voltage controlled voltage source or an arbitrary voltage source. It is legal for an expression used in an arbitrary source to reference itself e.g.:

```
B1 n1 n2 V=100*I(B1)
```

Implements a 100 ohm resistor.



## Parameters

These are defined using the `.PARAM` statement. For example:

```
.PARAM res=100
B1 n1 n2 V=res*I(B1)
```

Also implements a 100 ohm resistor.

Circuit variables may be used `.PARAM` statements, for example:

```
.PARAM VMult = { V(a) * V(b) }
B1 1 2 V = Vmult + V(c)
```

Parameters that use circuit variables may only be used in places where circuit variables themselves are allowed. So, they can be used in arbitrary sources and they may be used to define the resistance of an Hspice style resistor which allows voltage and current dependence. (See “[Resistor - Hspice Compatible](#)” on page 93). They may also of course be used to define further parameters as long as they too comply with the above condition.

## Built-in Parameters

A number of parameter names are assigned by the simulator. These are:

Parameter name	Description
TIME	Resolves to time for transient analysis. Resolves to 0 otherwise including during the pseudo transient operation point algorithm. Note that this may only be used in an arbitrary source expression
TEMP	Resolves to current circuit temperature in Celsius
HERTZ	Resolves to frequency during AC sweep and zero in other analysis modes
PTARAMP	Resolves to value of ramp during pseudo transient operating point algorithm if used in arbitrary source expression. Otherwise this value resolves to 1.

## Constants

Apart from simple numeric values, arbitrary expressions may also contain the following built-in constants:

Constant name	Value	Description
PI	3.14159265358979323846	$\pi$
E	2.71828182845904523536	e
TRUE	1.0	
FALSE	0.0	
ECHARGE	1.6021918e-19	Charge on an electron in coulombs
BOLTZ	1.3806226e-23	Boltzmann’s constant

If the simulator is run from the front end in GUI mode, it is also possible to access variables defined on the Command Shell command line or in a script. The variable must be global and enclosed in braces. E.g.

```
B1 n1 n2 V = V(n3, n3) * { global:amp_gain }
```

amp\_gain could be defined in a script using the LET command. E.g. “Let global:amp\_gain = 100”

## Operators

These are listed below and are listed in order of precedence. Precedence controls the order of evaluation. So  $3*4 + 5*6 = (3*4) + (5*6) = 42$  and  $3+4*5+6 = 3 + (4*5) + 6 = 29$  as ‘\*’ has higher precedence than ‘+’.

Operator	Description
! -	Digital NOT, Logical NOT, Unary minus
^ or **	Raise to power.
*, /	Multiply, divide
+, -	Plus, minus
>=, <=, > <	Comparison operators
==, != or <>	Equal, not equal
&	Digital AND (see below)
	Digital OR (see below)
&&	Logical AND
	Logical OR
test ? true_expr : false_expr	Ternary conditional expression (see below)

## Comparison, Equality and Logical Operators

These are Boolean in nature either accepting or returning Boolean values or both. A Boolean value is either TRUE or FALSE. FALSE is defined as equal to zero and TRUE is defined as not equal to zero. So, the comparison and equality operators return 1.0 if the result of the operation is true otherwise they return 0.0.

The arguments to equality operators should always be expressions that can be guaranteed to have an exact value e.g. a Boolean expression or the return value from functions such as SGN. The == operator, for example, will return TRUE only if both arguments are *exactly* equal. So the following should never be used:

```
v(n1)==5.0
```

v(n1) may not ever be exactly 5.0. It may be 4.999999999 or 5.0000000001 but only by chance will it be 5.0.

These operators are intended to be used with the IF() function described in [“Ternary Conditional Expression” on page 22](#).

## Digital Operators

These are the operators '&', '|' and '~'. These were introduced in old SIMetrix version as a simple means of implementing digital gates in the analog domain. Their function has largely been superseded by gates in the event driven simulator but they are nevertheless still supported.

Although they are used in a digital manner the functions implemented by these operators are continuous in nature. They are defined as follows:

Expression	Condition	Result
out = x & y	x < vtl OR y < vtl	out = vl
	x > vth AND y > vth	out = vh
	x > vth AND vth > y > vtl	out = (y-vtl)*(vh-vl)/(vth-vtl)+vl
	vtl < x < vth AND y > vth	out = (x-vtl)*(vh-vl)/(vth-vtl)+vl
	vtl < x < vth AND vth > y > vtl	out = (y-vtl)*(x-vtl)*(vh-vl)/(vth-vtl) <sup>2</sup> +vl
out = x y	x < vtl AND y < vtl	out = vl
	x > vth OR y > vth	out = vh
	x < vtl AND vth > y > vtl	out = vh-(vth-y)*(vh-vl)/(vth-vtl)
	vtl < x < vth AND y < vtl	out = vh-(vth-x)*(vh-vl)/(vth-vtl)
	vtl < x < vth AND vth > y > vtl	out = vh-(vth-y)*(vth-x)*(vh-vl)/(vth-vtl) <sup>2</sup>
out = ~x	x < vtl	out = vh
	x > vth	out = vl
	vtl < x < vth	out = (vth-x)/(vth-vtl)*(vh-vl)+vl

Where:

vth = upper input threshold

vtl = lower input threshold

vh = output high

vl = output low

These values default to 2.2, 2.1, 5 and 0 respectively. These values are typical for high speed CMOS logic (74HC family). They can be changed with four simulator options set by the .OPTIONS simulator statement. These are respectively:

LOGICTHRESHHIGH,

LOGICTHRESHLOW,

LOGICHIGH,

LOGICLW

To change the lower input threshold to 1.9, add the following line to the netlist:

```
.OPTIONS LOGICTHRESHLOW=1.9
```

To find out how to add additional lines to the netlist when using the schematic editor, refer to [“Adding Extra Netlist Lines” on page 2](#).

### Ternary Conditional Expression

This is of the form:

```
test_expression ? true_expression : false_expression
```

The value returned will be *true\_expression* if *test\_expression* resolves to a non-zero value, otherwise the return value will be *false\_expression*. This is functionally the same as the IF() function described in the functions table below.

### Functions

Function	Description
ABS(x)	$ x $
ACOS(x), ARCCOS(x)	$\cos^{-1}(x)$
ACOSH(x)	$\cosh^{-1}(x)$
ASIN(x), ARCSIN(x)	$\sin^{-1}(x)$
ASINH(x)	$\sinh^{-1}(x)$
ATAN(x), ARCTAN(x)	$\tan^{-1}(x)$
ATAN2(x,y)	$\tan^{-1}(x/y)$ . Valid if $y \neq 0$
ATANH(x)	$\tanh^{-1}(x)$
COS(x)	$\cos(x)$
COSH(x)	$\cosh(x)$
DDT(x)	$dx/dt$
EXP(x)	$e^x$
FLOOR(x), INT(x)	Next lowest integer of $x$ .
IF(cond, x, y[, maxslew])	if cond is TRUE $result = x$ else $result = y$ . If $maxslew > 0$ the rate of change of the result will be slew rate controlled. See <a href="#">“IF() Function” on page 24</a> .
IFF(cond, x, y[, maxslew])	As IF(cond, x, y, maxslew)
LIMIT(x, lo, hi)	if $x < lo$ $result = lo$ else if $x > hi$ $result = hi$ else $result = x$
LIMITS(x, lo, hi, sharp)	As LIMIT but with smoothed corners. The ‘sharp’ parameter defines the abruptness of the transition. A higher number gives a sharper response. LIMITS gives better convergence than LIMIT. See <a href="#">“LIMITS() Function” on page 24</a> . below
LN(x)	$\ln(x)$ If $x < 10^{-100}$ $result = -230.2585093$
LNCOSH(x)	$\ln(\cosh(x)) = \int \tanh(x) dx$
LOG(x)	$\log_{10}(x)$ . If $x < 10^{-100}$ $result = -100$
LOG10(x)	$\log_{10}(x)$ . If $x < 10^{-100}$ $result = -100$
MAX(x, y)	Returns larger of $x$ and $y$
MIN(x,y)	Returns smaller of $x$ and $y$
PWR(x,y)	$x^y$
PWRS(x,y)	$x \geq 0: x^y, x < 0: -x^y$
SDT(x)	$\int x dt$

Function	Description
SGN(X)	$x > 0: 1, x < 0: -1, x = 0: 0$
SIN(x)	$\sin(x)$
SINH(x)	$\sinh(x)$
SQRT(x)	$x \geq 0: \sqrt{x}, x < 0: \sqrt{-x}$
STP(x)	$x \leq 0: 0, x > 0: 1$
TABLE(x,xy_pairs)	lookup table. Refer to <a href="#">“Lookup tables” on page 25</a>
TABLEX(x,xy_pairs)	Same as TABLE except end points extrapolated. Refer to <a href="#">“Lookup tables” on page 25</a>
TAN(x)	$\tan(x)$
TANH(x)	$\tanh(x)$
U(x)	as STP(x)
URAMP(x)	$x < 0: 0, x \geq 0: x$

### Monte Carlo Distribution Functions

To specify Monte Carlo tolerance for a model parameter, use an expression containing one of the following functions:

Name	Distribution	Lot?
DISTRIBUTION	<a href="#">“User defined distribution” on page 255</a>	No
DISTRIBUTIONL	User defined distribution	Yes
UD	Alias for DISTRIBUTION()	No
UDL	Alias for DISTRIBUTIONL()	Yes
GAUSS	Gaussian	No
GAUSSL	Gaussian	Yes
GAUSSTRUNC	Truncated Gaussian	No
GAUSSTRUNCL	Truncated Gaussian	Yes
UNIF	Uniform	No
UNIFL	Uniform	Yes
WC	Worst case	No
WCL	Worst case	Yes
GAUSSE	Gaussian logarithmic	No
GAUSSEL	Gaussian logarithmic	Yes
UNIFE	Uniform logarithmic	No
UNIFEL	Uniform logarithmic	Yes
WCE	Worst case logarithmic	No
WCEL	Worst case logarithmic	Yes

A full discussion on the use of Monte Carlo distribution functions is given in [“Specifying Tolerances” on page 253](#).

**IF() Function**

```
IF(condition, true-value, false-value[, max-slew])
```

The result is:

if *condition* is non-zero, result is *true-value*, else result is *false-value*.

If *max-slew* is present and greater than zero, the result will be slew-rate limited in both positive and negative directions to the value of *max-slew*.

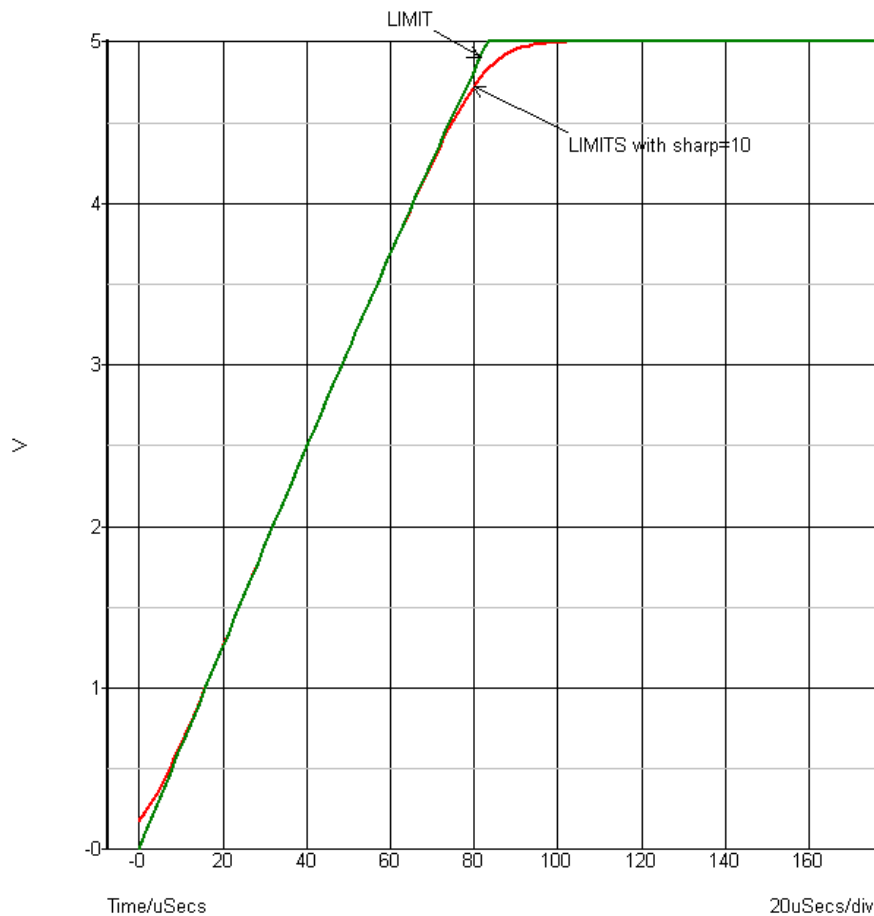
In some situations, for example if *true-value* and *false-value* are constants, the result of this function will be discontinuous when *condition* changes state. This can lead to non-convergence as there is no lower bound on the time-step. In these cases a *max-slew* parameter can be included. This will limit the slew rate so providing a controlled transition from the *true-value* to the *false-value* and vice-versa.

If the [option setting](#) *DISCONTINUOUSIFSLEWRATE* is non-zero, SIMetrix will automatically apply a *max-slew* parameter to all occurrences of the IF() function if both true-value and false-value are constants. This provides a convenient way of resolving convergence issues with third-party models that make extensive use of discontinuous if expressions. Note that the *DISCONTINUOUSIFSLEWRATE* option is also applied to conditional expressions using the C-style *condition ? true-value : false-value* syntax.

**LIMITS() Function**

```
LIMITS(x, low, high, sharp)
```

The LIMITS() function is similar to LIMIT but provides a smooth response at the corners which leads to better convergence behaviour. The behaviour is shown below



The LIMITS function follows this equation:

$$\text{LIMITS}(x, \text{low}, \text{high}, \text{sharp}) = 0.5 * ((\ln(\cosh(v1)) - \ln(\cosh(v2))) / v3 + (\text{low} + \text{high}))$$

Where

$$v1 = \text{sharp} / (\text{high} - \text{low}) * (x - \text{low})$$

$$v2 = \text{sharp} / (\text{high} - \text{low}) * (x - \text{high})$$

$$v3 = \text{sharp} / (\text{high} - \text{low})$$

### Look-up Tables

Expressions may contain any number of look-up tables. This allows a transfer function of a device to be specified according to - say - measured values without having to obtain a mathematical equation. Look-up tables are specified in terms of x, y value pairs which describe a piece-wise linear transfer function. There are three ways to create a lookup table:

Method 1	Syntax in form: <code>TABLE[xy_pairs](input_expression)</code> .	
	<code>xy_pairs</code>	A sequence of comma separated pairs of constant values that define the input and output values of the table. For each pair, the first value is the x or input value and the second is the y or output value. Only explicit numeric constants may be used. Even internal constants such as PI may not be used.
	<code>input_expression</code>	Expression defining the input or x value of the table.
Method 2	Syntax in form: <code>TABLE(input_expression, xy_pairs)</code> .	
	<code>input_expression</code>	Expression defining the input or x value of the table.
	<code>xy_pairs</code>	A sequence of comma separated pairs of values that define the input and output values of the table. For each pair, the first value is the x or input value and the second is the y or output value. Unlike method 1, values do not need to be literal constants and may be expressions containing parameters and <a href="#">“circuit variables” on page 18</a> that reference voltages and currents in the circuit.
		The TABLE function retains the value of the end point for x values beyond the range of the table. For example, if the last point for the TABLE function is (10,5) then any input greater than 10 will give an output of 5.
		If any value references a circuit variable, the expression in which the TABLE function is used must ultimately be evaluated in an arbitrary source
Method 3	Syntax in form: <code>TABLEX(input_expression, xy_pairs)</code> .	
	<code>input_expression</code>	Expression defining the input or x value of the table.
	<code>xy_pairs</code>	Same as method 2 except that out-of-range points are extrapolated from the final segment. See <a href="#">“Table Lookup Example” on page 26</a>

Method 1 is more efficient at handling large tables (hundreds of values). However, method 2 is generally more flexible and is the recommended choice for most applications. Method 2 is also compatible with other simulators whereas method 1 is proprietary to SIMetrix.

For an example see [“Table Lookup Example” on page 26](#)

### 3.3.5 Examples

#### Table Lookup Example

The following arbitrary source definition implements a soft limiting function

**Using method 1:**



```
B1 n2 n3 V=table[-10, -5, -5, -4, -4, -3.5, -3, -3, 3, 3, 4,
+ 3.5, 5, 4, 10, 5](v(N1))
```

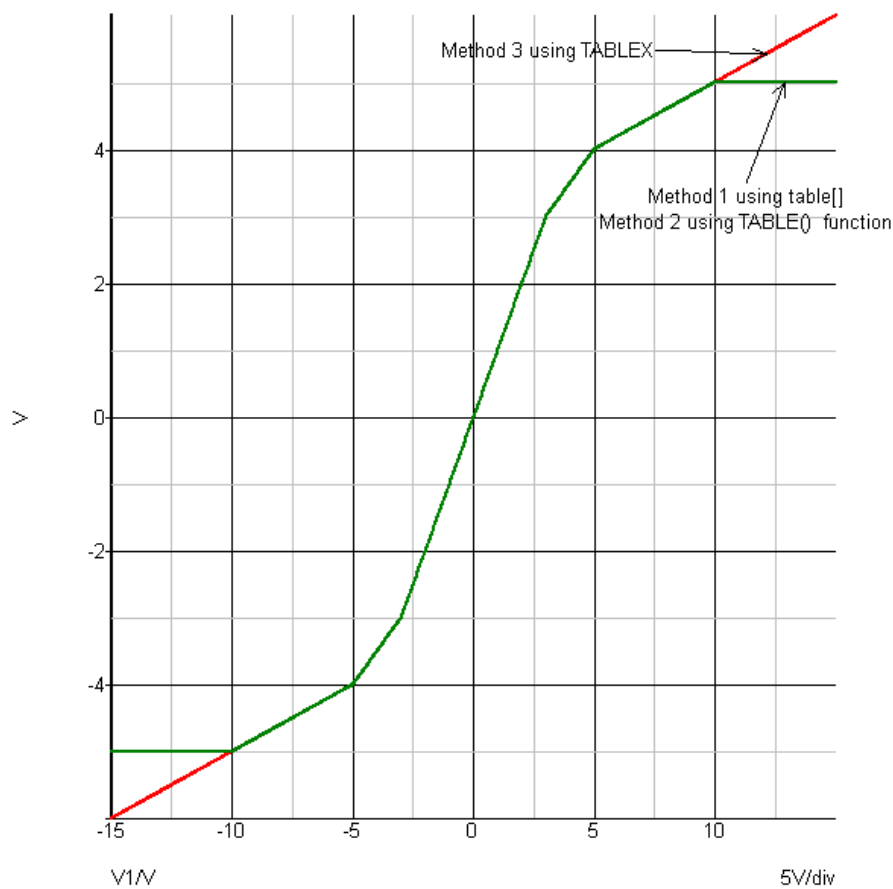
**Using method 2:**

```
B1 n2 n3 V=TABLE(v(N1), -10, -5, -5, -4, -4, -3.5, -3, -3, 3, 3, 4,
+ 3.5, 5, 4, 10, 5)
```

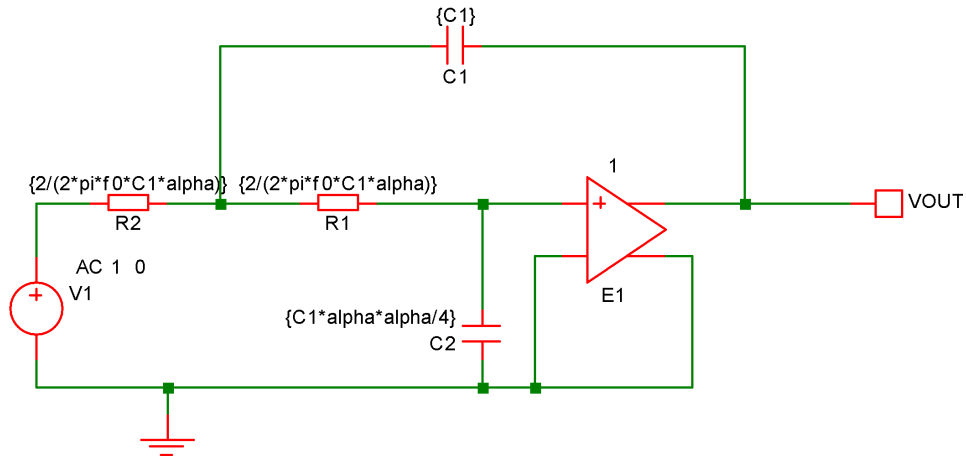
**Using method 3:**

```
B1 n2 n3 V=TABLEX(v(N1), -10, -5, -5, -4, -4, -3.5, -3, -3, 3, 3, 4,
+ 3.5, 5, 4, 10, 5)
```

The resulting transfer functions are illustrated in the following picture:

**Parameter Example**

It is possible to assign expressions to component values which are evaluated when the circuit is simulated. This has a number of uses. For example you might have a filter design for which several component values affect the roll off frequency. Rather than recalculate and change each component every time you wish to change the roll of frequency it is possible to enter the formula for the component's value in terms of this frequency.



The above circuit is that of a two pole low-pass filter.  $C1$  is fixed and  $R1=R2$ . The design equations are:

$$R1=R2=2/(2*\pi*f0*C1*\alpha)$$

$$C2=C1*\alpha*\alpha/4$$

where  $f0$  is the cut off frequency and  $\alpha$  is the damping factor.

The complete netlist for the above circuit is:

```
V1 V1_P 0 AC 1 0
C2 0 R1_P {C1*alpha*alpha/4}
C1 VOUT R1_N {C1}
E1 VOUT 0 R1_P 0 1
R1 R1_P R1_N {2/(2*pi*f0*C1*alpha)}
R2 R1_N V1_P {2/(2*pi*f0*C1*alpha)}
```

Before running the above circuit you must assign values to the variables. This can be done by one of three methods:

- With the `.PARAM` statement placed in the netlist.
- With `Let` command from the command line or from a script. (If using a script you must prefix the parameter names with `global`!)
- By sweeping the value with using parameter mode of a swept analysis (see “[General Sweep Specification](#)” on page 188) or multi-step analysis (see “[Multi Step Analyses](#)” on page 190).

Expressions for device values must be entered enclosed in curly braces (`{'}` and `'}`).

Suppose we wish a 1kHz roll off for the above filter.

Using the `.PARAM` statement, add these lines to the netlist

```
.PARAM f0 1k
.PARAM alpha 1
.PARAM C1 10n
```

Using the `Let` command, you would type:

```
Let f0=1k
Let alpha=1
Let C1=10n
```

If you then wanted to alter the damping factor to 0.8 you only need to type in its new value:

```
Let alpha=0.8
```

then re-run the simulator.

To execute the Let commands from within a script, prefix the parameter names with global:. E.g. “Let global:f0=1k”

In many cases the .PARAM approach is more convenient as the values can be stored with the schematic.

### 3.3.6 Optimisation

#### Overview

An optimisation algorithm may be enabled for expressions used to define arbitrary sources and any expression containing a swept parameter. This can improve performance if a large number of such expressions are present in a design.

The optimiser dramatically improves the simulation performance of the power device models developed by Infineon. See [“Optimiser Performance” on page 29](#).

#### Why is it Needed?

The simulator’s core algorithms use the Newton-Raphson iteration method to solve non-linear equations. This method requires the differential of each equation to be calculated and for arbitrary sources, this differentiation is performed symbolically. So as well as calculating the user supplied expression, the simulator must also evaluate the expression’s differential with respect to each dependent variable. These differential expressions nearly always have some sub-expressions in common with sub-expressions in the main equation and other differentials. Calculation speed can be improved by arranging to evaluate these sub-expressions only once. This is the main task performed by the optimiser. However, it also eliminates factors found on both the numerator and denominator of an expression as well as collecting constants together wherever possible.

#### Using the Optimiser

The optimiser is automatically enabled and no action is required to make use of it. If desired, it can be disabled using:

```
.OPTIONS optimise=0
```

#### Optimiser Performance

The optimisation algorithm was added to SIMetrix primarily to improve the performance of some publicly available power device models from Infineon. These models make extensive use of arbitrary sources and many expressions are defined using .FUNC.

The performance improvement gained for these model is in some cases dramatic. For example a simple switching PSU circuit using a SGP02N60 IGBT ran around 5 times faster with the optimiser enabled and there are other devices that show an even bigger improvement.

## Accuracy

The optimiser simply changes the efficiency of evaluation and doesn't change the calculation being performed in any way. However, performing a calculation in a different order can alter the least significant digits in the final result. In some simulations, these tiny changes can result in much larger changes in circuit solution. So, you may find that switching the optimiser on and off may change the results slightly.

## 3.4 Subcircuits

### 3.4.1 Overview

Subcircuits are a method of defining a circuit block which can be referenced any number of times by a single netlist line or schematic device. Subcircuits are the method used to define many device models such as op-amps.

### 3.4.2 Subcircuit Definition

Subcircuits begin with the .SUBCKT statement and end with .ENDS. A subcircuit definition is of the form:

```
.SUBCKT subcircuit_name nodelist [[params:] default_parameter_list]
definition_lines
.ENDS
```

subcircuit_name	Name of the subcircuit and is used to reference it in the main netlist.
nodelist	Any number of node names and are used for external connections. The subcircuit call (using an 'X' device) would use a matching number of nodes <i>in the same order</i> .
default_parameter_list	List of parameters and their default values in the form name=value. Subcircuit parameters are explained in <a href="#">“Using Expressions” on page 17</a> .
definition_lines	List of valid device and model lines. In addition, .NODESET, .IC and .KEEP lines may also be placed in a subcircuit.

### Example

This is an example of an opamp subcircuit called SXOA1000. VINP, VINN VOUT VCC and VEE are its external connections. The three .model lines define devices that are local, that is, they are only accessible within the subcircuit definition.

```
.subckt SXOA1000 VINP VINN VOUT VCC VEE
I2 D2_N VEE 100u
I1 Q3_E VEE 100u
C1 VOUT R1_P 10p
D1 Q7_C D1_N D1
D2 D1_N D2_N D1
D3 VEE Q3_E D1
Q2 VEE D2_N VOUT 0 P1
Q3 Q3_C R3_P Q3_E 0 N1
```

```

Q1 VCC Q7_C VOUT 0 N1
Q6 Q3_C Q3_C VCC 0 P1
Q7 Q7_C Q5_C VCC 0 P1
R1 R1_P Q5_C 100
Q4 Q5_C R2_N Q3_E 0 N1
R2 VINP R2_N 1K
Q5 Q5_C Q3_C VCC 0 P1
R3 R3_P VINN 1K

.model N1 NPN VA=100 TF=1e-9
.model P1 PNP VA=100 TF=1e-9
.model D1 D

.ends

```

### Where to Place Subcircuit Definition

Subcircuit definitions may be placed in a number of locations.

- Directly in the netlist. This is the best place if the subcircuit is specific to a particular design. If you are entering the circuit using the schematic editor, see [“Simulator Reference Manual/Running the Simulator/Using the Simulator with the SIMetrix Schematic Editor/Adding Extra Netlist Lines” on page 2](#) to find out how to add additional lines to the netlist.
- Put in a separate file and pull in to the schematic with `.INC` statement placed in the netlist.
- Put in a library file and reference in schematic with SIMetrix form of `“LIB”` on page 206 statement placed in the netlist. Similar to 2. but more efficient if library has many models not used in the schematic. Only the devices required will be read in.
- Put in a library file and install as a model library. See *User’s Manual/Device Library and Parts Management/Installing Models* for full details.

#### 3.4.3 Subcircuit Instance

Once a subcircuit has been defined, any number of instances of it may be created. These are of the form:

```
Xxxxx nodelist sub_circuitname [ [params:|:] parameters]
```

nodelist	List of nodes, each of which will connect to its corresponding node in the subcircuit’s definition. The number of nodes in the instance must exactly match the number of nodes in the definition.
sub_circuitname	Name of the subcircuit definition.
parameters	List of parameter names and their values in the form <i>name=value</i> . These may be referenced in the subcircuit definition. Subcircuit parameters are explained below.

#### 3.4.4 Passing Parameters to Subcircuits

You can pass parameters to a subcircuit. Consider the filter example provided in [“Using Expressions” on page 17](#). Supposing we wanted to define several filters with different characteristics. We could use a subcircuit to define the filter but the values of the components in the filter need to be

different for each instance. This can be achieved by passing the parameter values to each instance of the subcircuit.

So:

```

** Definition
.SUBCKT Filter IN OUT params: C1=1n alpha=1 f0=1k
C2 0 R1_P {C1*alpha*alpha/4}
C1 OUT R1_N {C1}
E1 OUT 0 R1_P 0 1
R1 R1_P R1_N {2/(2*pi*f0*C1*alpha)}
R2 R1_N IN {2/(2*pi*f0*C1*alpha)}
.ENDS

** Subcircuit instance
X1 V1_P VOUT Filter : C1=10n alpha=1 f0=10k

** AC source
V1 V1_P 0 AC 1 0

```

In the above example the parameters after *params:* in the `.subckt` line define default values should any parameters be omitted from the subcircuit instance line. It is not compulsory to define defaults but is generally recommended.

### Note

In the syntax definition for both subcircuit definitions and subcircuit instances, the *params:* specifier is shown as optional. If *params:* is included the '=' separating the parameter names and their values becomes optional.

### 3.4.5 Nesting Subcircuits

Subcircuit definitions may contain both calls to other subcircuits and local subcircuit definitions.

If a subcircuit definition is placed within another subcircuit definition, it becomes local. That is, it is only available to its host subcircuit.

Calls to subcircuits may not be recursive. A subcircuit may not directly or indirectly call its own definition.

### 3.4.6 Global Nodes

Sometimes it is desirable to refer to a node at the circuit's top level from within a subcircuit without having to explicitly pass it. This is sometimes useful for supply rails.

SIMetrix provides three methods.

- '#' prefix. Any node *within* a subcircuit prefixed with '#' will connect to a top level node of the same name *without* the '#' prefix.
- '\$g\_' prefix. Any node in the circuit prefixed '\$g\_' will be treated as global.
- Using [.GLOBAL](#).

The second approach is compatible with PSpice®. The third approach is compatible with Hspice®

Note the first two approaches are subtly different. In the second approach the '\$g\_' prefix must be applied to all connected nodes, whereas in the first approach the '#' prefix must be applied *only* to subcircuit nodes.

### 3.4.7 Subcircuit Preprocessing

SIMetrix features a netlist preprocessor that is usually used for SIMPLIS simulations and was developed for that purpose. The preprocessor has some features that aren't available in the native simulator and for this reason it would be useful to be able to use the preprocessor for SIMetrix simulations.

It is not necessary to apply the preprocessor to the entire netlist. Any subcircuit call that defines preprocessor variables using the 'vars:' specifier will be passed to the preprocessor. For example:

```
X$C1 R1_P 0 ELEC_CAP_L13 vars: LEVEL=3 CC=1m
+ RSH_CC=1Meg IC=0 RESR=10m LESL=100n USEIC=1
```

calls the ELEC\_CAP\_L13 subcircuit but passes it through the preprocessor first. This model is a model for an electrolytic capacitor and uses a number of .IF statements to select model features according to the LEVEL parameter.

The preprocessor also provides a means of generating multiple devices using .WHILE. For information on the preprocessor, see the *SIMPLIS Reference Manual/Running SIMPLIS/Netlist Preprocessor*.

## 3.5 Model Binning

### 3.5.1 Overview

Some devices can be *binned*. This means that a number of different model definitions can be provided for the same device with each being valid over a limited range of some device parameter or parameters. The simulator will automatically select the appropriate model according to the value given for the device parameters.

Currently only BSIM3, BSIM4 and HiSIM HV MOSFETs may be binned. The binning is controlled by the length and width device parameters (L and W) while the LMIN, LMAX, WMIN and WMAX model parameters specify the valid range for each model.

#### Important Note

The binned models should be placed directly in the netlist or called using either .INC or the Hspice® form of .LIB. They will not work correctly when installed as a model library or accessed with the SIMetrix form of .LIB.

### 3.5.2 Defining Binned Models

Binned models are defined as a set consisting of two or more .MODEL definitions. Each of the definitions must be named using the following format:

```
root_name.id
```

<i>root_name</i>	Name used by the device to call the model. Must be the same for all model definitions in a set
<i>id</i>	Arbitrary name that must be unique for each model in a set. This would usually be a number but this is not a requirement

Each model definition must also contain a MIN/MAX parameter pair for each bin control parameter. For the BSIM3 MOSFET there are two bin control parameters, namely L and W with

corresponding MIN/MAX pairs LMIN/LMAX and WMIN/WMAX. For a binned BSIM3 model, all four must be present. These parameters define the range of L and W over which the model is valid. When a model is required, the simulator searches all models with the same root\_name for a definition whose LMIN/LMAX and WMIN/WMAX parameters are compatible with the device's L and W.

### 3.5.3 Example

```
.MODEL N1.1 NMOS LEVEL=49 ... parameters ...
+ LMIN=1u LMAX=4u WMIN=1u WMAX=4u

.MODEL N1.2 NMOS LEVEL=49 ... parameters ...
+ LMIN=4u LMAX=10u WMIN=1u WMAX=4u

.MODEL N1.3 NMOS LEVEL=49 ... parameters ...
+ LMIN=1u LMAX=4u WMIN=4u WMAX=10u

.MODEL N1.4 NMOS LEVEL=49 ... parameters ...
+ LMIN=4u LMAX=10u WMIN=4u WMAX=10u

** This device will use N1.1
M1 1 2 3 4 N1 L=2u W=2u

** This device will use N1.2
M2 1 2 3 4 N1 L=6u W=2u

** This device will use N1.3
M3 1 2 3 4 L=2u W=7u

** This device will use N1.4
M4 1 2 3 4 L=6u W=7u
```

## 3.6 Language Differences

SIMetrix is compatible with some PSpice® and Hspice® extensions mainly so that it can read external model files. Some aspects of these alternative formats are incompatible with the SIMetrix native format and in such cases it is necessary to declare the language being used. See [“Language Declaration” on page 9](#) for details on how to do this.

The following sections describe the incompatibilities between the three languages.

### 3.6.1 Inline Comment

Hspice® uses the dollar ('\$') symbol for inline comments while SIMetrix and PSpice® use a semi-colon (;). The language declaration described above determines what character is used.

### 3.6.2 Unlabelled Device Parameters

The problem with unlabelled device parameters is illustrated with the following examples.

The following lines are legal in Hspice® mode but illegal in SIMetrix mode.

```
.PARAM area=2
Q1 C B E S N1 area
```



Q1 will have an area of 2. Conversely the following is legal in SIMetrix but is illegal in Hspice®:

```
.PARAM area=2
Q1 C B E S N1 area area
```

Again Q1 has an area of 2.

The problem is that SIMetrix does not require '=' to separate parameter names with their values whereas Hspice® does. *area* is a legal BJT parameter name so in the first example SIMetrix can't tell whether *area* refers to the name of the BJT parameter or the name of the .PARAM parameter defined in the previous line. Hspice® can tell the difference because if *area* meant the BJT parameter name it would be followed by an '='.

This line is legal and will be correctly interpreted in both modes

```
.PARAM area=2
Q1 C B E S N1 area=area
```

Although Hspice® always requires the '=' to separate parameter names and values, it continues to be optional in SIMetrix even in Hspice® mode. It only becomes compulsory where an ambiguity needs to be resolved as in the second example above.

### 3.6.3 LOG() and PWR()

The LOG() function means log to the base 10 in SIMetrix but in PSpice® and Hspice® means log to the base e. PWR() in PSpice® and SIMetrix means  $|x|^y$  whereas in Hspice® it means "if  $x \geq 0$ ,  $|x|^y$  else  $-|x|^y$ ". The language declaration only affects the definition when used in expressions to define model and device parameters. When used in arbitrary source expressions, the language assumed is controlled by the method of implementing the device as follows:

SIMetrix:

```
B1 1 2 V=expression
```

PSpice®

```
E1 1 2 VALUE = {expression }
```

Hspice®

```
E1 1 2 VOL = `expression'
```

Note that the function LN() always means log to base e and LOG10() always means log to base 10. We recommend that these functions are always used in preference to LOG to avoid confusion.

## 3.7 Customising Device Configuration

### 3.7.1 Overview

Models for discrete devices and for integrated circuit processes come from a variety of sources and are often designed for particular simulators, in particular, PSpice and Hspice. These simulators are not generally compatible with each other so it is not easy for SIMetrix to be simultaneously compatible with both. Further, SIMetrix itself needs to retain backward compatibility with its own earlier versions.

An example of conflict can be found with the standard diode. The SIMetrix diode with no level parameter specified is mainly compatible with PSpice. But the standard Hspice diode is quite different and not compatible. The SIMetrix Level=3 diode is however compatible with Hspice

both for level=1 and level=3. To use Hspice level=1 diode models the user has to edit the model so that level is changed to 3.

It is not always convenient to modify model files and for this reason SIMetrix provides an alternative in the form of the device configuration file. This provides a means of changing the access to particular device model including re-mapping level numbers. The following section describes how to setup a device configuration file.

### 3.7.2 What does the Device Configuration File do?

The device configuration file (DCF) edits or adds to an internal table used to map model names, level numbers and access letters to an actual device model. All device models (that is the binary code that implements the device equations) have an internal name that is used to uniquely identify it, but this name is not used externally. Instead .MODEL statements use their own name (e.g. nmos, pnp) coupled with an optional LEVEL parameter to define the actual device referred to. For example, the MOS level 3 device is referred internally as “MOS3” but the .MODEL statements use the names NMOS or PMOS and set the LEVEL parameter to 3. The mapping between NMOS and LEVEL 3 to “MOS3” is defined in an internal table which can be modified by specifying a device configuration file.

The DCF can add new entries to the table so providing additional methods of accessing a device. It can also modify existing entries to point to a new device.

### 3.7.3 Creating a Device Configuration File

The device configuration file (DCF) path and name are defined by the option variable DevConfigFile. By ‘option variable’, we mean the variables assigned using the command line Set command not simulator options set by .OPTIONS.

The default value for the setting is %SHAREPATH%/DeviceConfig.sxdcf, %SHAREPATH% resolves to the support directory under the installation root.

#### Format

Each line in the DCF maps a single device and consists of up to 4 assigned parameters. These are described in the following table.

Keyword	Description
ModelName	Model name used in .MODEL statement
Device	Internal device name. See table
Level	Level parameter
Letter	Device letter
Report	Value <b>on</b> or <b>off</b> . If on a report of the device mapping will be displayed in the command shell when SIMetrix starts.

To modify an existing mapping, you only need to provide the model name, device and level. The modelname and level must point to an existing combination that is already in use (see “[List of All Simulator Devices](#)” on page 37), e.g. ModelName=D and Level=1, and device would then be set to the new device that this combination is to point to, e.g. Diode3. So this is what the line would be:

```
ModelName=D,Level=1,Device=Diode3
```

The above would make level 1 diodes use the same model as level=3. Here is another example:

```
ModelName=R,Level=0,Device=HspiceRes
```

Level=0 is the level value when the LEVEL parameter is not specified. In the case of resistors, no .MODEL statement is required at all, so the above line will change the default model used for *all* resistors to the Hspice model instead of the native SIMetrix model.

It is also possible to add a new mapping in which case the level and modelname parameters must be currently unused. Also when creating a new mapping the ‘Letter’ parameter must be specified. ‘Letter’ is the first letter of the component reference traditionally used to identify the type of device in SPICE netlists. For example ‘Q’ refers to BJTs and ‘D’ refers to diodes.

For example, the following entries define LEVEL=69 as a valid level for accessing the PSP 1.03 model:

```
ModelName=nmos,Level=69,Device=psp103_n,report=on
ModelName=pmos,Level=69,Device=psp103_p,report=on
```

Note that two entries are required in order to support both n-channel and p-channel devices. The above doesn’t change the existing level but adds an additional level.

When defining a new mapping the letter must be specified and usually this should be the letter conventionally used for the class of device. If defining a new mapping for a MOSFET, the letter ‘M’ should be used, for a diode the letter ‘D’ should be used and so on. However, the letters, ‘N’, ‘P’, ‘W’, ‘U’ and ‘Y’ maybe used as well for any type of device.

### 3.7.4 List of All Simulator Devices

A list of all internal devices may be obtained using the show\_devices script. This will copy to the system clipboard a tab delimited table listing all internal devices. This is guaranteed to be accurate as it is generated directly by SIMetrix. To obtain this table proceed as follows:

1. Type this at the command line. (The edit box below the menu bar in the command shell. This is not available in the free SIMetrix Intro)

```
show_devices
```

2. You should see a message “Device information has been copied to the system clipboard” appear
3. Using a spreadsheet program, execute the **Paste** function. You should see the table appear.

The table has seven columns:

Column 1: Internal name. This is the device name

Column 2: Model name as used in the .MODEL statement

Column 3: Level.

Column 4: Minimum number of terminals that this device must have

Column 5: Maximum number of terminals that this device may have

Column 6: Device letter

Column 7: Model Version

Some internal devices have a model name beginning with ‘\$\$’. These device do not use a .MODEL statement and have no model parameters. The name is used internally only.

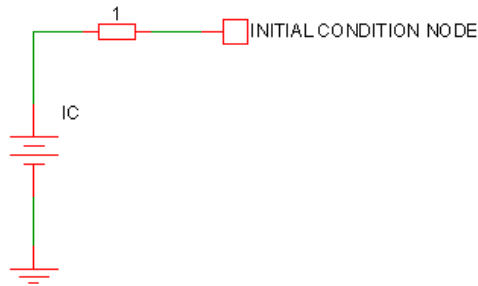
Devices with a minimum number of terminals of -1 do not have a minimum number. Similarly devices with zero maximum number of terminals do not have a maximum.

## 3.8 Initial Conditions

Initial conditions may be applied to capacitors and inductors and may also be applied to a single node using the .IC statement. Initial conditions force a voltage or current to be applied during the DC operating point analysis. Here we describe the various methods to apply an initial condition.

### 3.8.1 Node Initial Condition

A voltage initial condition may be applied to a node using the .IC statement, see [“.IC” on page 201](#). This method applies the initial condition through a fixed resistor. In effect the following circuit is applied to the node during the DC operating point then removed when the main analysis starts:



The above shows a driving resistance of  $1\Omega$ . This is the default value but can be changed using the ICRES option:

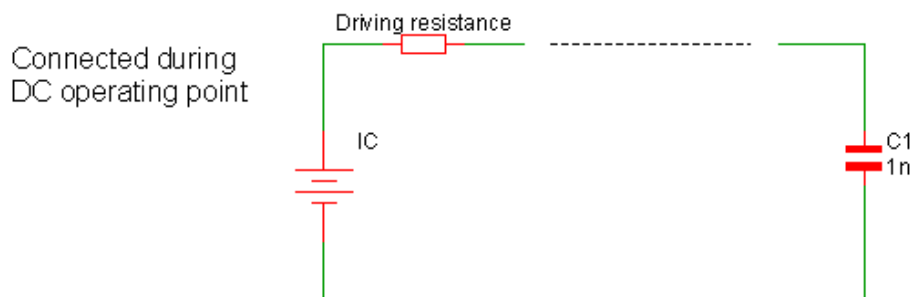
```
.OPTIONS ICRES=1m
```

The above sets the resistance to  $1m\Omega$ .

Note that an initial condition may also be applied to a node or across a pair of nodes using a capacitor with a value of zero. See next section.

### 3.8.2 Capacitor Initial Condition

An initial condition may be defined for a capacitor using the IC parameter. The following diagram shows how this is configured:



The actual interpretation of the IC parameter depends on the INITCONDMODE option setting:

```
.OPTIONS INITCONDMODE=0|1|2
```

It also depends on the BRANCH parameter on the capacitor:

```
Cxxxx n1 n2 capacitance IC=init_condition BRANCH=0|1
```

The different configurations have come about because of a need for compatibility with other simulators, namely SIMPLIS, Berkeley SPICE and PSpice.

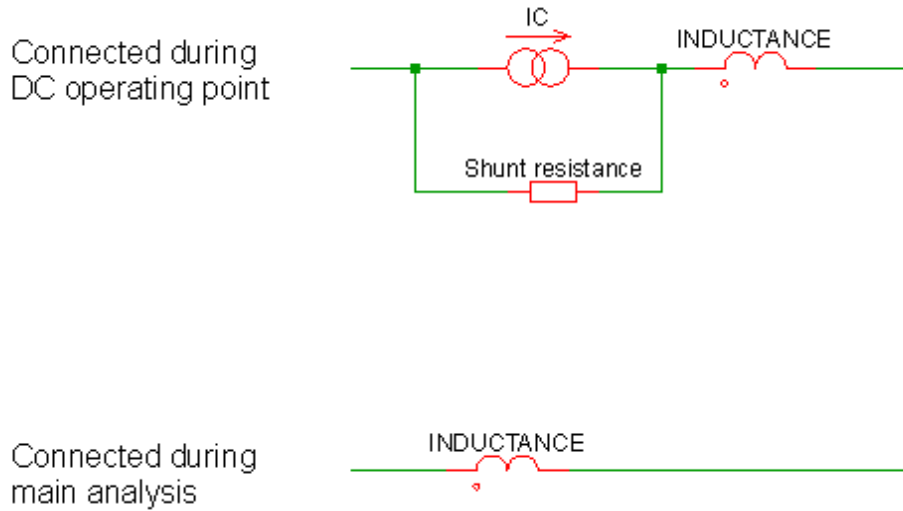
The following table describes the various configurations:

IC defined	BRANCH	INITCONDMODE	Configuration
NO	0	X	No initial condition applied
NO	1	X	Initial condition=0V, driving resistance=0 $\Omega$
YES	0	0	Berkeley SPICE compatible. Initial condition=IC only if UIC specified on .TRAN statement
YES	0	1	SIMPLIS compatible. Initial condition=IC, driving resistance=0 $\Omega$
YES	0	2	PSpice compatible. Initial condition=IC, driving resistance=ICRES (default=1 $\Omega$ )
YES	1	X	SIMPLIS compatible. Initial condition=IC, driving resistance=0 $\Omega$

Note that for full PSpice compatibility, the ICRES option should be set to 1m. Alternatively the option setting PSPICECOMPAT may be set which sets ICRES to 1m and INITCONDMODE to 2.

### 3.8.3 Inductor Initial Condition

An initial condition may be defined for an inductor using the IC parameter. The following diagram shows how this is configured:



The actual interpretation of the IC parameter depends on the INITCONDMODE option setting:

```
.OPTIONS INITCONDMODE=0|1|2
```

It also depends on the BRANCH parameter on the inductor:

```
Lxxxx n1 n2 inductance IC=init_condition BRANCH=0|1
```

The different configurations have come about because of a need for compatibility with other simulators, namely SIMPLIS, Berkeley SPICE and PSpice.

The following table describes the various configurations:

IC defined	BRANCH	INITCONDMODE	Configuration
NO	1	X	No initial condition applied
NO	0	X	Initial condition=0A, shunt resistance= $\infty$
YES	1	0	Berkeley SPICE compatible. Initial condition=IC only if UIC specified on .TRAN statement
YES	1	1	SIMPLIS compatible. Initial condition=IC, shunt resistance= $\infty$
YES	1	2	PSpice compatible. Initial condition=IC, shunt resistance= $1e9 \Omega$
YES	0	X	SIMPLIS compatible. Initial condition=IC, shunt resistance= $\infty$

## Chapter 4

# Analog Device Reference

### 4.1 Overview

This chapter provides the full details of every option and parameter available with every *primitive* analog device that the simulator supports.

For documentation on digital and mixed signal devices supplied with SIMetrix, please see “[Digital/Mixed signal Device Reference](#)” on page 132.

### 4.2 Further Documentation

Some devices are fully documented by their developers and we have not repeated that documentation here. In all cases the documents may be found on the installation CDROM. We no longer ship a physical CDROM but its contents may be browsed and an image downloaded from our web site. Visit:

<http://www.simetrix.co.uk/app/product-installation.htm>

then click on Download links. You will need a user name and password to access this page. An automated system is available to obtain this and you will find details at the above link.

### 4.3 AC Table Lookup (including S-Parameters)

#### 4.3.1 Netlist Entry

```
Uxxx node_pairs modelname
```

Where

*node\_pairs*                Pairs of nodes for each port. So for example, a two port device has four nodes.

*modelname*                Model name

#### 4.3.2 Model Format

```
.MODEL modelname actable LOAD=filename [
```

```
NUMPORTS=number_of_ports ] [ DCMETHOD=extrapolate|extend ] [
DCPARAMS=[dcgainvalues] ]
```

Where:

filename	Name of file containing frequency table. File uses Touchstone format and may contain s-parameters or y-parameters. Other parameter types are not currently supported.
number_of_ports	Number of ports. Default value is 2. If y-parameters are supplied, any number of ports may be specified. If s-parameters are specified, the number of ports must be 1 or 2.
DCMETHOD	Has values of 'extrapolate' or 'extend'. This determines how the DC gains are calculated if they are not explicitly defined using the DCPARAMS parameter or with an explicit F=0 term in the definition file. With 'extrapolate', the dc values are calculated by extrapolating back to zero; with 'extend', the DC gain is the same as the lowest frequency gain.
dcgainvalues	Vector providing the DC gain values for the network. This is expected to be an n x n matrix where n is the number of ports.

### 4.3.3 AC Table Notes

The AC Table device implements a circuit device that is defined by a frequency lookup table. This device operates only in the small signal analysis modes, AC, Noise and TF. In transient and DC analyses it behaves like a simple linear DC gain block with no frequency dependence.

The lookup table for this device must be defined by a file and uses the industry standard 'Touchstone' format. The full details of this format are supplied as a separate document and maybe found on the SIMetrix install CDROM and at our web site. Please visit "[Further Documentation](#)" on [page 41](#) for details. The document is freely distributable under the terms described therein and may also be found at various Internet sites.

The SIMetrix implementation of the touchstone format includes the following:

1. Y-parameters to any number of ports
2. 1 and 2 port s-parameters

Z, H and G parameters are not supported. Also, noise parameters are not supported.

Touchstone files traditionally use the extension *snp* where *n* indicates the number of ports. Be aware that SIMetrix uses the NUMPORTS parameter in the .model statement to determine the number of ports and will ignore the value of *n* in the filename extension.

## 4.4 Arbitrary Source

### 4.4.1 Netlist Entry

Voltage source:

```
Bxxxx n+ n- [MIN=min_value] [MAX=max_value] V=expression
```

Current source:

```
Bxxxx n+ n- [MIN=min_value] [MAX=max_value] [M=multiplier] I=expression
```



Charge source:

Bxxxx n+ n- [M=multiplier] Q=expression

Flux source:

Bxxxx n+ n- FLUX=expression

An arbitrary source is a voltage or current source whose output can be expressed as an arbitrary relationship to other circuit voltages or currents.

<i>expression</i>	Algebraic expression describing voltage or current output in terms of circuit nodes or sources. See for full details.
<i>min_value</i>	Minimum value of source
<i>max_value</i>	Maximum value of source
<i>multiplier</i>	Scale factor. Source will behave as if there multiplier devices in parallel
Bxxxx	Component reference
n+	Positive output node.
n-	Negative output node.

The small-signal AC behaviour of the non-linear source is a linear dependent source with a proportionality constant equal to the derivative (or derivatives) of the source at the DC operating point.

Note that if MIN and/or MAX parameters are specified, they must precede the defining expression.

Charge and flux sources implement capacitors and inductors respectively. See “[charge and Flux Devices](#)” on page 44 for details.

If the source is a current, the direction of flow is into the positive node (n+).

#### 4.4.2 Notes on Arbitrary Expression

It is essential that the expression used for an arbitrary source is *well conditioned*. This means that it must be valid for all values (i.e. from  $-\infty$  to  $+\infty$ ) of its input variables (i.e. circuit voltages and currents) and that it is continuous. It is also desirable - although not always absolutely necessary - for the function to be continuous in its first derivative; i.e. it does not have any abrupt changes in slope.

A badly designed expression will lead to poor convergence, non-convergence or slow run times. This is especially the case if the source is used in a feedback loop. If the arbitrary source is used open loop then the above conditions can sometimes be relaxed especially if the input signal is well defined e.g. derived directly from a signal source.

Some functions are not continuous in nature. E.g. the STP() and SGN() functions are not. These may nevertheless be used in an expression as long as the end result is continuous.

Similarly, the IF() function (or ternary conditional using ‘?’ and ‘:’) should be used with care. The following IF() function *is* continuous:

IF(v1>v2, 0, (v1-v2)\*2)

When v1=v2 both true and false values equate to zero so the function has no abrupt change. The function still has a discontinuous first derivative with respect to both v1 and v2 which is still undesirable but will work satisfactorily in most situations.

The following example is *not* continuous:

```
IF(v1>v2, 0, 5)
```

The result of this will switch abruptly from 0 to 5 when  $v1=v2$ . This is not something that the simulator can be guaranteed to handle and cannot be implemented in real life.

A better, albeit less intuitive method, of achieving the intent of the above is:

```
(TANH((v2-v1)*factor)+1)*2.5+2.5
```

where factor is some number that determines the abruptness of the switching action. For a value of 147, 95% of the full output will be achieved with just 10mV overdrive.

Alternatively the IF functions slew rate feature may be used:

```
IF(v1>v2, 0, 5, 1e9)
```

See “[IF\(\) Function](#)” on page 24 for further details.

### 4.4.3 Charge and Flux Devices

It is possible to define capacitors and inductors directly using the arbitrary source. Capacitors must be defined in terms of their charge and inductors by their flux. These are defined in the same as voltage and current arbitrary sources but using ‘q’ or ‘flux’ instead of ‘v’ or ‘i’. E.g. the following defines a simple linear capacitor:

```
B1 n1 n2 Q = C*V(n1,n2)
```

Similarly a linear inductor is:

```
B1 n1 n2 flux = L * i(B1)
```

The main benefit of this feature is that it makes it possible to define non-linear capacitors and inductors directly. It is also possible to use the ddt() and sdt() functions to create capacitors and inductors using regular current and voltage sources. However, the above method is more efficient.

As with voltage and current arbitrary sources, it is possible to use any combination of voltages and currents in the expression. So, for example, the following defines a transformer:

```
Bprimary p1 p2 flux = Lp*i(Bprimary) + M*i(Bsecondary)
Bsecondary s1 s2 flux = Ls*i(Bsecondary) + M*i(Bprimary)
```

### 4.4.4 Arbitrary Source Examples

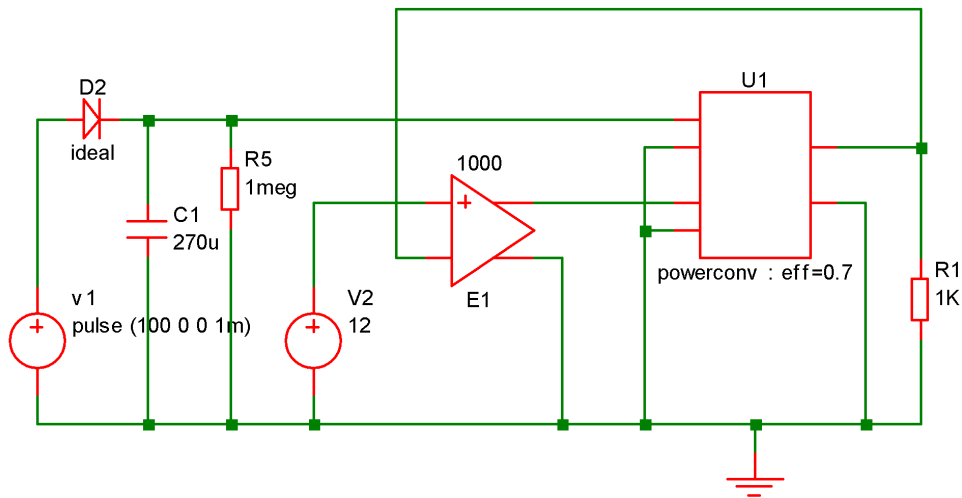
#### Example 1 - Ideal Power Converter

This examples also demonstrates the use of expressions within subcircuits (see “[Using Expressions](#)” on page 17).

The following subcircuit implements an idealised power converter with an efficiency of eff and whose output voltage is proportional to the input voltage (vinn,vinp) multiplied by the control voltage (vcp,vcn). It is intended to simulate the voltage/current characteristics of a switching power converter.

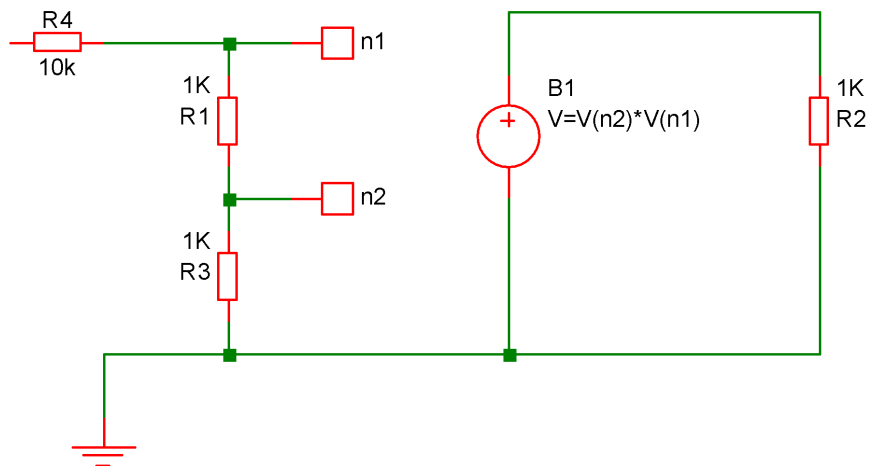
```
.subckt powerconv voutp voutn vinp vinn vcp vcn
biin1 vinp vinn i=-v(voutp,voutn)/v(vinp,vinn)*i(vout1)/{eff}
vout1 bmult1_n voutn 0
bmult1 voutp bmult1_n v=v(vinp,vinn)*v(vcp,vcn)
r1 vcp vcn 1meg
.ends
```

Once again, with an appropriate schematic symbol, the device can be placed on the schematic as a block as shown below:



### Example 2 - Voltage Multiplier

The expression for an arbitrary source must refer to other voltages and/or currents on the schematic. Currents are referenced as voltage sources and voltages as netnames. Netnames are usually allocated by the netlister. For information on how to display and edit the schematic's netnames, refer to [“Displaying Net and Pin Names”](#) on page 2.

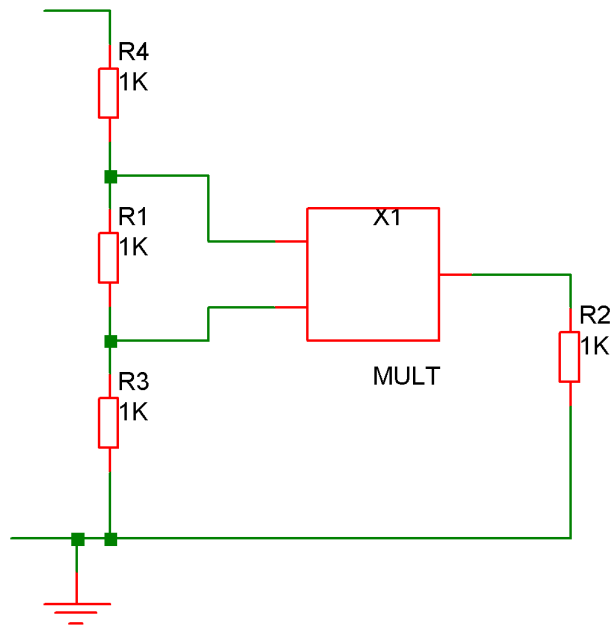


In the above circuit the voltage across B1 will be equal to the product of the voltages at nodes n1 and n2.

An alternative approach is to define the arbitrary source within a subcircuit. E.g.

```
.subckt MULT out in1 in2
B1 out 0 V=V(in1)*V(in2)
.ends
```

which can be added to the netlist manually. (To find out how to add additional lines to the netlist when using the schematic editor, refer to “Adding Extra Netlist Lines” on page 2). A symbol could be defined for it and then placed on the schematic as a block as shown below:



### Example 3 - Voltage comparator

```
B3 q3_b 0 V=atan(V(n1,n2)*1000)
```

This can also be added to the schematic in the same way as for the multiplier described above.

#### 4.4.5 PSpice and Hspice syntax

SIMetrix supports the PSpice® and Hspice® syntax for arbitrary sources. This is for compatibility with some manufacturers device models. For PSpice® the VALUE = and TABLE = devices are supported and for Hspice® VOL= and CUR= are supported.

## 4.5 Bipolar Junction Transistor (SPICE Gummel Poon)

### 4.5.1 Netlist Entry

```
Qxxxx collector base emitter [substrate] modelname [area] [OFF] [IC=vbe,vce]
    [TEMP=local_temp] [M=mult] [DTEMP=dtemp]
```

<i>collector</i>	Collector node name
<i>base</i>	Base node name
<i>emitter</i>	Emitter node name
<i>substrate</i>	Substrate node name
<i>modelname</i>	Name of model. Must begin with a letter but can contain any character except whitespace and ‘.’

<i>area</i>	Area multiplying factor. Area scales up the device. E.g. an area of 3 would make the device behave like 3 transistors in parallel. Default is 1.
OFF	Instructs simulator to calculate operating point analysis with device initially off. This is used in latching circuits such as thyristors and bistables to induce a particular state. See “OP” on page 214 for more details.
<i>vbe,vce</i>	Initial conditions for base-emitter and collector-emitter junctions respectively. These only have an effect if the UIC parameter is specified on the .TRAN statement (see “TRAN” on page 245).
<i>local_temp</i>	Local temperature. Overrides specification in .OPTIONS or .TEMP statements.
<i>mult</i>	Device multiplier. Equivalent to putting <i>mult</i> devices in parallel.
<i>dtemp</i>	Differential temperature. Similar to <i>local_temp</i> but is specified relative to circuit temperature. If both TEMP and DTEMP are specified, TEMP takes precedence.

#### 4.5.2 NPN BJT Model Syntax

```
.model modelname NPN ( parameters )
```

#### 4.5.3 PNP BJT Model Syntax

```
.model modelname PNP ( parameters )
```

#### 4.5.4 Lateral PNP BJT Model Syntax

```
.model modelname LPNP ( parameters )
```

#### 4.5.5 BJT Model Parameters

The symbols ‘×’ and ‘÷’ in the Area column means that the specified parameter should be multiplied or divided by the *area* factor respectively.

Name	Description	Units	Default	Area
IS	Transport saturation current	A	1e-16	∞
BF	Ideal maximum forward beta		100	
NF	Forward current emission coefficient		1.0	
VA, VAF, VA	Forward Early voltage	V	∞	
IK, IKF, IK	Corner for forward beta high current roll-off	A	∞	∞
ISE	B-E leakage saturation current	A	0	∞
NE	B-E leakage emission coefficient		1.5	
BR	Ideal maximum reverse beta		1	
NR	Reverse current emission coefficient		1	

Name	Description	Units	Default	Area
VAR	Reverse Early voltage	V	$\infty$	
IKR	Corner for reverse beta high current roll-off	A	$\infty$	$\infty$
ISC	B-C leakage saturation current	A	0	$\infty$
NC	B-C leakage emission coefficient		2	
NK, NKF			0.5	
RB	Zero bias base resistance	$\Omega$	0	
IRB	Current at which base resistance falls halfway to its minimum value	A	$\infty$	$\infty$
RBM	Minimum base resistance at high currents	$\Omega$	RB	
RE	Emitter resistance	$\Omega$	0	
RC	Collector resistance	$\Omega$	0	
CJE	B-E zero-bias depletion capacitance	F	0	$\infty$
VJE, PE	B-E built in potential	V	0.75	
MJE, ME	B-E junction exponential factor		0.33	
TF	Ideal forward transit time	Sec.	0	
XTF	Coefficient for bias dependence of TF		0	
VTF	Voltage describing VBC dependence of TF	V	$\infty$	
ITF	High-current parameter for effect on TF	A	0	$\infty$
PTF	Excess phase at freq=1.0/(TF $\times$ 2 $\pi$ )	degree	0	
CJC	B-C zero-bias depletion capacitance	F	0	$\infty$
VJC, PC	B-C built-in potential	V	0.75	
MJC, MC	B-C junction exponential factor		0.33	
XCJC	Fraction of B-C depletion capacitance connected to internal base node		1	
TR	Ideal reverse transit time	Sec.	0	
ISS	Substrate diode saturation current	A	0	$\infty$
NS	Substrate diode emission coefficient		1	
CJS, CCS	Zero-bias collector substrate capacitance	F	0	$\infty$
VJS, PS	Substrate junction built-in potential	V	0.75	
MJS, MS	Substrate junction exponential factor		0	

Name	Description	Units	Default	Area
XTB	Forward and reverse beta temperature exponent		0	
EG	Energy gap	eV	1.11	
XTI	Temperature exponent for effect on IS		3	
FC	Coefficient for forward-bias depletion capacitance formula		0.5	
TNOM, TREF, t_measured	Reference temperature; the temperature at which the model parameters were measured	C	27	
T_ABS	If specified, defines the absolute model temperature overriding the global temperature defined using .TEMP	C	-	
T_REL_ GLOBAL	Offsets global temperature defined using .TEMP. Overridden by T_ABS	C	0	
KF	Flicker noise coefficient		0	
AF	Flicker noise exponent		1.0	
EF	Flicker noise exponent		1.0	
KFR	Reverse flicker noise coefficient		KF	
AFR	Reverse flicker noise exponent		AF	
EFR	Reverse flicker noise exponent		EF	
NOISMOD	Model selector. 1 (default) selects a corrected model for base shot and flicker noise. See to 0 for compatibility with earlier versions and other simulators		1	
VO		V	10.0	
QCO	Epitaxial region charge factor	coulomb	0.0	$\infty$
QUASIMOD	Quasi saturation temperature flag: QUASIMOD=0: no temperature dependence QUASIMOD=1: temperature dependence enabled		0	
RCO	Epitaxial region resistance. Set to non-zero to enable quasi saturation model		0.0	
GAMMA	Epitaxial region doping factor		1e-11	
VG	Quasi saturation extrapolated bandgap voltage at 0K	V	1.206	
D	Quasi saturation temp coeff for scattering limited hole carrier velocity		NPN: 0.87 PNP: :0.52	

Name	Description	Units	Default	Area
CN	Quasi saturation temp coeff for hole mobility		NPN: 2.42  PNP: 2.20	
NEPI			1.0	
SUBS	If set to -1, device is lateral		1.0	
TRE1	First order temperature coefficient, RE		0.0	
TRE2	Second order temperature coefficient, RE		0.0	
TRB1, TRB	First order temperature coefficient, RB		0.0	
TRB2	Second order temperature coefficient, RB		0.0	
TRM1	First order temperature coefficient, RBM		0.0	
TRM2	Second order temperature coefficient, RBM		0.0	
TRC1, TRC	First order temperature coefficient, RC		0.0	
TRC2	Second order temperature coefficient		0.0	

#### 4.5.6 Hspice Temperature Parameters

The parameters defined in the following table are temperature coefficients and apply if the Hspice temperature model is enabled. This is the case if one or more of the following parameters are defined in the .MODEL statement:

TLEV, TLEVC, TIKF1, TIKF2, TIKR1, TIKR2, TIRB1, TIRB2.

If none of these parameters are specified, the standard (SPICE) temperature model is enabled and the following parameters have no effect.

Name	Description	Units	Default
TLEV	Temperature selector. Valid values are 0, 1, 2 or 3.		
TLEVC	Capacitance temperature selector. Valid values are 0, 1, 2 and 3		
TIKF1	First order temperature coefficient, IKF		
TIKF2	Second order temperature coefficient, IKF		
TIKR1	First order temperature coefficient, IKR		
TIKR2	Second order temperature coefficient, IKR		
TIRB1	First order temperature coefficient, IRB		
TIRB2	Second order temperature coefficient, IRB		
TIS1	First order temperature coefficient, IS. (TLEV=3)		
TIS2	Second order temperature coefficient, IS. (TLEV=3)		



Name	Description	Units	Default
TBF1	First order temperature coefficient, BF		
TBF2	Second order temperature coefficient, BF		
TBR1	First order temperature coefficient, BR		
TBR2	Second order temperature coefficient, BR		
TISE1	First order temperature coefficient, ISE. (TLEV=3)		
TISE2	Second order temperature coefficient, ISE. (TLEV=3)		
TISC1	First order temperature coefficient, ISC. (TLEV=3)		
TISC2	Second order temperature coefficient, ISC. (TLEV=3)		
TISS1	First order temperature coefficient, ISS. (TLEV=3)		
TISS2	Second order temperature coefficient, ISS. (TLEV=3)		
TVAF1	First order temperature coefficient, VAF		
TVAF2	Second order temperature coefficient, VAF		
TVAR1	First order temperature coefficient, VAR		
TVAR2	Second order temperature coefficient, VAR		
TITF1	First order temperature coefficient, ITF		
TITF2	Second order temperature coefficient, ITF		
TTF1	First order temperature coefficient, TF		
TTF2	Second order temperature coefficient, TF		
TTR1	First order temperature coefficient, TR		
TTR2	Second order temperature coefficient, TR		
TNF1	First order temperature coefficient, NF		
TNF2	Second order temperature coefficient, NF		
TNR1	First order temperature coefficient, NR		
TNR2	Second order temperature coefficient, NR		
TNE1	First order temperature coefficient, NE		
TNE2	Second order temperature coefficient, NE		
TNC1	First order temperature coefficient, NC		
TNC2	Second order temperature coefficient, NC		
TNS1	First order temperature coefficient, NS		
TNS2	Second order temperature coefficient, NS		
TMJE1	First order temperature coefficient, MJE		
TMJE2	Second order temperature coefficient, MJE		
TMJC1	First order temperature coefficient, MJC		
TMJC2	Second order temperature coefficient, MJC		
TMJS1	First order temperature coefficient, MJS		
TMJS2	Second order temperature coefficient, MJS		
TVJE	VJE temperature coefficient. (TLEVC $\neq$ 0)		
TVJC	VJC temperature coefficient. (TLEVC $\neq$ 0)		
TVJS	VJS temperature coefficient. (TLEVC $\neq$ 0)		
CTE	CJE temperature coefficient. (TLEVC $\neq$ 0)		

Name	Description	Units	Default
CTC	CJC temperature coefficient. (TLEVC $\neq$ 0)		
CTS	CJS temperature coefficient. (TLEVC $\neq$ 0)		

### 4.5.7 Notes

The bipolar junction transistor model in SPICE is an adaptation of the integral charge control model of Gummel and Poon.

This modified Gummel-Poon model extends the original model to include several effects at high bias levels. The model will automatically simplify to the simpler Ebers-Moll model when certain parameters are not specified.

The dc model is defined by the parameters IS, BF, NF, ISE, IKF, and NE which determine the forward current gain characteristics, IS, BR, NR, ISC, IKR, and NC which determine the reverse current gain characteristics, and VAF and VAR which determine the output conductance for forward and reverse regions. Three ohmic resistances RB, RC, and RE are included, where RB can be high current dependent. Base charge storage is modelled by forward and reverse transit times, TF and TR, the forward transit time TF being bias dependent if desired, and non-linear depletion layer capacitances which are determined by CJE, VJE, and MJE for the B-E junction, CJC, VJC, and MJC for the B-C junction and CJS, VJS, and MJS for the C-S (Collector-Substrate) junction. The temperature dependence of the saturation current, IS, is determined by the energy-gap, EG, and the saturation current temperature exponent, XTI. Additionally base current temperature dependence is modelled by the beta temperature exponent XTB in the new model.

This implementation includes further enhancements to model quasi-saturation effects. This is governed by the model parameters RCO, QCO, GAMMA and for temperature dependence, QUASI-MOD, VG, D and CN. The quasi-saturation model is compatible with PSpice. Hspice models may be accommodated by setting RC to zero and RCO to the value of RC in the Hspice model.

### References

The Quasi-saturation model was developed from the following paper:

George M. Kull, Laurence W. Nagel, Shih-Wuu Lee, Peter Lloyd, E. James Prendergast and Heinz Dirks, "A Unified Circuit Model for Bipolar Transistors Including Quasi-Saturation Effects". IEEE Transactions on Electron Devices, Vol. ED-32, No 6 June 1985, pages 1103-1113

## 4.6 Bipolar Junction Transistor ( VBIC without self heating)

### 4.6.1 Netlist Entry

```
Qxxxx collector base emitter [substrate] modelname [M=multiplier] [AREA|SCALE=area]
```

<i>collector</i>	Collector node name
<i>base</i>	Base node name
<i>emitter</i>	Emitter node name
<i>substrate</i>	Substrate node name

<i>modelname</i>	Name of model. Must begin with a letter but can contain any character except whitespace and ‘:’.
<i>multiplier</i>	Device scale. Has an identical effect as putting multiplier devices in parallel.
<i>area</i>	Scales certain model parameters as described in the parameter table under Area column. A $\times$ entry means the parameter is multiplied by the area while a $\div$ means the parameter is divided by the area.

### 4.6.2 Model Syntax

```
.MODEL modelname NPN|PNP LEVEL=4 parameters
```

### 4.6.3 Model Parameters

Name	Description	Units	Default	Area
TNOM/TREF	Nominal ambient temperature	Celsius	27	
RCX	Extrinsic collector resistance	Ohms	0.0	$\div$
RCI	Intrinsic collector resistance	Ohms	0.0	$\div$
VO	Epi drift saturation voltage		0.0	
GAMM	Epi doping parameter		0.0	
HRCF	High-current RC factor		1.0	
RBX	Extrinsic base resistance		0.0	$\div$
RBI	Intrinsic base resistance		0.0	$\div$
RE	Emitter resistance		0.0	$\div$
RS	Substrate resistance		0.0	$\div$
RBP	Parasitic base resistance		0.0	$\div$
IS	Transport saturation current		1.0E-16	$\times$
NF	Forward emission coefficient		1.0	
NR	Reverse emission coefficient		1.0	
FC	Forward bias junction capacitance threshold		0.9	
CBE0/CBE0	Base-emitter small signal capacitance		0.0	$\times$
CJE	Base-emitter zero-bias junction capacitance		0.0	$\times$
PE	Base-emitter grading coefficient		0.75	
ME	Base-emitter junction exponent		0.33	
AJE	Base-emitter capacitance smoothing factor		-0.5	
CBC0/CBC0	Extrinsic base-collector overlap capacitance		0.0	$\times$
CJC	Base-collector zero-bias capacitance		0.0	$\times$
QCO/QC0	Collector charge at zero bias		0.0	$\times$

Name	Description	Units	Default	Area
CJEP	Base-emitter extrinsic zero-bias capacitance		0.0	×
PC	Base-collector grading coefficient		0.75	
MC	Base-collector junction exponent		0.33	
AJC	Base-collector capacitance smoothing factor		-0.5	
CJCP	Base-collector zero-bias extrinsic capacitance		0.0	×
PS	Collector-substrate grading coefficient		0.75	
MS	Collector-substrate junction exponent		0.33	
AJS	Collector-substrate capacitance smoothing factor		-0.5	
IBEI	Ideal base-emitter saturation current		1E-18	×
WBE	Portion of IBEI from Vbei, (1-WBE) from Vbex		1.0	
NEI	Ideal base-emitter emission coefficient		1.0	
IBEN	Non-ideal base-emitter saturation current		0.0	×
NEN	Non-ideal base-emitter emission coefficient		2.0	
IBCI	Ideal base-collector saturation current		1.0E-16	×
NCI	Ideal base-collector emission coefficient		1.0	
IBCN	Non-ideal base-collector saturation current		0.0	×
NCN	Non-ideal base-collector emission coefficient		2.0	
AVC1	Base-collector weak avalanche parameter 1		0.0	
AVC2	Base-collector weak avalanche parameter 2		0.0	
ISP	Parasitic transport saturation current		0.0	×
WSP	Portion of Iccp from Vbep, (1-WSP) from Vbci		1.0	
NFP	Parasitic forward emission coefficient		1.0	
IBEIP	Ideal parasitic base-emitter saturation current		0.0	×

Name	Description	Units	Default	Area
IBENP	Non-ideal parasitic base-emitter saturation current		0.0	×
IBCIP	Ideal parasitic base-collector saturation current		0.0	×
NCIP	Ideal parasitic base-collector emission coefficient		1.0	
IBCNP	Non-ideal parasitic base-collector saturation current		0.0	×
NCNP	Non-ideal parasitic base-collector emission coefficient		2.0	
VEF	Forward Early voltage (0=infinity)		0.0	
VER	Reverse Early voltage (0=infinity)		0.0	
IKF	Forward knee current, (0=infinity)		0.0	×
IKR	Reverse knee current, (0=infinity)		0.0	×
IKP	Parasitic knee current (0=infinity)		0.0	×
TF	Forward transit time		0.0	
QTF	Variation of TF with base width modulation		0.0	
XTF	Coefficient of TF bias dependence		0.0	
VTF	Coefficient of TF dependence on Vbc		0.0	
ITF	Coefficient of TF dependence of Icc		0.0	
TR	Ideal reverse transit time		0.0	
TD	Forward excess phase delay time		0.0	
KFN	Flicker noise coefficient		0.0	
AFN	Flicker noise exponent		1.0	
BFN	Flicker noise frequency exponent		1.0	
XRE	Temperature exponent of emitter resistance		0.0	
XRB	Temperature exponent of base resistance		0.0	
XRC	Temperature exponent of collector resistance		0.0	
XRS	Temperature exponent of substrate resistance		0.0	
XV0/XV0	Temperature exponent of Vo		0.0	
EA	Activation energy for IS		1.12	

Name	Description	Units	Default	Area
EAIE	Activation energy for IBEI		1.12	
EAIC	Activation energy for IB-CI/IBEIP		1.12	
EAIS	Activation energy for IBCIP		1.12	
EANE	Activation energy for IBEN		1.12	
EANC	Activation energy for IBC-N/IBENP		1.12	
EANS	Activation energy for IBCNP		1.12	
XIS	Temperature exponent of Is		3.0	
XII	Temperature exponent of IBEI/IB-CI/IBEIP/IBCIP		3.0	
XIN	Temperature exponent of IBEN/IBC-N/IBENP/IBCNP		3.0	
TNF	Temperature coefficient of NF		0.0	
TAVC	Temperature coefficient of AVC		0.0	

#### 4.6.4 Notes

The VBIC model is only available with *Elite* versions.

The Vertical Bipolar Inter-Company (VBIC) model is an advanced bipolar junction transistor model. This is the 4-terminal non-thermal version. There is also a version that supports self-heating effects and has 5 terminals, see “[Bipolar Junction Transistor \(VBIC with self heating\)](#)” on [page 56](#).

For more information about VBIC, please refer to this link:

*VBIC Reference*

## 4.7 Bipolar Junction Transistor (VBIC with self heating)

### 4.7.1 Netlist Entry

```
Qxxxx collector base emitter substrate thermal_node modelname
[M=multiplier] [AREA|SCALE=area]
```

<i>collector</i>	Collector node name
<i>base</i>	Base node name
<i>emitter</i>	Emitter node name
<i>substrate</i>	Substrate node name
<i>thermal_node</i>	See notes
<i>modelname</i>	Name of model. Must begin with a letter but can contain any character except whitespace and ‘.’.
<i>multiplier</i>	Device scale. Has an identical effect as putting <i>multiplier</i> devices in parallel.

*area* Scales certain model parameters as described in the parameter table under Area column. A  $\infty$  entry means the parameter is multiplied by the area while a  $\div$  means the parameter is divided by the area.

### 4.7.2 Model Syntax

```
.MODEL modelname NPN|PNP LEVEL=1004 parameters
```

### 4.7.3 Model Parameters

Model parameters are identical to the non-thermal version except for the addition of the following:

Name	Description	Units	Default	Area
RTH	Thermal resistance		0.0	$\div$
CTH	Thermal capacitance		0.0	$\times$

### 4.7.4 Notes

The VBIC model is only available with *Elite* versions.

This model is the same as the VBIC non-thermal model except for the addition of self-heating effects. Use the non-thermal version if you do not need self-heating as its implementation is simpler and will run faster.

The *thermal\_node* may be used to connect external thermal networks to model thermal flow. Power in watts is represented by current and temperature rise in Kelvin is represented by the voltage. Note that the voltage is temperature rise above the simulation temperature, not an absolute value.

## 4.8 Bipolar Junction Transistor (MEXTRAM)

See “NXP Compact Models” on page 123.

## 4.9 Bipolar Junction Transistor (HICUM)

### 4.9.1 Netlist Entry

```
Qxxxx collector base emitter [substrate] modelname
```

Where:

<i>collector</i>	Collector node
<i>base</i>	Base node
<i>emitter</i>	Emitter node
<i>substrate</i>	Substrate node
<i>modelname</i>	Model name as used with .MODEL statement

### 4.9.2 NPN Model Syntax

```
.MODEL modelname NPN LEVEL=8 parameters
```

OR

```
.MODEL modelname HICUM_211 PNP=0 parameters
```

### 4.9.3 PNP Model Syntax

```
.MODEL modelname PNP LEVEL=8 parameters
```

OR

```
.MODEL modelname HICUM_211 PNP=1 parameters
```

### 4.9.4 Notes

The model provided is “Level 2 version 2.11”.

The model was implemented from Verilog-A code. It has received only minor changes from the original supplied by the developers. These changes are to implement PNP devices and to overcome a problem in the original model whereby it is possible for it to converge to an erroneous state.

The SIMetrix implementation of this model has been tested using the benchmark results provided by the developers. The majority of the tests showed a match of better than 0.1%. A few were over 1% with one deviating by 7%. These were investigated and it was found that the reference data was in error probably because of insufficient convergence tolerance.

## 4.10 Capacitor

### 4.10.1 Netlist Entry

```
Cxxxx n1 n2 [model_name] value [IC=initial_condition] [TEMP=local_temp]
      [TC1=tc1] [TC2=tc2] [VC1=vc1] [VC2=vc2] [BRANCH=0|1] [M=mult] [DTEMP=dtemp]
      [ESR=esr]
```

<i>n1</i>	Node 1
<i>n2</i>	Node 2
<i>model_name</i>	(Optional) Name of model. Must begin with a letter but can contain any character except whitespace and period ‘.’
<i>value</i>	Capacitance (Farads)
<i>initial_condition</i>	Initial voltage if UIC specified on <a href="#">.TRAN</a> statement.
<i>local_temp</i>	Capacitor temperature (°C)
<i>tc1</i>	First order temperature coefficient
<i>tc2</i>	Second order temperature coefficient
<i>vc1</i>	First order voltage coefficient
<i>vc2</i>	Second order voltage coefficient



BRANCH	May be 0 or 1. 0 is the default. This parameter determines the internal formulation of the capacitor and affects how the IC parameter is implemented. When BRANCH=0, the capacitor looks like an open circuit during the DC operating point and the IC parameter has no effect unless UIC is specified for a transient analysis. If BRANCH=1, the capacitor looks like a voltage source during dc operating point with a magnitude equal to the value of the IC parameter. BRANCH=1 makes it possible to specify circuit startup conditions. See “ <a href="#">Alternative Initial Condition Implementations</a> ” on page 202 for an example.
<i>mult</i>	Device multiplier. Equivalent to putting <i>mult</i> devices in parallel.
<i>dtemp</i>	Differential temperature. Similar to <i>local_temp</i> but is specified relative to circuit temperature. If both TEMP and DTEMP are specified, TEMP takes precedence.
<i>esr</i>	Effective series resistance. If non-zero (the default value), a resistor of value <i>esr</i> will be connected in series with the capacitor. The resulting implementation of a series RC network is more efficient and offers better convergence than using a separate R and C. This is especially the case if the capacitor has a high value and is non-grounded.  <b>Important:</b> this resistor is noiseless; if the noise in the ESR is important in your design, you should use a separate resistor and omit this parameter in the capacitor.

#### 4.10.2 Model Syntax

```
.model modelname CAP ( parameters )
```

#### 4.10.3 Model Parameters

Name	Description	Units	Default
C	Capacitor multiplier		1
TC1	First order temperature coefficient	1/°C	0
TC2	Second order temperature coefficient	1/°C <sup>2</sup>	0
VC1	First order voltage coefficient	Volt-1	0
VC2	Second order voltage coefficient	Volt-2	0
TNOM, T_MEASURED	Reference temperature; the temperature at which the model parameters were measured	C	27
T_ABS	If specified, defines the absolute model temperature overriding the global temperature defined using .TEMP	C	-
T_REL_GLOBAL	Offsets global temperature defined using .TEMP. Overridden by T_ABS	C	0.0

## 4.11 Current Controlled Current Source

### 4.11.1 Netlist Entry

#### Linear Source

```
Fxxxx nout+ nout- vc current_gain
```

nout+	Positive output node
nout-	Negative output node
vc	Controlling voltage source
current_gain	Output current/Input current

SPICE2 polynomial sources are also supported in order to maintain compatibility with commercially available libraries for IC's. (Most operational amplifier models for example use several polynomial sources). In general, however the arbitrary source (see [“Arbitrary Source” on page 42](#)) is more flexible and easier to use.

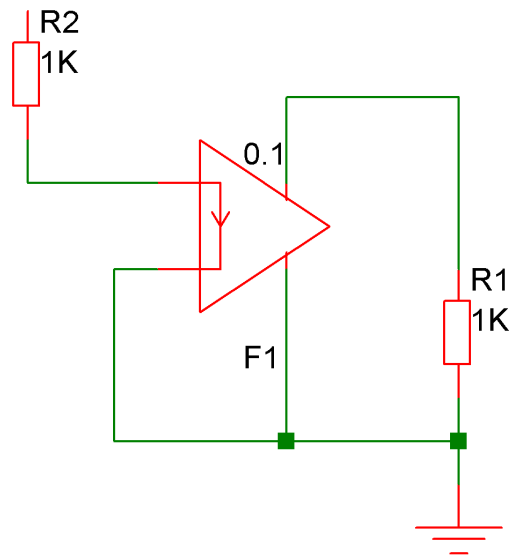
#### Polynomial Source

```
Fxxxx nout+ nout- POLY( num_inputs ) vc1 vc2 ...
+ polynomial_specification
```

<i>vc1, vc2</i>	Controlling voltage sources
<i>num_inputs</i>	Number of controlling currents for source.
<i>polynomial_specification</i>	See <a href="#">“Polynomial Specification” on page 61</a> .

The specification of the controlling voltage source or source requires additional netlist lines. The schematic netlister automatically generates these for the four terminal device supplied in the symbol library.

### 4.11.2 Example



In the above circuit, the current in the output of F1 (flowing from top to bottom) will be 0.1 times the current in R2.

### 4.11.3 Polynomial Specification

The following is an extract from the SPICE2G.6 user manual explaining polynomial sources.

SPICE allows circuits to contain dependent sources characterised by any of the four equations

$$i=f(v)$$

$$v=f(v)$$

$$i=f(i)$$

$$v=f(i)$$

where the functions must be polynomials, and the arguments may be multidimensional. The polynomial functions are specified by a set of coefficients  $p0, p1, \dots, pn$ . Both the number of dimensions and the number of coefficients are arbitrary. The meaning of the coefficients depends upon the dimension of the polynomial, as shown in the following examples:

Suppose that the function is one-dimensional (that is, a function of one argument). Then the function value  $fv$  is determined by the following expression in  $fa$  (the function argument):

$$fv = p0 + (p1.f a) + (p2.f a^2) + (p3.f a^3) + (p4.f a^4) + (p5.f a^5) + \dots$$

Suppose now that the function is two-dimensional, with arguments  $fa$  and  $fb$ . Then the function value  $fv$  is determined by the following expression:

$$fv = p0 + (p1.f a) + (p2.f b) + (p3.f a^2) + (p4.f a.f b) + (p5.f b^2) \\ + (p6.f a^3) + (p7.f a^2.f b) + (p8.f a.f b^2) + (p9.f b^3) + \dots$$

Consider now the case of a three-dimensional polynomial function with arguments  $fa$ ,  $fb$ , and  $fc$ . Then the function value  $fv$  is determined by the following expression:

$$fv = p0 + (p1.f a) + (p2.f b) + (p3.f c) + (p4.f a^2) + (p5.f a.f b) + (p6.f a.f c) + (p7.f b^2) + (p8.f b.f c) \\ + (p9.f c^2) + (p10.f a^3) + (p11.f a^2.f b) + (p12.f a^2.f c) + (p13.f a.f b^2) + (p14.f a.f b.f c) \\ + (p15.f a.f c^2) + (p16.f b^3) + (p17.f b^2.f c) + (p18.f b.f c^2) + (p19.f c^3) + (p20.f a^4) + \dots$$

**Note** If the polynomial is one-dimensional and exactly one coefficient is specified, then SPICE assumes it to be  $p1$  (and  $p0 = 0.0$ ), in order to facilitate the input of linear controlled sources.

## 4.12 Current Controlled Voltage Source

### 4.12.1 Netlist Entry

#### Linear Source

```
Hxxxx nout+ nout- vc transresistance
```

<i>nout+</i>	Positive output node
<i>nout-</i>	Negative output node
<i>vc</i>	Controlling voltage source
<i>transresistance</i>	Output current/Input current ( $\Omega$ )

SPICE2 polynomial sources are also supported in order to maintain compatibility with commercially available libraries for IC's. (Most Op-amp models use several polynomial sources). In general, however the arbitrary source is more flexible and easier to use.

#### Polynomial Source

```
Hxxxx nout+ nout- POLY( num_inputs ) vc1 vc2 ...
+ polynomial_specification
```

<i>vc1, vc2</i>	Controlling voltage sources
<i>num_inputs</i>	Number of controlling currents for source.
<i>polynomial_specification</i>	See <a href="#">“Polynomial Specification”</a> on page 61.

The specification of the controlling voltage source or source requires additional netlist lines. The schematic netlister automatically generates these for the four terminal device supplied in the symbol library.

## 4.13 Current Source

### 4.13.1 Netlist Entry

```
Ixxxx n+ n- [DC dcvalue] [AC magnitude [phase]] [transient_spec]
```

<i>n+</i>	Positive node												
<i>n-</i>	Negative node												
<i>dcvalue</i>	Value of source for dc operating point analysis												
<i>magnitude</i>	AC magnitude for AC sweep analysis.												
<i>phase</i>	phase for AC sweep analysis												
<i>transient_spec</i>	Specification for time varying source. Can be one of following: <table> <tr> <td>Pulse</td> <td>see <a href="#">“Pulse Source” on page 110</a></td> </tr> <tr> <td>Piece wise linear</td> <td>see <a href="#">“Piece-Wise Linear Source” on page 111</a></td> </tr> <tr> <td>Sine</td> <td>see <a href="#">“Sinusoidal Source” on page 113</a></td> </tr> <tr> <td>Exponential</td> <td>see <a href="#">“Exponential Source” on page 114</a></td> </tr> <tr> <td>Single frequency FM</td> <td>see <a href="#">“Single Frequency FM” on page 115</a></td> </tr> <tr> <td>Extended PWL Source</td> <td>see <a href="#">“Extended PWL Source” on page 115</a></td> </tr> </table>	Pulse	see <a href="#">“Pulse Source” on page 110</a>	Piece wise linear	see <a href="#">“Piece-Wise Linear Source” on page 111</a>	Sine	see <a href="#">“Sinusoidal Source” on page 113</a>	Exponential	see <a href="#">“Exponential Source” on page 114</a>	Single frequency FM	see <a href="#">“Single Frequency FM” on page 115</a>	Extended PWL Source	see <a href="#">“Extended PWL Source” on page 115</a>
Pulse	see <a href="#">“Pulse Source” on page 110</a>												
Piece wise linear	see <a href="#">“Piece-Wise Linear Source” on page 111</a>												
Sine	see <a href="#">“Sinusoidal Source” on page 113</a>												
Exponential	see <a href="#">“Exponential Source” on page 114</a>												
Single frequency FM	see <a href="#">“Single Frequency FM” on page 115</a>												
Extended PWL Source	see <a href="#">“Extended PWL Source” on page 115</a>												

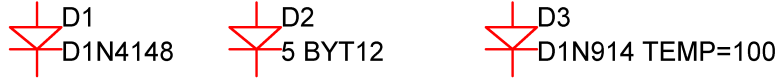
## 4.14 Diode - Level 1 and Level 3

### 4.14.1 Netlist Entry

```
Dxxxx n+ n- model_name [area] [OFF] [IC=vd] [TEMP=local_temp]
+ [PJ=periphery] [L=length] [W=width] [M=mult] [DTEMP=dtemp]
```

<i>n+</i>	Anode
<i>n-</i>	Cathode
<i>model_name</i>	Name of model defined in a <a href="#">.MODEL</a> statement. Must begin with a letter but can contain any character except whitespace and ‘:’.
<i>area</i>	Area multiplying factor. Area scales up the device. E.g. an area of 3 would make the device behave like 3 diodes in parallel. Default is 1.
OFF	Instructs simulator to calculate operating point analysis with device initially off. This is used in latching circuits such as thyristors and bistables to induce a particular state. See <a href="#">“OP” on page 214</a> for more details.
<i>vd</i>	Initial condition for diode voltage. This only has an effect if the UIC parameter is specified on the <a href="#">.TRAN</a> statement.
<i>local_temp</i>	Local temperature. Overrides specification in <a href="#">.OPTIONS</a> or <a href="#">.TEMP</a> statements.
<i>periphery</i>	Level 3 only. Junction periphery used for calculating sidewall effects.
<i>length</i>	Level 3 only. Used to calculate area. See below.
<i>width</i>	Level 3 only. Used to calculate area. See below.
<i>mult</i>	Device multiplier. Equivalent to putting <i>mult</i> devices in parallel.
<i>dtemp</i>	Differential temperature. Similar to <i>local_temp</i> but is specified relative to circuit temperature. If both TEMP and DTEMP are specified, TEMP takes precedence.

### 4.14.2 Examples



### 4.14.3 Diode Model Syntax

```
.model modelname D ( LEVEL=[1|3] parameters )
```

### 4.14.4 Diode Model Parameters - Level = 1

The symbols '×' and '÷' in the Area column means that the specified parameter should be multiplied or divided by the *area* factor respectively.

Name	Description	Units	Default	Area
IS	Transport saturation current	A	1e-14	×
ISR	Recombination current parameter	A	0	×
N	Emission coefficient		1	
NR	Emission Coefficient for ISR		2	
IKF	High injection knee current	A	∞	×
RS	Series resistance	Ω	0	÷
TT	Transit time	sec	0	
CJO or CJ0	Zero bias junction capacitance	F	0	×
VJ	Junction potential	V	1	
M	Grading coefficient		0.5	
EG	Energy gap	eV	1.11	
XTI	Saturation current temperature exponent		3	
KF	Flicker noise coefficient		0	
AF	Flicker noise exponent		1	
FC	Forward bias depletion capacitance coefficient		0.5	
BV	Reverse breakdown voltage	V	∞	
IBV	Current at breakdown voltage	A	1e-10	×
TNOM, T_MEASURED	Parameter measurement temperature	°C	27	

Name	Description	Units	Default	Area
T_ABS	If specified, defines the absolute model temperature overriding the global temperature defined using .TEMP	°C	-	
T_REL_GLOBAL	Offsets global temperature defined using .TEMP. Overridden by T_ABS	°C	0	
TRS1	First order tempco RS	/°C	0	
TRS2	Second order tempco RS	/°C <sup>2</sup>	0	
TBV1	First order tempco BV	/°C	0.0	
TBV2	Second order tempco BV	/°C <sup>2</sup>	0.0	
NBV	Reverse breakdown ideality factor		1.0	
NBVL	Low-level reverse breakdown ideality factor		1.0	
IBVL	Low-level reverse breakdown knee current	Amp	0.0	×
TIKF	IKF temperature coefficient		0.0	

**Notes** The dc characteristics of the diode are determined by the parameters IS, N, ISR, NR and IKF. An ohmic resistance, RS, is included. Charge storage effects are modelled by a transit time, TT, and a non-linear depletion layer capacitance which is determined by the parameters CJO, VJ, and M. The temperature dependence of the saturation current is defined by the parameters EG, the energy and XTI, the saturation current temperature exponent. Reverse breakdown is modelled by an exponential increase in the reverse diode current and is determined by the parameters BV and IBV (both of which are positive numbers).

#### 4.14.5 Diode Model Parameters - Level = 3

Name	Description	Units	Default
AF	Flicker noise exponent		1.0
BV, VB, VAR, VRB	Reverse breakdown voltage	V	∞
CJO, CJ	Zero bias junction capacitance	F	0.0
CJSW, CJP	Zero bias sidewall capacitance	F	0.0
CTA	CJO temp coefficient. (TLEV=1)	°C <sup>-1</sup>	
CTP	CJSW temp coefficient. (TLEV=1)	°C <sup>-1</sup>	
EG	Energy gap	ev	1.11
FC	Forward bias depletion capacitance coefficient		0.5

Name	Description	Units	Default
FCS	Forward bias sidewall capacitance coefficient		0.5
GAP1	7.02e-4 - silicon (old value) 4.73e-4 - silicon 4.56e-4 - germanium 5.41e-4 - gallium arsenide	eV/°	7.02e-4
GAP2	1108 - silicon (old value) 636 - silicon 210 - germanium 204 - gallium arsenide	°	1108
IBV	Current at breakdown voltage	A	1E-3
IKF, IK	High injection knee current	A	∞
IKR	Reverse high injection knee current	A	∞
IS, JS	Saturation current	A	1E-14
ISR	Recombination current	A	0
JSW	Sidewall saturation current	A	0
KF	Flicker noise exponent		0
MJ, M	Grading coefficient		0.5
MJSW	Sidewall grading coefficient		0.33
N, NF	Forward emission coefficient		1.0
NR	Recombination emission coefficient		2.0
PHP	Sidewall built in potential		PB
RS	Series resistance	Ω	0
SHRINK	Shrink factor		1.0
TCV	BV temp coefficient	°C-1	0
TLEV	Temperature model selector. Valid values: 0, 1, 2		0
TLEVC	Temperature model selector. Valid values: 0 or 1		0
TNOM, TREF	Parameter measurement temperature		27
TPB	VJ temp coefficient (TLEVC=1)	V/°C	0.0
TPHP	PHP temp. coefficient (TLEVC=1)	V/°C	0.0
TRS	RS temp. coefficient	°C <sup>-1</sup>	0.0
TT	Transit time	S	0.0
VJ, PB	Built-in potential	V	0.8
XW	Shrink factor		0.0
DCAP	Capacitance model (1 or 2)		1



The parameters CJSW and JSW are scaled by the instance parameter PJ whose default value is 0.0.

If L and W instance parameters are supplied, the diode is scaled by the factor:  $M*(L*SHRINK-XW)*(W*SHRINK-XW)$  otherwise it is scaled by  $M*AREA$ .

M and AREA are instance parameters which default to 1.0

## 4.15 Diode - Soft Recovery

### 4.15.1 Netlist Entry

```
Dxxxx n+ n- model_name [TEMP=local_temp]
```

<i>n+</i>	Anode
<i>n-</i>	Cathode
<i>model_name</i>	Name of model defined in a <a href="#">MODEL</a> statement. Must begin with a letter but can contain any character except whitespace and ‘.’.
<i>local_temp</i>	Local temperature. Overrides specification in <a href="#">.OPTIONS</a> or <a href="#">.TEMP</a> statements.

### 4.15.2 Diode Model Syntax

```
.model modelname SRDIO ( parameters )
```

### 4.15.3 Soft Recovery Diode Model Parameters

Name	Description	Units	Default
CJO	Zero bias junction capacitance	F	0.0
EG	Energy gap	ev	1.11
FC	Forward bias depletion capacitance coefficient		0.5
IS	Saturation current	A	1E-15
MJ	Grading coefficient		0.5
N	Forward emission coefficient		1.0
RS	Series resistance	$\Omega$	0
TNOM	Parameter measurement temperature		27
TT	Diffusion transit time	S	5e-6
TAU	Minority carrier lifetime		1e-5
VJ	Built-in potential	V	1
XTI	Saturation current temperature exponent		3

### 4.15.4 Basic Equations

The model is based on the paper “A Simple Diode Model with Reverse Recovery” by Peter Lauritzen and Cliff Ma. (See references). The model’s governing equations are quite simple and are

as follows:

$$i_d = \frac{q_e - q_m}{TT}$$

$$\frac{dq_m}{dt} + \frac{q_m}{TAU} - \frac{q_e - q_m}{TT} = 0$$

$$q_e = IS \cdot TAU \cdot \left( \exp\left(\frac{v_d}{N \cdot V_t}\right) - 1 \right)$$

In addition the model uses the standard SPICE equations for junction capacitance and temperature dependence of IS.

### 4.15.5 References

Peter O. Lauritzen, Cliff L. Ma, *A Simple Diode Model with Reverse Recovery*, IEEE Transactions on Power Electronics, Vol. 6, No 2, pp 188-191, April 1991.

## 4.16 GaAsFET

### 4.16.1 Netlist Entry

```
Zxxxx drain gate source modelname [area] [OFF] [IC=vds, vgs]
```

<i>drain</i>	Drain node
<i>gate</i>	Gate node
<i>source</i>	Source node
<i>modelname</i>	Name of model defined in a .model statement. Must begin with a letter but can contain any character except whitespace and period ‘.’
<i>area</i>	Area multiplying factor. Area scales up the device. E.g. an area of 3 would make the device behave like 3 transistors in parallel. Default is one.
OFF	Instructs simulator to calculate operating point analysis with device initially off. This is used in latching circuits such as thyristors and bistables to induce a particular state. See “ <a href="#">OP</a> ” on <a href="#">page 214</a> for more details.
<i>vds,vgs</i>	Initial conditions for drain-source and gate-source junctions respectively. These only have an effect if the UIC parameter is specified on the .TRAN statement.

### 4.16.2 GaAsFET Model Syntax

```
.model modelname NMF ( parameters )
```

### 4.16.3 GaAsFET Model Parameters

The symbols '×' and '÷' in the Area column means that parameter should be multiplied or divided by the area factor respectively.

Name	Description	Units	Default	Area
VTO	Pinch-off Voltage	V	-2.0	
BETA	Transconductance parameter	A/V <sup>2</sup>	2.5e-3	×
B	Doping tail extending parameter	1/V	0.3	
ALPHA	Saturation voltage parameter	1/V	2	
LAMBDA	Channel length modulation parameter	1/V	0	
RD	Drain ohmic resistance	Ω	0	÷
RS	Source ohmic resistance	Ω	0	÷
CGS	Zero bias gate source capacitance	F	0	×
CGD	Zero bias gate drain capacitance	F	0	×
PB	Gate junction potential	V	1	
IS	Gate p-n saturation current	A	1e-14	×
FC	Forward bias depletion capacitance coefficient		0.5	
KF	Flicker noise coefficient	0		
AF	Flicker noise exponent	1		

**Notes** The GaAsFET model is derived from the model developed by Statz. The DC characteristics are defined by parameters VTO, B and BETA, which determine the variation of drain current with gate voltage, ALPHA, which determines saturation voltage, and LAMBDA, which determines the output conductance. IS determines the gate-source and gate-drain dc characteristics.

Two ohmic resistances are included. Charge storage is modelled by total gate charge as a function of gate-drain and gate-source voltages and is defined by the parameters CGS, CGD and PB.

## 4.17 Inductor (Ideal)

### 4.17.1 Netlist Entry

```
Lxxxx n1 n2 value [IC=init_cond] [BRANCH=0|1]
```

*n1* Node 1

*n2* Node 2

*value* Value in henries

*init\_cond* Initial current in inductor. Only effective if UIC option is specified on .TRAN statement.

BRANCH set to 0 or 1. 1 is default value. This parameter determines the internal formulation of the inductor and affects how the IC parameter is implemented. When BRANCH=1, the inductor looks like a short circuit during DC operating point and the IC parameter has no effect unless UIC is specified for a transient analysis. If BRANCH=0, the inductor looks like a current source during dc operating point with a magnitude equal to the value of the IC parameter. BRANCH=0 makes it possible to specify circuit startup conditions.

#### 4.17.2 See Also

[“Mutual Inductor” on page 117.](#)

## 4.18 Inductor (Saturable)

### 4.18.1 Netlist Entry

```
Lxxxx n1 n2 modelname [N=num_turns] [LE=le] [AE=ae] [UE=ue]
```

<i>n1</i>	Node 1
<i>n2</i>	Node 2
<i>modelname</i>	Model name referring to a .MODEL statement describing the core characteristics. See details below.
<i>num_turns</i>	Number of turns on winding
<i>le</i>	Effective path length of core in metres. Default = PATH/100. PATH is defined in .MODEL.
<i>ae</i>	Effective area of core in metres <sup>2</sup> . Default = AREA/10000 where AREA is define in .MODEL.
<i>ue</i>	Effective permeability of core. Overrides model parameter of the same name.

### 4.18.2 Model format - Jiles-Atherton model with hysteresis

```
.MODEL model_name CORE parameters
```

### 4.18.3 Model format - simple model without hysteresis

```
.MODEL model_name CORENH parameters
```

### 4.18.4 Jiles-Atherton Parameters

Name	Description	Units	Default
PATH	Effective path length	cm	1
C	Domain flexing parameter		0.2
K	Domain anisotropy parameter	amp.m <sup>-1</sup>	500

Name	Description	Units	Default
MS	Magnetisation saturation		1E6
GAP	Air gap (centimetres)	cm	0
GAPM	Air gap (metres)	m	GAP/100
A	Thermal energy parameter	amp.m <sup>-1</sup>	1000
AREA	Effective area	cm <sup>2</sup>	0.1
UE	Effective permeability. Overrides GAP and GAPM if >0. See notes		
AHMODE	Anhysteretic function selector (see notes)		0

#### 4.18.5 Non-hysteresis Model Parameters

Name	Description	Units	Default
PATH	Effective path length	cm	1
MS	Magnetisation saturation		1E6
GAP	Air gap (centimetres)	cm	0
GAPM	Air gap (metres)	m	GAP/100
A	Thermal energy parameter	amp.m <sup>-1</sup>	1000
AREA	Effective area	cm <sup>2</sup>	0.1
AHMODE	Anhysteretic function selector (see notes)		0

#### 4.18.6 Notes on the Jiles-Atherton model

The Jiles-Atherton model is based on the theory developed by D.C. Jiles and D.L. Atherton in their 1986 paper “Theory of Ferromagnetic Hysteresis”. The model has been modified to correct non-physical behaviour observed at the loop tips whereby the slope of the B-H curve reverses. This leads to non-convergence in the simulator. The modification made is that proposed by Lederer et al. (See references below). Full details of the SIMetrix implementation of this model including all the equations are provided in a technical note. This is located on the install CDROM at Docs/Magnetics/Jiles-Atherton-Model.pdf. This is also available at our web site, please visit [“Further Documentation” on page 41](#) for details.

The AHMODE parameter selects the equation used for the anhysteretic function, that is the non-linear curve describing the saturating behaviour. When set to 0 the function is the same as that used by PSpice. When set to 1 the function is the original equation proposed by Jiles and Atherton. See the Jiles-Atherton-Model.pdf technical note for details.

If the UE parameter is specified either on the device line or in the model, an air gap value is calculated and the parameters GAP and GAPM are ignored. See the Jiles-Atherton-Model.pdf technical note for the formula used.

The parameter names and their default values for the Jiles-Atherton model are compatible with PSpice, but the netlist entry is different.

### 4.18.7 Notes on the non-hysteresis model

This is simply a reduced version of the Jiles-Atherton model with the hysteresis effects removed. The anhysteretic function and the air-gap model are the same as the Jiles-Atherton model.

### 4.18.8 Implementing Transformers

This model describes only a 2 terminal inductor. A transformer can be created using a combination of controlled sources along with a single inductor. The SIMetrix schematic editor uses this method.

The schematic editor provides a means of creating transformers and this uses an arrangement of controlled sources to fabricate a non-inductive transformer. Any inductor can be added to this arrangement to create an inductive transformer. The method is simple and efficient. The following shows how a non-inductive three winding transformer can be created from simple controlled sources:

```
F1 0 n1 E1 1
E1 W1A W1B n1 0 1
F2 0 n1 E2 1
E2 W2A W2B n1 0 1
F3 0 n1 E3 1
E3 W3A W3B n1 0 1
```

Connecting an inductor between n1 and 0 in the above provides the inductive behaviour. This is in fact how the SIMetrix schematic editor creates non-linear transformers.

Note that you cannot use the mutual inductor device with the saturable inductor.

### 4.18.9 Plotting B-H curves

Both models can be enabled to output values for flux density in Tesla and magnetising force in A.m<sup>-1</sup>. To do this, add the following line to the netlist:

```
.KEEP Lxxx#B Lxxx#H
```

Replace Lxxx with the reference for the inductor. (e.g. L23 etc.). You will find vectors with the names Lxxx#B Lxxx#H available for plotting in the waveform viewer.

### 4.18.10 References

1. Theory of Ferromagnetic Hysteresis, DC.Jiles, D.L. Atherton, Journal of Magnetism and Magnetic Materials, 1986 p48-60.
2. On the Parameter Identification and Application of the Jiles-Atherton Hysteresis Model for Numerical Modelling of Measured Characteristics, D Lederer, H Igarashi, A Kost and T Honma, IEEE Transactions on Magnetics, Vol. 35, No. 3, May 1999

## 4.19 Inductor (Table lookup)

### 4.19.1 Netlist Entry

```
Uxxxx n1 n2 model_name [IC=initial_condition] [USEIC=use_ic]
```

<i>n1</i>	node 1
<i>n2</i>	node 2
<i>initial_condition</i>	Initial condition in Amps. Only active if USEIC is non-zero
<i>use_ic</i>	If non-zero, enable initial condition. This will set the current in the inductor to the value of <i>initial_condition</i> during the DC operating point analysis

### 4.19.2 Model syntax

```
.MODEL model_name TABLE_INDUCTOR parameters
```

Name	Description	Units	Default
L	Inductance	1m	H
LTABLE	Saturation table		n/a
ITABLE	Current table	A	n/a
TABLE_SIZE	Number of elements in tables		2
RSERIES	Series resistance	$\Omega$	0.0
RSHUNT	Shunt resistance	$\Omega$	0.0 (sets to INF)
LMIN	Minimum inductance	H	0.0
SMOOTH	Smoothing option (0-3)		0

### Model Example

```
.MODEL TABLE_IND table_inductor L=1 USEIC=0 IC=0
+ RSERIES=0 RSHUNT=0 SMOOTH=2 TABLE_SIZE=7
+ ITABLE=[0, 8.3333, 16.666, 25, 33.3333, 41.666, 50]
+ LTABLE=[3.36e-07, 3.36e-07, 3.34e-07, 3.27e-07, 3.09e-07, 1.86e-07, 4.21e-08]
```

The above example has an inductance of 3.36e-07H at 0A falling to 4.21e-08 at 50A.

### 4.19.3 Boundary Inductance

The inductance for this device is defined by a lookup table over a specific range. However, the behaviour at currents beyond that defined in the table must also be defined. We refer to the inductance as the ‘boundary inductance’. This follows a characteristic of the form:

$$A/(C + i^2) + LMIN/L$$

Where  $A$  and  $C$  are chosen so that the absolute inductance and  $\frac{dL}{di}$  matches the table function at the final point.

### 4.19.4 Smoothing Function

The SMOOTH parameter can be set to an integer between 1 and 4 to select a smoothing function. The following table describes the alternative strategies available:

SMOOTH value	Function
0	No smoothing function is selected. Inductor follows a PWL (piece-wise-linear) characteristic
1	Local cubic. Fits a cubic polynomial between each pair of points such that the gradient at each point is the average of the slope on either side of the point. This is continuous in the first derivative but is not continuous in the second derivative
2	Cubic spline with boundary conditions: lower: $\frac{dL}{di} = 0$ upper: $\frac{d^2L}{di^2} = 0$
3	Cubic spline with boundary conditions: lower: $\frac{dL}{di} = 0$ upper: $\frac{dL}{di} = slope\_of\_final\_segment$

SMOOTH=2 and SMOOTH=3 select a cubic spline function. A cubic spline fits a series of cubic polynomials through all points such that the function is continuous in the first and second derivatives. Cubic splines generally require boundary conditions to be set; that is some condition to define the first and last points. This is the only difference between SMOOTH=2 and SMOOTH=3. SMOOTH=2 usually gives the best results but can, in some situations, result in a positive slope at the join with the boundary inductance function. This cannot be matched to the boundary inductance and in these circumstances the device will fail with the error message:

```
***ERROR*** instance <ref>: Cannot fit spline to table using SMOOTH=2 strategy.
Try using SMOOTH=1 or SMOOTH=3
```

In this case SMOOTH=1 or SMOOTH=3 can be selected.

## 4.20 Insulated Gate Bipolar Transistor

### 4.20.1 Netlist Entry

```
Zxxxx collector gate emitter modelname [AREA=area] [AGD=agd] [KP=kp]
+ [TAU=tau] [WB=wb]
```

<i>collector</i>	Collector node
<i>gate</i>	Gate node
<i>emitter</i>	Emitter node
<i>area</i>	Device area in m <sup>2</sup> (overrides model parameter of the same name)
<i>agd</i>	Gate-drain overlap area in m <sup>2</sup> (overrides model parameter of the same name)
<i>kp</i>	Transconductance (overrides model parameter of the same name)
<i>tau</i>	Ambipolar recombination lifetime (overrides model parameter of the same name)
<i>wb</i>	Base width in metres (overrides model parameter of the same name)



### 4.20.2 Model syntax

```
.MODEL model_name NIGBT parameters
```

Name	Description	Units	Default
AGD	Gate-drain overlap area	m <sup>2</sup>	5E-6
AREA	Device active area	m <sup>2</sup>	1E-5
BVF	Breakdown voltage nonplanar junction factor		1.0
BVN	Avalanche multiplication exponent		4.0
CGS	Gate-source capacitance per unit area	Fcm <sup>-2</sup>	1.24E-8
COXD	Gate-drain overlap oxide capacitance per unit area	Fcm <sup>-2</sup>	3.5E-8
JSNE	Emitter electron saturation current density	Acm <sup>-2</sup>	6.5E-13
KF	Triode region MOSFET transconductance factor		1.0
KP	MOSFET transconductance factor	AV <sup>-2</sup>	0.38
MUN	Electron mobility	cm <sup>-2</sup> (Vs) <sup>-1</sup>	1.5E3
MUP	Hole mobility	cm <sup>-2</sup> (Vs) <sup>-1</sup>	4.5E2
NB	Base doping concentration	cm <sup>-3</sup>	2E14
TAU	Ambipolar recombination lifetime	s	7.1E-6
THETA	Transverse field transconductance factor	V <sup>-1</sup>	0.02
VT	MOSFET channel threshold voltage	V	4.7
VTD	Gate-drain overlap depletion threshold	V	1E-3
WB	Metallurgical base width	m	9.0E-5

### 4.20.3 Notes

The IGBT model is based on the model developed by Allen R. Hefner at the National Institute of Standards and Technology. The parameter names, default values and units have been chosen to be compatible with the PSpice implementation of the same model.

For more information, please refer to:

*Modelling Buffer Layer IGBT's for Circuit Simulation*, Allen R. Hefner Jr, IEEE Transactions on Power Electronics, Vol. 10, No. 2, March 1995

*An Experimentally Verified IGBT Model Implemented in the Saber Circuit Simulator*, Allen R. Hefner, Jr., Daniel M. Diebolt, IEE Transactions on Power Electronics, Vol. 9, No. 5, September 1994

## 4.21 Junction FET

### 4.21.1 Netlist Entry

```
Jxxxx drain gate source modelname [area] [OFF] [IC=vds,vgs]
+ [TEMP=local_temp] [M=mult] [DTEMP=dtemp]
```

<i>drain</i>	Drain node
<i>gate</i>	Gate node
<i>source</i>	Source node
<i>modelname</i>	Name of model defined in a <code>.model</code> statement. Must begin with a letter but can contain any character except whitespace and period <code>∴</code> .
<i>area</i>	Area multiplying factor. Area scales up the device. E.g. an area of 3 would make the device behave like 3 transistors in parallel. Default is 1.
OFF	Instructs simulator to calculate operating point analysis with device initially off. This is used in latching circuits such as thyristors and bistables to induce a particular state. See “ <a href="#">OP</a> ” on page 214 for more details.
<i>vds,vgs</i>	Initial conditions for drain-source and gate-source junctions respectively. These only have an effect if the UIC parameter is specified on the <code>.TRAN</code> statement.
<i>local_temp</i>	Local temperature. Overrides specification in <code>.OPTIONS</code> or <code>.TEMP</code> statements.
<i>mult</i>	Device multiplier. Equivalent to putting <i>mult</i> devices in parallel.
<i>dtemp</i>	Differential temperature. Similar to <i>local_temp</i> but is specified relative to circuit temperature. If both TEMP and DTEMP are specified, TEMP takes precedence.

#### 4.21.2 N Channel JFET: Model Syntax

```
.model modelname NJF ( parameters )
```

#### 4.21.3 P Channel JFET: Model Syntax

```
.model modelname PJF ( parameters )
```

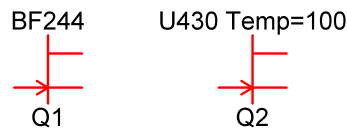
#### 4.21.4 JFET: Model Parameters

The symbols ‘×’ and ‘÷’ in the Area column means that parameter should be multiplied or divided by the area factor respectively.

Name	Description	Units	Default	Area
VTO	Threshold voltage	V	-2.0	
VTOTC	VTO temp coefficient	V/°C	0	
BETA	Transconductance parameter	A/V <sup>2</sup>	1e-4	×
BETATCE	BETA temperature coefficient	%	0	
LAMDA	Channel length modulation parameter	1/V	0	
ALPHA	Impact ionisation coefficient		0	
VK	Impact ionisation knee voltage	V	0	
RS	Source ohmic resistance	Ω	0	÷

Name	Description	Units	Default	Area
CGS	Zero-bias G-S junction capacitance	F	0	÷
CGD	Zero-bias G-D junction capacitance	F	0	÷
M	Grading coefficient		1.0	
PB	Gate junction potential	V	1	
IS	Gate junction saturation current	A	1e-14	×
N	Gate junction emission coefficient		1	
ISR	Recombination current		0	
NR	ISR emission coefficient			
XTI	IS temperature coefficient		3	
KF	Flicker noise coefficient		0	
AF	Flicker noise exponent		1	
FC	Coefficient for forward bias depletion capacitance		0.5	
NLEV	Select noise model		2	
GDSNOI	Channel noise coefficient. Use with NLEV=3		1.0	
TNOM, T_MEASURED	Reference temperature; the temperature at which the model parameters were measured	°C	27	
T_ABS	If specified, defines the absolute model temperature overriding the global temperature defined using .TEMP	°C	-	
T_REL_GLOBAL	Offsets global temperature defined using .TEMP. Overridden by T_ABS	°C	0.0	

#### 4.21.5 Examples



Q2 is a U430 with a local temperature of 100°C.

## 4.22 Lossy Transmission Line

### 4.22.1 Netlist Entry

```
0xxxx p1 n1 p2 n2 modelname [IC=v1,i1,v2,i2]
```

<i>p1</i>	Positive input port 1
<i>n1</i>	Negative input port 1
<i>p2</i>	Positive input port 2
<i>n2</i>	Negative input port 2
<i>modelname</i>	Name of model defined in a <a href="#">.MODEL</a> statement. Must begin with a letter but can contain any character except whitespace and period <code>?</code> .
<i>v1,i1,v2,i2</i>	Initial conditions for voltage at port 1, current at port 1, voltage at port 2 and current at port 2 respectively. These only have an effect if the UIC parameter is specified on the <a href="#">.TRAN</a> statement.

### 4.22.2 Model Syntax

```
.model modelname LTRA ( parameters )
```

### 4.22.3 Model Parameters

Name	Description	Units	Default
R	Resistance/unit length	$\Omega$ /unit length	0.0
L	Inductance/unit length	Henrys/unit length	0.0
G	Conductance/unit length	Siemens(mhos)/unit length	0.0
C	Capacitance/unit length	Farads/unit length	0.0
LEN	Length		Required
REL	Relative rate of change of derivative for breakpoint	1.0	
ABS	Absolute rate of change of derivative for breakpoint	1.0	

The parameters REL and ABS control the way the line is simulated rather than its electrical characteristics. More accurate results (at the expense of simulation time) can be obtained by using lower values.

#### Notes

The uniform RLC/RC/LC/RG transmission line model (LTRA) models a uniform constant-parameter distributed transmission line. The LC case may also be modelled using the lossless transmission line model. The operation of the lossy transmission line model is based on the convolution of the transmission line's impulse responses with its inputs.

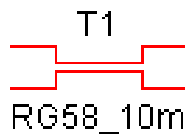
The following types of lines have been implemented:

RLC	Transmission line with series loss only
RC	Uniform RC line
LC	Lossless line
RG	Distributed series resistance and parallel conductance

All other combinations will lead to an error.

REL and ABS are model parameters that control the setting of breakpoints. A breakpoint is a point in time when an analysis is unconditionally performed. The more there are the more accurate the result but the longer it will take to arrive. Reducing REL and/or ABS will yield greater precision.

#### 4.22.4 Example



The above could represent a 10 metre length of RG58 cable. The parameters would be described in a .model statement e.g.

```
.model RG58_10m LTRA(R=0.1 C=100p L=250n LEN=10)
```

## 4.23 MOSFET

### Note

Level 1, 2, 3 and 17 MOSFETs are described in this section. For other devices:

[“BSIM3” on page 85](#)

[“BSIM4” on page 87](#)

[“HiSim HV” on page 88](#)

[“PSP” on page 89](#)

MOS9, MOS11 and other NXP devices see [“NXP Compact Models” on page 123](#)

#### 4.23.1 Netlist Entry

```
Mxxxx drain gate source bulk modelname [L=length] [W=width]
+ [AD=drain_area] [AS=source_area]
+ [PD=drain_perimeter] [PS=source_perimeter]
+ [NRD=drain_squares] [NRS=source_squares]
+ [NRB=bulk_squares]
+ [OFF] [IC=vds,vgs,vbs] [TEMP=local_temp] [M=area]
```

<i>drain</i>	Drain node
<i>gate</i>	Gate node
<i>source</i>	Source node
<i>bulk</i>	Bulk (substrate) node
<i>modelname</i>	Name of model. Must begin with a letter but can contain any character except whitespace and period ‘

(The following 8 parameters are not supported by the level 17 MOSFET model)

<i>length</i>	Channel length (metres).
<i>width</i>	Channel width (metres).
<i>drain_area</i>	Drain area (m <sup>2</sup> ).
<i>source_area</i>	Source area (m <sup>2</sup> ).
<i>drain_perimeter</i>	Drain perimeter (metres).
<i>source_perimeter</i>	Source perimeter (metres).
<i>drain_squares</i>	Equivalent number of squares for drain resistance
<i>source_squares</i>	Equivalent number of squares for source resistance
<i>gate_squares</i>	Equivalent number of squares for gate resistance. Level=3 only
<i>bulk_squares</i>	Equivalent number of squares for gate resistance. Level=3 only
OFF	Instructs simulator to calculate operating point analysis with device initially off. This is used in latching circuits such as thyristors and bistables to induce a particular state. See “ <a href="#">.OP</a> ” on page 214 for more details.
<i>vds, vgs, vbs</i>	Initial condition voltages for drain-source gate-source and bulk(=substrate)-source respectively. These only have an effect if the UIC parameter is specified on the <a href="#">.TRAN</a> statement.
<i>local_temp</i>	Local temperature. Overrides specification in <a href="#">.OPTIONS</a> or <a href="#">.TEMP</a> statements.
<i>dtemp</i>	Differential temperature. Similar to <i>local_temp</i> but is specified relative to circuit temperature. If both TEMP and DTEMP are specified, TEMP takes precedence. Currently implemented only for LEVEL 1,2 and 3.

**Notes** SIMetrix supports four types of MOSFET model specified in the model definition. These are referred to as levels 1, 2, 3 and 7. Levels 1,2, and 3 are the same as the SPICE2 and SPICE3 equivalents. Level 17 is proprietary to SIMetrix. For further information see Level 17 MOSFET parameters below.

#### 4.23.2 NMOS Model Syntax

```
.model modelname NMOS ( level=level_number parameters )
```

#### 4.23.3 PMOS Model Syntax

```
.model modelname PMOS ( level=level_number parameters )
```

## 4.23.4 MOS Levels 1, 2 and 3: Model Parameters

Name	Description	Units	Default	Levels
VTO or VT0	Threshold voltage	V	0.0	all
KP	Transconductance parameter	A/V <sup>2</sup>	2.0e-5	all
GAMMA	Bulk threshold parameter	$\frac{V}{V}$	0.0	all
PHI	Surface potential	V	0.6	all
LAMBDA	Channel length modulation	1/V	0.0	all
RG	Gate ohmic resistance	$\Omega$	0.0	1,3
RD	Drain ohmic resistance	$\Omega$	0.0	all
RS	Source ohmic resistance	$\Omega$	0.0	all
RB	Bulk ohmic resistance	$\Omega$	0.0	3
RDS	Drain-source shunt resistance	$\Omega$	$\infty$	3
CBD	B-D junction capacitance	F	0.0	all
CBS	B-S junction capacitance	F	0.0	all
IS	Bulk junction sat. current	A	1.0e-14	all
PB	Bulk junction potential	V	0.8	all
CGSO	Gate-source overlap capacitance	F/m	0.0	all
CGDO	Gate-drain overlap capacitance	F/m	0.0	all
CGBO	Gate-bulk overlap capacitance	F/m	0.0	all
RSH	Drain and source diffusion resistance	$\Omega/\text{sq.}$	0.0	all
CJ	Zero bias bulk junction bottom capacitance/sq-metre of junction area	F/m <sup>2</sup>	See note	all
MJ	Bulk junction bottom grading coefficient		0.5	all
CJSW	Zero bias bulk junction sidewall capacitance	F/m	0.0	all
MJSW	Bulk junction sidewall grading coefficient		0.5	1
MJSW	as above		0.33	2,3
JS	Bulk junction saturation current/sq-metre of junction area	A/m <sup>2</sup>	0.0	all
JSSW	Bulk p-n saturation sidewall current/length	A/m	0.0	3
TT	Bulk p-n transit time	secs	0.0	3
TOX	Oxide thickness	metre	1e-7	all
NSUB	Substrate doping	1/cm <sup>2</sup>	0.0	all
NSS	Surface state density	1/cm <sup>2</sup>	0.0	all
NFS	Fast surface state density	1/cm <sup>2</sup>	0.0	2,3

Name	Description	Units	Default	Levels
TPG	Type of gate material: +1 opposite. to substrate -1 same as substrate 0 Al gate			all
XJ	Metallurgical junction depth	metre	0.0	2,3
LD	Lateral diffusion	metre	0.0	all
UO	Surface mobility	cm <sup>2</sup> /Vs	600	all
UCRIT	Critical field for mobility	V/cm	0.0	2
UEXP	Critical field exponent in mobility degradation		0.0	2
UTRA	Transverse field coefficient (mobility)		0.0	1,3
VMAX	Maximum drift velocity of carriers	m/s	0.0	2,3
NEFF	Total channel charge (fixed and mobile) coefficient		1.0	2
FC	Forward bias depletion capacitance coefficient		0.5	all
TNOM, T_MEASURED	Reference temperature; the temperature at which the model parameters were measured	°C	27	all
T_ABS	If specified, defines the absolute model temperature overriding the global temperature defined using .TEMP	°C	.TEMP	all
T_REL_GLOBAL	Offsets global temperature defined using .TEMP. Overridden by T_ABS	°C	0.0	all
KF	Flicker noise coefficient		0.0	all
AF	Flicker noise exponent		1.0	all
DELTA	Width effect on threshold voltage		0.0	2,3
THETA	Mobility modulation	1/V	0.0	3
ETA	Static feedback		0.0	3
KAPPA	Saturation field factor		0.2	3
W	Width	metre	DEFW	all
L	Length	metre	DEFL	all
NLEV	Noise model		2	all

#### 4.23.5 CJ Default

If not specified CJ defaults to

$$\sqrt{\epsilon_s q \times \text{NSUB} \times 1e6 / (2 \times \text{PB})}$$

where



$\epsilon_s = 1.03594314e-10$  (permittivity of silicon)

$q = 1.6021918e-19$  (electronic charge)

NSUB, PB model parameters

### 4.23.6 Notes for levels 1, 2 and 3:

The three levels 1 to 3 are as follows:

LEVEL 1	Shichman-Hodges model. The simplest and is similar to the JFET model
LEVEL 2	A complex model which models the device according to an understanding of the device physics
LEVEL 3	Simpler than level 2. Uses a semi-empirical approach i.e. the device equations are partly based on observed effects rather than the theory governing its operation

The L and W parameters perform the same function as the L and W parameters on the device line. If omitted altogether they are set to the option values (set with `.OPTIONS` statement) DEFL and DEFW respectively. These values in turn default to 100 microns.

The above models differ from all other SIMetrix (and SPICE) models in that they contain many geometry relative parameters. The geometry of the device (length, width etc.) is entered on a per component basis and various electrical characteristics are calculated from parameters which are scaled according to those dimensions. This is approach is very much geared towards integrated circuit simulation and is inconvenient for discrete devices. If you are modelling a particular device by hand we recommend you use the level 17 model which is designed for discrete vertical devices.

### 4.23.7 MOS Level 17: Model Parameters

Name	Description	Units	Default
VTO or VT0	Threshold voltage	V	0.0
KP	Transconductance parameter	A/V <sup>2</sup>	2.0e-5
GAMMA	Bulk threshold parameter	$\sqrt{V}$	0.0
PHI	Surface potential	V	0.6
LAMBDA	Channel length modulation	1/V	0.0
RD	Drain ohmic resistance	$\Omega$	0.0
RS	Source ohmic resistance	$\Omega$	0.0
CBD	B-D junction capacitance	F	0.0
CBS	B-S junction capacitance	F	0.0
IS	Bulk junction sat. current	A	1.0e-14
PB	Bulk junction potential	V	0.8
CGSO	Gate-source overlap capacitance	F	0.0
CGBO	Gate-bulk overlap capacitance	F	0.0
CJ	Zero bias bulk junction bottom capacitance	F	0.0
MJ	Bulk junction bottom grading coefficient		0.5
CJSW	Zero bias bulk junction sidewall capacitance	F	0.0

Name	Description	Units	Default
MJSW	Bulk junction sidewall grading coefficient		0.5
FC	Forward bias depletion capacitance coefficient		0.5
TNOM	Parameter measurement temperature	°C	27
KF	Flicker noise coefficient		0.0
AF	Flicker noise exponent		1.0
CGDMAX	Maximum value of gate-drain capacitance	F	0.0
CGDMIN	Minimum value of gate-drain capacitance	F	0.0
XG1CGD	cgd max-min crossover gradient		1.0
XG2CGD	cgd max-min crossover gradient		1.0
VT CGD	cgd max-min crossover threshold voltage	V	0.0
TC1RD	First order temperature coefficient of RD	1/°C	0.0
TC2RD	Second order temperature coefficient of RD	1/°C <sup>2</sup>	0.0

#### 4.23.8 Notes for level 17

In SIMetrix version 5.2 and earlier, this model used a level parameter value of 7 instead of the current 17. The number was changed so that a PSpice compatible BSIM3 model (level=7) could be offered. In order to retain backward compatibility, any level 7 model containing the parameters cgdmax, cgdmin, xg1cgd, xg2cgd or vt cgd will automatically be switched to level=17.

The level 17 MOSFET was developed to model discrete vertical MOS transistors rather than the integrated lateral devices that levels 1 to 3 are aimed at. Level 17 is based on level 1 but has the following important additions and changes:

- New parameters to model gate-drain capacitance
- 2 new parameters to model rdson variation with temperature.
- All parameters are absolute rather than geometry relative. (e.g. capacitance is specified in farads not farads/meter)

All MOSFET models supplied with SIMetrix are level 17 types. Many models supplied by manufacturers are subcircuits made up from a level 1, 2 or 3 device with additional circuitry to correctly model the gate-drain capacitance. While the latter approach can be reasonably accurate it tends to be slow because of its complexity.

Gate-drain capacitance equation:

$$C_{gd} = \left( 0.5 - \frac{1}{\pi} \tan^{-1} ((VT CGD - v) - XG1CGD) \right) CGDMIN \\ + \left( 0.5 - \frac{1}{\pi} \tan^{-1} ((VT CGD - v) XG2CGD) \right) CGDMAX$$

where  $v$  is the gate-drain voltage. This is an empirical formula devised to fit measured characteristics. Despite this it has been found to follow actual measured capacitance to remarkable accuracy.

To model gate-drain capacitance quickly and to acceptable accuracy set the five  $C_{gd}$  parameters as follows:

1. Set CGDMIN to minimum possible value of  $C_{gd}$  i.e. when device is off and drain voltage at maximum.
2. Set CGDMAX to maximum value of  $C_{gd}$  i.e. when device is on with drain-source voltage low and gate-source voltage high. If this value is not known use twice the value of  $C_{gd}$  for  $V_{gd} = 0$ .
3. Set XG2CGD to 0.5, XG1CGD to 0.1 and leave VTCCGD at default of 0.

Although the parasitic reverse diode is modelled, it is connected inside the terminal resistances, RD and RS which does not represent real devices very well. Further, parameters such as transit time (TT) which model the reverse recovery characteristics of the parasitic diode are not included. For this reason it is recommended that the reverse diode is modelled as an external component. Models supplied with SIMetrix are subcircuits which include this external diode.

## 4.24 BSIM3 MOSFETs

### 4.24.1 Notes

The BSIM3 model is available with *Pro* and *Elite* versions. versions of SIMetrix. Three versions are supplied namely 3.1, 3.24 and 3.3. Our implementation of version 3.1 includes all bug fixes applied to the latest version but the device equations and supported parameters are for the original version 3.1. See below to find out how to switch versions.

BSIM3 models can be accessed using one of four values for the LEVEL parameter:

LEVEL=7 specifies a PSpice compatible model

LEVEL=8 specifies the standard Berkeley BSIM3 model.

LEVEL=49 specifies the Hspice® implementation using the Hspice® junction capacitance model.

LEVEL=53 is also a Hspice® version but uses the standard Berkeley junction cap model.

The following PSpice parameters are supported when using level 7: TT, L, W, RG, RD, RS, RB, RDS, JSSW

The following Hspice® parameters are supported when using level 49/53: CJGATE, HDIF, LDIF, WMLT, XL, XW, IS, N, NDS, VNDS, PHP, LMLT, CTA, CTP, PTA, PTP, TREF, RD, RS, RDC, RSC, CBD, CBS, FC, TT, LD, WD, EG, GAP1, GAP2, XLREF, XWREF, ACM, CALCACM, TLEV, TLEVC

The Hspice® noise model is also supported for NLEV=0,1 and 2.

The 'M' instance parameter has also been implemented with all variants. This specifies the number of equivalent parallel devices.

Additional temperature parameters: All variants support the TEMP and DTEMP instance parameters. TEMP specifies absolute temperature (Celsius) while DTEMP specifies the temperature relative to the circuit global temperature.

All variants support the model parameters T\_MEASURED (equivalent to TNOM), T\_ABS (as TEMP instance parameter) and T\_REL\_GLOBAL (as DTEMP instance parameter)

### 4.24.2 Version Selector

The VERSION parameter can be specified to select which version is used. As detailed above, SIMetrix supports three different BSIM3 versions although 8 versions have been released by Berke-

ley. The following table shows which version will actually be used according to the VERSION parameter value.

VERSION parameter	Use BSIM3 Version
3.0	3.1
3.1	3.1
3.2	3.24
3.21	3.24
3.22	3.24
3.23	3.24
3.24	3.24
3.3	3.3
not specified	3.3

Note that a second decimal point will be ignored so 3.2.4 is the same as 3.24. If the version parameter is set to a value not listed above, SIMetrix will raise an error condition. This can be overridden by setting .OPTION AnyVersion.

### 4.24.3 Model Parameters

The parameters describing BSIM3 are documented in the original Berkeley manual. See below. The following table lists parameters that are non-standard.

Name	Description	Units	Default
TNOM, T_MEASURED	Reference temperature; the temperature at which the model parameters were measured	°C	27
T_ABS	If specified, defines the absolute model temperature overriding the global temperature defined using .TEMP	°C	.TEMP
T_REL_GLOBAL	Offsets global temperature defined using .TEMP. Overridden by T_ABS	°C	0.0
VFBFLAG	Capacitor model selector used by Hspice. An error will be raised if this parameter and the CAPMOD parameter are set to values not supported by SIMetrix		0
BINFLAG	Parameter used by Hspice. An error will be raised if this parameter is set to a value other than zero		0
LREF	Ignored		
WREF	Ignored		
SFVTFLAG	Ignored		
TT	Level = 7 only. Reverse diode transit time	S	0.0
L	Level = 7 only. Channel length. Overridden by instance parameter	m	DEFL option

Name	Description	Units	Default
W	Level = 7 only. Channel width. Overridden by instance parameter	m	DEFW option
RG	Level = 7 only. Gate resistance		0.0
RD	Level = 7 only. Drain resistance	$\Omega$	0.0
RS	Level = 7 only. Source resistance	$\Omega$	0.0
RB	Level = 7 only. Bulk resistance	$\Omega$	0.0
RDS	Level = 7 only. Drain-source leakage resistance	$\Omega$	$\infty$
JSSW	Level = 7 only. Alias for JSW.	F/m	0.0

#### 4.24.4 Further Documentation

Original Berkeley documentation is provided on the CDROM and at our web site. Please visit [“Further Documentation” on page 87](#) for details.

#### 4.24.5 Process Binning

BSIM3 devices may be binned according to length and width. Refer to [“Model Binning” on page 33](#) for details.

## 4.25 BSIM4 MOSFETs

### 4.25.1 Notes

The BSIM4 model is only available with the *Elite* versions of SIMetrix.

BSIM4 models are accessed using LEVEL=14.

Versions 4.21, 4.3, 4.4, 4.5, 4.60, 4.61, 4.62, 4.63, 4.64, 4.65 and 4.70 are currently supported. To set the version to be used, use the VERSION parameter as defined in the following table:

VERSION parameter	Use BSIM4 version
4.0	4.21
4.1	4.21
4.2	4.21
4.21	4.21
4.3	4.3
4.4	4.4
4.5	4.5
4.6	4.6
4.61	4.61
4.62	4.62
4.63	4.63

VERSION parameter	Use BSIM4 version
4.64	4.64
4.65	4.65
4.70	4.70
Omitted	4.70
Other	See notes

Note that a second decimal point will be ignored so 4.2.1 is the same as 4.21. If the version parameter is set to a value not listed above, SIMetrix will raise an error condition. This can be overridden by setting .OPTION AnyVersion.

The implementation is standard Berkeley but with the addition of the ‘M’ instance parameter which specifies the number of equivalent parallel devices.

### 4.25.2 Further Documentation

Original Berkeley documentation is provided on the CDROM and at our web site. Please visit [“Further Documentation” on page 88](#) for details. Note the document covers version 4.70 of the model. Earlier versions are available from the BSIM3/4 web site at *BSIM Reference*.

### 4.25.3 Process Binning

BSIM4 devices may be binned according to length and width. Refer to [“Model Binning” on page 33](#) for details. Note the multi-fingered devices are binned according to width per finger.

## 4.26 HiSim HV MOSFET

### 4.26.1 Notes

The HiSim HV model is accessed as LEVEL=62 and is available with the *Elite* versions of SIMetrix. The device may have up to 6 terminals and the netlist format is as follows:

```
Mxxx drain gate source bulk [ substrate [ temperature ]]
      modelname instance_parameters
```

The substrate and temperature nodes are internally connected to ground if they are omitted. Currently we have no information about whether this is the expected behaviour.

Most mainstream models that we implement, such as BSIM3 and BSIM4, we alter to clean up the various error and warning messages that they emit. In particular we make the appropriate changes to ensure the messages are displayed in the list file. This is a time consuming task and generally has to be repeated for new versions. We have not done this work for this model and so most of the warning and error messages are as the original designers provided and are directed to “stdout” or “stderr”. This means that you will not see them when using SIMetrix via the GUI unless you specifically enable a feature that directs the simulator’s stdout and stderr output to the front end. This can be done by typing the following at the command line:

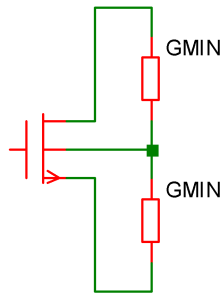
```
Set EnableSimStdout
Set EnableSimStderr
```

If running the simulator in ‘console’ mode, the stdout and stderr messages will be displayed in the console without needing any special configuration.

This model may be binned on length and width in a similar manner to the BSIM3 model. See “Model Binning” on page 33.

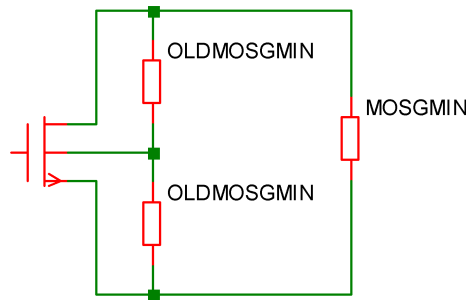
## 4.27 MOSFET GMIN Implementation

GMIN is a conductance added to all non-linear devices to improve DC convergence. For LEVEL 1-3 and LEVEL 17 MOSFETs, the default GMIN is implemented as shown below:



This is compatible with SPICE and earlier versions of SIMetrix.

For BSIM3 and BSIM4 devices, and also for LEVEL1-3 and LEVEL 17 devices if the NEWGMIN .OPTIONS setting is set, the GMIN implementation is:



OLDMOSGMIN is a .OPTIONS setting with the default value of zero. MOSGMIN is also a .OPTIONS setting with the default value of GMIN. Using the above configuration with OLD-MOSGMIN =0 often converges faster especially if the Junction GMIN stepping algorithm is used.

## 4.28 PSP MOSFET

### 4.28.1 Netlist Entry

```
Mxxxx drain gate source bulk modelname [instance_parameters]
```

Where:



<i>drain</i>	Drain node
<i>gate</i>	Gate node
<i>source</i>	Source node
<i>bulk</i>	Bulk node
<i>modelname</i>	Model name referring to a .MODEL statement
<i>instance_parameters</i>	List of name/parameter pairs in form name=value. name maybe any of the following: W, L, AS, AD, PS, PD, MULT, SA, SB, ABSOURCE, LSSOURCE, LGSOURCE, ABDRAIN, LSDRAIN, LGDRAIN Refer to PSP documentation (see below) for further details.

#### 4.28.2 NMOS Model Syntax Version 101.0

```
MODEL modelname NMOS LEVEL=1010 parameters
```

OR

```
.MODEL modelname PSP101 type=1 parameters
```

#### 4.28.3 PMOS Model Syntax Version 101.0

```
.MODEL modelname PMOS LEVEL=1010 parameters
```

OR

```
.MODEL modelname PSP101 type=-1 parameters
```

#### 4.28.4 NMOS Model Syntax Version 102.3

```
MODEL modelname NMOS LEVEL=1023 parameters
```

OR

```
.MODEL modelname PSP102 type=1 parameters
```

#### 4.28.5 PMOS Model Syntax Version 102.3

```
.MODEL modelname PMOS LEVEL=1023 parameters
```

OR

```
.MODEL modelname PSP102 type=-1 parameters
```

Refer to PSP documentation (see below) for details of parameters

#### 4.28.6 Notes

This is a model jointly developed by NXP (formerly Philips Semiconductor) and Pennsylvania State University.

Two versions are provided:

1. 101.0, non-binning, non-NQS geometric version.
2. 102.3, non-binning, non-NQS geometric version.

The model was implemented from the Verilog-A description.

Other versions of the PSP model are available from the NXP SIMKIT devices. See “SIMKIT Devices” on page 124.

Documentation for the model is supplied on the install CDROM and at our web site. Please refer to “Further Documentation” on page 41 for details.

## 4.29 Resistor

### 4.29.1 Netlist Entry

```
Rxxxx n1 n2 [model_name] [value] [L=length] [W=width] [ACRES=ac_resistance]
      [TEMP=local_temp] [TC1=tc1] [TC2=tc2] [M=mult] [DTEMP=dtemp]
```

<i>n1</i>	Node 1
<i>n2</i>	Node 2
<i>model_name</i>	(Optional) Name of model. Must begin with a letter but can contain any character except whitespace and ‘?’
<i>value</i>	Resistance (W)
<i>length</i>	Length of resistive element in metres. Only used if value is omitted. See notes below
<i>width</i>	Width of resistive element in metres. Only used if value is omitted. See notes below
<i>ac_resistance</i>	Resistance used for AC analyses and for the calculation of thermal noise. If omitted, value defaults to final resistance value.
<i>local_temp</i>	Resistor temperature (°C)
<i>tc1</i>	First order temperature coefficient
<i>tc2</i>	Second order temperature coefficient
<i>mult</i>	Device multiplier. Equivalent to putting mult devices in parallel.
<i>dtemp</i>	Differential temperature. Similar to <i>local_temp</i> but is specified relative to circuit temperature. If both TEMP and DTEMP are specified, TEMP takes precedence.

### 4.29.2 Notes

- If *model\_name* is omitted, *value* must be specified.
- If *model\_name* is present and *value* is omitted, *length* and *width* must be specified in which case the value of the resistance is  $RES * RSH * L/W$  where RSH is the sheet resistance model parameter and RES is the resistance multiplier. See model parameters below. If ACRES is specified and non-zero its value will be used unconditionally for AC analyses and the calculation of thermal noise.

### 4.29.3 Resistor Model Syntax

```
.model modelname R ( parameters )
```

#### 4.29.4 Resistor Model Parameters

Name	Description	Units	Default
RES	Resistance multiplier		1
TC1	First order temperature coefficient	1/°C	0
TC2	Second order temperature coefficient	1/°C <sup>2</sup>	0
RSH	Sheet resistance	Ω/sq	0
KF	Flicker noise coefficient	m <sup>2</sup> /Ω <sup>2</sup>	0
EF	Flicker noise exponent		1
TNOM, T_MEASURED	Reference temperature; the temperature at which the model parameters were measured	°C	27
T_ABS	If specified, defines the absolute model temperature overriding the global temperature defined using .TEMP	°C	.TEMP
T_REL_GLOBAL	Offsets global temperature defined using .TEMP. Overridden by T_ABS	°C	0.0

#### 4.29.5 Notes

The flicker noise parameters are proprietary to SIMetrix. Flicker noise voltage is:

$$V_n^2 = KF \cdot RSH^2 / (L \cdot W) \cdot V_r^2 \cdot \Delta f / f^{EF}$$

Where:

$V_r$  = Voltage across resistor.

The equation has been formulated so that KF is constant for a given resistive material.

If one of L, W is not specified, the flicker noise voltage becomes:

$$V_n^2 = KF \cdot R^2 \cdot V_r^2 \cdot \Delta f / f^{EF}$$

Where R is the final resistance.

i.e. the noise current is independent of resistance. This doesn't have any particular basis in physical laws and is implemented this way simply for convenience. When resistor dimensions and resistivity are unavailable, the value of KF will need to be extracted for each individual value.

### 4.30 Resistor - Hspice Compatible

#### 4.30.1 Netlist Entry

```
Rxxxx n1 n2 [model_name] [value] [L=length] [W=width] [AC=ac_resistance] [TC1=tc1]
[TC2=tc2] [M=mult] [SCALE=scale] [DTEMP=dtemp] [C=c]
```

<i>model_name</i>	Name of .MODEL. This is compulsory unless this model is re-mapped as the default resistor using a device configuration file. See “ <a href="#">Customising Device Configuration</a> ” on page 35.
<i>value</i>	Value of resistor. This may be an expression relating parameters defined using .PARAM and circuit variables in the form V(n1,n2) and I(device). Expressions must be enclosed in curly braces or quotation marks. Typically the expression relates to the resistor’s own terminals in order to define voltage dependence
<i>length</i>	Length in metres
<i>width</i>	Width in metres
<i>ac_resistance</i>	Value of resistor for AC analyses. Like the main value, this may also be an expression. See above under <i>value</i> for details
<i>tc1</i>	First order temperature coefficient
<i>tc2</i>	Second order temperature coefficient
<i>mult</i>	Device multiplier. Equivalent to putting <i>mult</i> devices in parallel, but note that this value does not have to be integral
<i>scale</i>	Scales resistance and capacitance values. E.g. $R_{eff} = scale * R$
<i>dtemp</i>	Differential temperature. Device temperature = global temperature + <i>dtemp</i>
<i>c</i>	Capacitance to reference node

### 4.30.2 Resistor Model Syntax

```
.model modelname R (LEVEL=2 parameters )
```

Name	Description	Units	Default
BULK	Bulk connection for capacitance		Ground
CAP	Device capacitance	F	0.0
CAPSW	Sidewall capacitance	F/m	0.0
COX	Capacitance per unit area	F/m <sup>2</sup>	0.0
CRATIO	Capacitance terminal distribution		0.5
DI	Dielectric constant		0.0
DL	Difference between drawn length and actual length for capacitance calculation	m	DW
DLR	Difference between drawn length and actual length for resistance calculation	m	0.0
DW	Difference between drawn width and actual width	m	0.0
L, ML	Length	m	0.0
W, MW	Width	m	0.0
NOISE	Noise multiplier		1.0
RAC	AC resistance	$\Omega$	
RES	Resistance	$\Omega$	0.0
RSH	Sheet resistance	$\Omega/sq$	0.0

Name	Description	Units	Default
SHRINK	Shrink factor		1.0
TC1C	Capacitance first order temperature coefficient	1/C	0.0
TC1R	Resistance first order temperature coefficient	1/C	0.0
TC2C	Capacitance second order temperature coefficient	1/C <sup>2</sup>	0.0
TC2R	Resistance second order temperature coefficient	1/C <sup>2</sup>	0.0
THICK	Dielectric thickness	m	0.0
TREF	Measurement temperature	C	TNOM
ACRESMOD	AC resistance model selector. See <a href="#">“ACRESMOD Parameter” on page 97</a>		0
KF	Flicker noise coefficient		0
AF	Flicker noise current exponent		2.0
LF	Flicker noise length exponent		1.0
WF	Flicker noise width exponent		1.0
EF	Flicker noise frequency exponent		1.0

### 4.30.3 Resistance Calculation

In the following  $reff$  is the effective non-temperature adjusted resistance used for DC analyses,  $reffac$  is the effective non-temperature adjusted resistance used for AC analyses.

If instance resistance is specified:

$$reff = value * SCALE/M$$

otherwise if  $w_{eff} * l_{eff} * RSH > 0$

$$reff = SCALE * RSH * l_{eff} / (w_{eff} * M)$$

where:

$$w_{eff} = SHRINK * W - 2 * DW$$

$$l_{eff} = SHRINK * L - 2 * DLR$$

otherwise

$$reff = SCALE * RES / M$$

If instance AC parameter is specified:

$$raceff = AC * SCALE / M$$

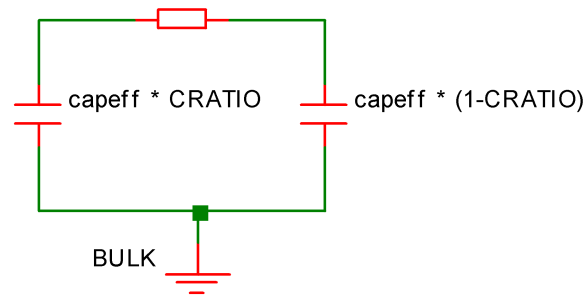
otherwise if RAC given

$$raceff = SCALE * RAC / M$$

otherwise

$$raceff = reff$$

## 4.30.4 Capacitance Calculation



$capeff$  is the non temperature adjusted capacitance.

If instance parameter C is given:

$$capeff = M*SCALE*C$$

otherwise if model parameter CAP is given

$$capeff = M*SCALE*CAP$$

otherwise

$$capeff = (leffc*weffc*coxmod + 2*((leffc+weffc)*CAPSW))*M*SCALE$$

where:

$$leffc = SHRINK*L - 2*DL$$

$$weffc = SHRINK*W - 2*DW$$

See below for  $coxmod$  calculation.

**Calculation of COX**

If COX given

$$coxmod = COX$$

otherwise if THICK  $\langle \rangle$  0 AND DI  $\langle \rangle$  0

$$coxmod = 8.8542149e-012*DI/THICK$$

otherwise if THICK  $\langle \rangle$  0 AND DI=0

$$coxmod = 3.453148e-011/THICK$$

otherwise

$$coxmod = 0.0$$

### 4.30.5 Temperature Scaling

#### Resistance

$$R(t) = r_{\text{eff}} * t_{\text{scale}}$$

where:

$$t_{\text{scale}} = 1 + (tc1_{\text{inst}} + t_{\text{delta}} * tc2_{\text{inst}}) * t_{\text{delta}}$$

where

$$t_{\text{delta}} = t_{\text{inst}} - T_{\text{REF}} - 273.15$$

$$tc1_{\text{inst}} = \text{if instance TC1 given: TC1 else TC1R}$$

$$tc2_{\text{inst}} = \text{if instance TC2 given: TC2 else TC2R}$$

$$t_{\text{inst}} = [\text{global circuit temperature}] + DTEMP \text{ (Kelvin)}$$

#### Capacitance

$$C(t) = c_{\text{eff}} * t_{\text{scale}}$$

where

$$t_{\text{cscale}} = 1 + (TC1C + t_{\text{delta}} * TC2C) * t_{\text{delta}}$$

$t_{\text{delta}}$  defined above.

### 4.30.6 Flicker Noise

$$I_n = \frac{KF \times I^{AF}}{L_{\text{eff}}^{LF} \times W_{\text{eff}}^{WF} \times f^{EF}}$$

### 4.30.7 ACRESMOD Parameter

This parameter controls the calculation of resistance in AC analysis. With ACRESMOD=0 AC analysis uses the large signal resistance value, that is the value of resistance calculated during the DC analysis. If ACRESMOD=1, the small signal resistance is used, that is, the value of  $dv/di$  at the operating point. If the resistance is defined as an expression containing circuit variables (i.e. it is voltage dependent), the large signal resistance is different to the small signal resistance.

This resistor model has been developed primarily for compatibility with Hspice models. Hspice itself always uses the large signal resistance. However, this will create a discrepancy between AC analysis and a transient analysis of a small signal. To resolve this discrepancy, set ACRESMOD to 1.

In summary, to be compatible with Hspice, use ACRESMOD=0, for consistent results between AC and transient analyses, use ACRESMOD=1.

In noise analysis the large signal value is always used.

### 4.30.8 Making the Hspice Resistor the Default

This resistor model requires the specification of a model name and the creation of a .MODEL statement with LEVEL=2. This is likely to be inconvenient if a model file containing Hspice resistors is being used.

To overcome this, a device configuration file can be created that maps this resistor model to the default. For full details see [“Customing Device Configuration” on page 35](#). The line required to make this resistor the default is:

```
ModelName=R,Device=HspiceRes,Level=0
```

## 4.31 CMC Resistor

### 4.31.1 Netlist entry

```
Uxxxx n1 nc n2 model_name parameters
```

### 4.31.2 Model Format

```
.MODEL model_name R3_CMC model_parameters
```

Full details of this model can be found in the document [r3\\_cmc\\_release1.0.0\\_2007Jun12.pdf](#) which may be found on the CDROM and at our web site. Please refer to [“Further Documentation” on page 41](#) for details.

## 4.32 S-domain Transfer Function Block

### 4.32.1 Netlist entry

```
Axxxx input output model_name
```

### 4.32.2 Connection details

Name	Description	Flow	Default type	Allowed types
in	Input	in	v	v, vd, i, id
out	Output	out	v	v, vd, i, id

### 4.32.3 Model format

```
.MODEL model_name s_xfer parameters
```

### 4.32.4 Model parameters

Name	Description	Type	Default	Limits	Vector bounds
in_offset	Input offset	real	0	none	n/a
gain	Gain	real	1	none	n/a



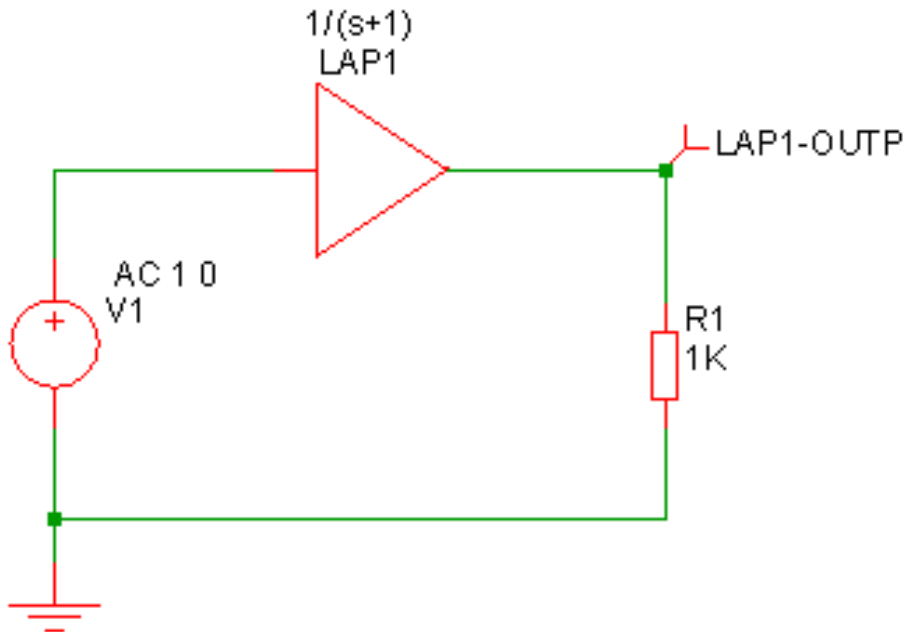
Name	Description	Type	Default	Limits	Vector bounds
laplace	Laplace expression (overrides num_coeff and den_coeff)	string	none	none	n/a
num_coeff	Numerator polynomial coefficient	real vector	none	none	1 - ∞
den_coeff	Denominator polynomial coefficient	real vector	none	none	1 - ∞
int_ic	Integrator stage initial conditions	real vector	0	none	none
denormalized_freq	Frequency (radians/second) at which to denormalize coefficients	real	1	none	n/a

### 4.32.5 Description

This device implements an arbitrary linear transfer function expressed in the frequency domain using the 'S' variable. The operation and specification of the device is illustrated with the following examples.

### 4.32.6 Examples

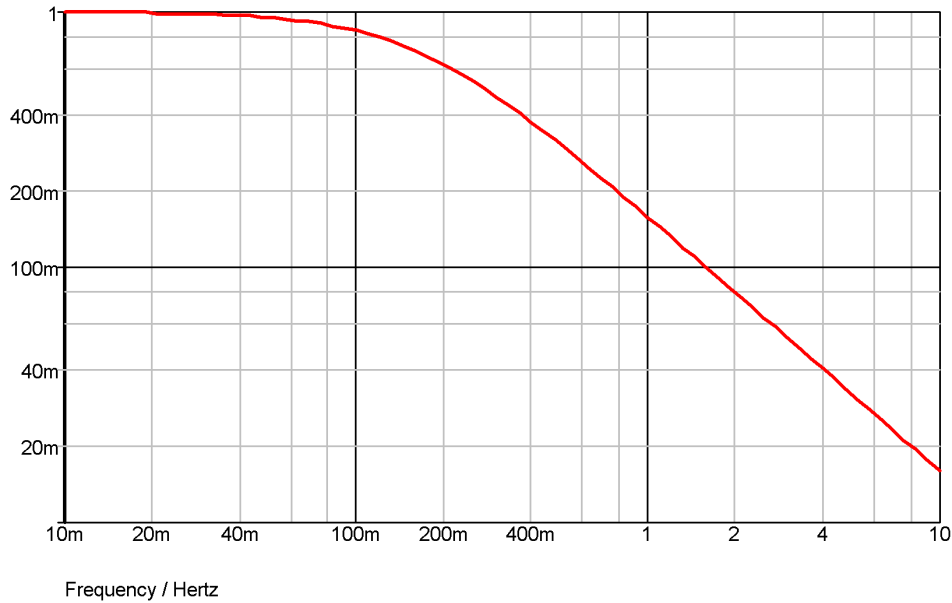
#### Example 1 - A single pole filter



Model for above device:

```
.model Laplace s_xfer laplace="1/(s+1)" denormalized_freq=1
```

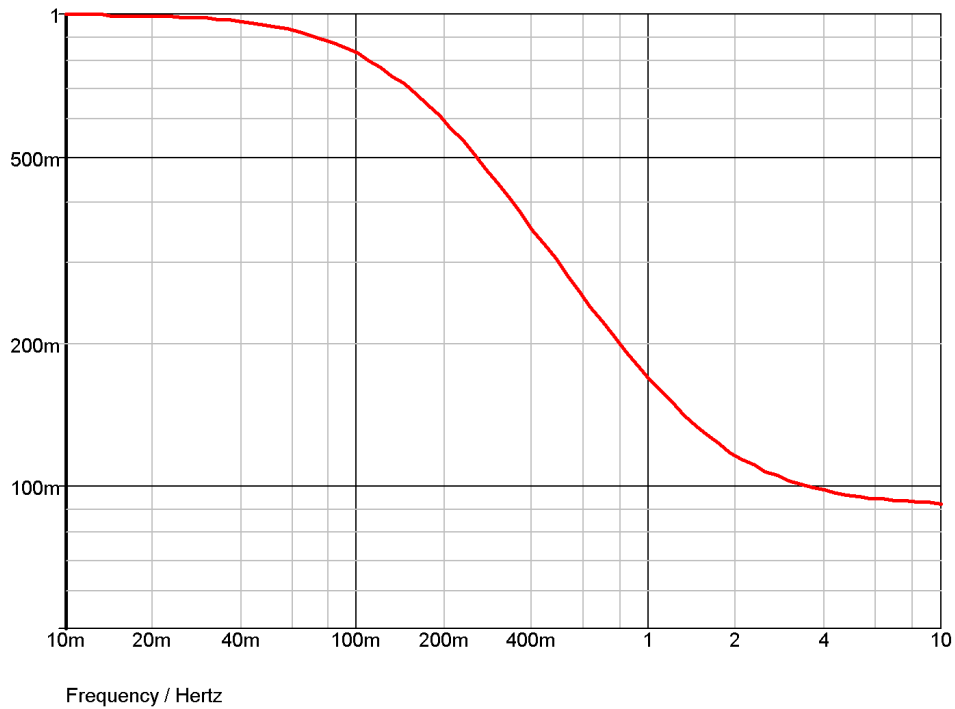
This is a simple first order roll off with a 1 second time constant as shown below



### Example 2 - Single pole and zero

```
.model Laplace s_xfer
+ laplace="(1/s)/(1/s + 1/(0.1*s+1))"
+ denormalized_freq=1
```

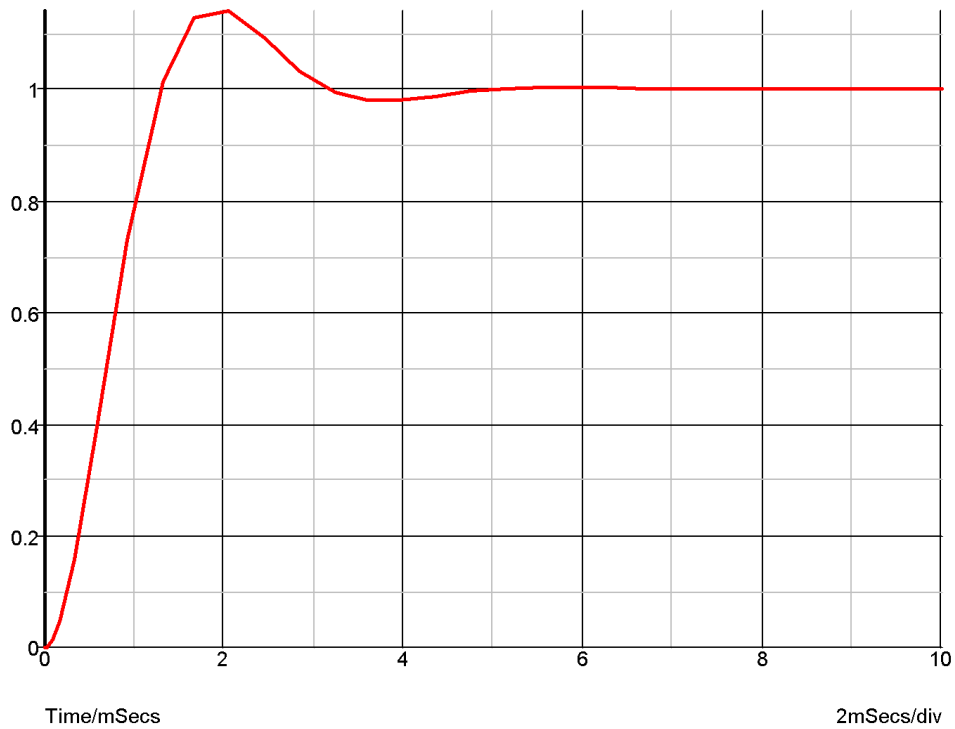
The laplace expression has been entered how it might have been written down without any attempt to simplify it. The above actually simplifies to  $(0.1*s+1)/(1.1*s+1)$ .



### Example 3 - Underdamped second order response

```
.model Laplace s_xfer
+ laplace="1/(s2+1.1*s+1)"
+ denormalized_freq=2k
```

The above expression is a second order response that is slightly underdamped. The following graph shows the transient response.

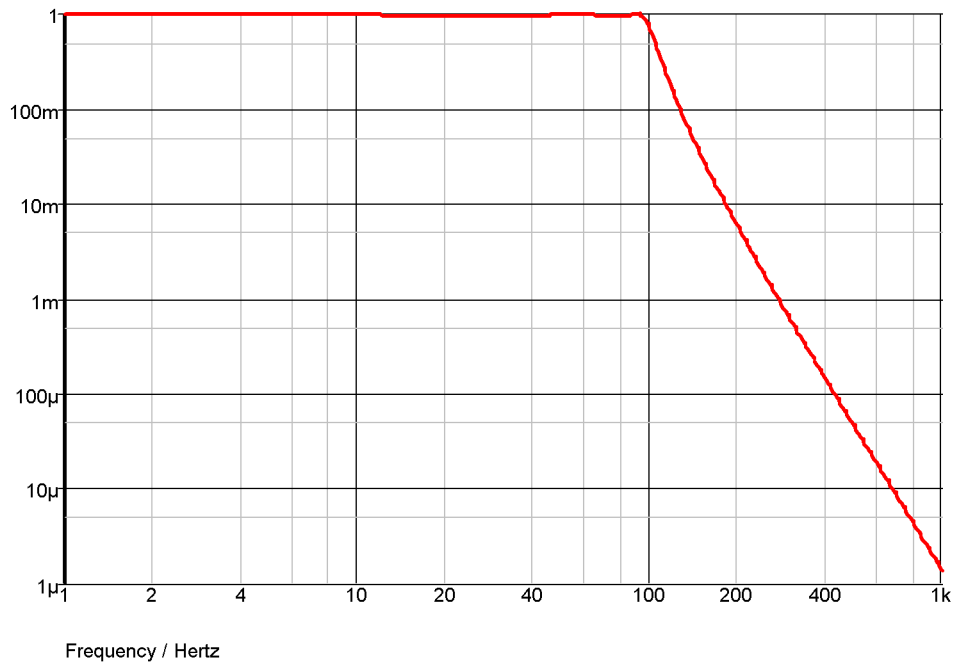


#### Example 4 - 5th order Chebyshev low-pass filter

The S-domain transfer block has a number of built in functions to implement standard filter response. Here is an example. This is a 5th order chebyshev with -3dB at 100Hz and 0.5dB passband ripple.

```
.model Laplace s_xfer
+ laplace="chebyshevLP(5,100,0.5)"
+ denormalized_freq=1
```

and the response:



#### 4.32.7 The Laplace Expression

As seen in the above examples, the transfer function of the device is defined by the model parameter LAPLACE. This is a text string and must be enclosed in double quotation marks. This may be any arithmetic expression containing the following elements:

Operators:

$$+ - * / ^$$

where  $^$  means raise to power. Only integral powers may be specified.

Constants

Any decimal number following normal rules. SPICE style engineering suffixes are accepted.

S Variable

This can be raised to a power with  $^$  or by simply placing a constant directly after it (with no spaces). E.g.  $s^2$  is the same as  $s2$ .

Filter response func- These are:  
tions

BesselLP(order, cut-off) Bessel low-pass  
 BesselHP(order, cut-off) Bessel high-pass  
 ButterworthLP(order, cut-off) Butterworth low-pass  
 ButterworthHP(order, cut-off) Butterworth high-pass  
 ChebyshevLP(order, cut-off, passband\_ripple) Chebyshev low-pass  
 ChebyshevHP(order, cut-off, passband\_ripple) Chebyshev high-pass

Where:

order Integer specifying order of filter. There is no maximum limit but in practice orders larger than about 50 tend to give accuracy problems.  
 cut-off -3dB Frequency in Hertz  
 passband\_ripple Chebyshev only. Passband ripple spec. in dB

#### 4.32.8 Defining the Laplace Expression Using Coefficients

Instead of entering a Laplace expression as a string, this can also be entered as two arrays of numeric coefficients for the numerator and denominator. In general this is less convenient than entering the expression directly, but has the benefit that it supports the use of parameters. In this method, use the NUM\_COEFF and DEN\_COEFF parameters instead of the LAPLACE expression.

The following simple example, demonstrates the method

```
.param f0=10
.param w0 = {2*3.14159265*f0}

.model laplace s_xfer num_coeff = [1] den_coeff = [{1/w0},1]
```

#### 4.32.9 Other Model Parameters

- DENORMALISED\_FREQ is a frequency scaling factor.
- INT\_IC specifies the initial conditions for the device. This is an array of maximum size equal to the order of the denominator. The right-most value is the zero'th order initial condition.
- NUM\_COEFF and DEN\_COEFF - see [“Defining the Laplace Expression Using Coefficients” on page 104](#).
- GAIN and IN\_OFFSET are the DC gain and input offset respectively.

#### 4.32.10 Limitations

SIMetrix expands the expression you enter to create a quotient of two polynomials. If the constant terms of both numerator and denominator are both zero, both are divided by S. That process is repeated until one or both of the polynomials has a non-zero constant term.

The result of this process must satisfy the following:

- The order the denominator must be greater than or equal to that of the numerator.

- The constant term of the denominator may not be zero.

#### 4.32.11 The XSPICE S\_XFER model

The SIMetrix Laplace transfer model is compatible with the original XSPICE version but the transient analysis portion of it has been completely rewritten. The original XSPICE version was seriously flawed and would only give accurate results if the timestep was forced to be very small. Further, convergence would fail if the device was used inside a feedback loop.

The ability to enter the laplace transform as an arbitrary expression is a SIMetrix enhancement. The original version required the user to enter the coefficients of the numerator and denominator explicitly. The filter response functions are also a SIMetrix enhancement.

### 4.33 Subcircuit Instance

#### 4.33.1 Netlist Entry

```
Xxxxx n1 n2 n3 ... subcircuit_name [pinnames: pin1 pin2 pin3 ...] [[params:]
[M=m] expression1 expression2 ....]
```

<i>n1, n2</i> etc.	Subcircuit nodes
<i>pin1, pin2</i> etc.	If the <i>pinnames:</i> keyword is included the names following it will be used to name subcircuit current vectors generated by the simulator.
<i>subcircuit_name</i>	Subcircuit name referred to in subcircuit definition (i.e. with <a href="#">.SUBCKT</a> statement)
<i>m</i>	Multiplier. If present, the subcircuit will be multiplied by <i>m</i> as if there were <i>m</i> devices in parallel. <i>m</i> may be an expression in which case it must be enclosed by curly braces: '{', '}'.  Note that the multiplication is performed by scaling the internal devices not by actually replicating the subcircuit. Non integral values of <i>m</i> are thus permitted. Some types of device can not currently be scaled and subcircuits containing them will not support <i>M</i> . An error will displayed in this case.  <i>M</i> will be interpreted as a regular parameter and will not scale the subcircuit instance if <i>M</i> is declared as a parameter in the <a href="#">.SUBCKT</a> line or the following option setting is included in the netlist: <a href="#">.OPTIONS DisableSubcktMultiplier</a>
<i>expression1</i> etc.	Parameter expressions. See <a href="#">“Using Expressions” on page 17</a> .

See [“Subcircuits” on page 30](#) for more information.

### 4.34 Transmission Line

#### 4.34.1 Netlist Entry

```
Txxxx p1 n1 p2 n2 Z0=impedance [TD=delay] [F=frequency [NL=norm_length]]
[rel=rel] [abs=abs]
```

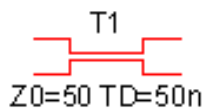
<i>p1</i>	Positive input port 1
<i>n1</i>	Negative input port 2
<i>p2</i>	Positive input port 1
<i>n2</i>	Negative input port 2
<i>impedance</i>	characteristic impedance
<i>delay</i>	Line delay (Seconds)
<i>frequency</i>	Alternative means of specifying <i>delay</i> = <i>norm_length/frequency</i>
<i>norm_length</i>	See <i>frequency</i> . Default 0.25 if omitted.

TD takes precedence over NL/F. Either TD or F must be specified.

These remaining parameters control the way the line is simulated rather than its electrical characteristics. More accurate results (at the expense of simulation time) can be obtained by using lower values.

<i>rel</i>	Relative rate of change of derivative for breakpoint
<i>abs</i>	Absolute rate of change of derivative for breakpoint

#### 4.34.2 Example



The above line has an impedance of  $50\Omega$  and a delay of  $1\mu\text{s}$ .

## 4.35 Voltage Controlled Current Source

### 4.35.1 Netlist Entry

```
Gxxxx nout+ nout- vc+ vc- transconductance
```

<i>nout+</i>	Positive output node
<i>nout-</i>	Negative output node
<i>vc+</i>	Positive control node
<i>vc-</i>	Negative control node
<i>transconductance</i>	Output current/Input voltage (Siemens or mhos)

SPICE2 polynomial sources are also supported in order to maintain compatibility with commercially available libraries for IC's. (Most operational amplifier models for example use several polynomial sources). In general, however the [arbitrary source](#) is more flexible and easier to use.



The netlist format for a polynomial source is:

```
Gxxxx nout+ nout- POLY( num_inputs ) vc1+ vc1- vc2+ vc2- ...
+ polynomial_specification
```

*vc1+ etc.* Controlling nodes  
*num\_inputs* Number of controlling node pairs for source.  
*polynomial\_specification* See “Polynomial Specification” on page 61.

## 4.36 Voltage Controlled Switch

### 4.36.1 Netlist Entry

```
Sxxxx nout1 nout2 vc+ vc- modelname IC=ic
```

*nout1* Switch node 1  
*nout2* Switch node 2  
*vc+* Positive control node  
*vc-* Negative control node  
*modelname* Name of model. Must begin with a letter but can contain any character except whitespace and period ‘.’.  
*ic* Initial condition. Hysteresis mode only. Defines initial state of switch if control voltage is between upper and lower thresholds. 0 for ‘OFF’  
 1 for ‘ON’

### 4.36.2 Voltage Controlled Switch Model Syntax

```
.model modelname VSWITCH ( parameters )
```

OR

```
.model modelname SW ( parameters )
```

### 4.36.3 Voltage Controlled Switch Model Parameters

Name	Description	Units	Default
RON	On resistance	$\Omega$	1
ROFF	Off resistance	$\Omega$	Hysteresis mode: 1.0E12. Continuous mode: 1.0E6
VON	Voltage at which switch begins to turn on. (continuous mode)	V	1
VOFF	Voltage at which switch begins to turn off. (continuous mode)	V	0
VT	If present enables hysteresis mode. Sets threshold voltage	V	0.5

Name	Description	Units	Default
VH	Hysteresis voltage. (hysteresis mode)	V	1.0
TON	On time. (hysteresis mode)	s	1ns
TOFF	Off time. (hysteresis mode)	s	1n
TD	Delay time. (hysteresis mode)	s	0
TD_ON	On delay. (hysteresis mode)	s	TD
TD_OFF	Off delay. (hysteresis mode)	s	TD
TIMETOL	Time tolerance. (hysteresis mode)	s	10p

#### 4.36.4 Voltage Controlled Switch Notes

The voltage controlled switch has two modes of operation:

1. Continuous mode: Behaves like a voltage controlled resistor. Between VON and VOFF the resistance varies gradually following a cubic law as described with the following equation:

where:

$$R = 1/\exp(-Lm - Lr * factor * (1.5 - 2 * factor * factor))$$

$$factor = V_{control} - 0.5$$

$$Lm = -0.5 * \ln(g_{on} * g_{off})$$

$$Lr = \ln(g_{off}/g_{on})$$

$$g_{off} = ROFF <> 0 : 1/ROFF, ROFF = 0 : GMIN$$

$$g_{on} = RON <> 0 : 1/RON, RON = 0 : GMIN$$

2. Hysteresis mode: Switches in a controlled time with a hysteresis characteristic. This mode is enabled if the VT parameter is defined. The switch transitions to the on state when:

$$V_{control} > VT + VH$$

and to the off state when:

$$V_{control} < VT - VH$$

The transition will be delayed by TD and the transition time will be TON when changing from OFF state to ON state and TOFF when changing from ON state to OFF state.

The transition will follow the same characteristic as continuous mode. That is, during the transition period the actual resistance of the switch will follow the continuous mode characteristic with the control voltage following a linear transition between VON and VOFF.

Hysteresis mode is similar and usually compatible with what is known as short-transition mode in PSpice. The difference is that in short-transition mode, the switching time is uncontrolled whereas in SIMetrix hysteresis mode the transition time is controlled by the TON and TOFF parameters.

GMIN is a simulation parameter which defaults to 10E-12 but which can be changed using the [.OPTIONS](#) statement.

The SIMetrix voltage controlled switch is compatible with PSpice® but note that in hysteresis mode, the SIMetrix switches in a controlled time whereas the PSpice version switches abruptly.

## 4.37 Voltage Controlled Voltage Source

### 4.37.1 Netlist Entry

```
Exxxx nout+ nout- vc+ vc- gain
```

<i>nout+</i>	Positive output node
<i>nout-</i>	Negative output node
<i>vc+</i>	Positive control node
<i>vc-</i>	Negative control node
<i>gain</i>	Output voltage/Input voltage

SPICE2 polynomial sources are also supported in order to maintain compatibility with commercially available libraries for ICs. (Most opamp models for example use several polynomial sources). In general, however the arbitrary source is more flexible and easier to use.

The netlist format for a polynomial source is:

```
Exxxx nout+ nout- POLY( num_inputs ) vc1+ vc1- vc2+ vc2-
... polynomial_specification
```

<i>vc1+ etc.</i>	Controlling nodes
<i>num_inputs</i>	Number of controlling node pairs for source.
<i>polynomial_specification</i>	See <a href="#">“Polynomial Specification” on page 61</a>

## 4.38 Voltage Source

### 4.38.1 Netlist Entry

```
Vxxxx n+ n- [[DC] dcvalue] [DCOP] [INFCAP] [AC magnitude [phase]]
[transient_spec]
```

<i>N+</i>	Positive node
<i>N-</i>	Negative node
DCOP	If this is specified, the voltage source will only be active during the DC operating point solution. In other analyses, it will behave like an open circuit. This is an effective method of creating a ‘hard’ initial condition. See <a href="#">“Alternative Initial Condition Implementations” on page 202</a> for an example.
INFCAP	If specified, the voltage source will behave as an infinite capacitor. During the DC operating point solution it will behave like an open circuit. In the subsequent analysis, it will behave like a voltage source with a value equal to the solution found during the operating point. Note that the device is inactive for DC sweeps - as all capacitors are.
<i>dcvalue</i>	Value of source for dc operating point analysis
<i>magnitude</i>	AC magnitude for AC sweep analysis.
<i>phase</i>	phase for AC sweep analysis

*transient\_spec* Specification for time varying source as described in the following table.

Type	Description
PULSE	Pulse source. Also generates, ramps, sawtooths and triangles
PWL	Piece wise linear source. Can create any waveform
PWLFILE	As PWL but get definition from a file
SIN	Sine wave
“EXP” on page 114	Exponential signal
“SFFM” on page 115	Single frequency FM
“NOISE” on page 115	Real time noise source

### 4.38.2 Pulse Source

```
PULSE ( v1 v2 [td [tr [tf [pw [per ]]]]] )
```

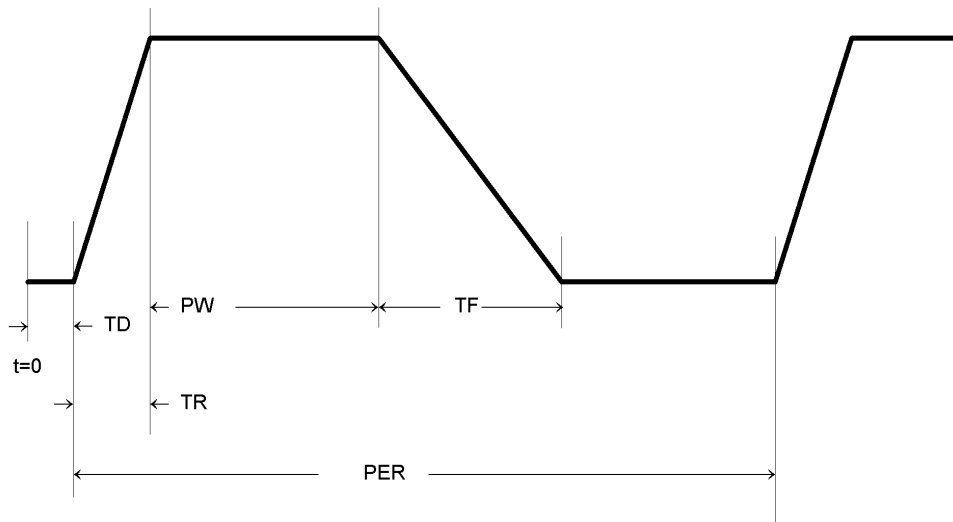
Where:

Name	Description	Default
v1	Initial value (V,A)	Compulsory
v2	Pulsed value (V,A)	Compulsory
td	Delay time (S)	Default if omitted = 0
tr	Rise time (S)	Default if omitted, negative or zero = Time step <sup>a</sup>
tf	Fall time (S)	Default if omitted, negative or zero = Time step
pw	Pulse width (S)	Default if omitted or negative = Stop time <sup>b</sup>
per	Period (S)	Default if omitted, negative or zero = Stop time

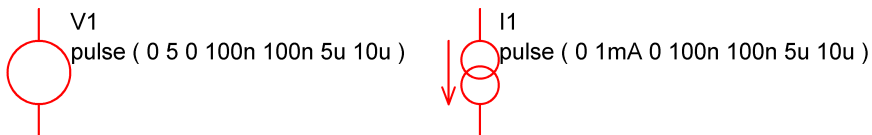
- a. *Time step* is set up by the .TRAN simulator statement which defines a transient analysis. Refer to “[.TRAN](#)” on [page 245](#).
- b. *Stop time* refers to the end time of the transient analysis.

SIMetrix deviates from standard SPICE in the action taken for a pulse width of zero. Standard SPICE treats a zero pulse width as if it had been omitted and changes it to the stop time. In SIMetrix a zero pulse width means just that.

Both the above examples give a pulse lasting  $5\mu\text{S}$  with a period of  $10\mu\text{S}$ , rise and fall times of  $100\text{nS}$  and a delay of 0. The voltage source has a 0V base line and a pulse of 5V while the current source has a 0mA base line and a pulse of 1mA.



### Examples



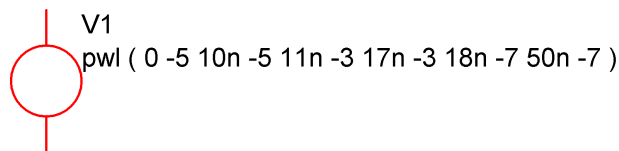
### 4.38.3 Piece-Wise Linear Source

PWL ( t1 v1 [t2 v2 [t3 v3 [... ]]] )

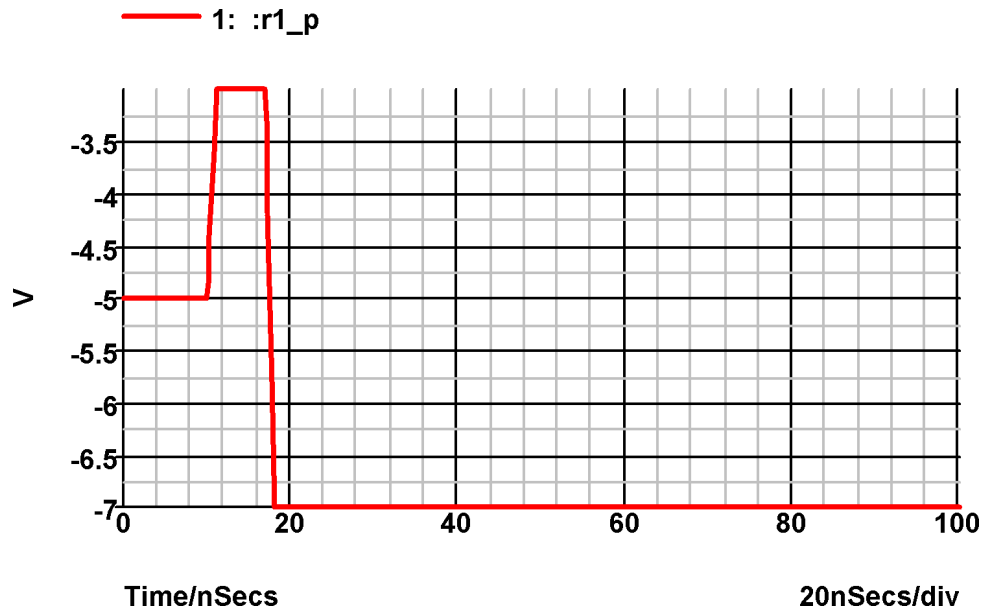
Each pair of values ( $t_i$   $v_i$ ) specifies that the value of the source is  $v_i$  at time =  $t_i$ . The value of the source at intermediate values of time is determined by using linear interpolation on the input values.

Although the example given below is for a voltage source, the PWL stimulus may be used for current sources as well.

#### Example



Gives:



#### 4.38.4 PWL File Source

PWLFILE filename

This performs the same function as the normal piece wise linear source except that the values are read from a file named *filename*.

The file contains a list of time voltage pairs in text form separated by any whitespace character (space, tab, new line). It is not necessary to add the '+' continuation character for new lines but they will be ignored if they are included. Any non-numeric data contained in the file will also be ignored.

##### Notes

The PWLFILE source is *considerably* more efficient at reading large PWL definitions than the standard PWL source. Consequently it is recommended that all PWL definitions with more than 200 points are defined in this way.

The data output by `Show /file` is directly compatible with the PWLFILE source making it possible to save the output of one simulation and use it as a stimulus for another. It is recommended, however, that the results are first interpolated to evenly spaced points using the `Interp()` function.

The use of engineering suffixes (e.g. k, m, p etc.) is *not* supported by PWLFILE.

The PWLFILE source is a feature of SIMetrix and does not form part of standard SPICE.

Note, you can use the simulator statements `.FILE` and `.ENDF` to define the contents of the file. E.g.

```
Vpw11 N1 N2 PWLFILE pw1Source
...
.FILE pw1Source
...
...
.ENDF
```

This will be read in much more efficiently than the standard PWL and is recommended for large definitions. See [“.FILE and .ENDF” on page 195](#).

### 4.38.5 Sinusoidal Source

SIN[E] ( vo va [freq [delay [theta [ phase]]]] )

Where:

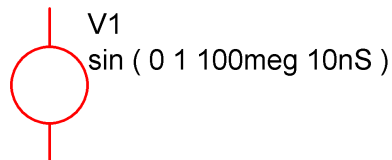
Name	Description	Default
vo	Offset (V,A)	Compulsory
va	Peak (V,A)	Compulsory
freq	Frequency (Hz)	Default if omitted or zero= 1/Stop time <sup>a</sup>
delay	Delay (seconds)	Default if omitted = 0
theta	Damping factor (1/seconds)	Default if omitted = 0
phase	Phase in degrees	Default if omitted = 0

a. *Stop time* refers to the end time of the transient analysis.

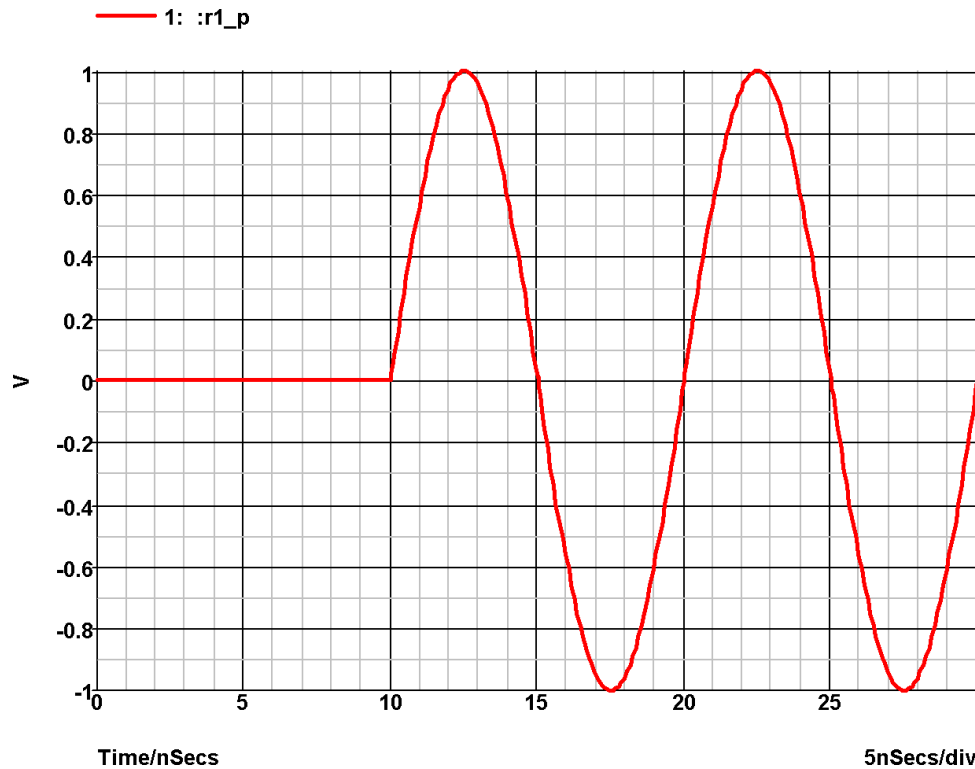
The shape of the waveform is described by:

0 to delay: vo  
 $delay$  to  $Stop$   $vo + va \cdot e^{-(t-delay) \cdot theta} \cdot \sin(2\pi(freq \cdot (t - delay) + phase/360))$   
 $time$

#### Example



Gives output of:



#### 4.38.6 Exponential Source

```
EXP ( v1 v2 [td1 [tau1 [td2 [tau2 ]]] ] )
```

Where:

Name	Description	Default
v1	Initial value (V,A)	Compulsory
v2	Pulsed value (V,A)	Compulsory
td1	Rise delay time	Default if omitted or zero: 0
tau1	Rise time constant	Default if omitted or zero: Time step <sup>a</sup>
td2	Fall delay time	Default if omitted or zero: td1 + Time step
tau2	Fall time constant	Default if omitted or zero: Time step

- a. Time step is set up by the .TRAN simulator directive which defines a transient analysis. Refer to [“.TRAN” on page 245](#).

Defined by:

$$\text{td1 to td2: } v1 + (v2 - v1) \cdot [1 - e^{-(t-td1)/\tau_1}]$$

$$\text{td2 to stop time: } v1 + (v2 - v1) \cdot [1 - e^{-(t-td1)/\tau_1}] + v1 + (v2 - v1) \cdot [1 - e^{-(t-td2)/\tau_2}]$$



### 4.38.7 Single Frequency FM

```
SFFM ( vo va [fc [mdi [fs ]]] )
```

Where:

Name	Description	Default
vo	Offset (V,A)	Compulsory
va	Amplitude (V,A)	Compulsory
fc	Carrier frequency (Hz)	Default if omitted or zero = 1/Stop time <sup>a</sup>
mdi	Modulation index	Default if omitted = 0
fs	Signal frequency (Hz)	Default if omitted or zero = 1/Stop time

- a. *Stop time* refers to the end time of the transient analysis.

Defined by:  $vo + va \cdot \sin[2\pi \cdot fc \cdot t + mdi \cdot \sin(2\pi \cdot fs \cdot t)]$

### 4.38.8 Noise Source

```
noise interval rms_value [start_time [stop_time]]
```

Source generates a random value at *interval* with distribution such that spectrum of signal generated is approximately flat up to frequency equal to  $1/(2 \cdot interval)$ . Amplitude of noise is *rms\_value* volts. *start\_time* and *stop\_time* provide a means of specifying a time window over which the source is enabled. Outside this time window, the source will be zero. If *stop\_time* is omitted or zero a value of infinity will be assumed.

### 4.38.9 Extended PWL Source

```
PWLS [TIME_SCALE_FACTOR=time_factor] [VALUE_SCALE_FACTOR=value_factor]
pwl_spec [ pwl_spec ... ]
```

Where:

<i>time_factor</i>	Scales all time values in definition by <i>time_factor</i>
<i>value_factor</i>	Scales all magnitude values by <i>value_factor</i>
<i>pwl_spec</i>	may be one of the following:
<i>(time, value)</i>	Creates a single data point. <i>time</i> is relative to the current context.
<i>(+time, value)</i>	Creates a single data point. <i>time</i> is relative to the previous point.
REPEAT FOR <i>n pwl_spec</i> ENDREPEAT	Repeats <i>pwl_spec</i> <i>n</i> times.
REPEAT FOR- EVER <i>pwl_spec</i> EN- DREPEAT	Repeats <i>pwl_spec</i> forever
SIN <i>sine_parameters</i> END	Creates a sinusoid. See table below for definition of <i>sine_parameters</i>
PULSE <i>pulse_parameters</i> END	Creates a pulse train. See table below for definition of <i>pulse_parameters</i>

**Sine Parameters**

Name	Description	Default	Compulsory
FREQ	Frequency	N/A	Yes
PEAK	Peak value of sine	1.0	No
OFFSET	Offset	0.0	No
DELAY	Delay before sine starts.	0.0	No
PHASE	Phase	0.0	No
CYCLES	Number of cycles. Use -1.0 for infinity	-1.0	No
MINPOINTS	Minimum number of timesteps used per cycle	13	No
RAMP	Frequency ramp factor	0.0	No

The sine value is defined as follows:

```

if t>0 OR DELAY<0
    PEAK * SIN(f*2π*t+PHASE*π/180) + OFFSET
else
    PEAK * SIN(PHASE*π/180) + OFFSET

```

Where:

$$f = \text{FREQ} + t \times \text{RAMP}$$

$$t = \text{time} - \text{tref} - \text{DELAY}$$

*time* is the global simulation time

*tref* is the reference time for this spec

**Pulse Parameters**

Name	Description	Default	Compulsory
V0	Offset	0	No
V1	Positive pulse value	1.0	No
V2	Negative pules value	-1.0	No
RISE	Rise time i.e time to change from V2 to V1	PERIOD/1000	No
FALL	Fall time i.e time to change from V1 to V2	PERIOD/1000	No
WIDTH	Positive pulse width	(PERIOD-RISE-FALL)/2	No
PERIOD	Period	N/A	Yes
DELAY	Delay before start	0	No
CYCLES	Number of complete cycles. -1 means infinity	-1	No

RISE, FALL, WIDTH and PERIOD must be greater than zero. DELAY must be greater than or equal to zero

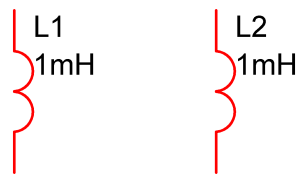
## 4.39 Mutual Inductor

Specifies coupling between two inductors.

### 4.39.1 Netlist Entry

```
Kxxxx l1 l2 coupling_factor
```

<i>l1</i>	Component reference of first inductor
<i>l2</i>	Component reference of second inductor
<i>coupling_factor</i>	Coupling factor, K



If mutual inductance is M then:

$$v_{L_1} = L_1 \frac{di_{L_1}}{dt} + M \frac{di_{L_2}}{dt}$$

$$v_{L_2} = L_2 \frac{di_{L_2}}{dt} + M \frac{di_{L_1}}{dt}$$

$$K = \frac{M}{\sqrt{L_1 \cdot L_2}}$$

K cannot be greater than 1.

### 4.39.2 Notes

You can only couple ideal inductors using this method. The saturable inductor devices may not be coupled in this way. See [“Inductor \(Saturable\)” on page 70](#) for more information.

To use the mutual inductor directly on a schematic you will need to add the device line to the netlist. See [“Adding Extra Netlist Lines” on page 2](#) for information about how to do this.

If you wish to couple more than two inductors, the coupling coefficient (K value) must be specified for every possible combination of two inductors. An error will result if this is not done.

For iron cored transformers values of K between 0.99 and 0.999 are typical. For ferrites lower values should be used. If the windings are concentric (i.e. one on top of the other) then 0.98 to 0.99 are reasonable. If the windings are side by side on a sectioned former, K values are lower - perhaps 0.9 to 0.95. The addition of air gaps tends to lower K values.

### 4.39.3 Example

A transformer with 25:1 turns ratio and primary inductance of 10mH

```

** Inductors
Lprimary N1 N2 10m
Lsecondary N3 N4 16u

** Coupling of 0.99 typical for ungapped ferrite
K1 Lprimary Lsecondary 0.99

```

## 4.40 Verilog-HDL Interface (VSXA)

### 4.40.1 Overview

The VSXA device provides digital functionality defined by a Verilog-HDL definition. The connections to the VSXA device map directly to input and output ports defined within the Verilog-HDL module and may be connected to analog or digital SIMetrix components or other VSXA devices.

The Verilog-HDL simulation is performed by an external Verilog simulator and at least one such simulator is supplied with SIMetrix and is pre-installed with no additional setup or configuration required. Communication between the external Verilog-HDL simulator is achieved through the VPI programming interface and in principle this can allow any VPI compliant Verilog-HDL simulator to be used for this purpose.

This section describes details of the VSXA device. For more general information about using the Verilog-HDL feature, refer to Chapter 13 in the User's Manual.

#### Netlist

```
Uxxxx nodes modelname
```

*nodes* Nodes connecting to Verilog device. Nodes that appear here map directly to the port connections in the top level module in the Verilog file defined in the associated .MODEL statement. If the Verilog definition contains vector connections, the sizes of those connections may be defined using the PORTSIZES model parameter. See below for details.

*modelname* Name of model. Used to reference .MODEL statement

#### Model Syntax

```
MODEL modelname vsxa parameters
```

Name	Description	Units	Default
LOAD	Path to file name of Verilog definition.	n/a	Compulsory

Name	Description	Units	Default
IN_LOW	Input analog low threshold voltage. A logic zero will be detected when the analog voltage drops below this threshold	V	2.2
IN_HIGH	Input analog high threshold voltage. A logic one will be detected when the analog voltage rises above this threshold	V	2.3
OUT_LOW	Output voltage for a logic zero	V	0
OUT_HIGH	Output voltage for a logic one	V	5
T_RISE	Output rise time	sec	100p
T_FALL	Output fall time	sec	100p
IN_RES	Input resistance	Ohms	1e12
OUT_RES	Output resistance for logic zero and logic one states	Ohms	100
OUT_RES_HIZ	Output resistance for the high impedance state	Ohms	1e12
TIME_TOL	Input threshold time tolerance. This parameter works in the same way as the TIME_TOL parameter defined for the A-D Interface bridge used in the built-in digital simulator. This is described in <a href="#">“Time Step Control - TIME_TOL parameter”</a> on page 175	sec	100p
DISABLE_INTERNAL_VECTORS	VSXA instances that are connected to each other but not to any other SIMetrix device still generate digital vectors to allow plotting of those nodes. Setting this parameter to 1 disables this		0 (false)
DISABLE_MODULE_CACHE	No cache data will be created for this model.		0 (false)

Name	Description	Units	Default
PORTSIZES	<p>Array of values defining the size of each port. If any of the Verilog ports are vectors, SIMetrix needs to know their size. If this parameter is not specified, it will assume they are the size defined in the Verilog module. If any is actually smaller, this needs to be defined in this parameter.</p> <p>This is a vector value with one value for each port. So if there are three ports, PORTSIZES would be set like this for example:</p> <pre>PORTSIZES=[2,3,5]</pre> <p>which would set the first port to size 2, the second to size 3 and the last to size 5</p>		see description
PORTINIT	<p>Initial state for input ports if dc solution lies between <code>in_low</code> and <code>in_high</code>. This is a vector value with one value for each input port. So if there are two input ports, PORTINIT would be set like this for example:</p> <pre>PORTINIT=[1,1]</pre> <p>which would set both ports to a logic one indicating if the analog input lies between the defined thresholds. If a PORTINIT value is set to 2, the port will be set to the UNKNOWN state.</p> <p>Note that vector ports are treated as one for this parameter.</p>		0

As well as the above parameters, you can also define values for parameters declared in the associated Verilog file. These carry the same name as the Verilog parameter.

#### 4.40.2 Analog Input Interface

Any port in the Verilog definition that is defined as an input will be treated by the analog simulator as a VSXA input connection. This has the following characteristics:

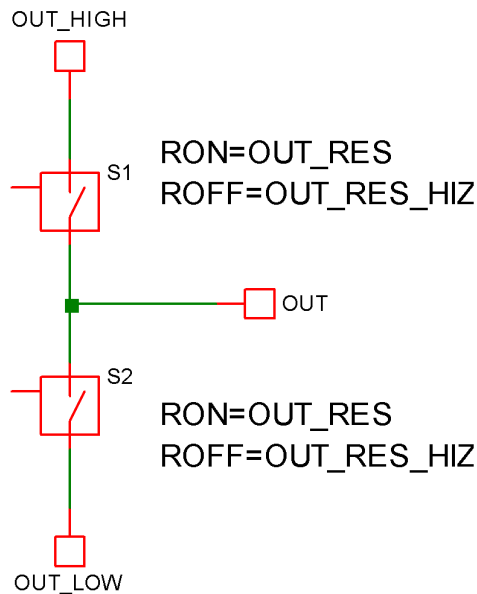
1. Input resistance equal to the value of the `in_res` model parameter.

2. Detects a logic one when the input signal rises above a voltage equal to the *in\_high* model parameter.
3. Detects a logic low when the input signal drops below a voltage equal to the *in\_low* model parameter.
4. When the input voltage is between the *in\_low* and *in\_high* values, the signal detected will be the most recent value detected, that is it will hold its value like a schmitt trigger. For DC and  $t=0$  the value will be that defined by the PORTINIT parameter. This is logic zero by default. A PORTINIT value of 1 will set this to logic one and any other value will set it to an unknown state.
5. The analog system will only send an UNKNOWN state to a Verilog input if the DC voltage lies between the thresholds and the corresponding PORTINIT value is other than 0 or 1. Once an input has acquired a logic zero or logic one state, it will thereafter behave as a schmitt trigger.

**Important:** VSXA inputs that are only connected to other VSXA inputs and no more than one VSXA output are implemented entirely within the Verilog domain and are not connected to the analog simulator. The digital data for such connections is nevertheless made available. See for further details.

### 4.40.3 Analog Output Interface

Any port in the Verilog definition that is defined as an output will be treated by the analog simulator as a VSXA output connection. This is modelled as shown in the following diagram:



Each switch has an on state resistance of `OUT_RES` and an off state resistance of `OUT_RES_HIZ`. In the logic one state, `S1` is on, in the logic zero state `S2` on, while in the high-impedance state, neither switch is on. When transitioning from one state to another state, each switch's resistance changes linearly to the new state's value in the time determined by the parameters `T_RISE` and `T_FALL`.

**Important:** A VSXA output that is only connected to VSXA inputs is implemented entirely within the Verilog domain and are not connected to the analog simulator.

#### 4.40.4 Data Vector Output

##### Voltage Data

Connections between VSXA devices and any other SIMetrix device (including non-Verilog digital devices) are analog nodes in every way and will generate voltage data vectors in the usual way.

Connections between VSXA devices *and* other VSXA devices that do not connect to anything else and do not connect more than one Verilog module output port are implemented entirely within the Verilog simulator domain and do not interface to the analog simulator. For such connections, digital data vectors are created. These transition between the values OUT\_LOW and OUT\_HIGH with rise and fall times equal to the timing resolution set by the VerilogResolution option setting. This defaults to 1fs.

In some situations it is possible that the overhead of creating this data could slow down the simulation. This would be the case where such internally connected signals carry high speed data that is much faster than the analog time steps. In these cases the output of this data can be disabled using the DISABLE\_INTERNAL\_VECTORS parameter for the VSXA device that carries the output driving port. They can also be globally disabled using the VerilogDisableInternalVectors [.OPTION](#) setting.

##### Current Data

VSXA devices generate current vectors in the normal way for all connections that connect to analog signals. These vectors are named as follows:

```
ref#port_name
```

In the case of vector ports port\_name is the name of the port appended with the index of the wire within the port. For example, with the following Verilog definition:

```
module adder(in1, in2, out) ;
    input [3:0] in1 ;
    input [3:0] in2 ;
    output [3:0] out ;
endmodule
```

the *port\_names* for the out port would be out0, out1, out2 and out3.

#### 4.40.5 Module Cache

##### Operation

Before starting a simulation and also when creating a symbol from a Verilog design, SIMetrix needs to gather some information about each Verilog module used in the circuit. It does this by starting a Verilog simulation then interrogating the Verilog simulator via VPI. This process can take some time if there are many Verilog modules in the circuit. To speed things up, SIMetrix caches the information obtained for future use.

The cache mechanism calculates the MD5 checksum of the Verilog file and stores this with the cached information in the cache file. When the cached information is required, SIMetrix calculates the MD5 checksum of the Verilog file and looks to see whether there is a cache item with that MD5 value. If there is, it will use the cached data. If not it will retrieve the information via the Verilog simulator.



## Location

The cache file is located at *vdatapath/module-cache.sxche*

Where *vdatapath* is a directory defined by the `VIDataPath` global option setting. This can be set using the `Set` command typed at the command line. E.g.

```
Set VIDataPath=path
```

The default value of *path* is:

```
simetrix_app_data_dir/veriloghdl
```

*simetrix\_app\_data\_dir* is the directory where SIMetrix configuration settings are stored and defaults to `C:\Users\login-name\AppData\Roaming`. Refer to *User's Manual/Sundry Topics/-Configuration Settings/Application Data Directory* for details about the Application Data path *simetrix\_app\_data\_dir*.

Be aware that this file is created when a simulation is closed. This takes place when a new simulation is started, when the `Reset` script command is executed or when the simulator process terminates.

## Limitations

The cache mechanism only looks at the contents of the Verilog file referenced. It does not take account of include files for example. However, the only information stored in the cache are the module name, names and direction of the module ports and the names, types and default values of any parameters. It would be unusual to store these items in an include file but of course this is perfectly legal.

If the top level ports or/and parameters for your Verilog design are not defined in the main file but in an include file, then you should either redesign the Verilog file or alternatively disable the cache for that module.

The cache can be disabled by setting the `DISABLE_MODULE_CACHE` model parameter. **Important:** the `DISABLE_MODULE_CACHE` parameter disables the creation of cached information; it does not disable using cached information if it already exists. This is because the cache is read before model parameters are read. You may wish to clear the cache altogether when setting this parameter. This can be done from the front end with menu **Verilog | Clear Verilog-HDL Module Info Cache**.

The cache can also be globally disabled using the `.OPTIONS` setting `VerilogDisableModuleCache`.

## 4.41 NXP Compact Models

### 4.41.1 Introduction

SIMetrix supports a range of device models developed by NXP Semiconductor.

This supersedes the old Philips compact models (PCM) interface, however, the older devices are still available if needed. Versions of devices that are available through both interfaces (e.g MOS 9.03) will now default to the SIMKIT interface but the old version is still available by selecting a different level number. PCM devices do not support multi-core execution and so usually the Simkit versions will run faster.

The table below shows the models available. Model statements should be in the form:

```
.model model_name model_type_name LEVEL=level_number parameters
```

E.g.

```
.model my_model nmos LEVEL=103 ...
```

defines a MOS 9 nmos device.

To instantiate the device line must start with the letter as defined in the Device Letter column in the table below. The number of nodes must be within the range specified in the table.

#### 4.41.2 SIMKIT Devices

The following table shows all available SIMKIT NXP models

Device Name	Model Type Name	Device Letter	Max num Terms.	Min num Terms.	Level	Description
mos903e_n	nmos	M	4	4	103	MOS 9 Electrical N chan
mos903e_p	pmos	M	4	4	103	MOS 9 Electrical P chan
mos903_n	nmos	M	4	4	203	MOS 9 Geom. N chan
mos903_p	pmos	M	4	4	203	MOS 9 Geom. P chan
mos903t_n	nmos	M	5	4	223	MOS 9 Thermal N chan
mos903t_p	pmos	M	5	4	223	MOS 9 Thermal P chan
bjt504_n	npn	Q	4	3	104	Mextram 4 term NPN
bjt504_p	pnp	Q	4	3	104	Mextram 4 term PNP
bjt504t_n	npn	Q	5	3	124	Mextram Thermal NPN
bjt504t_p	pnp	Q	5	3	124	Mextram Thermal PNP
bjt3500_n	npn	Q	4	3	304	BJT 3500 NPN
bjt3500_p	pnp	Q	4	3	304	BJT 3500 PNP
bjt3500t_n	npn	Q	5	3	324	BJT 3500 Thermal NPN

Device Name	Model Type Name	Device Letter	Max num Terms.	Min num Terms.	Level	Description
bjt3500t_p	pnp	Q	5	3	324	BJT 3500 Thermal PNP
bjt500_p	pnp	Q	4	3	200	BJT Level 500 Lateral PNP
bjt500t_p	pnp	Q	5	3	220	BJT Level 500 Lateral PNP, thermal
psp1020_n	nmos	M	4	4	902	PSP 1.02 nmos
psp1020_p	pmos	M	4	4	902	PSP 1.02 pmos
psp1021_n	nmos	M	4	4	912	PSP 1.02 nmos binned version
psp1021_p	pmos	M	4	4	912	PSP 1.02 pmos binned version
psp102e_n	nmos	M	4	4	802	PSP 1.02 nmos electrical
psp102e_p	pmos	M	4	4	802	PSP 1.02 pmos electrical
pspnqs1020_n	nmos	M	4	4	942	PSP 1.02 nmos, non-quasi static
pspnqs1020_p	pmos	M	4	4	942	PSP 1.02 pmos, non-quasi static
pspnqs1021_n	nmos	M	4	4	952	PSP 1.02 nmos, non-quasi static, binned
pspnqs1021_p	pmos	M	4	4	952	PSP 1.02 pmos, non-quasi static, binned
pspnqs102e_n	nmos	M	4	4	842	PSP 1.02 nmos, non-quasi static, electrical

Device Name	Model Type Name	Device Letter	Max num Terms.	Min num Terms.	Level	Description
pspnqs102e_p	pmos	M	4	4	842	PSP 1.02 pmos, non-quasi-static, electrical
psp103_n	nmos	M	4	4	903	PSP 1.03 nmos
psp103_p	pmos	M	4	4	903	PSP 1.03 pmos
pspnqs103_n	nmos	M	4	4	943	PSP 1.03 nmos, non-quasi-static
pspnqs103_p	pmos	M	4	4	943	PSP 1.03 pmos, non-quasi-static
mos1102e_n	nmos	M	4	4	502	MOS 11, 1102 nmos, electrical
mos1102e_p	pmos	M	4	4	502	MOS 11, 1102 pmos, electrical
mos1102et_n	nmos	M	5	4	522	MOS 11, 1102 nmos, electrical, thermal
mos1102et_p	pmos	M	5	4	522	MOS 11, 1102 pmos, electrical, thermal
mos11020_n	nmos	M	4	4	602	MOS 11, 1102 nmos, geometric
mos11020_p	pmos	M	4	4	602	MOS 11, 1102 pmos, geometric
mos11020t_n	nmos	M	5	4	622	MOS 11, 1102 nmos, geometric, thermal
mos11020t_p	pmos	M	5	4	622	MOS 11, 1102 pmos, geometric, thermal

Device Name	Model Type Name	Device Letter	Max num Terms.	Min num Terms.	Level	Description
mos11021_n	nmos	M	4	4	612	MOS 11, 1102 nmos, geometric, binned
mos11021_p	pmos	M	4	4	612	MOS 11, 1102 pmos, geometric, binned
mos11021t_n	nmos	M	5	4	632	MOS 11, 1102 nmos, geometric, binned, thermal
mos11021t_p	pmos	M	5	4	632	MOS 11, 1102 pmos, geometric, binned, thermal
mos1101e_n	nmos	M	4	4	501	MOS 11, 1101 nmos, electrical
mos1101e_p	pmos	M	4	4	501	MOS 11, 1101 pmos, electrical
mos1101et_n	nmos	M	5	4	521	MOS 11, 1101 nmos, electrical, thermal
mos1101et_p	pmos	M	5	4	521	MOS 11, 1101 pmos, electrical, thermal
mos11010_n	nmos	M	4	4	601	MOS 11, 1101 nmos, geometric
mos11010_p	pmos	M	4	4	601	MOS 11, 1101 pmos, geometric
mos11010t_n	nmos	M	5	4	621	MOS 11, 1101 nmos, geometric, thermal
mos11010t_p	pmos	M	5	4	621	MOS 11, 1101 pmos, geometric, thermal

Device Name	Model Type Name	Device Letter	Max num Terms.	Min num Terms.	Level	Description
mos11011_n	nmos	M	4	4	611	MOS 11, 1101 nmos, geometric, binned
mos11011_p	pmos	M	4	4	611	MOS 11, 1101 pmos, geometric, binned
mos11011t_n	nmos	M	5	4	631	MOS 11, 1101 nmos, geometric, binned, thermal
mos11011t_p	pmos	M	5	4	631	MOS 11, 1101 pmos, geometric, binned, thermal
juncap	d	D	2	2	101	JUNCAP
juncap200	d	D	2	2	102	JUNCAP 200
mos2002_n	nmos	M	4	4	1302	MOS Model 20 level 2002, nmos
mos2002_p	pmos	M	4	4	1302	MOS model 20 level 2002, pmos
mos2002e_n	nmos	M	4	4	1202	MOS Model 20 level 2002, nmos, electrical
mos2002e_p	pmos	M	4	4	1202	MOS Model 20 level 2002, pmos, electrical
mos2002t_n	nmos	M	5	4	1322	MOS Model 20 level 2002, nmos, thermal
mos2002t_p	pmos	M	5	4	1322	MOS Model 20 level 2002, pmos, thermal
mos2002et_n	nmos	M	5	4	1222	MOS Model 20 level 2002, nmos, electrical, thermal

Device Name	Model Type Name	Device Letter	Max num Terms.	Min num Terms.	Level	Description
mos2002et_p	pmos	M	5	4	1222	MOS Model level 2002, pmos, electrical, thermal
mos3100_n	nmos	M	4	4	700	MOS Model Level 3100, nmos
mos3100_p	pmos	M	4	4	700	MOS Model Level 3100, pmos
mos3100t_n	nmos	M	5	4	720	MOS Model Level 3100, nmos, thermal
mos3100t_p	pmos	M	5	4	720	MOS Model Level 3100, pmos, thermal
mos40_n	nmos	M	4	4	400	MOS model Level 40, nmos
mos40_p	pmos	M	4	4	400	MOS model Level 40, pmos
mos40t_n	nmos	M	5	4	420	MOS model Level 40, nmos, thermal
mos40t_p	pmos	M	5	4	420	MOS model Level 40, pmos, thermal

### 4.41.3 Notes on SIMKIT Models

#### Binned Models

Binned models are not yet integrated with the library binning system. So, to use the binning features of binned models, you will need to manually generate separate model names for each bin.

#### Real Time Noise

Some models do not fully implement real-time noise. Many MOS models include frequency dependent gate noise and this is not included in real-time noise analyses. Also some models include

correlated noise which is also not included. In most cases these effects are small anyway and have little effect.

You can set this option in AC small-signal noise:

```
.options noMos9GateNoise
```

to disable the same effects in AC small signal noise. A comparison can then be made to estimate the effect these noise sources may have in real-time noise. Although the option name suggests that it only applies to MOS9, this does in fact work with all applicable models.

In the case of PSP 102 models, you can instead invoke the Verilog-A based model which fully supports all noise effects in real-time noise analysis. See next section for details.

## PSP 102

The PSP 102 nmos and pmos geometric models (level 902) are also available as level 1023. However the two models are implemented differently. Level 902 is implemented through the SIMKIT interface. The model code itself in this case is created using ADMS from the Verilog-A description. However, it seems that the noise model for this is not created from the Verilog-A code and appears to have been hand coded.

The Level 1023 version is built entirely from the Verilog-A code using the SIMetrix Verilog-A compiler but using a more advanced commercial C-compiler than the open source version supplied with SIMetrix. This version has the benefit over the Simkit version that it fully supports real-time noise including correlated effects and gate noise. It is however a little slower - typically about 5-10% compared to the SIMKIT version.

We have done extensive side by side tests of both models and both give identical results to a high degree of accuracy.

### 4.41.4 PCM Devices

The following table shows the older PCM (Philips Compact Model) devices still supported by the level numbers used for SIMetrix versions 6.2 and earlier. These are provided only for backward compatibility. Note that the PCM interface does not support multi-core simulation and so will run slower than the SIMKIT devices.

Description	NXP name	SPICE model type	SPICE Level	Device letter	Number of terms
MOS 9 Electrical, version 9.02	MNE_902 MPE_902	nmos, pmos	102	M	4
MOS 9 Electrical, version 9.03	MNE_903 MPE_903	nmos, pmos	103	M	4
MOS 9 Geometric, version 9.02	MN_902 MP_902	nmos, pmos	202	M	4
MOS 9 Geometric, version 9.03	MN_903 MP_903	nmos, pmos	203	M	4
MOS 11 Electrical	MNE_1100 MPE_1100	nmos, pmos	500	M	4
MOS 11 Geometric	MN_1100 MP_1100	nmos, pmos	600	M	4



Description			NXP name	SPICE model type	SPICE Level	Device letter	Number of terms
Mextram 5.03	4	term	TNS_503, TPS_503	npn, pnp	103	Q	4

#### 4.41.5 Notes on PCM Models

##### MOS9/11 and Real Time Noise

The gate thermal noise of the MOS9/11 device is not implemented for real-time noise analysis. In practice the effect of this noise component is usually small and only occurs at high frequencies. To investigate the contribution of this component to overall circuit behaviour, it can be disabled in AC noise analysis by setting the option NoMos9GateNoise.

#### 4.41.6 Documentation

Original NXP documentation on these models can be found in a number of PDF files on the installation CDROM and at our web site. Please visit [“Further Documentation”](#) on page 41 for details.

## Chapter 5

# Digital/Mixed Signal Device Reference

## 5.1 Digital Device Overview

### 5.1.1 Common Parameters

A number of model parameters are common to most of the digital models. These are described below.

#### Family Parameters

These identify the logic family to which the input and outputs belong. See [“Logic families” on page 282](#) for a detailed explanation. Most models have three family parameters:

Family name	Description
in_family	Specifies family for inputs. If omitted, the input family is specified by the FAMILY parameter
out_family	Specifies family for outputs. If omitted, the output family is specified by the FAMILY parameter
family	Default value for IN_FAMILY and OUT_FAMILY

#### Output Parameters

Parameter name	Description
out_res	This is used to calculate loading delay. It has dimensions of Ohms so is referred to as a resistance. The additional loading delay is calculated by multiplying OUT_RES by the total capacitive load detected on the node to which the output connects.

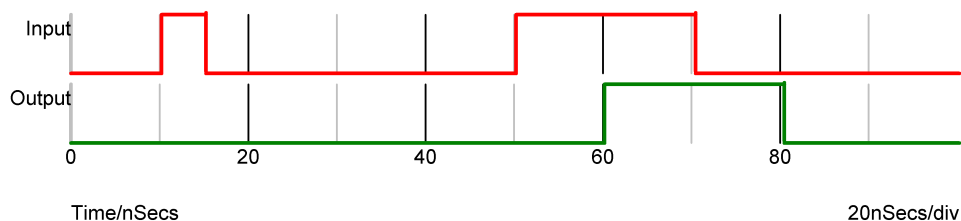
Parameter name	Description
min_sink	Used to calculate static loading effects. This is the current that the device is able to sink. Current flowing out of the pin is positive so this parameter is usually negative. If the total sink load current is arithmetically smaller (i.e. more negative) than this parameter then the output will be forced to an UNKNOWN state. This is used to implement fan out limitations in bipolar logic.
max_source	Used to calculate static loading effects. This is the current that the device is able to source. Current flowing out of the pin is positive. If the total source load current is larger than this parameter then the output will be forced to an UNKNOWN state. This is used to implement fan out limitations in bipolar logic.

### Input Parameters

Parameter name	Description
sink_current	Current that the input sinks. Positive current flows into the device so this parameter is usually negative. The total of all the input sink currents are added together when a node is in the logic '0' state. If the total sink load current is arithmetically smaller (i.e. more negative) than the MIN_SINK parameter of the device driving the node, then it will be forced to an UNKNOWN state. This is used to implement fan out limitations in bipolar logic.
source_current	Current that the input sources. Positive current flows into the device. The total of all the input source currents are added together when a node is in the logic '1' state. If the total source load current is larger than the MAX_SOURCE parameter of the device driving the node, then it will be forced to an UNKNOWN state. This is used to implement fan out limitations in bipolar logic.

### 5.1.2 Delays

Most digital devices have at least one model parameter that specifies a time delay. Unless otherwise noted, all delays are *inertial*. This means that glitches shorter than the delay time will be swallowed and not passed on. For example, the following waveforms show the input and output of a gate that has a propagation delay of 10nS. The first pulse is only 5nS so does not appear at the output. The second pulse is 20nS so therefore is present at the output delayed by 10nS.



The Buffer device has an optional *stored delay* (also known as transport delay) parameter that makes possible the specification of pure delays.

## 5.2 And Gate

### 5.2.1 Netlist entry:

```
Axxxx [ in_0 in_1 .. in_n ] out model_name
```

### 5.2.2 Connection details

Name	Description	Flow	Type	Vector bounds
in	Input	in	d, vector	$2 - \infty$
out	Output	out	d	n/a

### 5.2.3 Model format

```
.MODEL model_name d_and parameters
```

### 5.2.4 Model parameters

Name	Description	Type	Default	Limits
rise_delay	Rise delay	real	1nS	1e-12 - $\infty$
fall_delay	Fall delay	real	1nS	1e-12 - $\infty$
input_load	Input load value (F)	real	1pF	none
family	Logic family	string	UNIV	none
in_family	Input logic family	string	UNIV	none
out_family	Output logic family	string	UNIV	none
out_res	Digital output resistance	real	100	0 - $\infty$
out_res_pos	Digital output res. pos. slope	real	out_res	0 - $\infty$
out_res_neg	Digital output res. neg. slope		out_res	0 - $\infty$
open_c	Open collector output	boolean	FALSE	none
min_sink	Minimum sink current	real	-0.001	none
max_source	Maximum source current	real	0.001	none
sink_current	Input sink current	real	0	none
source_current	Input source current	real	0	none

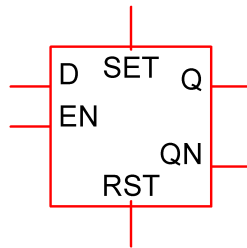
### 5.2.5 Device operation

- If the model parameter OPEN\_C is false, The output will be at logic '0' if either input is at logic '0'. Otherwise, if any input is UNKNOWN, the output will be UNKNOWN. Otherwise

the output will be at logic '1'.

- If the model parameter OPEN\_C is true the device will be open collector. In this case the output logic state is always '0'. The state of the inputs instead determines the *strength* of the output. If either input is at logic '0' the output strength will be STRONG. Otherwise if any input is UNKNOWN the output strength will be UNDETERMINED. Otherwise the output strength will be HI-IMPEDANCE allowing a pull-up resistor to force it to the logic '1' state.

## 5.3 D-type Latch



### 5.3.1 Netlist entry

```
Axxxx data enable set reset out nout model_name
```

### 5.3.2 Connection details

Name	Description	Flow	Type
data	Input data	in	d
enable	Enable	in	d
set	Asynchronous set	in	d
reset	Asynchronous reset	in	d
out	Data output	out	d
nout	Inverted data output	out	d

### 5.3.3 Model format

```
.MODEL model_name d_dlatch parameters
```

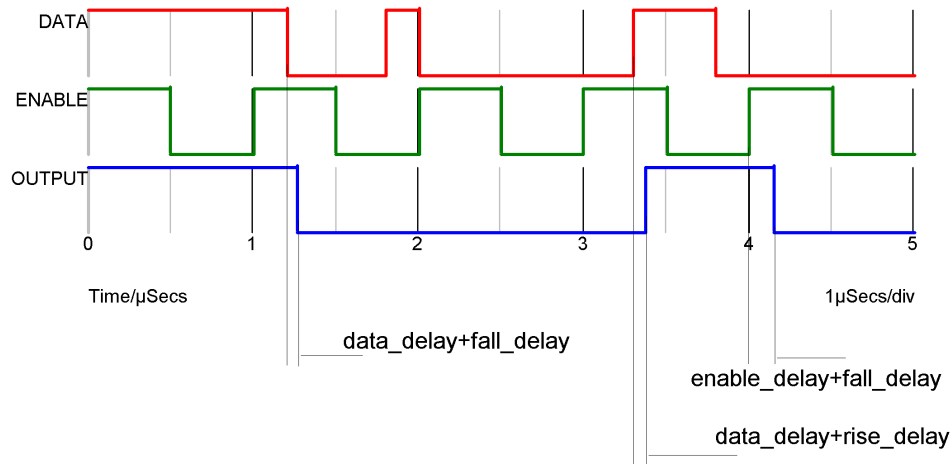
### 5.3.4 Model parameters

Name	Description	Type	Default	Limits
data_delay	Delay from data	real	1nS	1e-12 $-\infty$
enable_delay	Delay from enable	real	1nS	1e-12 $-\infty$

Name	Description	Type	Default	Limits
set_delay	Delay from set	real	1nS	1e-12 $-\infty$
reset_delay	Delay from reset	real	1nS	1e-12 $-\infty$
ic	Output initial state 0: logic '0' 1: logic '1' 2: UNKNOWN	integer	0	0 - 2
rise_delay	Rise delay	real	1nS	1e-12 $-\infty$
fall_delay	Fall delay	real	1nS	1e-12 $-\infty$
data_load	Data load value (F)	real	1pF	none
enable_load	Enable load value (F)	real	1pF	none
set_load	Set load value (F)	real	1pF	none
reset_load	Reset load value (F)	real	1pF	none
family	Logic family	string	UNIV	none
in_family	Input logic family	string	UNIV	none
out_family	Output logic family	string	UNIV	none
out_res	Digital output resistance	real	100	0 $-\infty$
out_res_pos	Digital output res. slope pos.	real	out_res	0 $-\infty$
out_res_neg	Digital output res. slope neg.	real	out_res	0 $-\infty$
min_sink	Minimum sink current	real	-0.001	none
max_source	Maximum source current	real	0.001	none
sink_current	Input sink current	real	0	none
source_current	Input source current	real	0	none

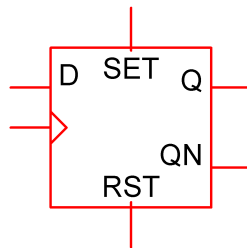
### 5.3.5 Device Operation

The device is a level triggered latch with a single data input, complimentary outputs and active high asynchronous set and reset. The operation of the device is illustrated in the following diagram:



The asynchronous inputs (set and reset) override the action of the enable and data lines.

## 5.4 D-type Flip Flop



### 5.4.1 Netlist entry

```
Axxxx data clk set reset out nout model_name
```

### 5.4.2 Connection details

Name	Description	Flow	Type
data	Input data	in	d
clk	Clock	in	d
set	Asynchronous set	in	d
reset	Asynchronous reset	in	d
out	Data output	out	d
nout	Inverted data output	out	d

### 5.4.3 Model format

```
.MODEL model_name d_dff parameters
```

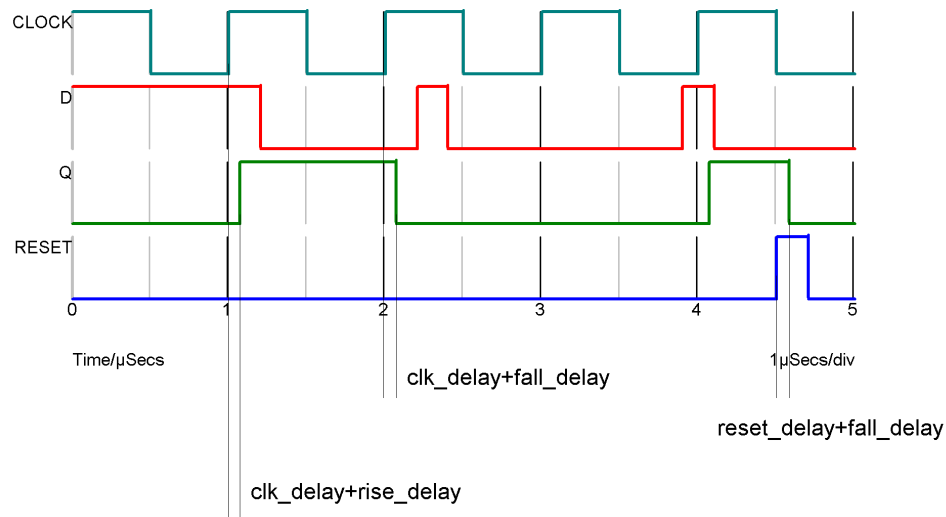
### 5.4.4 Model parameters

Name	Description	Type	Default	Limits
clk_delay	Delay from clk	real	1nS	1e-12 $-\infty$
set_delay	Delay from set	real	1nS	1e-12 $-\infty$
reset_delay	Delay from reset	real	1nS	1e-12 $-\infty$
ic	Output initial state 0: logic '0' 1: logic '1' 2: UNKNOWN	integer	0	0 - 2
rise_delay	Rise delay	real	1nS	1e-12 $-\infty$
fall_delay	Fall delay	real	1nS	1e-12 $-\infty$
data_load	Data load value (F)	real	1pF	none
clk_load	Clk load value (F)	real	1pF	none
set_load	Set load value (F)	real	1pF	none
reset_load	Reset load value (F)	real	1pF	none
family	Logic family	string	UNIV	none
in_family	Input logic family	string	UNIV	none
out_family	Output logic family	string	UNIV	none
out_res	Digital output resistance	real	100	0 $-\infty$
out_res_pos	Digital output res. slope pos.	real	out_res	0 $-\infty$
out_res_neg	Digital output res. slope neg.	real	out_res	0 $-\infty$
min_sink	Minimum sink current	real	-0.001	none
max_source	Maximum source current	real	0.001	none
sink_current	Input sink current	real	0	none
source_current	Input source current	real	0	none

### 5.4.5 Device Operation

The device is an edge triggered D-type flip flop with active high asynchronous set and reset. The operation of the device is illustrated by the following diagram:





## 5.5 Buffer

### 5.5.1 Netlist entry

```
Axxxx in out model_name
```

### 5.5.2 Connection details

Name	Description	Flow	Type
in	Input	in	d
out	Output	out	d

### 5.5.3 Model format

```
.MODEL model_name d_buffer parameters
```

### 5.5.4 Model parameters

Name	Description	Type	Default	Limits
rise_delay	Rise delay	real	1nS	1e-12 $-\infty$
fall_delay	Fall delay	real	1nS	1e-12 $-\infty$
stored_delay	Stored delay (overrides rise_delay and fall_delay)	real	0	0 $-\infty$
input_load	Input load value (F)	real	1pF	none
family	Logic family	string	UNIV	none
in_family	Input logic family	string	UNIV	none

Name	Description	Type	Default	Limits
out_family	Output logic family	string	UNIV	none
out_res	Digital output resistance	real	100	0 – ∞
out_res_pos	Digital output res. pos. slope	real	out_res	0 – ∞
out_res_neg	Digital output res. neg. slope		out_res	0 – ∞
open_c	Open collector output	boolean	FALSE	none
min_sink	Minimum sink current	real	-0.001	none
max_source	Maximum source current	real	0.001	none
sink_current	Input sink current	real	0	none
source_current	Input source current	real	0	none
open_e	Open emitter output	boolean	FALSE	none

### 5.5.5 Device Operation

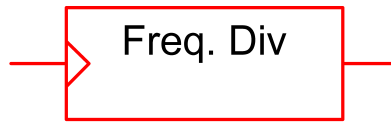
This device is a simple buffer with a single input and output. It can optionally be specified to have an open collector (`open_c` parameter) or open emitter (`open_e` parameter) output. Further, if the `stored_delay` parameter is specified, the device will act as a pure delay. This means that it will pass pulses that are shorter than the delay time whereas normally (delay specified by `rise_delay` and `fall_delay`) such pulse would be swallowed (`stored_delay` is also known as *transport delay*).

The following table describes the device operation in detail

OPEN_C parameter	OPEN_E parameter	Input	Output state	Output strength
FALSE	FALSE	0	0	STRONG
FALSE	FALSE	1	1	STRONG
FALSE	FALSE	UNKNOWN	UNKNOWN	STRONG
FALSE	TRUE	0	0	HI-IMPEDANCE
FALSE	TRUE	1	1	STRONG
FALSE	TRUE	UNKNOWN	UNKNOWN	UNDETERMINED
TRUE	FALSE	0	0	STRONG
TRUE	FALSE	1	0	HI-IMPEDANCE
TRUE	FALSE	UNKNOWN	0	UNDETERMINED
TRUE	TRUE	0	1	HI-IMPEDANCE
TRUE	TRUE	1	0	HI-IMPEDANCE
TRUE	TRUE	UNKNOWN	UNKNOWN	UNDETERMINED

Note the difference between open emitter and open collector operation. These modes have been designed to be as close to as possible to real devices, in particular their behaviour into an open circuit. An open emitter output, when switching from high to low is likely to follow the voltage on the device's base due to the base-emitter capacitance so the output state follows the input state. An open collector (or open drain) output on the other hand will remain in the low state when its input switches.

## 5.6 Frequency Divider



### 5.6.1 Netlist entry

```
Axxxx freq_in freq_out model_name
```

### 5.6.2 Connection details

Name	Description	Flow	Type
freq_in	Frequency input	in	d
freq_out	Frequency output	out	d

### 5.6.3 Model format

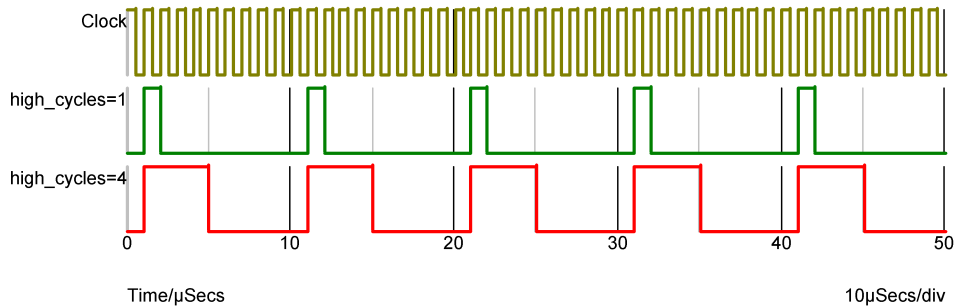
```
.MODEL model_name d_fdiv parameters
```

### 5.6.4 Model parameters

Name	Description	Type	Default	Limits
div_factor	Divide factor	integer	2	1 – $\infty$
high_cycles	Number of high clock cycles	integer	1	1 – $\infty$
i_count	Output initial count value	integer	0	0 – $\infty$
rise_delay	Rise delay	real	1nS	1e-12 – $\infty$
fall_delay	Fall delay	real	1nS	1e-12 – $\infty$
freq_in_load	Freq_in load value (F)	real	1pF	none
family	Logic family	string	UNIV	none
in_family	Input logic family	string	UNIV	none
out_family	Output logic family	string	UNIV	none
out_res	Digital output resistance	real	100	0 – $\infty$
out_res_pos	Digital output res. pos. slope	real	out_res	0 – $\infty$
out_res_neg	Digital output res. neg. slope		out_res	0 – $\infty$
min_sink	Minimum sink current	real	-0.001	none
max_source	Maximum source current	real	0.001	none
sink_current	Input sink current	real	0	none
source_current	Input source current	real	0	none

### 5.6.5 Device Operation

This device is a positive edge triggered frequency divider. Three model parameters allow arbitrary definition of the divide ratio, output duty cycle, output phase and initial delay. Operation of the frequency divider is illustrated by the following diagram which shows the output of a frequency divider with a DIV\_FACTOR of 10 and two alternative values of HIGH\_CYCLES.



The above was carried out with I\_COUNT=0. I\_COUNT is the initial value of the internal counter. The output first goes high when it attains a value of 1 or 1+DIVIDE\_RATIO so when I\_COUNT is zero (the default) the output first goes high after the first rising edge. If I\_COUNT is set to 5 the output first goes high after the 6th rising edge and if I\_COUNT is -20, the 21st rising edge.

## 5.7 Digital Initial Condition

### 5.7.1 Netlist entry

```
Axxxx out model_name
```

### 5.7.2 Connection details

Name	Description	Flow	Type
out	Output	out	d

### 5.7.3 Model format

```
.MODEL model_name d_init parameters
```

### 5.7.4 Model parameters

Name	Description	Type	Default	Limits
ic	Initial state	integer	0	none
is	Initial strength 1 = STRONG 0 = RESISTIVE	integer	1	none
out_family	Output logic family	string	UNIV	none

### 5.7.5 Device Operation

This device has the defined initial state (IC parameter) and initial strength (IS parameter) during the DC operating point solution, then reverts to HI-IMPEDANCE for the remainder of the analysis.

## 5.8 Digital Pulse

### 5.8.1 Netlist entry

```
Axxxx out model_name : parameters
```

### 5.8.2 Connection details

Name	Description	Flow	Type
out	Output	out	d

### 5.8.3 Instance parameters

Name	Description	Type
period	Pulse period	real
delay	Delay	real
duty	Duty cycle	real
width	Pulse width	real
open_out	Open emitter output	boolean

### 5.8.4 Model format

```
.MODEL model_name d_pulse parameters
```

### 5.8.5 Model parameters

Name	Description	Type	Default	Limits
duty	Duty cycle	real	0.5	1e-06 - 0.999999
delay	Initial delay	real	0	0 - $\infty$
period	Period. If zero, a single pulse will be output	real	1 $\mu$ S	1e-12 - $\infty$
width	Pulse width (overrides duty if specified)	real	period * duty	0 - $\infty$
open_out	Open emitter output	boolean	FALSE	none
out_family	Output logic family	string	UNIV	none

Name	Description	Type	Default	Limits
out_res	Digital output resistance	real	100	0 – ∞
out_res_pos	Digital output res. pos. slope	real	out_res	0 – ∞
out_res_neg	Digital output res. neg. slope		out_res	0 – ∞
min_sink	Minimum sink current	real	-0.001	none
max_source	Maximum source current	real	0.001	none

### 5.8.6 Device Operation

This device supplies a repetitive or single pulse of defined period, delay and width. Optionally, the device may be specified to have an open emitter output allowing several pulse sources to be wire OR'ed to create complex pulses. All 5 main .MODEL parameters may also be specified on the device line as instance parameters in which case they override any values specified in the .MODEL statement.

If OPEN\_OUT is specified and true, a pull down resistor must be connected to the output.

## 5.9 Digital Signal Source

### 5.9.1 Netlist entry

```
Axxxx [ out_0 out_1 .. out_n ] model_name
```

### 5.9.2 Connection details

Name	Description	Flow	Type
out	Output	out	d, vector

### 5.9.3 Model format

```
.MODEL model_name d_source parameters
```

### 5.9.4 Model parameters

Name	Description	Type	Default	Limits
input_file	Digital input vector filename	string	none	none
out_family	Output logic family	string	UNIV	none
out_res	Digital output resistance	real	100	0 – ∞
out_res_pos	Digital output res. pos. slope	real	out_res	0 – ∞
out_res_neg	Digital output res. neg. slope		out_res	0 – ∞

Name	Description	Type	Default	Limits
min_sink	Minimum sink current	real	-0.001	none
max_source	Maximum source current	real	0.001	none

### 5.9.5 Device Operation

The digital signal source provides a multi bit arbitrary digital signal defined in a file.

### 5.9.6 File Format

The file is in ASCII format and is in the form of a table each row being on a new line. The first column defines the time values while the entries in the remaining columns define the output value for each of the outputs. So the total number of columns must be the number of outputs plus one. The output values must appear in the same order as the outputs in the netlist entry. So, the values for out\_0 will be in column 2, out\_1 in column 3 etc.

The file may include blank lines and comment lines beginning with a ‘\*’.

The output values must specify the state as well as the strength using the following codes:

Code	State-Strength
0S	LOW-STRONG
1S	HIGH-STRONG
US	UNKNOWN-STRONG
0R	LOW-RESISTIVE
1R	HIGH-RESISTIVE
UR	UNKNOWN-RESISTIVE
0Z	LOW-HI-Z
1Z	HIGH-HI-Z
UZ	UNKNOWN-HI-Z
0U	LOW-UNDETERMINED
1U	HIGH-UNDETERMINED
UU	UNKNOWN-UNDETERMINED

Note, these codes are not case sensitive.

### 5.9.7 Example

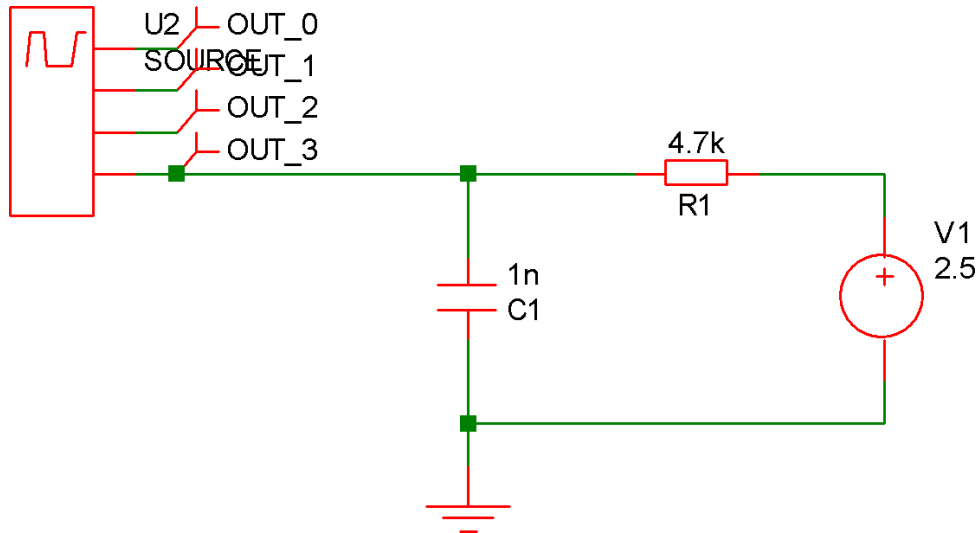
The following file:

```
* This is an example source file
0.0 0s 0s 0r 1s
1u 0s 0s 0r 0z
2u 0s 0s 1r 0z
5u 1s 0s 1r 0z
22e-6 1s 1s 1r 0z
```

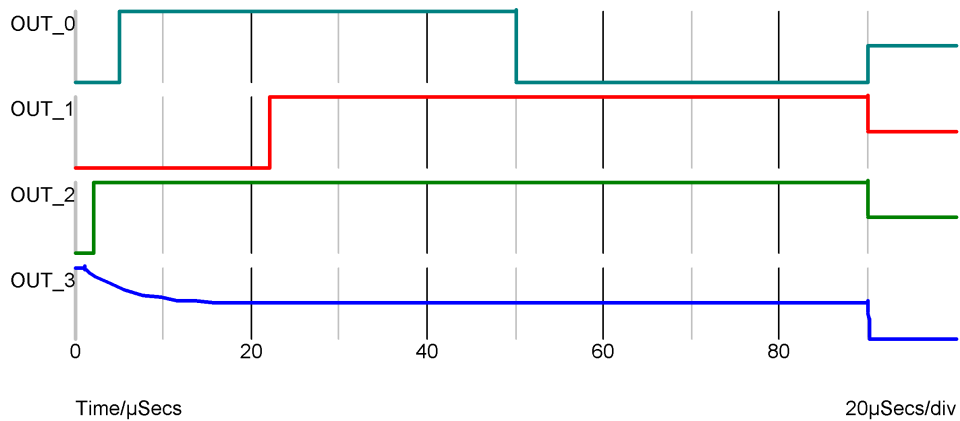
```

50u 0s 1s 1r 0z
60u 0s 1s 1r 0z
70u 0s 1s 1r 0z
80u 0s 1s 1r 0z
90u Us Us Ur 0s
    
```

and this circuit:



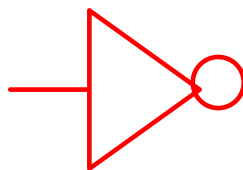
Produces the following waveforms



An error will result if the file fails in any way to comply with the format. There must be the exact number of entries in each row and the time values must be monotonic. Totally blank lines or lines containing only white space are permitted but any other non-comment line not complying with the format will fail.



## 5.10 Inverter



### 5.10.1 Netlist entry

```
Axxxx in out model_name
```

### 5.10.2 Connection details

Name	Description	Flow	Type
in	Input	in	d
out	Output	out	d

### 5.10.3 Model format

```
.MODEL model_name d_inverter parameters
```

### 5.10.4 Model parameters

Name	Description	Type	Default	Limits
rise_delay	Rise delay	real	1nS	1e-12 $-\infty$
fall_delay	Fall delay	real	1nS	1e-12 $-\infty$
input_load	Input load value (F)	real	1pF	none
family	Logic family	string	HC	none
in_family	Input logic family	string	UNIV	none
out_family	Output logic family	string	UNIV	none
out_res	Digital output resistance	real	100	0 $-\infty$
out_res_pos	Digital output res. pos. slope	real	out_res	0 $-\infty$
out_res_neg	Digital output res. neg. slope		out_res	0 $-\infty$
open_c	Open collector output	boolean	FALSE	none
min_sink	Minimum sink current	real	-0.001	none
max_source	Maximum source current	real	0.001	none
sink_current	Input sink current	real	0	none
source_current	Input source current	real	0	none

### 5.10.5 Device Operation

If the `OPEN_C` parameter is not specified or is `FALSE`, this device simply inverts the state of its input. I.e. if the input is logic '0' the output will be logic '1' and vice-versa. If the input is `UNKNOWN` the output will also be `UNKNOWN`.

If `OPEN_C` is `TRUE`, the output state is always at logic '0' and the input determines its strength. If the input is at logic '1' the output strength is `STRONG` and if it is at logic '0' the output strength is `HI-IMPEDANCE`. The output strength will be `UNDETERMINED` if the input is `UNKNOWN`.

## 5.11 JK Flip Flop

### 5.11.1 Netlist entry

```
Axxxx j k clk set reset out nout model_name
```

### 5.11.2 Connection details

Name	Description	Flow	Type
j	J input	in	d
k	K input	in	d
clk	Clock	in	d
set	Asynchronous set	in	d
reset	Asynchronous reset	in	d
out	Data output	out	d
nout	Inverted data output	out	d

### 5.11.3 Model format

```
.MODEL model_name d_jkff parameters
```

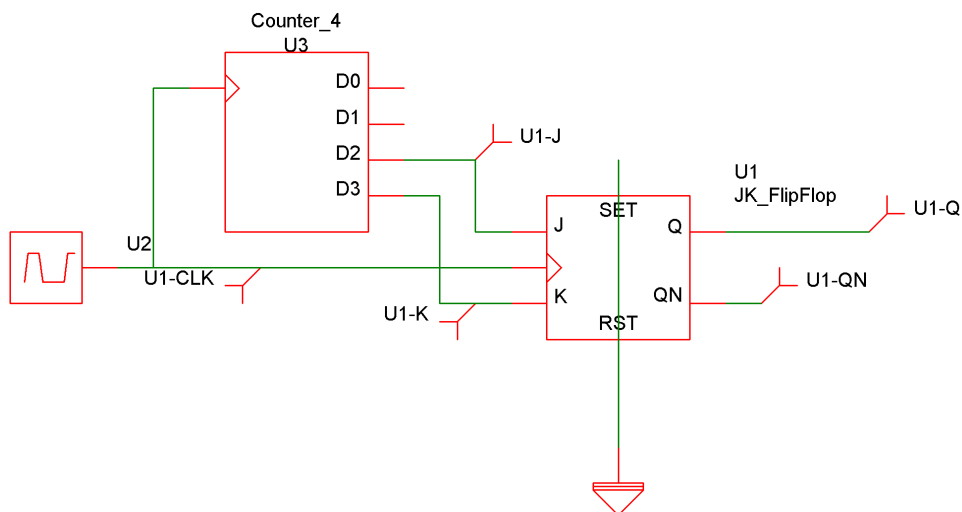
### 5.11.4 Model parameters

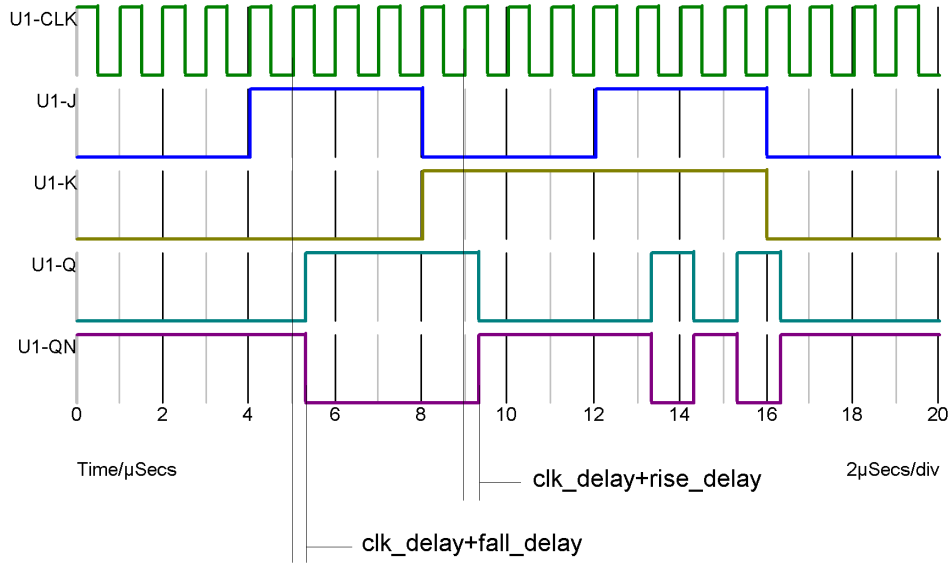
Name	Description	Type	Default	Limits
clk_delay	Delay from clk	real	1nS	1e-12 $-\infty$
set_delay	Delay from set	real	1nS	1e-12 0 $-\infty$
reset_delay	Delay from reset	real	1nS	1e-12 0 $-\infty$
ic	Output initial state	integer	0	0 $- 2$
rise_delay	Rise delay	real	1nS	1e-12 0 $-\infty$
fall_delay	Fall delay	real	1nS	1e-12 0 $-\infty$
jk_load	J,k load values (F)	real	1pF	none
clk_load	Clk load value (F)	real	1pF	none
set_load	Set load value (F)	real	1pF	none

Name	Description	Type	Default	Limits
reset_load	Reset load value (F)	real	1pF	none
family	Logic family	string	UNIV	none
in_family	Input logic family	string	UNIV	none
out_family	Output logic family	string	UNIV	none
out_res	Digital output resistance	real	100	0 – $\infty$
out_res_pos	Digital output res. pos. slope	real	out_res	0 – $\infty$
out_res_neg	Digital output res. neg. slope		out_res	0 – $\infty$
min_sink	Minimum sink current	real	-0.001	none
max_source	Maximum source current	real	0.001	none
sink_current	Input sink current	real	0	none
source_current	Input source current	real	0	none

### 5.11.5 Device Operation

The following circuit and graph illustrate the operation of this device:





The following table describes the operation of the device when both inputs are at known states: The output can only change on a positive edge of the clock.

J input	K input	Output
0	0	No change
0	1	0
1	0	1
1	1	toggle

When either input is UNKNOWN, the situation is more complicated. There are some circumstances when a known state can be clocked to the output even if one of the inputs is unknown. The following table describes the operation for all possible input states. X means UNKNOWN.

J input	K input	old output	new output
0	0	0	0
0	0	1	1
0	0	X	X
0	1	0	0
0	1	1	0
0	1	X	0
0	X	0	0
0	X	1	X
0	X	X	X
1	0	0	1
1	0	1	1
1	0	X	1

J input	K input	old output	new output
1	1	0	1
1	1	1	0
1	1	X	X
1	X	0	1
1	X	1	X
1	X	X	X
X	0	0	X
X	0	1	1
X	0	X	X
X	1	0	X
X	1	1'	0
X	1	X	X
X	X	0	X
X	X	1	X
X	X	X	X

## 5.12 Arbitrary Logic Block

### 5.12.1 Netlist entry

```
Axxxx [ in_0 in_1 .. in_n ] [ out_0 out_1 .. out_n ]
+ model_name : parameters
```

### 5.12.2 Connection details

Name	Description	Flow	Type
in	Input	in	d, vector
out	Output	out	d, vector

### 5.12.3 Instance Parameters

Name	Description	Type
trace_file	Trace file	string
user	User device params	real vector

### 5.12.4 Model format

```
.MODEL model_name d_logic_block parameters
```

### 5.12.5 Model parameters

Name	Description	Type	Default	Limits	Vector bounds
file	Definition file name	string	none	none	n/a
def	Definition	string	none	none	n/a
out_delay	Default output delay	real	1n	1p – $\infty$	n/a
reg_delay	Default internal register delay	real	1n	0 – $\infty$	n/a
setup_time	Default level triggered setup time	real	0	0 – $\infty$	n/a
hold_time	Default edge triggered hold time	real	0	0 – $\infty$	n/a
min_clock	Default minimum clock width	real	0	0 – $\infty$	n/a
trace_file	Trace log file	string		none	n/a
user	User defined parameters	real vector	none	none	none
user_scale	Scale of user values	real	1	0 – $\infty$	n/a
input_load	Input load value (F)	real	1p	none	n/a
family	Logic family	string	UNIV	none	n/a
in_family	Input logic family	string	UNIV	none	n/a
out_family	Output logic family	string	UNIV	none	n/a
out_res	Digital output resistance	real	100	0 – $\infty$	n/a
out_res_pos	Digital output res. pos. slope	real	out_res	0 – $\infty$	n/a
out_res_neg	Digital output res. neg. slope		out_res	0 – $\infty$	n/a
sink_current	Input sink current	real	0	none	n/a
source_current	Input source current	real	0	none	n/a

### 5.12.6 Device Operation

See “Arbitrary Logic Block - User Defined Models” on page 287.

## 5.13 Nand Gate

### 5.13.1 Netlist entry

```
Axxxx [ in_0 in_1 .. in_n ] out model_name
```

### 5.13.2 Connection details

Name	Description	Flow	Type	Vector bounds
in	Input	in	d, vector	2 – $\infty$
out	Output	out	d	n/a

### 5.13.3 Model format

```
.MODEL model_name d_nand parameters
```

### 5.13.4 Model parameters

Name	Description	Type	Default	Limits
rise_delay	Rise delay	real	1nS	1e-12 $-\infty$
fall_delay	Fall delay	real	1nS	1e-12 $-\infty$
input_load	Input load value (F)	real	1pF	none
family	Logic family	string	UNIV	none
in_family	Input logic family	string	UNIV	none
out_family	Output logic family	string	UNIV	none
out_res	Digital output resistance	real	100	0 $-\infty$
out_res_pos	Digital output res. pos. slope	real	out_res	0 $-\infty$
out_res_neg	Digital output res. neg. slope		out_res	0 $-\infty$
open_c	Open collector output	boolean	FALSE	none
min_sink	Minimum sink current	real	-0.001	none
max_source	Maximum source current	real	0.001	none
sink_current	Input sink current	real	0	none
source_current	Input source current	real	0	none

### 5.13.5 Device operation

- If the model parameter OPEN\_C is false, The output will be at logic '1' if either input is at logic '0'. Otherwise, if any input is UNKNOWN, the output will be UNKNOWN. Otherwise the output will be at logic '0'.
- If the model parameter OPEN\_C is true the device will be open collector. In this case the output logic state is always '0'. The state of the inputs instead determines the strength of the output. If either input is at logic '0' the output strength will be HI-IMPEDANCE allowing a pull-up resistor to force it to the logic '1' state. Otherwise if any input is UNKNOWN the output strength will be UNDETERMINED. Otherwise the output strength will be STRONG.

## 5.14 Nor Gate

### 5.14.1 Netlist entry

```
Axxxx [ in_0 in_1 .. in_n ] out model_name
```

### 5.14.2 Connection details

Name	Description	Flow	Type	Vector bounds
in	Input	in	d, vector	$2 - \infty$
out	Output	out	d	n/a

### 5.14.3 Model format

```
.MODEL model_name d_nor parameters
```

### 5.14.4 Model parameters

Name	Description	Type	Default	Limits
rise_delay	Rise delay	real	1nS	1e-12 $-\infty$
fall_delay	Fall delay	real	1nS	1e-12 $-\infty$
input_load	Input load value (F)	real	1pF	none
family	Logic family	string	UNIV	none
in_family	Input logic family	string	UNIV	none
out_family	Output logic family	string	UNIV	none
out_res	Digital output resistance	real	100	0 $-\infty$
out_res_pos	Digital output res. pos. slope	real	out_res	0 $-\infty$
out_res_neg	Digital output res. neg. slope	real	out_res	0 $-\infty$
open_c	Open collector output	boolean	FALSE	none
min_sink	Minimum sink current	real	-0.001	none
max_source	Maximum source current	real	0.001	none
sink_current	Input sink current	real	0	none
source_current	Input source current	real	0	none

### 5.14.5 Device operation

- If the model parameter OPEN\_C is false, The output will be at logic '0' if either input is at logic '1'. Otherwise, if any input is UNKNOWN, the output will be UNKNOWN. Otherwise the output will be at logic '1'.
- If the model parameter OPEN\_C is true the device will be open collector. In this case the output logic state is always '0'. The state of the inputs instead determines the *strength* of the output. If either input is at logic '1' the output strength will be STRONG. Otherwise if any input is UNKNOWN the output strength will be UNDETERMINED. Otherwise the output strength will be HI-IMPEDANCE allowing a pull-up resistor to force it to the logic '1' state.

## 5.15 Open-Collector Buffer

### 5.15.1 Netlist entry



```
Axxxx in out model_name
```

### 5.15.2 Connection details

Name	Description	Flow	Type
in	Input	in	d
out	Output	out	d

### 5.15.3 Model format

```
.MODEL model_name d_open_c parameters
```

### 5.15.4 Model parameters

Name	Description	Type	Default	Limits
open_delay	Open delay	real	1nS	$1e^{-12} - \infty$
fall_delay	Fall delay	real	1nS	$1e^{-12} - \infty$
input_load	Input load value (F)	real	1pF	none

### 5.15.5 Device Operation

This device is included for compatibility with other XSPICE products. It is recommended that you use the digital buffer device (see “[Buffer](#)” on page 139) for new designs as this supports the additional common parameters such as static input loads and families.

The logic description for the open-collector buffer is described by the following table

Input	Output state	Output strength
0	0	STRONG
1	1	HI-IMPEDANCE
UNKNOWN	UNKNOWN	UNDETERMINED

## 5.16 Open-Emitter Buffer

### 5.16.1 Netlist entry

```
Axxxx in out model_name
```

### 5.16.2 Connection details

Name	Description	Flow	Type
in	Input	in	d
out	Output	out	d

### 5.16.3 Model format

```
.MODEL model_name d_open_e parameters
```

### 5.16.4 Model parameters

Name	Description	Type	Default	Limits
rise_delay	Rise delay	real	1nS	$1e^{-12} - \infty$
open_delay	Open delay	real	1nS	$1e^{-12} - \infty$
input_load	Input load value (F)	real	1pF	none

### 5.16.5 Device Operation

This device is included for compatibility with other XSPICE products. It is recommended that you use the digital buffer device (see [“Buffer” on page 139](#)) for new designs as this supports the additional common parameters such as static input loads and families.

The logic description for the open-collector buffer is described by the following table

Input	Output state	Output strength
0	0	HI-IMPEDANCE
1	1	STRONG
UNKNOWN	UNKNOWN	UNDETERMINED

## 5.17 Or Gate

### 5.17.1 Netlist entry

```
Axxxx [ in_0 in_1 .. in_n ] out model_name
```

### 5.17.2 Connection details

Name	Description	Flow	Type	Vector bounds
in	Input	in	d, vector	$2 - \infty$
out	Output	out	d	n/a

### 5.17.3 Model format

```
.MODEL model_name d_or parameters
```

### 5.17.4 Model parameters

Name	Description	Type	Default	Limits
rise_delay	Rise delay	real	1nS	$1e^{-12} - \infty$
fall_delay	Fall delay	real	1nS	$1e^{-12} - \infty$
input_load	Input load value (F)	real	1pF	none
family	Logic family	string	UNIV	none
in_family	Input logic family	string	UNIV	none
out_family	Output logic family	string	UNIV	none
out_res	Digital output resistance	real	100	$0 - \infty$
out_res_pos	Digital output res. pos. slope	real	out_res	$0 - \infty$
out_res_neg	Digital output res. neg. slope	real	out_res	$0 - \infty$
open_c	Open collector output	boolean	FALSE	none
min_sink	Minimum sink current	real	-0.001	none
max_source	Maximum source current	real	0.001	none
sink_current	Input sink current	real	0	none
source_current	Input source current	real	0	none

### 5.17.5 Device operation

- If the model parameter OPEN\_C is false, The output will be at logic '1' if either input is at logic '1'. Otherwise, if any input is UNKNOWN, the output will be UNKNOWN. Otherwise the output will be at logic '0'.
- If the model parameter OPEN\_C is true the device will be open collector. In this case the output logic state is always '0'. The state of the inputs instead determines the strength of the output. If either input is at logic '1' the output strength will be HI-IMPEDANCE allowing a pull-up resistor to force it to the logic '1' state. Otherwise if any input is UNKNOWN the output strength will be UNDETERMINED. Otherwise the output strength will be STRONG.

## 5.18 Pulldown Resistor

### 5.18.1 Netlist entry

```
Axxxx out model_name
```

### 5.18.2 Connection details

Name	Description	Flow	Type
out	Output	out	d

### 5.18.3 Model format

```
.MODEL model_name d_pulldown parameters
```

### 5.18.4 Model parameters

Name	Description	Type	Default	Limits
load	Load value (F)	real	0	none
strong	Strong output	boolean	FALSE	none
out_family	Output logic family	string	UNIV	none

### 5.18.5 Device Operation

This is a single terminal device that can provide either a RESISTIVE or STRONG logic '0'. When resistive it can be used for wire-OR connected open emitter outputs. If STRONG is specified (by the STRONG parameter) its main application is as a digital ground connection.

## 5.19 Pullup Resistor

### 5.19.1 Netlist entry

```
Axxxx out model_name
```

### 5.19.2 Connection details

Name	Description	Flow	Type
out	Output	out	d

### 5.19.3 Model format

```
.MODEL model_name d_pullup parameters
```

### 5.19.4 Model parameters

Name	Description	Type	Default	Limits
load	Load value (F)	real	0	none

Name	Description	Type	Default	Limits
strong	Strong output	boolean	FALSE	none
out_family	Output logic family	string	UNIV	none

### 5.19.5 Device Operation

This is a single terminal device that can provide either a RESISTIVE or STRONG logic '1'. When resistive it can be used for wire-AND connected open collector outputs. If STRONG is specified (by the STRONG parameter) its main application is as a digital VCC connection.

## 5.20 Random Access Memory

### 5.20.1 Netlist entry

```
Axxxx [ data_in_0 data_in_1 .. data_in_n ] [ data_out_0 data_out_1 ..
+ data_out_n ] [ address_0 address_1 .. address_n ] write_en
+ [ select_0 select_1 .. select_n ] model_name
```

### 5.20.2 Connection details

Name	Description	Flow	Type	Vector bounds
data_in	Data input line(s)	in	d, vector	1 - $\infty$
data_out	Data output line(s)	out	d, vector	1 - $\infty$
address	Address input line(s)	in	d, vector	1 - $\infty$
write_en	Write enable	in	d	n/a
select	Chip select line(s)	in	d, vector	1 - 16

### 5.20.3 Model format

```
.MODEL model_name d_ram parameters
```

### 5.20.4 Model parameters

Name	Description	Type	Default	Limits
select_value	Decimal active value for select line comparison	integer	1	0 - 32767
ic	Initial bit state @ DC	integer	2	0 - 2
read_delay	Read delay from address/select/write_en active	real	1.00E-07	$1e^{-12} - \infty$
data_load	Data_in load value (F)	real	1pF	none
address_load	Address line load value (F)	real	1pF	none
select_load	Select load value (F)	real	1pF	none
enable_load	Enable line load value (F)	real	1pF	none

### 5.20.5 Device Operation

This device is provided for compatibility with other XSPICE products and is not recommended for new designs. In some circumstances, this device can consume large quantities of system (i.e. your PC's) RAM as it uses an inefficient method of storing state history. RAM's can also be implemented using the arbitrary logic block (see [“Arbitrary Logic Block - User Defined Models” on page 287](#)) which is much more efficient. An example of a simple 256X8 RAM can be found amongst the supplied example circuits (Examples/ALB\_Examples/RAM.sxsch and RAM.ldf).

## 5.21 Set-Reset Flip-Flop

### 5.21.1 Netlist entry

```
Axxxx s r clk set reset out nout model_name
```

### 5.21.2 Connection details

Name	Description	Flow	Type
s	S input	in	d
r	R input	in	d
clk	Clock	in	d
set	Asynchronous set	in	d
reset	Asynchronous reset	in	d
out	Data output	out	d
nout	Inverted data output	out	d

### 5.21.3 Model format

```
.MODEL model_name d_srff parameters
```

### 5.21.4 Model parameters

Name	Description	Type	Default	Limits
clk_delay	Delay from clk	real	1nS	$1e^{-12} - \infty$
set_delay	Delay from set	real	1nS	$1e^{-12} - \infty$
reset_delay	Delay from reset	real	1nS	$1e^{-12} - \infty$
ic	Output initial state	integer	0	0 - 2
rise_delay	Rise delay	real	1nS	$1e^{-12} - \infty$
fall_delay	Fall delay	real	1nS	$1e^{-12} - \infty$
sr_load	S,r load values (F)	real	1pF	none
clk_load	Clk load value (F)	real	1pF	none
set_load	Set load value (F)	real	1pF	none

Name	Description	Type	Default	Limits
reset_load	Reset load value (F)	real	1pF	none
family	Logic family	string	UNIV	none
in_family	Input logic family	string	UNIV	none
out_family	Output logic family	string	UNIV	none
out_res	Digital output resistance	real	100	0 – $\infty$
out_res_pos	Digital output res. pos. slope	real	out_res	0 – $\infty$
out_res_neg	Digital output res. neg. slope	real	out_res	0 – $\infty$
open_c	Open collector output	boolean	FALSE	none
min_sink	Minimum sink current	real	-0.001	none
max_source	Maximum source current	real	0.001	none
sink_current	Input sink current	real	0	none
source_current	Input source current	real	0	none

### 5.21.5 Device Operation

The SR flip flop is similar to a JK flip flop except that the output is UNKNOWN when both S and R inputs are high. In a JK the output toggles in the same circumstances.

The following table describes the operation of the device when both inputs are at known states: The output can only change on a positive edge on the clock.

S input	R input	Output
0	0	No change
0	1	0
1	0	1
1	1	UNKNOWN

When either input is UNKNOWN, the situation is more complicated. There are some circumstances when a known state can be clocked to the output even if one of the inputs is unknown. The following table describes the operation for possible input states. X means UNKNOWN.

S input	R input	old output	new output
0	0	0	0
0	0	1	1
0	0	X	X
0	1	0	0
0	1	1	0
0	1	X	0
0	X	0	0
0	X	1	X
0	X	X	X

S input	R input	old output	new output
1	0	0	1
1	0	1	1
1	0	X	1
1	1	0	X
1	1	1	X
1	1	X	X
1	X	0	X
1	X	1	X
1	X	X	X
X	0	0	X
X	0	1	1
X	0	X	X
X	1	0	X
X	1	1	X
X	1	X	X
X	X	0	X
X	X	1	X
X	X	X	X

## 5.22 SR Latch

### 5.22.1 Netlist entry

```
Axxxx s r enable set reset out nout model_name
```

### 5.22.2 Connection details

Name	Description	Flow	Type
s	S input	in	d
r	R input	in	d
enable	Enable	in	d
set	Asynchronous set	in	d
reset	Asynchronous reset	in	d
out	Data output	out	d
nout	Inverted data output	out	d

### 5.22.3 Model format

```
.MODEL model_name d_srlatch parameters
```



### 5.22.4 Model parameters

Name	Description	Type	Default	Limits
sr_delay	Delay from s or r input change	real	1nS	$1e^{-12} - \infty$
enable_delay	Delay from clk	real	1nS	$1e^{-12} - \infty$
set_delay	Delay from set	real	1nS	$1e^{-12} - \infty$
reset_delay	Delay from reset	real	1nS	$1e^{-12} - \infty$
ic	Output initial state	integer	0	0 - 2
rise_delay	Rise delay	real	1nS	$1e^{-12} - \infty$
fall_delay	Fall delay	real	1nS	$1e^{-12} - \infty$
sr_load	S & r load values (F)	real	1pF	none
enable_load	Clk load value (F)	real	1pF	none
set_load	Set load value (F)	real	1pF	none
reset_load	Reset load value (F)	real	1pF	none
family	Logic family	string	UNIV	none
in_family	Input logic family	string	UNIV	none
out_family	Output logic family	string	UNIV	none
out_res	Digital output resistance	real	100	0 - $\infty$
out_res_pos	Digital output res. pos. slope	real	out_res	0 - $\infty$
out_res_neg	Digital output res. neg. slope	real	out_res	0 - $\infty$
min_sink	Minimum sink current	real	-0.001	none
max_source	Maximum source current	real	0.001	none
sink_current	Input sink current	real	0	none
source_current	Input source current	real	0	none

### 5.22.5 Device Operation

This device is identical to the SR flip flop except that it is level not edge triggered. That is the output may change whenever the enable input is high.

## 5.23 State Machine

### 5.23.1 Netlist entry

```
Axxxx [ in_0 in_1 .. in_n ] clk reset [ out_0 out_1 .. out_n ] model_name
```

### 5.23.2 Connection details

Name	Description	Flow	Type	Vector bounds
in	Input	in	d, vector	none
clk	Clock	in	d	n/a

Name	Description	Flow	Type	Vector bounds
reset	Reset	in	d	n/a
out	Output	out	d, vector	1 - no upper bound

### 5.23.3 Model format

```
.MODEL model_name d_state parameters
```

### 5.23.4 Model parameters

Name	Description	Type	Default	Limits
clk_delay	Delay from CLK	real	1nS	none
reset_delay	Delay from reset	real	1nS	none
state_file	State transition specification file name	string	none	none
reset_state	Default state on RESET & at DC	integer	0	none
input_load	Input loading capacitance (F)	real	1pF	none
clk_load	Clock loading capacitance (F)	real	1pF	none
reset_load	Reset loading capacitance (F)	real	1pF	none
family	Logic family	string	UNIV	none
in_family	Input logic family	string	UNIV	none
out_family	Output logic family	string	UNIV	none

### 5.23.5 File Syntax

The following is a formal description of the state machine file syntax using Backus-Naur form (BNF). “ and ’ mean “zero or more” of the enclosed items.

```
state_machine_def :: state_def state_def
```

```
state_def :: header_line continuation_line
```

```
header_line :: STATENUM outputs inputs SEPARATOR STATE_DEST
```

```
continuation_line :: inputs SEPARATOR STATE_DEST
```

```
outputs :: OUTPUT_VALUE OUTPUT_VALUE
```

```
inputs :: INPUT_VALUE INPUT_VALUE
```

**STATENUM** :: 0 based integer indicating state number.

**SEPARATOR** :: Any sequence of characters but not whitespace. ‘->’ is conventional

**STATE\_DESTINATION** :: integer indicating state number.

**OUTPUT\_VALUE** :: two digit sequence to define one of the 12 output states. First character can be 0, 1 or U. Second character can be s, r, z or u for ‘strong’, ‘resistive’, ‘high-z’, and ‘undefined’ respectively.

**INPUT\_VALUE** :: 0, 1, x, or X

The idea is to have N *state\_def*'s where N is the number of states. Each *state\_def* has one *header\_line* and a number of following *continuation\_lines*. Both define the destination state for a given combination of inputs. The *header\_line* additionally defines the state being defined and the output value for that state. Header lines and continuation lines are distinguished by counting the tokens. The system does currently not appear to fail gracefully if this is wrong. A *header\_line* should have (num\_inputs+num\_outputs+3) tokens and a *continuation\_line* should have (num\_inputs+2).

The number of inputs and outputs is defined in the netlist line which is in the form:

```
Axxx [ inputs ] clk reset [ outputs ] modelname
```

### 5.23.6 Notes

Currently this model is unsupported as it has not undergone testing or analysis. It is part of the original XSPICE system and should be compatible with other implementations but this cannot be guaranteed.

The following is an example of a state transition specification file

```
* This is a simple example of a state machine state file
* It is a 2 bit up down counter with synchronous reset
```

*Present *State	Outputs for state	Inputs (reset, up/down)	State destination
0	0S 0S	0 0	-> 3
		0 1	-> 1
		1 0	-> 0
		1 1	-> 0
1	0S 1S	0 0	-> 0
		0 1	-> 2
		1 0	-> 0
		1 1	-> 0
2	1S 0S	0 0	-> 1
		0 1	-> 3
		1 0	-> 0
		1 1	-> 0
3	1S 1S	0 0	-> 2
		0 1	-> 0
		1 0	-> 0
		1 1	-> 0

See Examples/Digital\_Devices/state\_updown.sxsch

## 5.24 Toggle Flip Flop

### 5.24.1 Netlist entry

```
Axxxx t clk set reset out nout model_name
```

### 5.24.2 Connection details

Name	Description	Flow	Type
t	Toggle input	in	d
clk	Clock	in	d
set	Asynchronous set	in	d
reset	Asynchronous reset	in	d
out	Data output	out	d
nout	Inverted data output	out	d

### 5.24.3 Model format

```
.MODEL model_name d_tff parameters
```

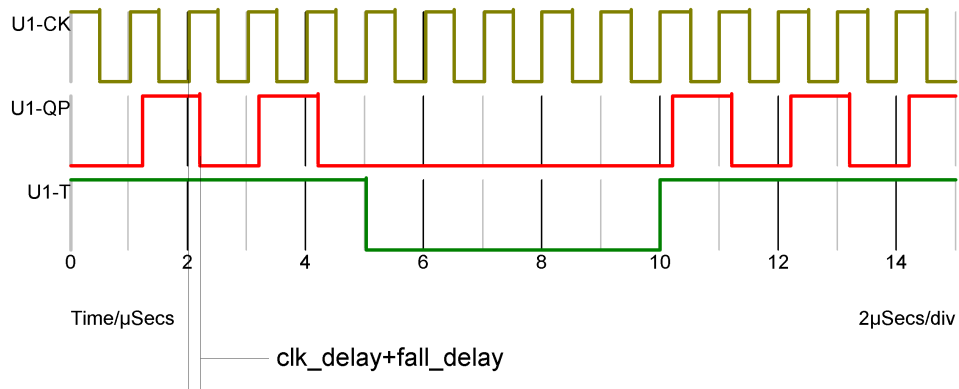
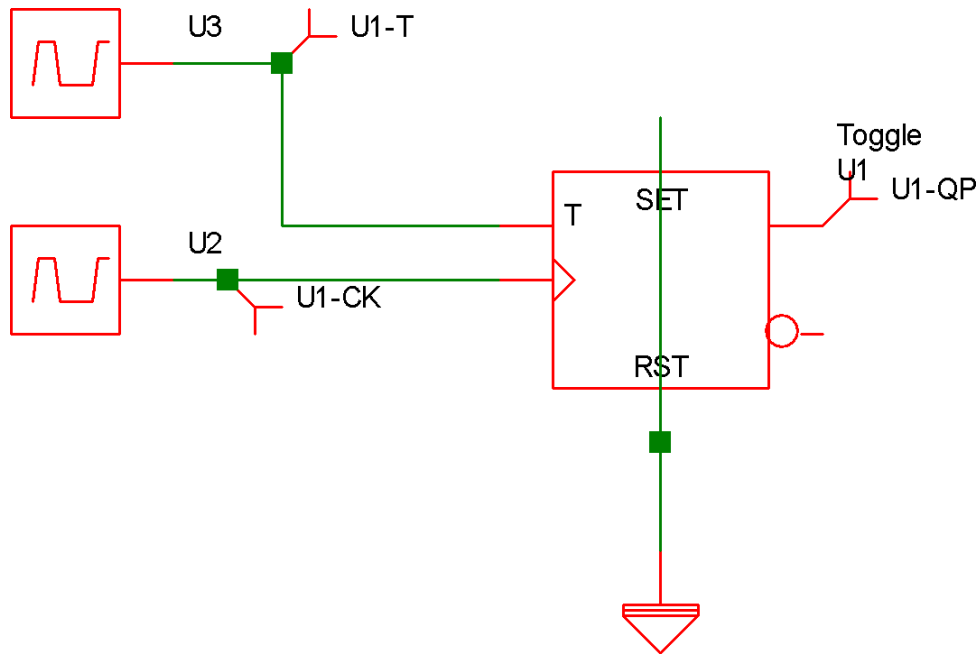
### 5.24.4 Model parameters

Name	Description	Type	Default	Limits
clk_delay	Delay from clk	real	1nS	$1e^{-12} - \infty$
set_delay	Delay from set	real	1nS	$1e^{-12} - \infty$
reset_delay	Delay from reset	real	1nS	$1e^{-12} - \infty$
ic	Output initial state	integer	0	0 - 2
rise_delay	Rise delay	real	1nS	$1e^{-12} - \infty$
fall_delay	Fall delay	real	1nS	$1e^{-12} - \infty$
t_load	Toggle load value (F)	real	1pF	none
clk_load	Clk load value (F)	real	1pF	none
set_load	Set load value (F)	real	1pF	none
reset_load	Reset load value (F)	real	1pF	none
family	Logic family	string	UNIV	none
in_family	Input logic family	string	UNIV	none
out_family	Output logic family	string	UNIV	none
out_res	Digital output resistance	real	100	0 - $\infty$
out_res_pos	Digital output res. pos. slope	real	out_res	0 - $\infty$
out_res_neg	Digital output res. neg. slope	real	out_res	0 - $\infty$
min_sink	Minimum sink current	real	-0.001	none
max_source	Maximum source current	real	0.001	none
sink_current	Input sink current	real	0	none
source_current	Input source current	real	0	none

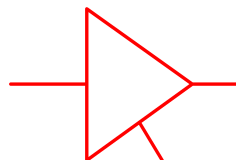
### 5.24.5 Device Operation

The operation of the toggle flip flop is illustrated by the following diagrams. When the T input is high, the output toggles on each rising edge of the clock. If the T input is UNKNOWN the output

will be UNKNOWN.



## 5.25 Tri-State Buffer



### 5.25.1 Netlist entry

```
Axxxx in enable out model_name
```

### 5.25.2 Connection details

Name	Description	Flow	Type
in	Input	in	d
enable	Enable	in	d
out	Output	out	d

### 5.25.3 Model format

```
.MODEL model_name d_tristate parameters
```

### 5.25.4 Model parameters

Name	Description	Type	Default	Limits
delay	Delay	real	1nS	$1e^{-12} - \infty$
input_load	Input load value (F)	real	1pF	none
enable_load	Enable load value (F)	real	1pF	none
family	Logic family	string	UNIV	none
in_family	Input logic family	string	UNIV	none
out_family	Output logic family	string	UNIV	none
out_res	Digital output resistance	real	100	$0 - \infty$
out_res_pos	Digital output res. pos. slope	real	out_res	$0 - \infty$
out_res_neg	Digital output res. neg. slope	real	out_res	$0 - \infty$
min_sink	Minimum sink current	real	-0.001	none
max_source	Maximum source current	real	0.001	none
sink_current	Input sink current	real	0	none
source_current	Input source current	real	0	none

### 5.25.5 Device Operation

This is a three terminal buffer device. The output state is equal to the input state and the output strength is determined by the enable input as follows:

Enable	Output Strength
0	HI-IMPEDANCE
1	STRONG
UNKNOWN	UNDETERMINED

## 5.26 Exclusive NOR Gate

### 5.26.1 Netlist entry

```
Axxxx [ in_0 in_1 .. in_n ] out model_name
```

### 5.26.2 Connection details

Name	Description	Flow	Type	Vector bounds
in	Input	in	d, vector	$2 - \infty$
out	Output	out	d	n/a

### 5.26.3 Model format

```
.MODEL model_name d_xnor parameters
```

### 5.26.4 Model parameters

Name	Description	Type	Default	Limits
rise_delay	Rise delay	real	1nS	$1e^{-12} - \infty$
fall_delay	Fall delay	real	1nS	$1e^{-12} - \infty$
input_load	Input load value (pF)	real	1	$0 - \infty$
family	Logic family	string	UNIV	none
in_family	Input logic family	string	UNIV	none
out_family	Output logic family	string	UNIV	none
out_res	Digital output resistance	real	100	$0 - \infty$
out_res_pos	Digital output res. pos. slope	real	out_res	$0 - \infty$
out_res_neg	Digital output res. neg. slope	real	out_res	$0 - \infty$
open_c	Open collector output	boolean	FALSE	none
min_sink	Minimum sink current	real	-0.001	none
max_source	Maximum source current	real	0.001	none
sink_current	Input sink current	real	0	none
source_current	Input source current	real	0	none

### 5.26.5 Device Operation

- If the OPEN\_C parameter is FALSE, the output is at logic '1' if an even number of inputs are at logic '1'. If any input is UNKNOWN the output will be UNKNOWN, otherwise the output will be at logic '0'.
- If the model parameter OPEN\_C is true the device will be open collector. In this case the output logic state is always '0'. The state of the inputs instead determines the strength

of the output. If n even number of inputs are at logic '1' the output strength will be HI-IMPEDANCE allowing a pull-up resistor to force it to the logic '1' state. If any input is UNKNOWN the output strength will be UNDETERMINED. Otherwise the output strength will be STRONG.

## 5.27 Exclusive OR Gate

### 5.27.1 Netlist entry

```
Axxxx [ in_0 in_1 .. in_n ] out model_name
```

### 5.27.2 Connection details

Name	Description	Flow	Type	Vector bounds
in	Input	in	d, vector	$2 - \infty$
out	Output	out	d	n/a

### 5.27.3 Model format

```
.MODEL model_name d_xor parameters
```

### 5.27.4 Model parameters

Name	Description	Type	Default	Limits
rise_delay	Rise delay	real	1nS	$1e^{-12} - \infty$
fall_delay	Fall delay	real	1nS	$1e^{-12} - \infty$
input_load	Input load value (F)	real	1pF	none
family	Logic family	string	UNIV	none
in_family	Input logic family	string	UNIV	none
out_family	Output logic family	string	UNIV	none
out_res	Digital output resistance	real	100	$0 - \infty$
out_res_pos	Digital output res. pos. slope	real	out_res	$0 - \infty$
out_res_neg	Digital output res. neg. slope	real	out_res	$0 - \infty$
open_c	Open collector output	boolean	FALSE	none
min_sink	Minimum sink current	real	-0.001	none
max_source	Maximum source current	real	0.001	none
sink_current	Input sink current	real	0	none
source_current	Input source current	real	0	none



### 5.27.5 Device Operation

- If the OPEN\_C parameter is FALSE, the output is at logic '1' if an odd number of inputs are at logic '1'. If any input is UNKNOWN the output will be UNKNOWN, otherwise the output will be at logic '0'.
- If the model parameter OPEN\_C is true the device will be open collector. In this case the output logic state is always '0'. The state of the inputs instead determines the *strength* of the output. If an odd number of inputs are at logic '1' the output strength will be HI-IMPEDANCE allowing a pull-up resistor to force it to the logic '1' state. If any input is UNKNOWN the output strength will be UNDETERMINED. Otherwise the output strength will be STRONG.

## 5.28 Analog-Digital Converter

### 5.28.1 Netlist entry

```
Axxxx analog_in clock_in [ data_out_0 data_out_1 .. data_out_n ]
+ data_valid model_name
```

### 5.28.2 Connection details

Name	Description	Flow	Type	Allowed types	Vector bounds
analog_in	Analog input	in	v	v, vd, i, id	n/a
clock_in	Clock input	in	d	d	n/a
data_out	Data output	out	d, vector	d	1 - 32
data_valid	Data valid output	out	d	d	n/a

### 5.28.3 Model format

```
.MODEL model_name ad_converter parameters
```

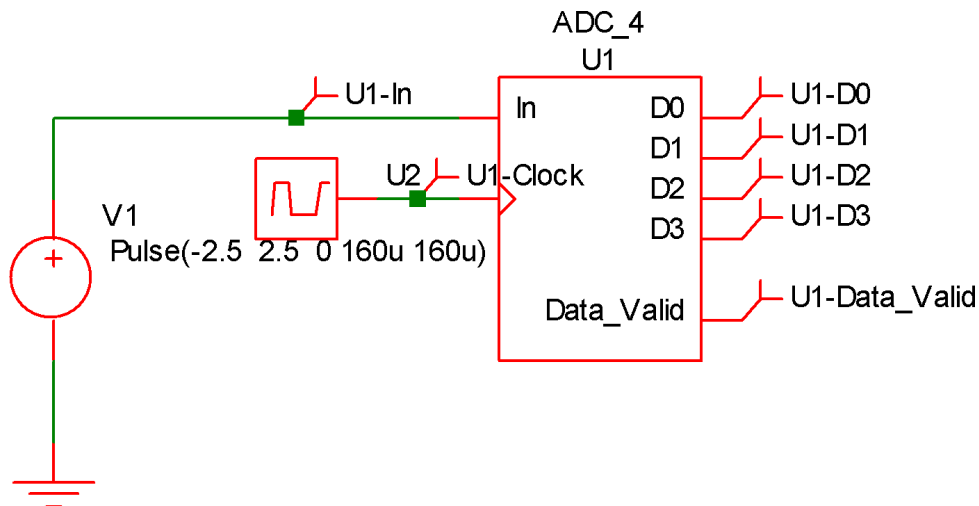
### 5.28.4 Model parameters

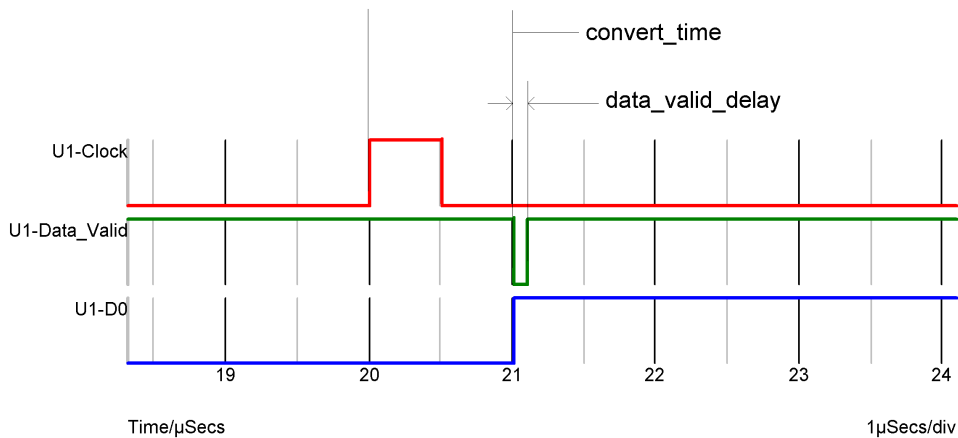
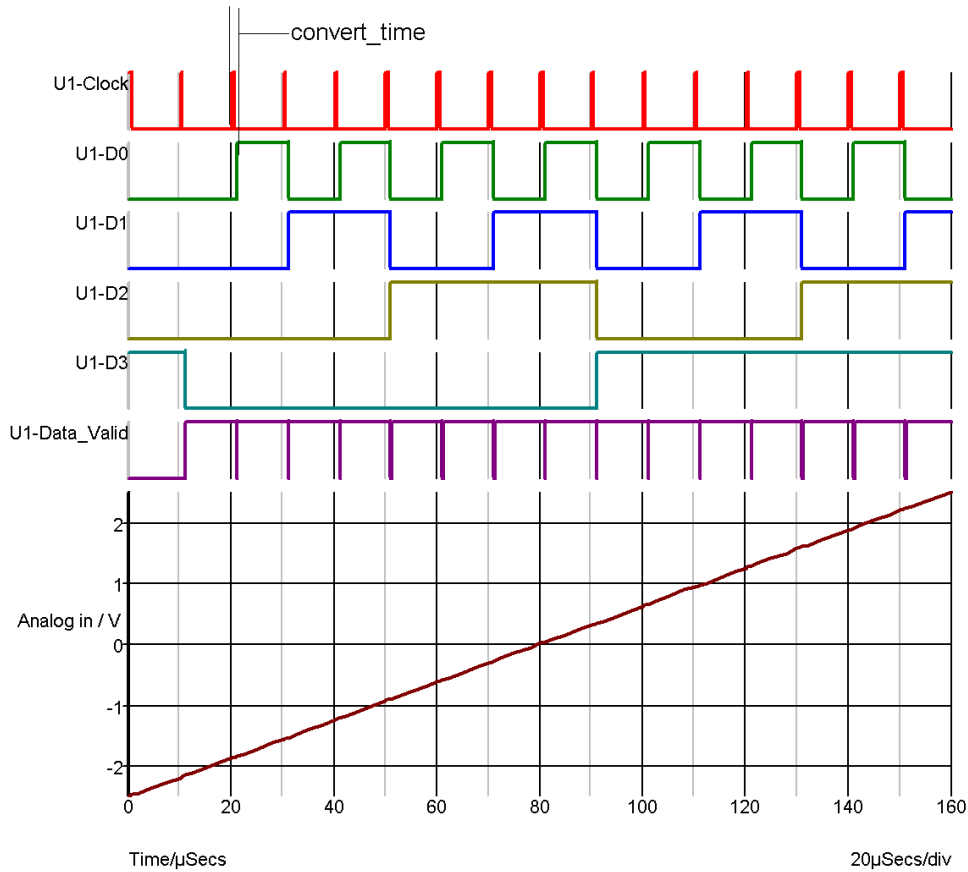
Name	Description	Type	Default	Limits
input_offset	Offset voltage	real	0	none
input_range	Input full scale signal range	real	1	none
twos_complement	Use 2's complement output. (default - offset binary)	boolean	FALSE	none
convert_time	Total conversion time	real	1 $\mu$ S	0 - $\infty$
min_clock	Minimum clock period	real	500n	0 - $\infty$
data_valid_delay	Data valid inactive time	real	100n	0 - $\infty$
in_family	Input logic family	string	UNIV	none
out_family	Output logic family	string	UNIV	none
family	Logic family	string	UNIV	none

Name	Description	Type	Default	Limits
input_load	Input load	real	1pF	0 – $\infty$
out_res	Digital output resistance	real	100	0 – $\infty$
out_res_pos	Digital output res. pos. slope	real	out_res	0 – $\infty$
out_res_neg	Digital output res. neg. slope	real	out_res	0 – $\infty$
min_sink	Minimum sink current	real	-0.001	none
max_source	Maximum source current	real	0.001	none
sink_current	Input sink current	real	0	none
source_current	Input source current	real	0	none

### 5.28.5 Device Operation

This is a 1-32 bit analog to digital converter. The operation of this device is illustrated by the following diagrams:





Conversion timings.

The ADC starts the conversion at the rising edge of the clock. The analog input signal is also sampled at this point. The output data changes in response to this, CONVERT\_TIME seconds later. At the same time the data\_valid output goes low (inactive) then high again after a delay equal to DATA\_VALID\_DELAY. It is possible to start a new conversion before the previous conversion is complete provided it is started later than MIN\_CLOCK seconds after the previous conversion was started. MIN\_CLOCK must always be less than CONVERT\_TIME. If the MIN\_CLOCK specification is violated, the conversion will not start.

## 5.29 Analog-Digital Interface Bridge

### 5.29.1 Netlist entry

```
Axxxx in out model_name
```

### 5.29.2 Connection details

Name	Description	Flow	Type
in	Input	inout	g
out	Output	out	d

### 5.29.3 Model format

```
.MODEL model_name adc_bridge parameters
```

### 5.29.4 Model parameters

Name	Description	Type	Default	Limits
in_low	Maximum 0-valued analog input	real	0.1	none
in_high	Minimum 1-valued analog input	real	0.9	none
rise_delay	Rise delay	real	1nS	$1e^{-12} - \infty$
fall_delay	Fall delay	real	1nS	$1e^{-12} - \infty$
time_tol	Threshold time tolerance	real	100pS	$1e^{-12} - \infty$
out_low	Used to calculate reflected static load. See text	real	0	none
out_high	Used to calculate reflected static load. See text	real	5	none
clamp_low	Clamp threshold 'ZERO' digital input. Default to out_low	real	out_low	none
clamp_high	Clamp threshold 'ONE' digital input. Default to out_high	real	out_high	none
clamp_res	Clamp minimum resistance	real	1	$1e-06 - \infty$
clamp_bias	Clamp voltage	real	0.8	0.2 - 2
out_family	Output logic family	string	UNIV	none

### 5.29.5 Device Operation

The analog-digital interface bridge is the main device used to connect analog signals to digital inputs. The device produces a digital signal that is in the logic '1' state when the analog input is above the high threshold (IN\_HIGH) and a logic '0' state when it is below the low threshold (IN\_LOW). When the analog input is in between these two states the output will be in the

UNKNOWN state. The changes in state will be delayed according to the RISE\_DELAY and FALL\_DELAY parameters.

### 5.29.6 Analog input load

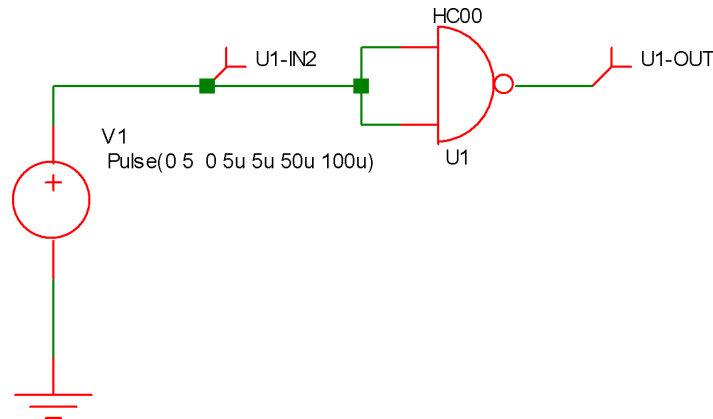
The analog input presents a load to its driving circuit according to the digital load that is being driven. In other words the digital load is reflected to the analog input. Both static (i.e. DC) and dynamic (i.e. capacitance) elements of the load are reflected. To accurately reflect the sink and source currents, the interface bridge needs to know the voltage levels of the device it is driving. The digital device will (usually) have a SINK\_CURRENT and a SOURCE\_CURRENT model parameter each of which apply at defined logic voltage levels. These levels must be specified in the OUT\_LOW and OUT\_HIGH parameters of the AD interface bridge model. The input is modelled by a current source in parallel with a resistor. The values of these components are calculated from the above mentioned parameters and the digital load.

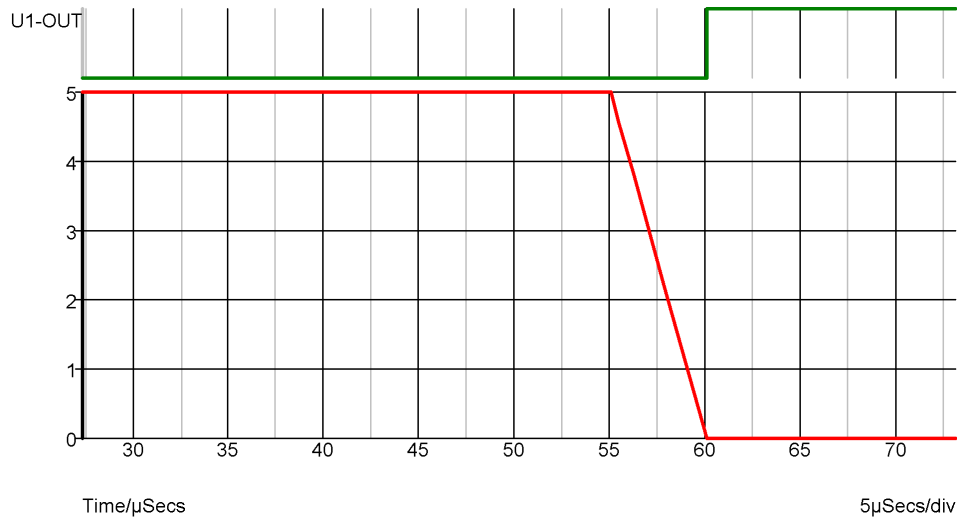
### 5.29.7 Input clamp

The analog input is clamped at the voltages specified by CLAMP\_LOW and CLAMP\_HIGH. The clamping device has a characteristic similar but not identical to a junction diode in series with a resistance. Basically it has the characteristic of a diode up to a voltage excess of CLAMP\_BIAS after which it becomes resistive with a dynamic resistance of CLAMP\_RES. The diode characteristics are calculated so that the transition between the two regions is smooth.

### 5.29.8 Time Step Control - TIME\_TOL parameter

Consider the following circuit and waveform



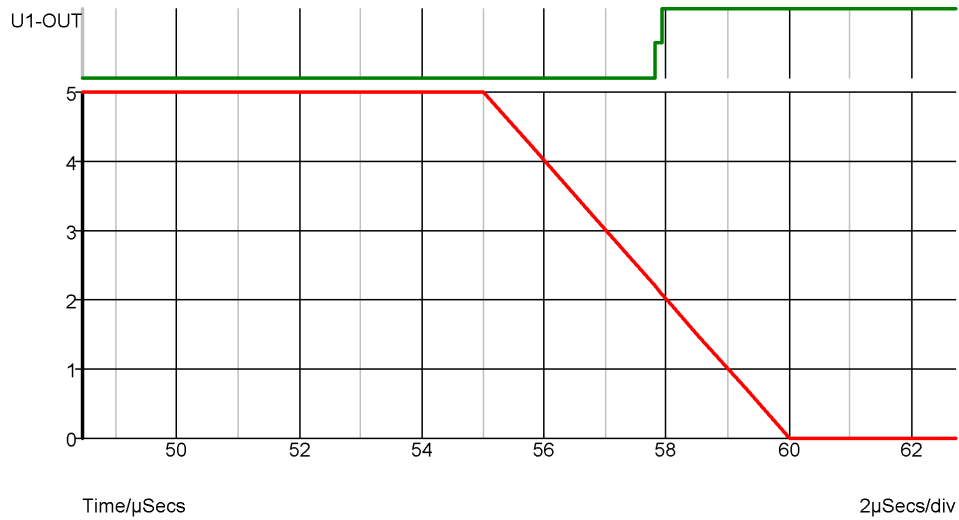


The graph shows the input and output of the NAND gate. Because the input is analog an implicit AD interface bridge will have been connected by the simulator. In the above example the parameters for this bridge have been set to:

```
.model HC_adc adc_bridge
+ in_low=2.1
+ in_high=2.2
+ rise_delay=1e-12
+ fall_delay=1e-12
+ out_family = "HC"
+ out_low = 0
+ out_high = 5
+ clamp_bias=0.5
+ clamp_res=10
+ time_tol=10u
```

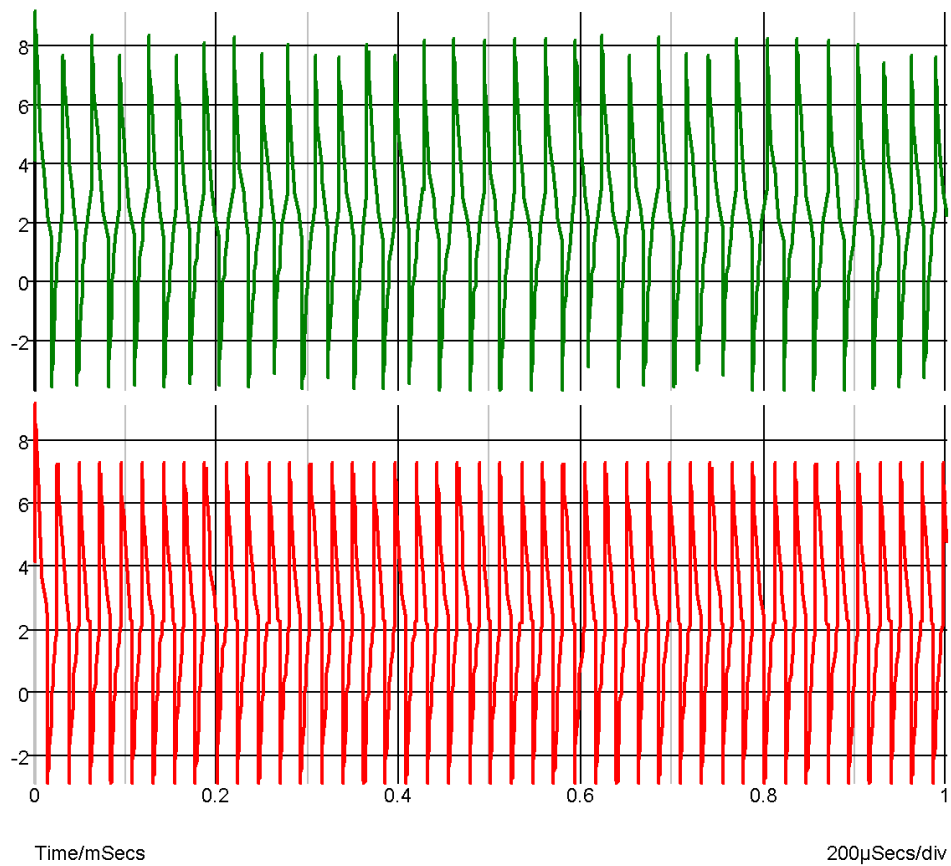
The last parameter, `TIME_TOL` has been deliberately set ridiculously high to demonstrate what happens without time step control on the input. The input thresholds of the HC gate are 2.1 and 2.2 volts yet the output in the above example doesn't switch until the input has reached 0V. Because there is little activity in the analog circuit, the time steps are quite large. In fact in the above example the transient timepoints are at 55uS, 55.04uS, 56.2uS, 57.8uS and 60uS. The timepoint at 57.8u is just before the 2.2 volt threshold is reached and it isn't until the next time point, 2.2uS later that the lower threshold is broken. The result is the location of the negative edge at the output is delayed by approx. 2.2uS from where it should be. The problem is that the analog system knows nothing of what is happening in the digital domain so carries on with large timesteps oblivious to the errors in the digital system.

To overcome this problem. SIMetrix features a mechanism (not in the original XSPICE system) that detects that the threshold has been passed and cuts back the time step to ensure that the digital edge occurs at an accurate point. The accuracy of this mechanism is controlled by the `TIME_TOL` parameter. The smaller this parameter, the more accurately the exact threshold will be hit at the expense of short time steps and longer simulation runs. `TIME_TOL` defaults to 100pS and in most applications this is a good choice. The following shows the result when `TIME_TOL` is set to the default.



Here you can see the edge at the correct time.

The effect of not correctly simulating the threshold point has serious consequences when attempting to simulate relaxation oscillators constructed with digital inverters as the following graphs illustrate:



The top trace is without threshold control and the bottom trace is with it.

## 5.30 Digital-Analog Converter

### 5.30.1 Netlist entry

```
Axxxx [ digital_in_0 digital_in_1 .. digital_in_n ]
      + analog_out model_name
```

### 5.30.2 Connection details

Name	Description	Flow	Type	Allowed types	Vector bounds
digital_in	Data output	in	d	d	1 - 32
analog_out	Analog output	out	v	v, vd, i, id	n/a

### 5.30.3 Model format

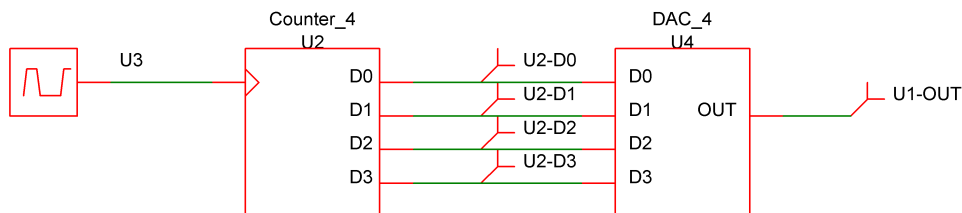
```
.MODEL model_name da_converter parameters
```

### 5.30.4 Model parameters

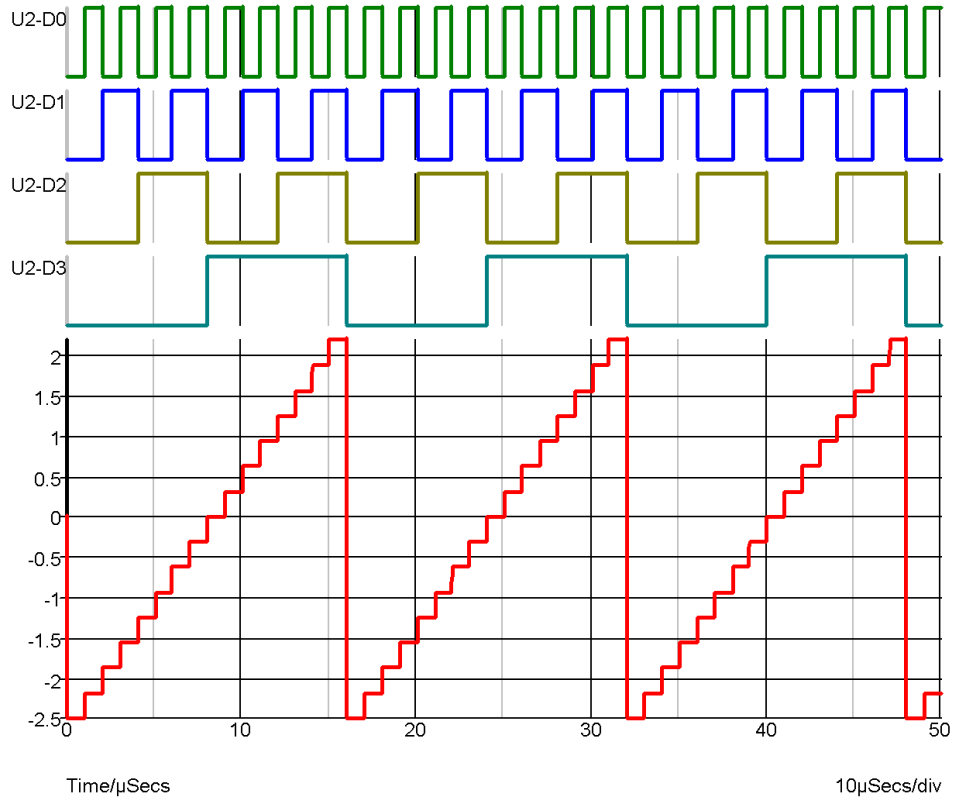
Name	Description	Type	Default	Limits
output_offset	Offset voltage	real	0	none
output_range	Input signal range	real	1	none
twos_complement	Use 2's complement input. (Default is offset binary)	boolean	FALSE	none
output_slew_time	Output slew time	real	10nS	$1e^{-12} - \infty$
in_family	Input logic family	string	UNIV	none
input_load	Input load	real	1pF	$0 - \infty$
sink_current	Input sink current	real	0	none
source_current	Input source current	real	0	none

### 5.30.5 Device Operation

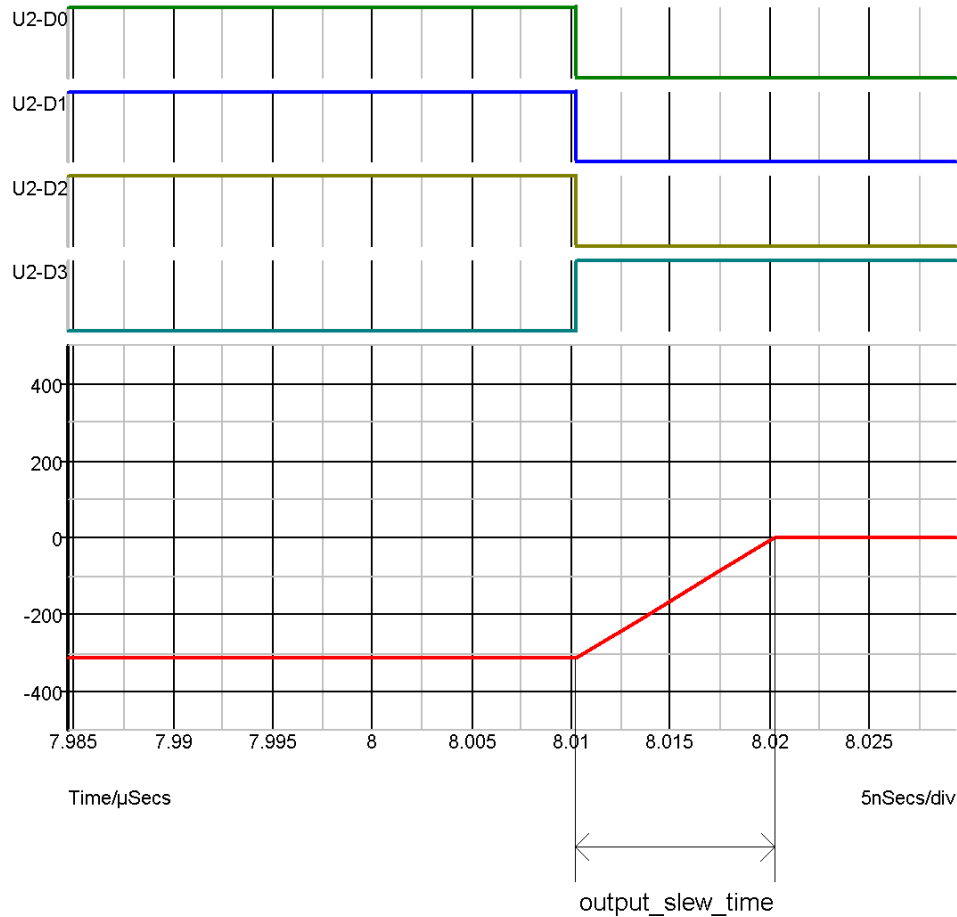
This device is a 1-32 bit digital to analog converter. Its operation is illustrated by the following diagrams.







DAC Waveforms



DAC waveforms expanded to show output slew

The device illustrated above has the following model definition:

```
.model DAC_4 da_converter
+ output_slew_time 1e-08
+ output_range 5
+ output_offset 0
```

In offset binary mode the D-A converter produce an output voltage equal to:

$$-\text{OUTPUT\_RANGE}/2 + \text{OUTPUT\_OFFSET} + \text{code} * \text{OUTPUT\_RANGE}/2^n$$

where  $n$  is the number of bits and code is the digital input code represented as an unsigned number between 0 and  $2^n - 1$ .

In 2's complement mode the output is:

$$\text{OUTPUT\_OFFSET} + \text{code} * \text{OUTPUT\_RANGE}/2^n$$

where  $n$  is the number of bits and code is the digital input code represented as a signed number between  $-2^{n/2}$  and  $2^{n/2} - 1$ .

Whenever the input code changes, the output is set on a trajectory to reach the target value in the time specified by `OUTPUT_SLEW_TIME`. UNKNOWN states are ignored. That is the input will be assumed to be at the most recent known state.

## 5.31 Digital-Analog Interface Bridge

### 5.31.1 Netlist entry

```
Axxxx in out model_name
```

### 5.31.2 Connection details

Name	Description	Flow	Type
in	Input	in	d
out	Output	inout	g

### 5.31.3 Model format

```
.MODEL model_name dac_bridge parameters
```

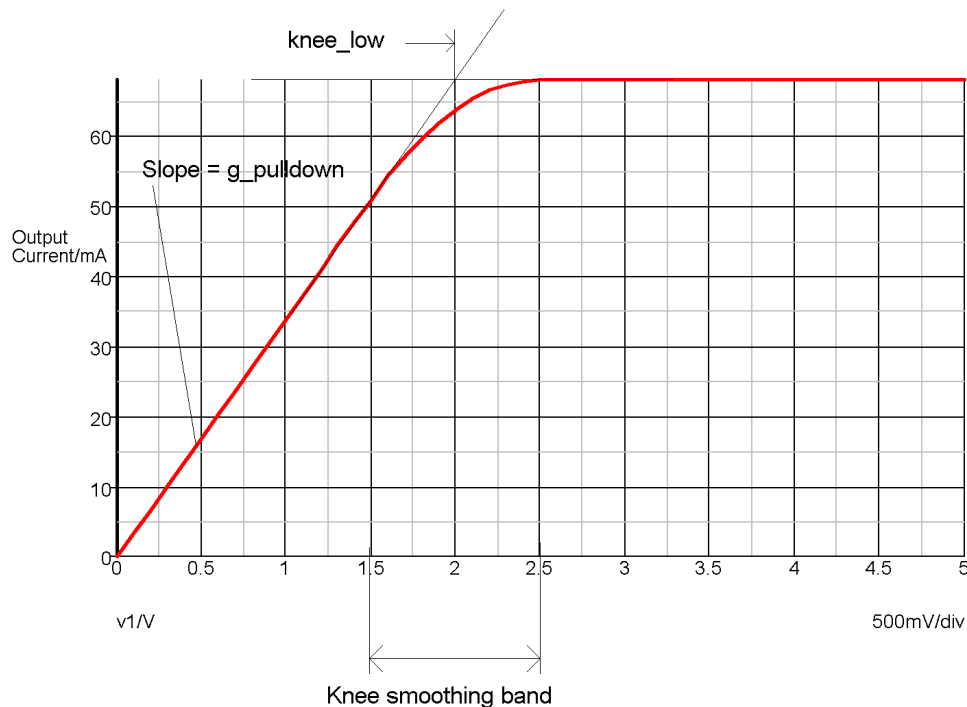
### 5.31.4 Model parameters

Name	Description	Type	Default	Limits
out_low	Analog output for 'ZERO' digital input	real	0	none
out_high	Analog output for 'ONE' digital input	real	5	none
g_resistive	Output conductance for 'RESISTIVE' digital input	real	0.001	none
g_pullup	Output conductance for 'STRONG' digital high input	real	0.01	none
g_pulldown	Output conductance for 'STRONG' digital low input	real	0.01	none
g_hiz	Output conductance for 'HI_IMPEDANCE' strength	real	1.00E-09	none
input_load	Capacitive input load (F)	real	1pF	none
t_rise	Rise time 0 -> 1	real	1nS	$1e^{-12} - \infty$
t_fall	Fall time 1 -> 0	real	1nS	$1e^{-12} - \infty$
knee_high	Knee voltage logic high state	real	3	none
knee_low	Knee voltage logic low	real	2	none
sink_current	Input sink current	real	0	none
source_current	Input source current	real	0	none
v_smooth	Smoothing function offset voltage	real	0	$0 - \infty$
in_family	Input logic family	string	UNIV	none

### 5.31.5 DC characteristics

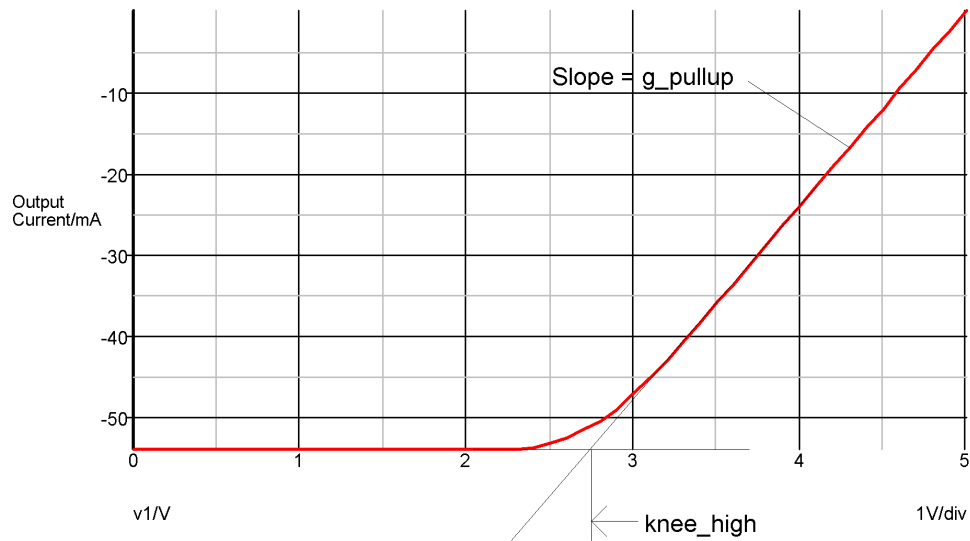
This digital to analog interface bridge is the main device used to connect digital signals to analog devices. The output provides an analog voltage and source resistance according to the state and strength of the driving digital input. The output has a non-linear characteristic that is a simplified model of a typical digital output stage. The following graphs show the output characteristics for the supplied high speed CMOS DA bridge. This has the following model parameters:

```
.model HC_dac dac_bridge
+ out_high=5      ; Logic high voltage
+ input_load=-31p ; Compensates for added rise and fall time
+ t_rise=2n       ; Output rise time
+ t_fall=2n       ; Output fall time
+ g_pullup=0.024  ; 1/(logic high output resistance)
+ g_pulldown=0.034 ; 1/(logic low output resistance)
+ g_hiz=1e-9      ; 1/(high impedance output res)
+ knee_low = 2.0   ; voltage at resistive/constant current
+                 ; knee logic low
+ knee_high =2.75  ; voltage at resistive/constant current
+                 ; knee logic high
+ v_smooth = 0.5   ; Knee smoothing band
+ in_family="HC"
```



Logic '0' state - strength = STRONG

In the above graph, the slope of the curve at  $V=0$  is determined by the  $G\_PULLDOWN$  parameter. The 'knee smoothing band' is a transitional area where the output switches from a constant resistance to a constant current. The smoothing characteristic is a quadratic and is calculated to be smooth at all points. This is required for good convergence behaviour. The knee smoothing band starts at  $KNEE\_LOW - V\_SMOOTH$  and finishes at  $KNEE\_LOW + V\_SMOOTH$ .



Logic '1' state - strength = STRONG

If a state with RESISTIVE strength is applied to the input of a digital to analog interface bridge, the output has the characteristic of a pure resistor connected to the voltage associated with the input's state. In the example given above, this would be a 1k resistor connected to 0V for the logic '0' state and a 1k resistor connected to +5V for the logic '1' state. (1k is  $1/G\_RESISTIVE$ )

For the HI-IMPEDANCE strength, the output will look like a resistor of value  $1/G\_HIZ$  connected to a voltage half way between the two analog output states. (1G connected to 2.5V in the above example.)

When the input state is UNKNOWN the output will be as if it were half way between the two known states. This is a compromise solution. The UNKNOWN state does not have a parallel in the analog domain so instead it is treated as a transitional state. In some cases the UNKNOWN state occurs in transitional cases although this is not the correct meaning of UNKNOWN.

### 5.31.6 Switching Characteristics

When the logic state at the input changes, the output will transition from the current state to the target state in a time determined by  $T\_RISE$  or  $T\_FALL$  according to the direction of the state change.

## 5.32 Controlled Digital Oscillator

### 5.32.1 Netlist entry

```
Axxxx cntl_in out model_name : parameters
```

### 5.32.2 Connection details

Name	Description	Flow	Type	Allowed types
cntl_in	Control input	in	v	v, vd, i, id
out	Output	out	d	d

### 5.32.3 Instance Parameters

Name	Description	Type
init_phase	Initial phase	real

### 5.32.4 Model format

```
.MODEL model_name d_osc parameters
```

### 5.32.5 Model parameters

Name	Description	Type	Default	Limits	Vector bounds
cntl_array	Control array	real vector	N/A	none	2 – $\infty$
freq_array	Frequency array	real vector	N/A	0 – $\infty$	2 – $\infty$
duty_cycle	Output duty cycle	real	0.5	1 $\mu$ -0.999999	n/a
init_phase	Initial phase of output	real	0	-180 - +360	n/a
rise_delay	Rise delay	real	1n	0 – $\infty$	n/a
fall_delay	Fall delay	real	1n	0 – $\infty$	n/a
phase_tol	Phase tolerance/degrees	real	10	0 - 45	n/a
out_family	Output logic family	string	UNIV	none	n/a
out_res	Digital output resistance	real	100	0 – $\infty$	n/a
out_res_pos	Digital output res. pos. slope	real	out_res	0 – $\infty$	n/a
out_res_neg	Digital output res. neg. slope	real	out_res	0 – $\infty$	n/a

### 5.32.6 Device Operation

This device produces an output frequency controlled by an analog input signal following an arbitrary piece-wise linear law. The input to output frequency characteristic is defined by two parameters CNTL\_ARRAY and FREQ\_ARRAY. The following is an example of a .MODEL statement:

```
.model vco d_osc
+ cntl_array=[-1,0,1,2,3,4,5]
+ freq_array=[0,10000,40000,90000,160000,250000,360000]
```

The frequency characteristic described by the above example follows a square law. The two arrays CNTL\_ARRAY and FREQ\_ARRAY must be the same length. These define the frequency output for a given analog input.

### 5.32.7 Time Step Control

In order to control the accuracy of the phase of the output signal, this model may cut back the analog time step. At each analog time point, the required frequency is calculated and the digital output is set at that frequency. If the analog input changes by too large an amount between time points, the digital output phase could be substantially in error as the frequency is constant between analog time points. The actual error is calculated and if this exceeds PHASE\_TOL, the time point is rejected and a time point at which the error will be in tolerance is estimated.

Note: This model was included with the original XSPICE code but the SIMetrix version has been completely re-written. The original did not have any phase error control and could not give accurate results unless the analog time step was artificially kept small.

## 5.33 Analog-Digital Schmitt Trigger

### 5.33.1 Netlist entry

```
Axxxx in out model_name
```

### 5.33.2 Connection details

Name	Description	Flow	Type	Allowed types
in	Input	inout	g	g, gd
out	Output	out	d	d

### 5.33.3 Model format

```
.MODEL model_name adc_schmitt parameters
```

### 5.33.4 Model parameters

Name	Description	Type	Default	Limits
in_low	Maximum 0-valued analog input	real	0.1	none
in_high	Minimum 1-valued analog input	real	0.9	none
rise_delay	Rise delay	real	1nS	$1e^{-12} - \infty$
fall_delay	Fall delay	real	1nS	$1e^{-12} - \infty$
time_tol	Threshold time tolerance	real	100pS	$1e^{-12} - \infty$
out_low	Analog out for 'ZERO' input	real	0	none
out_high	Analog output 'ONE' input	real	5	none
clamp_res	Clamp minimum resistance	real	1	$1e-06 - \infty$
clamp_bias	Clamp voltage	real	0.8	0.2 - 2
out_family	Output logic family	string	UNIV	none
init_cond	Initial condition	real	0	none

### 5.33.5 Device Operation

This device is basically identical to the [“Analog-Digital Interface Bridge” on page 174](#). The only difference is the behaviour of the device when the analog input lies between the threshold voltages. With the interface bridge, the output is UNKNOWN under these circumstances but with this Schmitt Trigger, the output retains its previous value and so is always in a known state. In summary, the output will only switch from low to high when the input exceeds the higher threshold (IN\_HIGH) and will only switch from high to low when the input descends below the lower threshold (IN\_LOW).

If initial input voltage lies between the hysteresis thresholds, the output state is determined by the `init_cond` parameter.



# Chapter 6

## Command Reference

### 6.1 Overview

Simulator commands instruct the simulator how to read in and simulate the circuit. All simulator commands begin with a period ( . ) .

For the remainder of this chapter and elsewhere in this manual, simulator commands are referred to as ‘Statements’ to distinguish them from commands entered in the command shell.

The schematic editor supports some of the statements described in this chapter but not all. Unsupported analysis statements may be added manually to the schematic’s netlist. See [“Adding Extra Netlist Lines” on page 2](#) for details.

The following simulator statements are recognised by SIMetrix.

- .AC
- .DC
- .ENDF
- .ENDS
- .FILE
- .FUNC
- .GLOBAL
- .GRAPH
- .IC
- .INC
- .INCLUDE
- .KEEP
- .LOAD
- .LIB
- .MODEL
- .NOCONV
- .NODESET
- .NOISE

.OP  
 .OPTION  
 .OPTIONS  
 .PARAM  
 .PARAMETER  
 .POST\_PROCESS  
 .PRINT  
 .SENS  
 .SETSOA  
 .SUBCKT  
 .TEMP  
 .TF  
 .TRACE  
 .TRAN

The following statement is only recognised in model library files.

.ALIAS

## 6.2 General Sweep Specification

### 6.2.1 Overview

SIMetrix features a common sweeping algorithm which is used to define the swept analysis modes: .DC, .AC, .NOISE and (now) .TF, along with multiple analyses such as Monte Carlo.

The sweep algorithm has 6 modes:

- Device. Sweeps a single default value of a specified device. E.g. voltage of a voltage source, resistance of a resistor or the capacitance of a capacitor.
- Temperature
- Parameter. Parameter can be referenced in an expression for a model or instance parameter.
- Model parameter. Named model parameter.
- Frequency. (Not applicable to .DC)
- Monte Carlo. Perform a specified number of steps with distribution functions (i.e tolerances) enabled.

Standard SPICE only provides a subset of the above. .DC can only sweep voltage and current sources, .AC and .NOISE can only sweep frequency while .TF can't be swept at all.

As well as providing 6 modes, each of the modes can sweep in four different ways. These are linear, decade, octave and list.

## 6.2.2 Syntax

All the swept analysis modes use the same general syntax to specify the sweep parameters. However, to maintain compatibility with SPICE and its derivatives including earlier versions of SIMetrix, each analysis mode allows variations to this standard syntax. The general syntax is described below while the variations allowed for each analysis mode are described in the section dedicated to that analysis mode.

All of the analysis modes can optionally be entered in a similar manner to .MODEL statements i.e. as an unordered list of parameter names followed by their values. For example, the following is a perfectly legal noise analysis specification:

```
.noise V=vout DEVICE=V1 VN=0 F=1k LIN=(100 -10m 10m)
+ INSRC=V1
```

In the various forms of the syntax described in the following sections, some of the parameter names may be omitted as long as they are entered in a particular order. It is sometimes, however, easier to remember parameter names rather than a default order, so the method described above may be more convenient for some users.

### General syntax for swept analyses

```
.AC|.DC|.NOISE|.TF sweep_spec [ analysis specific parameters ]
```

sweep\_spec: One of the following:

```
DEVICE device_name step_spec F frequency
TEMP step_spec F frequency
PARAM param_name step_spec F frequency
MODEL model [PARAM] mod_param_name step_spec F frequency
FREQ step_spec
MONTE num_steps F frequency
```

Where

<i>device_name</i>	Name of device to be swept. The following components may be swept: Capacitors, all controlled sources, fixed current source, fixed voltage source, inductors and resistors.
<i>param_name</i>	Name of parameter used in expression. Expressions may be used to define an instance or model parameter and may also be used in arbitrary sources.
<i>model</i>	Name of model containing parameter to be swept
<i>mod_param_name</i>	Name of model parameter
<i>num_steps</i>	Number of steps to be performed for Monte Carlo sweep.
<i>frequency</i>	Specified frequency for which .NOISE, .AC and .TF analyses are to be performed. May be zero for .AC and .TF.
<i>step_spec</i>	One of the following: <pre>STP <i>start</i> <i>stop</i> <i>step</i> LIN <i>num_points</i> <i>start</i> <i>stop</i> DEC <i>num_points</i> <i>decade</i> <i>start</i> <i>stop</i> OCT <i>num_points</i> <i>octave</i> <i>start</i> <i>stop</i> LIST <i>val1</i> [ <i>val2</i> ... ]</pre>

Where:

<i>start</i>	First value
<i>stop</i>	Last value (inclusive)
<i>step</i>	Interval
<i>num_points</i>	Total number of points
<i>num_points_decade</i>	Number of points per decade
<i>num_points_octave</i>	Number of points per octave

STP and LIN modes are both linear sweeps but specified differently. STP specifies start, stop and a step size, while LIN specifies start, stop and the total number of points.

## 6.3 Multi Step Analyses

### 6.3.1 Overview

The sweep specification described in [“General Sweep Specification” on page 188](#) can also be applied to define multiple analyses including Monte Carlo analysis. This can be applied to the swept modes .DC, .AC, .NOISE and .TF along with .TRAN. The analyses .SENS, .PZ and .OP cannot be run in multi-step mode. A multi-step .OP is in fact the same as .DC so this is not required. Monte Carlo analysis is the subject of its own chapter (see [“Monte Carlo Analysis” on page 250](#)) but it is invoked in the same way as other multi-step modes. As well as the standard 6 sweep modes, small-signal multi-step analyses can be run in snapshot mode which uses snapshots created by a previous transient analysis.

### 6.3.2 Syntax

The general form is:

```
.analysis_name analysis_parameters SWEEP
+ [sweep_spec] | [SNAPSHOT STP snapstart snapstop snapstep] |
  [SCRIPTCOUNT=numscriptruns SCRIPT=script] [ NUMCORES=num_cores]
```

Where:

<i>.analysis_name</i>	Dot statement for analysis
<i>analysis_parameters</i>	Specific parameters for that analysis
<i>sweep_spec</i>	See <a href="#">“General Sweep Specification” on page 188</a> .
SNAPSHOT	Use snapshots created by a previous transient analysis. For full details, see <a href="#">“Snapshots” on page 247</a> .
<i>snapstart</i>	Index of first snapshot. Snapshots are counted in the order in which they are created. The first is 0. Use STP 0 0 0 to specify all available snapshots.
<i>snapstop</i>	Index of last snapshot
<i>snapstep</i>	Snapshot interval (usually 1)
<i>numscriptruns</i>	Number of repeat steps using <i>script</i> . If present, the script <i>script</i> is called for each step. The script may use the function GetCurrentStepValue() to determine the step number (base 1, i.e. the first step is 1, the second 2 etc.). The functions SetInstanceParamValue() and SetModelParamValue() may be used to change model or instance parameters

<i>script</i>	Script called for each step
<i>num_cores</i>	If specified and greater than 1, the work for the run will be shared amongst <i>num_cores</i> processor cores using multiple processes. More information about using multiple cores can be found in <i>User's Manual/Analysis Modes/Using Multiple Cores for Multi-step Analyses</i> .

## Examples

Run 10 Monte Carlo runs for 1mS transient analysis

```
.TRAN 1m SWEEP MONTE 10
```

As above but does 1000 steps split over 4 cores. So each core will do 250 steps. Requires a system equipped with at least 4 physical processor cores.

```
.TRAN 1m SWEEP MONTE 1000 NUMCORES=4
```

Sweep V1 from 0 to 5 volts in 0.1V steps for 200us transient

```
.TRAN 200u SWEEP DEVICE V1 STP 0 5 0.1
```

AC sweep of voltage source V5 from -300mV to 300mV. Repeat 6 times for parameter restail from 450 to 550.

```
.AC DEVICE=V5 LIN 100 -300m 300m F=100000
+ SWEEP PARAM=restail LIN 6 450 550
```

Run AC sweep using all available snapshots

```
.AC DEC 100k 10G SWEEP SNAPSHOT STP 0 0 0
```

## 6.4 .AC

### 6.4.1 Syntax

```
.AC inner_sweep_spec [ F frequency ] [RUNNAME=runname] [ SWEEP outer_sweep_spec ]
```

Spice compatible frequency sweep:

```
.AC DEC|LIN|OCT num_points start stop
```

Instructs the simulator to perform a swept small signal AC analysis. SIMetrix AC analysis is not limited to a frequency sweep as it is with generic SPICE and derivatives. See [“General Sweep Specification” on page 188](#) and examples below for more details.

<i>frequency</i>	Frequency at which analysis will be performed for non-frequency sweeps. Default 0.
<i>inner_sweep_spec</i>	See <a href="#">“General Sweep Specification” on page 188</a> for syntax. Defines sweep mode. FREQ keyword is optional.
<i>outer_sweep_spec</i>	If specified, analysis will be repeated according to this specification. See <a href="#">“General Sweep Specification” on page 188</a> for syntax.
<i>num_points</i>	LIN: total number of points DEC: number of points per decade OCT: number of points per octave

<i>start</i>	Start frequency for SPICE compatible mode
<i>stop</i>	Stop frequency for SPICE compatible mode
<i>runname</i>	If specified, the value for <i>runname</i> will be passed to the simulation data group as a string variable with name <i>UserRunName</i> . This may be used to identify which analysis generated the data which is useful when running netlists with multiple analyses defined

Except for frequency sweep, the frequency at which the analysis is being performed should be specified. If omitted, the frequency will be assumed to be zero.

For non-frequency sweeps, a new dc operating point may be calculated at each step depending on what is being swept. If a capacitor, inductor or an ‘AC only’ model parameter is being swept, then no new dc operating point will be required. Otherwise one will be performed. An ‘AC only’ parameter is one that does not affect DC operating point such as device capacitance.

### 6.4.2 Notes

An AC analysis calculates the small signal frequency response of the circuit about the dc operating point. The latter is automatically calculated prior to commencing the frequency sweep. One or more inputs may be specified for AC analysis by using voltage or current sources with the AC specification (See “[Voltage Source](#)” on page 109). The results of an AC analysis are always complex.

### 6.4.3 Examples

SPICE compatible. Sweep frequency from 1kHz to 1Meg

```
.AC DEC 25 1k 1MEG
```

Sweep voltage source V1 100 points from -100mV to 100mV. Frequency = 100kHz

```
.AC DEVICE V1 LIN 100 -100m 100m F=100k
```

Sweep parameter Rscale from 0.5 to 3 in steps of 0.1. Frequency=20Meg

```
.AC PARAM Rscale STP 0.5 3 0.1 F=20Meg
```

Sweep resistor R1 with values 10k 12k 15k 18k 22k 27k 33k, Frequency =1.1KHz

```
.AC DEVICE R1 LIST 10k 12k 15k 18k 22k 27k 33k F=1.1K
```

Monte Carlo sweep 100 steps. Frequency = 10K. This is useful if - say - you are interested in the gain of an amplifier at one frequency and it needs to lie within a defined tolerance. Previously you would need to repeat an AC sweep at a single frequency to achieve this which could take a long time especially if the circuit has a difficult to find operating point. The analysis defined by the following line will take very little time even for a large circuit.

```
.AC MONTE 100 F=10K
```

### 6.4.4 Examples of Nested Sweeps

As Monte Carlo above but repeated from 0 to 100C

```
.AC MONTE 100 F=10K SWEEP TEMP STP 0 100 10
```

... and at a number of frequencies

```
.AC MONTE 100 SWEEP FREQ DEC 5 1k 100k
```

## 6.5 .ALIAS

### 6.5.1 Syntax

```
.ALIAS alias_name device_name device_type
```

This statement may only be used in device model library files. It is not recognised by the simulator. It permits a device model or subcircuit to be referenced by a different name. This allows one model definition to be used for multiple part numbers.

<i>alias_name</i>	Alias name
<i>device_name</i>	Device to which alias refers
<i>device_type</i>	Type of device to which alias refers. Must be one of the following C, D, LTRA, NJF, NMF, NMOS, NPN, PJF, PMF, PMOS, PNP, R, SW or SUBCKT. see <a href="#">“.MODEL” on page 208</a> for more details.

### 6.5.2 Example

```
.MODEL BC547C NPN
+   IS=7.59E-15 VAF=19.3 BF=500 IKF=0.0710 NE=1.3808
+   ISE=7.477E-15 IKR=0.03 ISC=2.00E-13 NC=1.2 NR=1 BR=5
+   RC=0.75 CJC=6.33E-12 FC=0.5 MJC=0.33 VJC=0.65
+   CJE=1.25E-11 MJE=0.55 VJE=0.65 TF=4.12E-10 ITF=0.4 VTF=3
+   XTF=12.5 RB=172 IRB=0.000034 RBM=65

.ALIAS BC549C BC547C NPN
```

The above would provide identical definitions for both BC547C and BC549C bipolar transistors.

**Notes** .ALIAS definitions will recognise models defined in other files provided the file in which the alias resides and the file in which the model definition resides are part of the same library specification. A library specification is a single pathname possibly with a wildcard ('?' or '\*') to refer to multiple files. E.g. /simetrix/models/\*.mod is a library specification and refers to all files with the extension 'mod' in the directory /simetrix/models.

Aliases must refer directly to a model or subcircuit definition and not to other aliases.

## 6.6 .DC

### 6.6.1 Syntax

```
.DC inner_sweep_spec [RUNNAME=runname] [ SWEEP outer_sweep_spec ]
```

Spice compatible:

```
.DC device_name start stop step
```

The remainder are SIMetrix 2.5 - 3.1 compatible:

```
.DC TEMP start stop step
```

```
.DC PARAM param_name start stop step
```

```
.DC MODEL model [PARAM] mod_param_name start stop step
```

Instructs simulator to perform a DC sweep analysis. A dc analysis performs a dc operating point analysis for a range of values according to the sweep specification. SIMetrix DC analysis is not limited to sweeping a voltage or current source as with generic SPICE. Any mode defined by the general sweep specification (see “[General Sweep Specification](#)” on page 188) may be used although frequency sweep has no useful purpose.

<i>inner_sweep_spec</i>	See “ <a href="#">General Sweep Specification</a> ” on page 188 for syntax. Defines sweep mode. DEVICE keyword is optional.
<i>outer_sweep_spec</i>	If specified, analysis will be repeated according to this specification. See “ <a href="#">Multi Step Analyses</a> ” on page 190 for details.
<i>device_name</i>	Component reference of voltage source, current source, resistor or controlled source to be swept. (Only voltage and current sources are SPICE compatible).
<i>start</i>	Start value for sweep
<i>stop</i>	Stop value for sweep
<i>step</i>	Increment at each point
<i>param_name</i>	Parameter name. This would be used in an expression to define a component or model value.
<i>model_name</i>	Model name e.g. Q2N2222
<i>model_parameter_name</i>	Model parameter name e.g. IS
<i>runname</i>	If specified, the value for runname will be passed to the simulation data group as a string variable with name UserRunName. This may be used to identify which analysis generated the data which is useful when running netlists with multiple analyses defined.

If *start* is arithmetically greater than *stop* then *step* must be negative.

It is not necessary to declare parameters with .PARAM if using parameter sweep.

### 6.6.2 Examples

SPICE compatible. Sweep V1 from 0 to 5 volts in steps of 0.1 volt

```
.DC V1 0 5 0.1
```

SIMetrix 3.1 compatible temperature sweep

```
.DC TEMP 0 100 2
```

Decade (i.e. logarithmic) sweep. Sweep V1 from 1mV to 1V with 25 points per decade

```
.DC V1 DEC 25 1m 1v
```

Note that the DEVICE keyword has been omitted. This is the default sweep mode for .DC.

Do 1000 Monte Carlo steps. This performs the same task as a Monte Carlo analysis applied to a DC operating point. In other products and earlier versions of SIMetrix this task would take a long time as the operating point is solved from scratch each time. With the mode described by the following example, the operating point need only be calculated from scratch once. All subsequent steps are seeded by the previous one and usually require only a few iterations. The end result is a sometimes spectacular increase in speed.



```
.DC MONTE 1000
```

### 6.6.3 Examples of Nested Sweeps

Decade sweep at temperatures 0 to 100 in steps of 10

```
.DC V1 DEC 25 1m 1v SWEEP TEMP STP 0 100 10
```

Note the STP keyword is necessary to signify the start-stop-step method of defining a linear sweep. Alternatively LIN can be used which defines the sweep in terms of the total number of points. The following is equivalent to the above:

```
.DC V1 DEC 25 1m 1v SWEEP TEMP LIN 11 0 100
```

Do 100 run Monte Carlo analysis for temperature sweep

```
.DC TEMP 0 100 2 SWEEP MONTE 100
```

## 6.7 .FILE and .ENDF

### 6.7.1 Syntax

```
.FILE filename
file_contents
.ENDF
```

The .FILE statement allows the contents of a file referenced in a .MODEL statement to be placed directly in the netlist. Files are referenced in arbitrary logic blocks (see [“Arbitrary Logic Block - User Defined Models” on page 287](#)), PWLFILE voltage and current sources (see [“PWL File Source” on page 112](#)), digital sources (see [“Digital Signal Source” on page 144](#)) and digital state machines (see [“State Machine” on page 163](#)). Each of these may refer to files defined using .FILE and .ENDF.

### 6.7.2 Example

```
.MODEL COUNT_8 d_logic_block file=counter_def

.FILE counter_def
PORT (DELAY = 10n) CountOut out[0:7] ;

EDGE (DELAY=5n, WIDTH=8, CLOCK=in[0]) Count ;

ount = Count + 1 ;

CountOut = count ;
.ENDF
```

The .MODEL statement refers to a file called ‘counter\_def’. This could be a real disk file called counter\_def or counter\_def.ldf, but in the above example it is instead defined directly in the netlist using .FILE and .ENDF.

### 6.7.3 Important Note

.FILE and .ENDF will *not* be recognised in library files.

## 6.8 .FUNC

```
.FUNC name ( [arglist] ) { body }
```

<i>name</i>	Name of function. Must begin with a letter and not match one of the built in functions.
<i>arglist</i>	List of comma separated argument names. May be empty in which case the function may be called without the parentheses. This is useful for creating random variables for Monte Carlo analysis.
<i>body</i>	Body of function. This is an expression referring to the names in arglist that defines the operation performed by the function

.FUNC defines a function that can be used in a model or device parameter expression, a parameter defined using .PARAM or in an arbitrary source expression.

### 6.8.1 Examples

```
.FUNC FREQ(V) { (V)*120K }
.FUNC SWEEP(V) { SIN(TIME*FREQ(v)*2*PI) }
.FUNC RV1() { GAUSS(0.1) }
```

The third example may be called without parentheses as it has no arguments. E.g.:

```
.PARAM random1 = rv1 random2 = rv1
```

In the above, random1 and random2 will have different values when run in a Monte Carlo analysis.

### 6.8.2 Optimiser

Any expression that uses a function defined with .FUNC will be automatically processed by an optimisation algorithm. For more information see [“Optimisation” on page 29](#).

The optimiser attempts to speed simulations by making the expression evaluation more efficient. The optimiser is effective when .FUNC is used to create very complex expressions perhaps to develop a semiconductor device. In simple applications it may not make a noticeable improvement to performance. The optimiser can be enabled for *all* expressions and can also be disabled completely. To enable for all expressions use:

```
.OPTIONS optimise=2
```

To disable:

```
.OPTIONS optimise=0
```

## 6.9 .GLOBAL

```
.GLOBAL node [ node... ]
```

Identifies nodes as global. This allows nodes specified at the top level of a circuit to be accessed within a subcircuit definition. For more information see [“Subcircuits” on page 30](#).

## 6.10 .GRAPH

### 6.10.1 Parameters

```

.GRAPH signal_name|"expression"
+ [ persistence = persistence ]
+ [ axisname = axisname ]
+ [ graphname = graphname ]
+ [ axistype = digital|grid|axis|auto ]
+ [ curvelabel = curvelabel ]
+ [ xlabel = xlabel ]
+ [ ylabel = ylabel ]
+ [ xunit = xunit ]
+ [ yunit = yunit ]
+ [ xmin = xmin ]
+ [ ymin = ymin ]
+ [ xmax = xmax ]
+ [ ymax = ymax ]
+ [ analysis = analyses_list ]
+ [ ylog = lin|log|auto ]
+ [ xlog = lin|log|auto ]
+ [ nowarn = true|false ]
+ [ initXLims = true|false]
+ [ complete = true|false ]
+ [ order = order ]
+ [ colour = colour ]

```

.GRAPH instructs SIMetrix to plot a graph of the specified signal or expression. The graph can be plotted incrementally as the simulation proceeds or may be delayed until the run is complete.

Parameter name	Type	Description
signal_name   expression	string	Specifies item to be plotted. If this is an expression, then it must be enclosed in double quotation marks or curly braces.
persistence	integer	Number of curves to be displayed at once. On repeated runs, any curves from earlier runs remain until the number of curves exceeds this value at which point the oldest is deleted automatically. If this parameter is absent or zero, the curves are never deleted.
graphname	string	If specified, the curves will be directed to their own graph sheet within the current window. The value of graphname is arbitrary and is used to identify the graph so that multiple .graph statements can specify the same one. It works in a similar way to axisname an example of which is given below. This name is not used as a label for display purposes but simply as a means of identification.

Parameter name	Type	Description
axistype	string	<p>Can be one of four values to specify type of y-axis:</p> <ul style="list-style-type: none"> <li>• <b>DIGITAL</b>. Use a digital axis. This is a small axis that carries only one curve. It is intended for digital signals but may also carry analog curves.</li> <li>• <b>GRID</b>. Use a separate grid stacked on top of the main one. The <b>AXISNAME</b> parameter may be used to identify a particular grid used by another <b>.GRAPH</b> statement.</li> <li>• <b>AXIS</b>. Use a separate y-axis alongside the main one. The <b>AXISNAME</b> parameter may be used to identify a particular axis used by another <b>.GRAPH</b> statement.</li> <li>• <b>AUTO</b>. This is the default value. A suitable axis is chosen automatically.</li> </ul>
axisname	string	This is only used if <b>AXISTYPE</b> is specified. The value of <b>AXISNAME</b> is arbitrary and is used to identify the axis so that multiple <b>.GRAPH</b> statements can specify the same one. An example of this is given below. This name is not used as a label for display purposes but simply as a means of identification. Axes can be labelled using <b>ylabel</b> and <b>xlabel</b> .
curvelabel	string	Label for curve displayed in graph legend. If omitted, the label will be the signal name or expression.
xlabel	string	Label for x-axis. Default is reference of curve being plotted (E.g. time, frequency etc.)
ylabel	string	Label for y-axis. If there is only a single curve, this will default to the label for the curve otherwise the default is blank.
xunit	string	Units for x-axis. Default is units of reference.
yunit	string	Units for y-axis. Default is units of curves plotted provided they are all the same. If any conflict, the default will be blank
xmin	real	Minimum limit for x-axis. Must be used with <b>xmax</b> .
xmax	real	Maximum limit for x-axis. Must be used with <b>xmin</b> .
ymin	real	Minimum limit for y-axis. Must be used with <b>ymax</b> .
ymax	real	Maximum limit for y-axis. Must be used with <b>ymin</b> .
analysis	string	<p>Specifies for what analysis modes the plot should be enabled. By default it will be enabled for all analysis modes. Any combination of the following strings, separated by a pipe (' ') symbol.</p> <ul style="list-style-type: none"> <li>• <b>TRAN</b>. Transient analysis</li> <li>• <b>AC</b>. AC analysis</li> <li>• <b>DC</b>. DC sweep analysis</li> <li>• <b>NOISE</b>. Noise analysis</li> <li>• <b>POP</b>. POP analysis - <b>SIMPLIS</b> only</li> </ul> <p>Other analysis modes do not produce results that can be probed</p>

Parameter name	Type	Description
ylog	string	One of three values LIN     Use linear axis LOG     Use log axis AUTO    Axis will be log if x values are log spaced. (E.g for decade AC sweep) and all values are positive. Default if omitted: LIN
xlog	string	One of three values LIN     Use linear axis LOG     Use log axis AUTO    Axis will be log if x values are log spaced. (E.g for decade AC sweep) and all values are positive. Default if omitted: AUTO
nowarn	Boolean	If true, no warnings are given if an attempt is made to plot a non-existent signal. Default: false.
initXLims	Boolean	When this is TRUE, the x-axis limits are initialised according to the analysis. E.g. if the analysis is transient and runs from 0 to 1mS, the x-axis will start with these limits. If set to FALSE, the x-axis limits are calculated to fit the curve and updated incrementally. You should set this to FALSE if you are plotting an expression whose x values are not the same as the x values for the analysis e.g. using the XY() function for an X-Y plot. The default value of this option is usually true but can be changed using the option NoInitXAxisLimits . Type at the command line: “Set NoInitXAxisLimits” to change default to false.
complete	Boolean	If true, the plot is not produced until the analysis is completed. Otherwise the plot is updated at a rate determined by the global option ProbeUpdatePeriod. This is forced for some types of plot as certain expressions cannot be plotted incrementally. This can be set using the options dialog box ( <b>File   Options   General...</b> ). Default: false.
order	string	Arbitrary string used to control the display order of digital traces. Digital traces are displayed in an order that is determined by the alphanumeric sort order of the order value. If omitted, the curvelabel value is used instead.
colour	string	Number representing an RGB value of the colour of the final trace. The number, when converted to hexadecimal, is in the form: bbgrr where bb is the blue value, gg is the green value and rr is the red value. So, 16711680 - FF0000 in hexadecimal is deep blue.

The .GRAPH statement is the underlying simulator mechanism used by the schematic’s fixed probes. See *User’s Manual/Graphs, Probes and Data Analysis/Fixed Probes* for details.

.GRAPH supersedes the older and less flexible .TRACE. The latter is, however, still supported

and may sometimes be convenient for specifying multiple signals on one line.

### 6.10.2 Using Multiple .GRAPH Statements

If specifying several .GRAPH statements to plot a number of curves on the same graph, you should make sure that the various parameters are consistent. If for example, a conflict arises if you specify xmin and xmax for two .GRAPHS that plot curves in the same graph sheet, and the values for xmin and xmax are different for each. You can specify xmin and ymin for just one of the .GRAPH statements or you can specify for all and make sure they are all the same. The same applies to other non-Boolean parameters i.e. ymin, ymax, xlabel, ylabel, xunits and yunits. The parameter initXLims, however must be specified with the same value for all .GRAPH statements specifying the same graph sheet.

Conflicting values of ylog and xlog are resolved by plotting the curves on separate axes or graph sheets respectively.

### 6.10.3 Creating X-Y Plots

To create an X-Y plot, use the XY() function (*Script Reference Manual/Function Reference/XY* for full details of available functions). You should also specify "initXLims=false". E.g.

```
.GRAPH "XY( imag(vout), real(vout) )" initXLims=false
+ xlog=LIN complete=true
```

The above will create a Nyquist plot of the vector VOUT.

### 6.10.4 Using .GRAPH in Subcircuits

.GRAPH maybe used in a subcircuit in which case a plot will be produced for all instances of that subcircuit. Note, however, that it will only work for single values and not for expressions when inside a subcircuit. The value of the *curveLabel* parameter will be prefixed with the instance name so that the displayed curves can be correctly identified.

### 6.10.5 Using Expressions with .GRAPH

You can enter an expression as well as single vectors to be plotted. A problem arises when plotting expressions incrementally that are regularly updated while the simulation is running. SIMetrix versions prior to v5 could not incrementally evaluate expressions, so each time the plot of an expression was updated, the expression had to be recalculated from the beginning. This was inefficient and it has always been recommended that the complete=true flag was added in these circumstance to inhibit incremental plotting.

SIMetrix - from version 5 - now has the ability to incrementally evaluate some expressions and there is no longer a recommendation to set complete=true. However, certain expression cannot be incrementally evaluated and when such expressions are entered, incremental plotting will automatically be disabled and the plot won't appear until the run is complete.

A notable example of expressions that cannot be incrementally evaluated is anything containing the phase() function. This is because the phase() function uses a state machine to determine when the phase wraps from -180 to 180 and back. An offset is then applied to make the phase plot continuous. Because of the state machine, it is always necessary to evaluate this function from start to finish which makes incremental evaluation difficult. An alternative is to use instead the arg() function. This is the same as phase, but does not have the state machine and always gives an output that lies between +/- 180 degrees.

### 6.10.6 Plotting Spectra with .GRAPH

You can use .GRAPH to create spectrum plots using FFTs or Fourier. However, FFT is quite difficult to use on its own as it needs interpolated data. So, a new user defined function called Spectrum() has been developed that is especially designed for use with .GRAPH. Usage is:

```
Spectrum(vector, numPoints [, start [, stop]])
```

Where:

vector	Vector or expression
numPoints	FFT size - must be a binary power of 2
start	Start time - default = 0
stop	Stop time - default = end of data

Spectrum() cannot be incrementally evaluated and so incremental plotting will automatically be disabled for any .GRAPH statement that uses it. See [“Using Expressions with .GRAPH” on page 200](#).

#### Examples

```
.GRAPH C2_P curveLabel="Amplifier output" nowarn=true
```

Plots the vector C2\_P and gives it the label ‘Amplifier output’. As NOWARN is TRUE, no warning will be given if C2\_P does not exist.

```
.GRAPH vout_quad
+ axisType="grid"
+ axisName="grid1"
+ persistence=2
+ curveLabel="Quadrature"
+ nowarn=true
+ analysis = TRAN|DC
```

```
.GRAPH vout
+ axisType="grid"
+ axisName="grid1"
+ persistence=2
+ curveLabel="In Phase"
+ yLabel="Filter Outputs"
+ nowarn=true
+ analysis = TRAN|DC
```

The above illustrates the use of the parameters AXISTYPE and AXISNAME. Both the vectors specified by the above .GRAPH statements will be plotted on the same but separate grid. Because both grids have been given the AXISNAME grid1, each curve will be plotted on the same one. If the values of axisname for the above were different, each curve would be plotted on a *separate* grid. The ANALYSIS parameter has been specified in both cases, so plots will only be created for transient and dc sweep analyses.

## 6.11 .IC

```
.IC V(node1)=val1 [ V(node2)=val2 ]...
```

OR

```
.IC node1 val1 [ node2 val2 ]
```

This statement sets transient analysis initial conditions.

<i>node1, node2</i> etc.	Name of circuit node (or net) to which initial condition is to be applied. See notes below.
<i>val1, val2</i> etc.	Voltage to be applied to net as initial condition. May be an expression containing parameters defined using .PARAM.

If the UIC parameter is specified with the .TRAN statement no DC operating point will be calculated so an initial condition will set the bias point in the same way as an IC=... parameter on a BJT, capacitor, diode, JFET or MOSFET.

If the UIC parameter is absent from the .TRAN statement then a DC operating point is calculated before the transient analysis. In this case the net voltages specified on the .IC statement are forced to the desired initial values during the DC operating point solution. Once transient analysis begins this constraint is released. By default the voltage force is effectively carried out via a 1Ω resistor. This can be changed with the option setting ICRES (see “[OPTIONS](#)” on page 216).

### 6.11.1 Alternative Initial Condition Implementations

An initial condition can also be specified using a voltage source with the DCOP parameter specified. E.g.

```
VIC1 2 3 3.5 DCOP
```

Will force a voltage of 3.5 volts between nodes 2 and 3 during the DC operating point solution. This has two advantages over .IC:

1. It has zero force resistance
2. It can be applied differentially

You can also use a capacitor with the BRANCH parameter set to 1. E.g.:

```
C1 2 3 10u BRANCH=1 IC=3.5
```

This will behave identically to the voltage source in the above example during the DC operating point but during a subsequent small-signal or transient analysis will present a 10 F capacitance to nodes 2 and 3.

See also: “[Capacitor](#)” on page 58 and “[Voltage Source](#)” on page 109.

## 6.12 .INC

```
.INC pathname
```

Insert the contents of the specified file.

<i>pathname</i>	File system pathname for file to be included
-----------------	--

The .INC statement is replaced by the specified file in its entirety as if was part of the original file. .INC statements may also be nested i.e. there may be .INC statements within the included file. Nesting may be to any level.



## 6.13 .KEEP

```
.KEEP signal_spec [signal_spec ...]
```

This statement tells the simulator what values to store during a simulation. By default all signals at the top level and defined inside a hierarchical subcircuit are saved. .KEEP may be used in conjunction with some .OPTIONS settings to increase or reduce the data saved.

<i>signal_spec</i>	<b>/TOP</b>   <b>/SUBS</b>   <b>/NOV</b>   <b>/NOI</b>   <b>/NODIG</b>   <b>/INTERNAL</b>   <b>*V</b>   <b>*I</b>   <b>*D</b>   <b>**V</b>   <b>**I</b>   <b>**D</b>   <i>subref.*V</i>   <i>subref.*I</i>   <i>subref.*D</i>   <i>subref.**V</i>   <i>subref.**I</i>   <i>subref.**D</i>   <i>^wildcard_filter</i>   <i>signal_name</i>
<i>subref</i>	Sub-circuit reference
<b>/NOV</b>	Don't store top level (i.e. not in a subcircuit) voltages. Equivalent to ".OPTIONS KeepNov"
<b>/NOI</b>	Don't store top level currents. Equivalent to ".OPTIONS KeepNoi"
<b>/NODIG</b>	Don't store top level digital data. Equivalent to ".OPTIONS KeepNod"
<b>/SUBS</b>	Store all subcircuit data. Equivalent to ".OPTIONS KeepAll"
<b>/TOP</b>	Overrides /subs. This is to inhibit storing signals in child schematics in hierarchical designs. Equivalent to ".OPTIONS KeepTop"
<b>/INTERNAL</b>	Save all internal device values. Some devices have internal nodes or sources. For example the bipolar transistor has internal nodes to implement terminal resistance. These internal values are not usually saved but may be by specifying /INTERNAL. Equivalent to ".OPTIONS KeepInternal"
<i>^wildcard_filter</i>	General specification that selects values to store based on their name alone. Would usually use one of the special characters '*' and '?'. '*' means 'match one or more characters' while '?' means 'match a single character'. Some examples: <ul style="list-style-type: none"> <li>* matches anything</li> <li>X1.* matches any signal name that starts with the three letters: X1.</li> <li>X?.* matches any name that starts with an X and with a '?' for the third letter.</li> <li>*.q10#c matches any name ending with q10#c.</li> </ul>
<b>*V</b>	Store all top level voltages. This is actually implicit and need not be specified at the top level of the netlist. It can be usefully used in sub-circuit definitions - see notes.
<b>*I</b>	Store all top level currents. This is actually implicit and need not be specified at the top level of the netlist. It can be usefully used in sub-circuit definitions - see notes.
<b>*D</b>	Store all top level digital data. This is actually implicit and need not be specified at the top level of the netlist. It can be usefully used in sub-circuit definitions - see notes.
<b>**V</b>	Store all voltages including those inside sub-circuits descending to all levels
<b>**I</b>	Store all currents including those inside sub-circuits descending to all levels

<b>**D</b>	Store all digital data including those inside sub-circuits descending to all levels
<i>subref.*V</i>	Store all voltages within sub-circuit <i>subref</i> excluding voltages within children of <i>subref</i> .
<i>subref.*I</i>	Store all currents within sub-circuit <i>subref</i> excluding currents within children of <i>subref</i> .
<i>subref.*D</i>	Store all digital data within sub-circuit <i>subref</i> excluding digital data within children of <i>subref</i> .
<i>subref.**V</i>	Store all voltages within sub-circuit <i>subref</i> including voltages within children of <i>subref</i> descending to all levels.
<i>subref.*I</i>	Store all currents within sub-circuit <i>subref</i> including currents within children of <i>subref</i> descending to all levels.
<i>subref.*D</i>	Store all digital data within sub-circuit <i>subref</i> including digital data within children of <i>subref</i> descending to all levels.
<i>signal_name</i>	Explicit voltage or current.

### 6.13.1 Option Settings

A number of option settings are available to control data output. These can be used in conjunction with .KEEP statements to define what data is saved. The Option settings are defined in the table below:

Option Name	Description
KeepNone	No data is saved except signals explicitly defined using .KEEP or .GRAPH. Takes precedence over all other keep options
KeepNov	No voltages will be saved except signals explicitly defined using .KEEP or .GRAPH. Takes precedence over other options except KeepNone
KeepNoi	No currents will be saved except signals explicitly defined using .KEEP or .GRAPH. Takes precedence over other options except KeepNone
KeepNod	No digital signals will be saved except signals explicitly defined using .KEEP or .GRAPH. Takes precedence over other options except KeepNone
KeepAll	All data saved including data inside subcircuits. Does not enable saving of internal data (use KeepInternal) or semiconductor AC currents (use KeepAllAci).
KeepTop	Disables saving of subcircuit signals
KeepAllAci	Save currents in semiconductor devices for AC analysis
KeepInternal	Save device internal signals
KeepSubcktDepth	Limits saving of data in subcircuits to the specified level. E.g. KeepSubcktDepth=2 will save data in top level, first level subcircuits and second level subcircuits
KeepQuotaFactor	Number between 0.0 and 1.0 restricts data output following precedence rules. 0.0 will save no data whereas 1.0 will save all data as defined by other options. KeepQuotaFactor is applied after all other keep options. Note that the factor is an estimate.

**Examples**

Default with no Keep options is to save all top level data and all signals inside hierarchical subcircuits. Data inside non-hierarchical subcircuits are not saved.

Don't save any data except signals defined in `.KEEP` or `.GRAPH` statements:

```
.OPTIONS KeepNone
```

Save all data except device internals and semiconductor currents in AC analyses. Includes data inside subcircuits and hierarchies:

```
.OPTIONS KeepAll
```

Save everything including device internals and semiconductor currents in AC analyses:

```
.OPTIONS KeepAll KeepAllAci KeepInternal
```

Don't save currents:

```
.OPTIONS KeepNoi
```

Save signals in the top level and the first level in the hierarchy:

```
.OPTIONS KeepSubCktDepth=1
```

Save about 20% of all data:

```
.OPTIONS KeepQuotaFactor=0.2
```

Store only voltages and currents in sub-circuit X1 excluding descendants.

```
.OPTIONS KeepNone
.KEEP X1.*v X1.*i
```

Store only voltages and currents in sub-circuit X1 including descendants.

```
.OPTIONS KeepNone
.KEEP X1.**v X1.**i
```

Store voltages within U3.U12 along with VOUT and VIN

```
.OPTIONS KeepNone
.KEEP U3.U12.*v VOUT VIN
```

Store all top level voltages and currents in U7

```
.OPTIONS KeepNone
.KEEP U7.*i
```

**Notes**

`.KEEP` may be used inside a sub-circuit definition in which case `.KEEP` operates at a local level. For example `.KEEP *v` inside a sub-circuit definition specifies that all voltages within that subcircuit (for all instances) will be saved. `.KEEP **v` does the same but also includes any descendant sub-circuit instances.

SIMetrix uses subcircuits to implement hierarchical schematics. Subcircuits are also used in other ways, for example to implement device macro models. SIMetrix is able to distinguish between subcircuits used for hierarchies and other subcircuits. It does this by placing a comment line below the `.SUBCKT` line as shown below:

```
.subckt fastamp VOUTP VN VINP VP VINN VOUTN
*#hierarchy
...
.ends
```

The comment line `*#hierarchy` marks the subcircuit as part of the schematic hierarchy. The schematic editor's netlist generator automatically adds `*#hierarchy` lines as appropriate.

## 6.14 *.LOAD*

```
.LOAD file [instparams=parameter_list] [nicenames=0|1] [goiters=goiters]
      [ctparams=ctparams] [suffix=suffix] [warn=warnlevel]
```

Loads a device file. This may be a Verilog-A file or a compiled binary (*.sxdev* file).

<i>file</i>	Specifies either a Verilog-A file or a <i>.SXDEV</i> file. If the extension is <i>.SXDEV</i> , no compilation will be performed and the specified file will be loaded directly. The remaining options will not be recognised in this case. Otherwise the file will be assumed to be a Verilog-A file and will be passed to the Verilog-A compiler. This will compile the file to a <i>.sxdev</i> binary and then load it
<i>parameter_list</i>	A list of parameter name separated by commas. There should be no spaces in this list. Each parameter in this list will be defined as an instance parameter. Refer to the Verilog-A User Manual for further details
<i>goiters</i>	Specifies the number of global optimiser iterations. The default is 3. A higher number may improve the execution speed of the code at the expense of a longer compilation time. In practice this will only have a noticeable effect on very large Verilog-A files. Setting the value to zero will disable the global optimiser. This is likely to slow execution speed a little. The global optimiser is an algorithm that cleans up redundant statements in the 'C' file.
<i>ctparams</i>	defines 'Compile-time parameters' and is a list of comma-separated parameter name/value pairs in the form name=value. Any parameters listed will be substituted with the constant value defined during compilation as if it were entered as a literal constant in the Verilog-A code. This feature is especially useful for items such as array sizes and vectored port sizes. A considerably more efficient result will be produced if the values of such items are known at compile time.
<i>warnlevel</i>	sets a filter for warning messages. If set to zero, no warnings will be displayed. If set to 2, all warnings will be displayed. The default is 1 which will cause most warnings to be displayed but will omit those that are less serious.

## 6.15 *.LIB*

There are two forms of *.LIB* and the behaviour of each is completely different from each other. The SIMetrix Native Form specifies a file or group of files to be searched for any model or subcircuit that has not yet been found. The HSPICE® version is a selective version of *.INC* but unlike *.INC* it doesn't include the whole file, just a specified portion of it.

### 6.15.1 SIMetrix Native Form

`.LIB pathname`

*pathname* File system path name specifying a single file or, by using a wildcard (\* or ?), a group of files. If the path name contains spaces, it must be enclosed in quotation marks (").

The SIMetrix form of this statement specifies a pathname to be searched for model and subcircuit libraries. Any number of .LIB statements may be specified and wildcards (i.e. \* and ? ) may be used.

If a model or subcircuit is called up by a device line but that definition was not present in the netlist, SIMetrix will search for it in files specified using the .LIB statement.

SIMetrix will also search for definitions for unresolved parameters specified in expressions. These are defined using [“PARAM” on page 232](#).

#### Example

The following statement instructs the simulator to search all files with the .mod extension in c:\Spice Model Library\ for any required subcircuits or device models.

```
.lib "c:\Spice Model Library\*.mod"
```

### 6.15.2 HSPICE Form

`.LIB `filename' entryname`

*filename* File system path name specifying a single file.

*entryname* Name used to identify sections within filename

When HSPICE® the form of .LIB is encountered, SIMetrix will search the file specified by *filename* for a section enclosed by:

```
.LIB entryname
```

and

```
.ENDL
```

.LIB calls may be nested as long as they are not recurrent. That is a .LIB call within a .LIB .ENDL block may not call itself but it may call another block within the same file. (HSPICE® itself does not permit this).

This form of .LIB is commonly used in model files issued by semiconductor fabrication plants which tend to be designed for use with HSPICE®. The entry name parameter is used for process corner and skew selection. Typically the model file would have entries for - say - slow, nominal and fast models. These would reside under entry names of, perhaps, SS, NOM, and FF respectively. You can very rapidly switch between these model sets simply by changing the entry name on the .LIB line e.g.

would select the nominal models. Changing to:

```
.LIB `c:\models\fab1\process_a\top.mod' NOM
```

would switch to the slow models.

## 6.16 .MODEL

```
.MODEL modelname modeltype ( param1=val1 [ param2=val2 ]... )
```

This statement specifies a set of model parameters that are used by one or more devices. .model statements often reside in model libraries.

<i>modelname</i>		Model name. Any text string to uniquely identify model. Must begin with a letter but may contain any legal ASCII character other than a space and period ‘.’.
<i>modeltype</i>		Model type. See tables below for possible values
param1, etc.	param2	Parameter name. Valid values depend on the model type. (See “ <a href="#">Simulator Devices</a> ” on page 15)
<i>val1, val2</i> etc.		Parameter value.

### 6.16.1 XSPICE Model Types

Model name	Description
ad_converter	analog-to-digital converter
adc_bridge	analog-to-digital interface bridge
adc_schmitt	analog-to-digital schmitt trigger
cm_cap	Capacitor with voltage initial condition
cm_ind	Inductor with current initial condition
d_and	digital n-input and gate
d_buffer	digital one-bit-wide buffer
d_cap	Digital capacitor
d_dff	digital d-type flip flop
d_dlatch	digital d-type latch
d_fdiv	digital frequency divider
d_init	Digital initial condition
d_inverter	digital one-bit-wide inverter
d_jkff	digital jk-type flip flop
d_logic_block	arbitrary logic block
d_nand	digital n-input nand gate
d_nor	digital n-input nor gate
d_open_c	digital one-bit-wide open-collector buffer
d_open_e	digital one-bit-wide open-emitter buffer
d_or	digital n-input or gate
d_osc	controlled digital oscillator
d_pulldown	digital pulldown resistor
d_pullup	digital pullup resistor
d_pulse	digital pulse
d_ram	digital random-access memory

Model name	Description
d_res	Digital resistor
d_source	digital signal source
d_srff	digital set-reset flip flop
d_srlatch	digital sr-type latch
d_state	digital state machine
d_tff	digital toggle flip flop
d_tristate	digital one-bit-wide tristate buffer
d_xnor	digital n-input xnor gate
d_xor	digital n-input xor gate
da_converter	digital-to-analog converter
dac_bridge	digital-to-analog interface bridge
s_xfer	s-domain transfer function block

### 6.16.2 SPICE Model Types

Model name	Description
ACTABLE	“AC Table Lookup (including S-Parameters)” on page 41
C, CAP	“Capacitor” on page 58
CORE	“Inductor (Saturable)” on page 70
CORENH	“Inductor (Saturable)” on page 70
D	“Diode - Level 1 and Level 3” on page 63
HICUM_211	“Bipolar Junction Transistor (HICUM)” on page 57
LPNP	Lateral PNP “Bipolar Junction Transistor (SPICE Gummel Poon)” on page 46
LTRA	“Lossy Transmission Line” on page 78
NIGBT	“Insulated Gate Bipolar Transistor” on page 74
NJF	N-channel “Junction FET” on page 75
NMF	N-channel “GaAsFET” on page 68
NMOS	N-channel “MOSFET” on page 79
	Also many other types. See table of contents
NPN	NPN “Bipolar Junction Transistor (SPICE Gummel Poon)” on page 46
	Also VBIC, Mextram and Hicm devices
PJF	P-channel “Junction FET” on page 75
PMF	P-channel “GaAsFET” on page 68
PMOS	P-channel “MOSFET” on page 79
	Also many other types. See table of contents

Model name	Description
PNP	PNP “Bipolar Junction Transistor (SPICE Gummel Poon)” on page 46
PSP102	“PSP MOSFET” on page 89
R, RES	“Resistor” on page 92
R3_CMC	“CMC Resistor” on page 98
SRDIO	“Diode - Soft Recovery” on page 67
SW, VSWITCH	“Voltage Controlled Switch” on page 107
VSXA	“Verilog-HDL Interface (VSXA)” on page 118

### 6.16.3 Safe Operating Area (SOA) Limits

It is possible to define SOA limits within the .MODEL statement. To do this, add one or more parameters in the following format:

```
LIMIT(name)=(min, max, xwindow)
```

<i>name</i>	Name of quantity to test. See format for access variables useable when MODEL is specified for a .SETSOA statement. This is described in “ <a href="#">.SETSOA</a> ” on page 236. E.g. use ‘LIMIT(vcb)’ to specify the limits for the collector-base voltage of a BJT.
<i>min, max</i>	As described in “ <a href="#">.SETSOA</a> ” on page 236.
<i>xwindow</i>	As described in “ <a href="#">.SETSOA</a> ” on page 236.

### 6.16.4 Example

The following is a model for a 1N5404 diode.

```
.MODEL D1n5404 D(Is=15.48f Rs=7.932m Ikf=0 N=1 Xti=3
+ Eg=1.11 Cjo=150p M=.3 Vj=.75 Fc=.5
+ Isr=120n Nr=2 Bv=525 Ibv=100u)
```

## 6.17 .NOCONV

```
.NOCONV V(node1)=val1 [ V(node2)=val2 ]...
```

Disables convergence testing for the specified nodes.

## 6.18 .NODESET

```
.NODESET V(node1)=val1 [ V(node2)=val2 ]...
```

OR



```
.NODESET node1 val1 [ node2 val2 ]
```

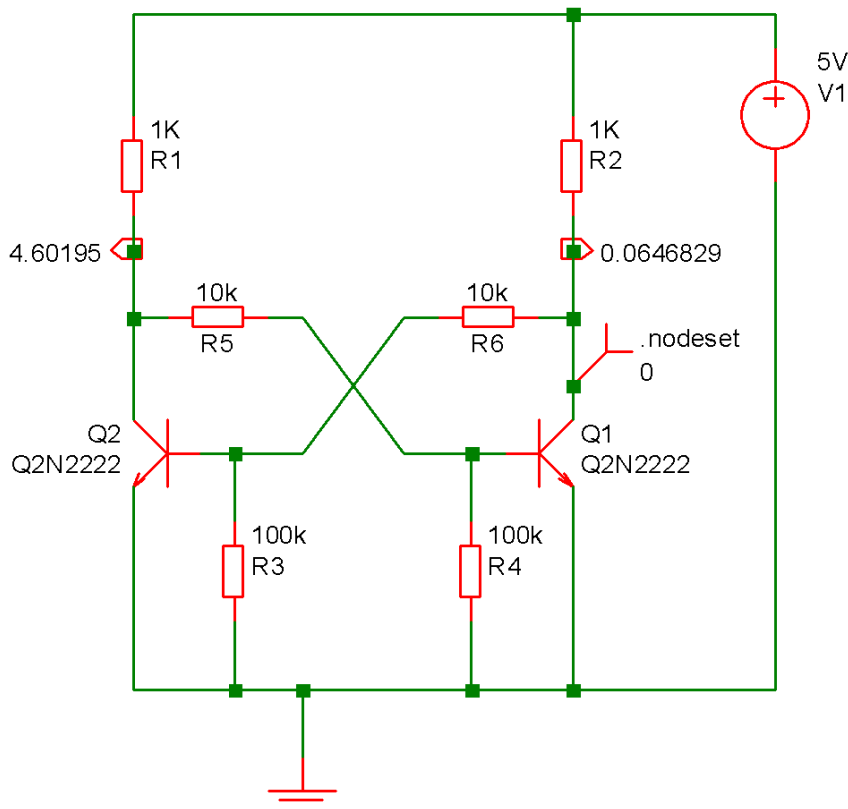
This statement sets an initial guess voltage at the specified node for the dc operating point solution.

*node1, node2* etc.            Name of circuit node (or net) to which nodeset is to be applied. See notes below.

*val1, val2* etc.            Nodeset voltage to be applied. May be an expression containing parameters defined using `.PARAM`

Initially nodesets work exactly the same way as initial conditions. The nodeset voltage is applied via a 1 Ohm (by default but can be changed using `NODESETRES` option - see [“OPTIONS” on page 216](#)) resistor and the solution is completed to convergence (by any of the methods). The nodeset is then released and the solution repeated. If the nodeset voltage is close to the actual solution the convergence of the second solution should be rapid.

Nodesets can be used to force a particular solution for circuits that have more than one stable state. Consider the following circuit:



A nodeset has been applied to the collector of Q1. This has forced Q1 to be on and Q2 to be off. If the nodeset were absent the solution would actually leave both Q1 and Q2 partially on. In real life this would not be stable but it is numerically accurate.

The other application of nodesets is to help convergence for the DC bias point. With SIMetrix, it is rarely necessary to use nodeset's to find the DC solution of a circuit. They can, however, be useful

for speeding up the operating point analysis for circuits that have already been solved. You may wish to do this for a Monte-Carlo analysis, for example. SIMetrix features a method of creating nodesets for this purpose using the SaveRhs command. See “Using Nodesets” on page 266.

Nodeset’s should not be confused with initial conditions. (see “IC” on page 201). Initial conditions tie a node to a particular voltage and keep it there throughout the DC operating point analysis. Nodesets merely suggest a possible solution but do not force it.

## 6.19 .NOISE

```
.NOISE inner_sweep_spec [ V ] pos_node [ VN ] neg_node
+ [[ INSRC ] in_source ]
+ [ F frequency ] [RUNNAME=runname] [SWEEP outer_sweep_spec]
```

Spice Compatible:

```
.NOISE V(pos_node [, neg_out_node ]) in_source
+ DEC|LIN|OCT num_points start stop interval
```

This statement instructs the simulator to perform a small signal noise analysis.

<i>pos_node</i>	Node on circuit at which noise is measured.
<i>neg_node</i>	Node to which <i>outputnode</i> is referenced. Defaults to ground if omitted.
<i>in_source</i>	Input source (i.e. voltage or current) to which the input noise measurement is referred.
<i>inner_sweep_spec</i>	See “General Sweep Specification” on page 188 for syntax. Defines sweep mode. FREQ keyword is optional.
<i>outer_sweep_spec</i>	If specified, analysis will be repeated according to this specification. See “General Sweep Specification” on page 188 for syntax.
LIN	Analysis points are linearly spaced.
DEC	Analysis points are logarithmically spaced in decades
OCT	Analysis points are logarithmically spaced in octaves
<i>num_points</i>	LIN: Total number of points DEC: Number of points per decade OCT: Number of points per octave
<i>start</i>	Start frequency
<i>stop</i>	Stop frequency
<i>interval</i>	Currently does nothing. Provided for backward compatibility.
<i>runname</i>	If specified, the value for <i>runname</i> will be passed to the simulation data group as a string variable with name <i>UserRunName</i> . This may be used to identify which analysis generated the data which is useful when running netlists with multiple analyses defined

### 6.19.1 Notes

During noise analysis the simulator calculates the total noise measured between *pos\_node* and *neg\_node* at each frequency point. It also calculates and outputs this noise referred back to an

input specified by *in\_source*. As for all other analysis modes a DC operating point analysis is carried out first but, unlike AC analysis, the results of this analysis are not made available. The simulator outputs vectors covering the contribution from each noise generating device to the total output noise. The names of these vectors begin with the component reference of the device followed by a suffix to indicate the source of the noise within the device. A listing of the suffixes is given below. It is important to note that it is not the noise being generated by each device that is output but the proportion of that noise that is propagated to the output.

It is not necessary to specify a separate AC analysis alongside the noise analysis as it is with SPICE2 and commercial derivatives of SPICE2.

The magnitude of any AC independent voltage or current source on the circuit has no effect on the results of a noise analysis. Unlike SPICE and earlier versions of SIMetrix, it is not necessary to specify an AC parameter for the source used for the noise input source. For the first form shown above, the input source is in fact optional. If it is omitted the input referred noise will not be calculated.

All noise results are in  $V/\sqrt{\text{Hz}}$  except input noise referred back to a current source which is in  $A/\sqrt{\text{Hz}}$ . In standard SPICE3 the noise values produced for MOS2 and BSIM3 devices are in  $V^2/\sqrt{\text{Hz}}$ . For consistency, these have now been changed to  $V/\sqrt{\text{Hz}}$ . The original SPICE3 behaviour can be restored by setting the simulator option OldMosNoise (see “[OPTIONS](#)” on page 216).

### 6.19.2 Device vector name suffixes

Device Type	Suffix and Description
BJT	#rc Noise due to collector resistance
	#rb Noise due to base resistance
	#re Noise due to emitter resistance
	#ic Shot noise in collector
	#ib Shot noise in base
	#1overf Flicker (1/f) noise
	no suffix Total transistor noise
Diode	#rs Noise due to series resistance
	#id Shot noise
	#1overf Flicker (1/f) noise
	no suffix Total diode noise
JFET and MOSFETs level 1-3 and BSIM3	#rd Noise due to drain resistance
	#rs Noise due to source resistance
	#id Shot noise in drain
	#1overf Flicker (1/f) noise
	no suffix Total FET noise

Device Type	Suffix and Description
NXP MOS9 (all types see “NXP Compact Models” on page 123)	#Sfl Flicker (1/f) noise
	#Sth Drain thermal noise
	#Sig Gate thermal noise
	#Sigth Gate-drain correlated thermal noise
	no suffix Total FET noise
Resistor	#therm Resistor thermal noise
	#1overf Flicker (1/f) noise
	#noise Total resistor noise
Voltage controlled switch	no suffix Total switch noise

### 6.19.3 Creating Noise Info File

Noise analysis generates vectors in the same way as all other swept analyses. Individual vectors may also be tabulated in the list file using the .PRINT statement.

A noise output file may also be created from the front end. Select the command shell menu **Graphs and Data | Create Noise Output File** to create a text file with a summary of noise results. Included is a list of the integrated noise output for every device listed in order of magnitude. Select **Graphs and Data | View Noise Output File** to view the file. Note that this is a front end feature and is not implemented by the simulator.

### 6.19.4 Examples

Run noise analysis from 100Hz to 1MHz with 25 points per decade. Calculate noise at node named vout and noise referred back to voltage source vin:

```
.NOISE V( vout ) vin dec 25 100 1meg
```

Decade sweep resistor RSource from 100 to 10K with 25 points per decade. Frequency = 1kHz

```
.NOISE DEVICE RSource DEC 25 100 10k F=1K
```

## 6.20 .OP

```
.OP
```

This statement instructs the simulator to perform a DC operating point analysis. Note that a DC operating point analysis is carried out automatically for transient (unless the UIC parameter is specified), AC, DC, transfer function and noise analyses.

DC operating point analysis attempts to find a stable bias point for the circuit. It does this by first applying an initial guess and then uses an iterative algorithm to converge on a solution. If it fails to find a solution by this method the simulator then attempts three further strategies.

For the first, a method known as ‘source stepping’ is employed. For this all voltage and current sources in the circuit are initially set to near zero and the solution found. The sources are then gradually increased until they reach their final value.

If this approach fails a second strategy ‘GMIN stepping’ is invoked. This conditions the solution matrix by increasing the diagonal term such that it is dominant. If large enough, convergence is virtually guaranteed. If successful then the diagonal term is reduced and a further solution sought using the previous solution as a starting point. This procedure is repeated until the diagonal term is returned to its correct value. Increasing the diagonal term is in a way similar, but by no means identical, to placing a small resistance at each node of the circuit.

If source stepping fails a final strategy, ‘pseudo transient analysis’ is invoked. This is the most powerful technique employed and nearly always succeeds. However, it is also the slowest which is why it is left until last. For more information on DC convergence see [“Convergence, Accuracy and Performance” on page 262](#).

If the final approach fails then the analysis will abort.

**IMPORTANT:** *It is not necessary to include .OP if other analyses are specified.* All other analysis modes will perform an operating point anyway so including .OP will simply cause it to be done twice. However, with .NOISE, .TF, .SENS and .PZ the results of the operating point analysis are not output. If the bias point of the circuit is required when running one of these analysis modes, a .OP will be needed.

### 6.20.1 ‘OFF’ Parameters

Some semiconductor devices feature the device parameter OFF. If there are devices in the circuit which specify this parameter, the bias point solution is found in two stages. In stage 1 the devices with OFF specified are treated as if their output terminals are open circuit and the operating point algorithm completes to convergence. In stage 2, The OFF state is then released and the solution restarted but initialised with the results of stage 1.

The result of this procedure is that OFF devices that are part of latching circuits are induced to be in the OFF state. Note that the OFF parameter only affects circuits that have more than one possible DC solution such as bistables. If the OFF parameter is specified in - say - an amplifier circuit - with a unique solution, the final result will be the same. It will just take a little longer to arrive at it.

### 6.20.2 Nodesets

Nodesets work in a similar way to the OFF parameter in that the solution is found in two stages. In the first the nodeset is applied and the solution found. It is then released and convergence continues. Nodeset are an aid to convergence and, like the OFF parameter, can coerce a particular solution if there is more than 1 stable state. See [“.NODESET” on page 210](#) for details.

### 6.20.3 Initial Conditions

Initial conditions force a particular voltage at a circuit node during bias point solution. The force is released for any subsequent analysis. See [“.IC” on page 201](#) for more details.

### 6.20.4 Operating Point Output Info

During the operating point analysis, operating point values of every device in the circuit are output to the list file (see [“The List File” on page 11](#)). This information is not usually output for other analysis modes unless explicitly requested. The output of operating point information is controlled by three simulator options:

NOOPINFO	If set, the operating point info file is not created for .OP analysis
----------	---

OPINFO	If set, the operating point info file is created for other analyses as well as .OP. (Does not apply to .SENS - operating point information is not available for this mode at all)
OPINFOFILE	Sets name of file to receive operating point info. Outputs to list file if this option is not specified.

## 6.21 .OPTIONS

```
.OPTIONS [ opt1 [=val1]] ...
```

This statement allows the setting of various options specific to the simulator.

<i>opt1</i>	Option name. Must be one specified in list below.
<i>val1</i>	Option value. Note, boolean options do not have a value. They are assigned “true” if the name is present and “false” if not.

### 6.21.1 List of simulator options

Option name	Default value	Description
ABSTOL	1p	Units = A The absolute current error tolerance. It is sometimes desirable to increase this for circuits that carry large currents (>1A) to speed the solution and aid convergence.
ACCT	false	Full simulation timing statistics are generated if this is enabled.
ALLACI	false	Instructs simulator to save all device currents in an AC analysis. Usually, only currents for simple devices are evaluated and stored. Equivalent to “.KEEP /allaci”, but unlike .KEEP, .OPTION values can be defined on the Run command line.
ANYVERSION	false	If true, BSIM3 and BSIM4 models will be unconditionally accepted even if an invalid version parameter is supplied.
BINDIAG	false	If enabled, a report about selection of binned models will be output to the list file. See <a href="#">“Model Binning” on page 33</a> .

Option name	Default value	Description
BINONTOTALWIDTH	false	For backward compatibility affecting BSIM4 models. Multi-fingered BSIM4 devices are binned according to width per finger. SIMetrix versions 5.3 and earlier binned according to total width. Set this option for version 5.3 behaviour.
CHGTOL	1e-14	Units = Coulombs The absolute charge tolerance.
CONV	0	Set to 2 to enable advanced iteration algorithm. The advanced iteration algorithm uses a modified iteration equation that reduces the error inherent in the iteration sequence. This improves convergence for some types of circuit, but sometimes incurs a small performance penalty
CSHUNT	0	Units = Farads. Capacitance placed at all top level nodes to ground. If CSHUNTSUB specified, capacitance is placed at all nodes in the circuit. No capacitance is placed to nodes that already have a capacitor connected to ground. By placing a small capacitance at every node, some transient analysis convergence problems can be solved. A very small value such as 100fF can often be effective
CSHUNTSUB	false	Boolean. If specified CSHUNT places capacitance to all nodes, not just those at the top level. This should be used with care if used in circuits with subcircuit models obtained from third-party vendors. Some have very high impedance internal nodes and their behaviour can be adversely affected by even very small additional capacitance.
DCOPSEQUENCE	gmin  source  pta	Operating point strategy sequence order. See <a href="#">“Controlling DC Method Sequence” on page 270</a> for details

Option name	Default value	Description
DEFAD	0	Unit = m <sup>2</sup> Default value for MOSFET AD device parameter. Applies to levels 1-3 and level 49/53. Does <i>not</i> apply to level 8 or NXP MOS9 devices
DEFAS	0	Unit = m <sup>2</sup> As DEFAD but for AS parameter
DEFL	100μ	Unit = metres As DEFAD but for L parameter
DEFNRD	0	As DEFAD but for NRD parameter
DEFNRS	0	As DEFAD but for NRS parameter
DEFPD	0	Unit = metres As DEFAD but for PD parameter
DEFPS	0	Unit = metres As DEFAD but for PS parameter
DEFW	100μ	Unit = metres As DEFAD but for W parameter
DEVACCT	false	If true, the simulator will measure load times for each device type during a simulator run. This information can be obtained using the GetDeviceStats() script function.
DIGMINTIME	1pS	Unit = Seconds Minimum digital resolution. Not yet fully supported
DISABLESUBCKTMULTIPLIER	false	If true, the subcircuit multiplier parameter, M, will be disabled. See <a href="#">“Subcircuit Instance” on page 105</a> .
DISCONTINUOUSIFSLEWRATE		Default=0. Sets slew rate of discontinuous conditional expressions. See <a href="#">“IF() Function” on page 24</a> for more information.
EXPAND	false	The netlist with subcircuits expanded is output to the list file if this is specified.
EXPANDFILE		Only applies if EXPAND also specified. Specifies a file instead of the list file to receive the expanded netlist.



Option name	Default value	Description
FASTPOINTTOL	1.0	Value for POINTTOL used during ‘Fast transient start’. See POINTTOL below.
FASTRELTOL	0.001	Value for RELTOL used during ‘Fast transient start’.
FLUXTOL	1e-11	Unit = V.secs The absolute flux tolerance for inductors.
FORCETRANOPGROUP	false	Forces a separate data group to be created for transient analysis operating point data. This happens anyway if tstart>0. Use this option when simulating a large circuit and you wish to make extensive use of schematic bias annotation. See <i>User’s Manual/Graphs, Probes and Data Analysis/Viewing DC Operating Point Results</i> for more details.
FULLEVENTREPORT	false	If true, the simulator will save all event information. When false, only major events are recorded. Events can be obtained from the GetSimulatorEvents() script function and can be useful for diagnosing failed runs.
GMIN	1e-12	Unit = Siemens (mhos) The minimum conductance allowed by the program. This has the effect of placing a resistor = 1/GMIN in parallel with every branch of the circuit.
GMINMAXITERS	1000	Maximum total number of iterations allowed for GMIN stepping operating point algorithm. See “ <a href="#">Source and GMIN Stepping</a> ” on <a href="#">page 263</a> for details.
GMINMULT	10	During GMIN stepping the value of GMIN is multiplied by a variable factor at each step. This option is the starting and maximum value of that factor.
GMINSTEPITERLIMIT	20	Iteration limit for each step in GMIN stepping. Increase to 100 for compatibility with SIMetrix 2.0x and earlier.
ICRES	1	Unit = ICRES. Initial condition resistive force. See “ <a href="#">IC</a> ” on <a href="#">page 201</a> for details

Option name	Default value	Description
INITCONDMODE	0	<p>Sets behaviour of capacitors and inductors when given an initial condition parameter (IC).</p> <p>May have these values:</p> <ul style="list-style-type: none"> <li>0 Berkeley SPICE compatible mode (default). IC parameter is ignored unless UIC is specified for transient analysis</li> <li>1 SIMPLIS compatible mode. Forces hard initial condition</li> <li>2 PSpice compatible mode. Forces soft initial condition</li> </ul> <p>For more information see <a href="#">“Initial Conditions” on page 38</a></p>
ITL1	100	DC iteration limit used for initial DC operating point.
ITL2	50	DC iteration limit used for swept and multi-step analyses.
ITL4	10	Normal transient timepoint iteration limit. The behaviour of this parameter is slightly different in SIMetrix than other SPICE based simulators. See <a href="#">“Convergence, Accuracy and Performance” on page 262</a> .
ITL7	40	Upper transient timepoint iteration limit. This is specific to SIMetrix.
KEEPNOV	false	Disables saving voltage data
KEEPNOI	false	Disables saving current data
KEEPNOD	false	Disables saving digital data
KEPPALLACI	false	Enables saving current data for semiconductor devices in AC analysis
KEEPINTERNAL	false	Enables saving device internal data. (Signals internal to primitive devices, not subcircuits)

Option name	Default value	Description
KEEPTOP	false	Save only the data at the top level. This is default behaviour but this option overrides KEEPALL if this is also specified
KEEPNONE	false	Disables saving all data except items explicitly requested using .GRAPH or .KEEP
KEEPALL	false	Keep data inside all subcircuits
KEEPSUBCKTDEPTH	-1	Keep data in subcircuits to defined depth
KEEPQUOTAFACOR	1.0	Reduces data saved to a proportion of the total specified by eliminating on a priority basis
LOGICHIGH	2.2	Unit = Volts Upper threshold for logic inputs. Other comments as for LogicThreshHigh
LOGICLOW	2.1	Unit = Volts Lower threshold for logic inputs. Other comments as for LogicThreshHigh
LOGICTHRESHHIGH	5	Unit = Volts Output voltage for logic high level. Used for &   and operators for arbitrary source. See <a href="#">“Arbitrary Source” on page 42</a> for more details.
LOGICTHRESHLOW	0	Unit = Volts Output voltage for logic low level. Other comments as for LogicThreshHigh
LOGPARAMEXPRESSIONS	false	If true, a log of parameter expressions in use will be output to the list file
MATCHEDSUBCIRCUITS	false	If set, components within subcircuits are treated as matched for Monte Carlo analysis. See <a href="#">“Monte Carlo Analysis” on page 250</a> .
MAXEVTITER	0 (sets internal default)	Maximum number of event driven passes allowed at each step. It is not usually necessary to change this value.
MAXOPALTER	0 (sets internal default)	Maximum number of alternations between analog and event-driven iterations. It is not usually necessary to change this value

Option name	Default value	Description
MAXORD	2	Maximum integration order. For METHOD=TRAP maximum value is 2. For METHOD=GEAR maximum value is 6. There is rarely any reason to change this value.
MAXVDELTAABS	0.5	with MAXVDELTAREL, sets a limit on the amount of change per timestep for each node. Inactive if MAXVDELTAREL less than or equal to zero. See <a href="#">“Voltage Delta Limit” on page 273</a> for further details.
MAXVDELTAREL	0.0	See <a href="#">MAXVDELTAABS</a> above.
MC_ABSOLUTE_RECT	false	If set Monte Carlo distribution will be rectangular for absolute tolerances. Otherwise the distribution will be Gaussian.
MC_MATCH_RECT	false	If set Monte Carlo distribution will be rectangular for matched tolerances. Otherwise the distribution will be Gaussian.
MCHSPICE	false	Boolean. Enables Hspice mode for Monte Carlo distribution functions. See <a href="#">“Enabling Hspice Distribution Functions” on page 260</a> for further information
MCLOGFILE	mclog.txt	File name to receive Monte Carlo log. See <a href="#">“Log File” on page 252</a> .
MCUSELINEARDISTRIBUTION	false	Use a linear distribution for default tolerances with Monte Carlo analysis. If using TOL or MATCH parameters the distribution used follows a logarithmic characteristic. Set this option to use a conventional linear distribution.
METHOD	trap	Numerical integration method. Either TRAP (default) or GEAR". More info: See <a href="#">“Integration Methods - METHOD option” on page 275</a> .

Option name	Default value	Description
MINBREAK	See notes	Unit = Seconds Minimum time between transient analysis breakpoints. A breakpoint is a point in time when an analysis is forced regardless of whether it is required by the timestep selection algorithm. Typically they are set at known turning points such as the start and end of a rising pulse. If two breakpoints are closer than MINBREAK they are merged into one. (there are exceptions to this e.g if the two breakpoints were generated by a single rising edge). Increasing MINBREAK can sometimes help convergence and simulation speed. The default value is MINTIMESTEP*100. (See below for MINTIMESTEP)
MINGMINMULTIPLIER	1.000001	In GMIN stepping, the step size is multiplied by variable factor at each step. This step is reduced if convergence fails. If it is reduced below this value, the GMIN algorithm will abort and the next DC operating point strategy will be invoked.
MINTIMESTEP	1e-9 * Max time step	Unit = Seconds Minimum transient time step. Simulation will abort if it reaches this value. See <a href="#">“.TRAN” on page 245</a> for value of Max time step.
MOSGMIN	GMIN	Value of GMIN used between drain and source of MOSFETs. See <a href="#">“MOSFET GMIN Implementation” on page 89</a> .
MPNUMTHREADS	0	Sets number of threads (i.e. cores) to be used for simulation. The simulator will choose if set to zero (default value). See <a href="#">“Using Multiple Cores for Single Step Runs” on page 277</a> .

Option name	Default value	Description
NEWGMIN	false	Changes the implementation of GMIN for ‘old’ MOS devices i.e. LEVELs 1-3. When this option is set, GMIN is implemented as a conductance between source and drain. Otherwise two conductances are added between drain and bulk and source and bulk. See <a href="#">“MOSFET GMIN Implementation”</a> on page 89.
NOCUR	false	Equivalent to “.KEEP /noi”. Inhibits the saving of current data.
NODELIMIT	1e50	Unit = Volts Maximum value allowed for circuit node during iteration. If exceeded, iteration will abort. (This does not usually mean the analysis will abort). Reducing this value can sometime solve floating point exceptions or unexplained singular matrices.
NODESETRES	1.0	Unit = Ohms Driving resistance of nodeset force. See <a href="#">“.NODESET”</a> on page 210 for details.
NOECHO	false	Inhibits display of netlist in list file.
NOMCLOG	false	If specified, no Monte Carlo log file will be created. See <a href="#">“Log File”</a> on page 252 for details.
NOMOD	false	If specified, no model parameter report will be output to the list file.
NOMOS9GATENOISE	false	If specified, the drain induced gate noise model for MOS9 devices will be disabled. See <a href="#">“NXP Compact Models”</a> on page 123.
NOOPALTER	false	If specified, only a single pass will be made to resolve the operating point for event driven devices.
NOOPINFO	false	Switches off creation of operating point info file for .OP analyses. See <a href="#">“.OP”</a> on page 214 for more details.
NOOPITER	false	Use GMIN stepping for DC operating point analysis first. (i.e skip normal iteration method)

Option name	Default value	Description
NORAW	false	Output transient analysis values at intervals of tstep only. See <a href="#">“.TRAN” on page 245</a> .
NOSENSFILE	false	Switches off creation of sensitivity analysis data file.
NoStopOnUnknownParam	See description	<p>Specifies action to be taken in the event of an unknown parameter being encountered in a .MODEL statement. Choices are:</p> <p>TRUE: No action taken, simulation continues normally.</p> <p>FALSE: An error will be raised and the simulation will abort.</p> <p>WARN: A warning will be displayed but the simulation will continue.</p> <p>The default value is set by a front end “Set” variable of the same name. This can be set using the menu <b>File   Options   General...</b> under Model Library tab. The “Set” variable default is WARN.</p> <p>If running in non-GUI mode the default will be controlled by the entry in the config file. See <a href="#">“Global Settings” on page 7</a>.</p>
NOWARNINGS	false	Inhibits simulation warnings.
NOVOLT	false	Equivalent to “.KEEP /nov”. Inhibits the saving of voltage data.
NUMDGT	10	Column width used for display of all values in list file and Monte Carlo log file. Minimum value is 8, maximum is 30. Note this value is column width not the number of significant digits.
OLDLIMIT	false	If set SPICE 2 MOS limiting algorithm is used. Affects MOS Level 1,2 and 3

Option name	Default value	Description
OLDMOSGMIN	0	Value of conductance placed between drain-bulk and source-bulk for BSIM3 and BSIM4 devices. Also applies to LEVEL 1-3 and LEVEL 17 MOSFETs if NEWGMIN parameter is set. See “ <a href="#">MOSFET GMIN Implementation</a> ” on page 89.
OLDMOSNOISE	false	MOS2 and BSIM3 devices return device noise in $V^2/Hz$ for SPICE3 and earlier versions of SIMetrix whereas other device’s noise is returned in $V/\sqrt{Hz}$ . From release 3 onwards all devices return noise in $V/\sqrt{Hz}$ . Setting this option restores to behaviour of earlier versions.
OPINFO	false	If set DC operating point info file <i>is</i> created for all analyses (except .SENS). Normally it is created only for .OP analyses.
OPINFOFILE	false	Specify name of operating point info file. This is OP.TXT by default.
OPTIMISE	2	Controls expression optimiser. 0=off, 1=on for .FUNC defined expressions, 2=on always. See “ <a href="#">Optimisation</a> ” on page 29.
PARAMLOG	Given	Control amount of detail for parameter log in list file. Choices: None: no parameters listed Brief: only parameters specified using an expression are listed Given: parameters explicitly specified in the netlist are listed Full: all parameters are listed



Option name	Default value	Description
PIVREL	1e-3	Tolerance for matrix pivot selection. This rarely needs to be altered. Reducing to 1e-4 can sometimes improve simulation speed a little but at higher risk of convergence failure. Setting this parameter to a high value e.g, 0.99 can sometimes fix convergence problems but may slow down the simulation. Valid values lie between 0 and 1.
PIVTOL	1e-13	Only effective when SP-SOLVER=KSPARSE  This affects the matrix solution and rarely needs to be altered. It is the absolute minimum value for a matrix entry to be accepted as a pivot. Unexplained <i>singular matrix</i> errors can sometimes be overcome by lowering this value. (But note that <i>singular matrix</i> errors are usually caused by errors in the circuit such as floating nodes or shorted voltage sources).
POINTTOL	0.001	A factor used to control the extent to which the maximum value attained by a signal is used to control its tolerance. This is new from release 4; set it to zero for pre release 4 behaviour. Increasing this value will speed up the simulation at the expense of precision. See <a href="#">“Accuracy and Integration Methods” on page 271</a> .
PTAACCEPTAT	0	If > 0, specifies a time when pseudo transient analysis results will be accepted unconditionally. This is useful when a circuit comes close to convergence during pseudo transient, but doesn't quite make it due to an oscillation. See <a href="#">“Pseudo Transient Analysis” on page 264</a> .
PSPICECOMPAT	false	Sets some option settings to values compatible with PSpice. Currently this sets ICRES=1m and INITCONDMODE=2

Option name	Default value	Description
PTACONFIG	0	Integer from 0 to 15 sets internal parameters for pseudo transient algorithm used to find DC operating point. See <a href="#">“Pseudo Transient Analysis”</a> on page 264.
PTAMAXITERS	20000	Maximum total number of iterations allowed for pseudo transient algorithm used to find DC operating point. See <a href="#">“Pseudo Transient Analysis”</a> on page 264.
PTAOUTPUTVECS	false	If specified, signal vectors will be output during pseudo transient analysis. This may be used to diagnose a failure. See <a href="#">“Pseudo Transient Analysis”</a> on page 264.
RELTOL	0.001	This is the relative tolerance that must be met for each analysis point. Reducing this number will improve accuracy at the expense of simulation time or/and convergence reliability. Simulation results can not be relied upon if its value is increased beyond 0.01. A more detailed discussion is given in <a href="#">“Accuracy and Integration Methods”</a> on page 271.
RESTHRESH	1e-6	Resistance threshold. If a resistor is specified that is below this value, SIMetrix will use a voltage based implementation ( $V=IR$ ) instead of the conventional current based implementation ( $V=I/R$ ). Voltage based resistors are slightly less efficient but allow $R=0$ without numerical overflow
RSHUNT	Infinite	If specified a resistor of the specified value is placed from every node to ground. This can resolve problems with floating nodes.
RTNSEED	0	Seed used for real time noise
SEED	0	Integer value. If non-zero will be used to initialise random number generator used for Monte Carlo analysis distribution functions. See <a href="#">“Seeding the Random Number Generator”</a> on page 252.

Option name	Default value	Description
SENSFILE	SENS.TXT	Specify name of sensitivity data file.
SNAPSHOTFILE		Specifies file name used to save snapshot data. Defaults to netlist name with .xsnp extension
SOADERATING	1.0	Scales min and max values used in <a href="#">.SETSOA</a> specification. This allows a de-rating policy to be globally applied to SOA limits.
SOAEND	-1	Specifies end time point for SOA. Use with SOASTART. -1 means end of simulation
SOAMODE	false	Controls the Safe Operating Area (SOA) test mode. See <a href="#">“.SETSOA” on page 236</a> for details on how to define a SOA test.  Can set to: <ul style="list-style-type: none"> <li>Off      SOA testing is not enabled. In this mode <a href="#">.SETSOA</a> statements will be read in and any errors reported, but no SOA testing will be performed during the run.</li> <li>Summary SOA testing enabled and results given in summary form with only the first violation for each expression given being output.</li> <li>Full      SOA testing enabled with full results given. Every violation will be reported in this mode.</li> </ul>

Option name	Default value	Description
SOAOUTPUT	list	<p>Can be:</p> <ul style="list-style-type: none"> <li>msg Results displayed in command shell message window, or console if run in “non-GUI” mode.</li> <li>list Results output to list file.</li> <li>msg list Results output to both list file and command shell message window.</li> <li>none Results not output to either list file or message window.</li> </ul> <p>Note that all results are always stored for retrieval using the script function GetSOAResults. So even if “none” is specified the SOA data is always available.</p>
SOASTART	0.0	Specifies start time for SOA. Use with SOAEND
SOAWRITEDEFS	false	If specified, SOA definitions are written to the list file
SOURCEMAXITERS	1000	Maximum total number of iterations permitted for source stepping algorithm. Set to zero to disable limit
SPSOLVER	KLU	Can be KLU or KSPARSE. Sets choice of matrix solver. See <a href="#">“Matrix Solver” on page 277</a> .
TEMP	27	Unit = °C Operating temperature of circuit. Note this value can be overridden locally for some devices. You can also use .TEMP for this.
TIMESTATS	false	Equivalent to ACCT
TLMINBREAK	See note	Minimum break point for transmission lines. Works in the same way as MINBREAK but only for break points generated by lossless transmission lines. Default = MINTIMESTEP * 5e-5
TNOM	27	Unit = °C Temperature at which model parameters are defined. This can be overridden in the model statement.

Option name	Default value	Description
TRTOL	7	This only affects transient analysis. It is a relative value that is used to determine an acceptable value for the ‘local truncation error’ before an analysis point is accepted. Reducing this value cause the simulator to model the effects of energy storage elements more accurately at the expense of simulation time. See <a href="#">“Accuracy and Integration Methods”</a> on page 271.
TRYTOCOMPACT	false	Forces compaction of data for lossy transmission lines. This speeds up simulation at the expense of accuracy.
VERILOGSIMULATOR		Verilog simulator used for mixed-signal Verilog-HDL simulation. Name specified references a section in the VerilogHDL.ini file. With the default configuration, this may be:  CVER - GPL Cver simulator  Icarus - Icarus Verilog simulator
VERILOGROOTFILE	vsx_root.v	SIMetrix creates the Verilog top-level module for each run and stores it in a file with this name
VERILOGROOTMODULE	vsx_root	Name given to Verilog top-level module created by SIMetrix
VERILOGPORTPREFIX	VSX\$_	Connection names within the SIMetrix-created top-level module have this prefix.
VERILOGRESOLUTION	1e-15	Timing resolution for Verilog simulations. This is the smallest time that can be resolved. The largest time is this value multiplied by $2^{64}$ .
VERILOGDISABLEMODULECACHE	false	Disable cache of module information. See <a href="#">“Module Cache”</a> on page 122 for further details

Option name	Default value	Description
VERILOGUSECONSOLE	false	If set, a console window will be created for the Verilog simulator. Any output messages emitted by the Verilog simulator will be output to this console.
VERILOGDISABLEINTERNALVECTORS	false	If set, no data for Verilog internal connections will be generated. See <a href="#">“Data Vector Output” on page 122.</a>
VNTOL	1 $\mu$	Unit = V The absolute voltage error tolerance. Circuits with large voltages present (>100) may benefit from an increase in this value. See <a href="#">“Accuracy and Integration Methods” on page 271.</a>
WIDTH	80	Number of columns used for list file output. This may be set to any reasonable value and not limited to the choice of 80 or 132 as with SPICE2
WIRETABLE	none	Define file containing wire table used for the digital simulator’s wire delay. See <a href="#">“Wire Delay” on page 286.</a>

## 6.22 .PARAM

```
.PARAM parameter_name [=] parameter_value [parameter_name [=] parameter_value]...
```

```
.PARAM parameter_name [=] AGAUSS(nominal, abs_variation, sigma, [multiplier]) ...
```

```
.PARAM parameter_name [=] AUNIF(nominal, abs_variation, [multiplier]) ...
```

```
.PARAM parameter_name [=] GAUSS(nominal, rel_variation, sigma, [multiplier]) ...
```

```
.PARAM parameter_name [=] UNIF(nominal, rel_variation, [multiplier]) ...
```

Defines a simulation variable for use in an expression. Expressions may be used to define device parameters, to define model parameters, for arbitrary sources and to define variables themselves. See [“Using Expressions” on page 17](#) for details.

The syntax for the first form is described below. For details of the remaining forms (using AGAUSS, AUNIF, GAUSS and UNIF) see [“Hspice Distribution Functions” on page 259.](#)

*parameter\_name* Sequence of alpha-numeric characters. Must begin with a letter or underscore. May not contain spaces.

*parameter\_value*            Either:  
                                  A constant  
                                  OR  
                                  An expression enclosed by '{' and '}'. See [“Using Expressions” on page 17.](#)

### 6.22.1 Examples

```
.PARAM Vthresh = 2.4
.PARAM Vthresh = {(Vhigh+Vlow)/2}
.PARAM F0 1k Alpha 1 C1 {2*c2}
.PARAM R1 {2/(2*pi*freq*C1*alpha)}
```

### 6.22.2 Netlist Order

.PARAM statements that resolve to a constant are order independent; they can be placed anywhere in a netlist. They can even be placed after another .PARAM expression that depends on its value (but note this does *not* apply in subcircuits). .PARAM statements that are defined as an expression that depends on other .PARAMs also defined as an expression must be placed in sequential order. For example, the following is OK:

```
.PARAM C2 {C1*alpha*alpha/4}
.PARAM C1 1n
.PARAM alpha 1
.PARAM R1 {2/(2*PI*F0*C2*alpha)}
```

The first .PARAM depends on `alpha` and `C1` which are defined later in netlist. This is OK (as long as it is *not* in a subcircuit) because `icodealpha` and `C1` are constants. The fourth .PARAM depends on `C2`, which is defined as an expression. The definition for `must` - and does in the above example - come before the definition of `R1`. The following would yield an error as the definition for `C2` comes after the definition of `R1`:

```
.PARAM R1 {2/(2*PI*F0*C2*alpha)}
.PARAM C1 1n
.PARAM alpha 1
.PARAM C2 {C1*alpha*alpha/4}
```

Note that .PARAMs inside subcircuits are local to the subcircuit. This is explained in next section.

### 6.22.3 Subcircuit Parameters

Parameters may be declared within sub circuits. E.g

```
.subckt ADevice n1 n2 n3 n4
.PARAM Vthresh 3.5
...
...
ends
```

In the above example, in reference to `Vthresh` within the subcircuit would use the value declared by the .PARAM declared inside the subcircuit. That value would not be available outside the subcircuit definition. Parameters may also be passed to subcircuits. E.g.

```
X1 1 2 3 4 ADevice : threshold=2.4
```

or

```
X1 1 2 3 4 ADevice params: threshold=2.4
```

Any reference to `threshold` within the subcircuit definition would use that value.

Default values for parameters may also be specified in subcircuit definition:

```
.subckt ADevice n1 n2 n3 n4 params: threshold=2.4
...
.ends
```

If that subcircuit is called without specifying `threshold` the default value of 2.4 will be used. Note that it is not compulsory to declare default values.

#### 6.22.4 Using .PARAM in Schematics

.PARAM statements may be appended to the netlist created by the schematic editor. For information on how to do this, refer to [“Adding Extra Netlist Lines” on page 2](#).

#### 6.22.5 .PARAM in Libraries

.PARAM statements may be included in libraries specified using .LIB or by global definitions. SIMetrix will search such libraries for any parameters used in expressions that are not found in the netlist.

### 6.23 .POST\_PROCESS

```
.POST_PROCESS scriptname [arguments]
```

Invokes the SIMetrix script *scriptname* at the end of a successful simulation. If present arguments will be passed to the script as a single string.

*scriptname* may be the name of an embedded file defined using .FILE and .ENDF. For example, the following will cause the text “Simulation Complete” to be displayed in the command shell when the run is complete:

```
.FILE on_complete
Echo "Simulation Complete"
.ENDF
.POST_PROCESS on_complete
```

.POST\_PROCESS may be used to perform measurements on simulation results for display in the command shell or written to a file.

.POST\_PROCESS scripts will function even if the simulator is operating in a standalone mode in which case any displayed messages created from, for example, Echo or Show, will be directed to the simulator’s output device. In console mode, this would be the console or terminal and in standalone GUI mode, this would be the message window in the simulator status box. As there is no environment available in the standalone mode, not all script commands and functions will be available.

For information about the SIMetrix script language, please refer to the SIMetrix script reference manual.

### 6.24 .PRINT



```
.PRINT TRAN|AC|DC|NOISE|TF vector|{expression} ...
```

Instructs the simulator to output selected simulation data to the list file in tabulated form.

Where:

*vector* Name of vector to print. May be in SIMetrix native format or traditional SPICE format (see notes below).

*expression* Arithmetic expression of vectors

### 6.24.1 Notes

A traditional SPICE2 command, this was not supported by SIMetrix until release 4.0. It is SPICE2 compatible but also supports some additional features:

- NOISE and TF results may be output as well as TRAN, AC and DC
- You can put expressions as well as single values enclosed in '{' and '}'. E.g.

```
.PRINT TRAN {vout-q5_c}
```

You can use the SPICE2 style method of accessing single voltages, differential voltages and device currents. These are of the form:

Single ended voltage

```
funcname(nodename)
```

Differential voltage

```
funcname(nodename, nodename)
```

Device current

```
funcname(device_name)
```

Where:

*funcname* Function to be applied. For available list, see below.

*nodename* Node name as specified in the netlist.

*device\_name* Name of device for current.

Available functions:

Function name	Argument	Analysis mode	Meaning
V	node name	Transient	Voltage at node
V	node name	AC	Voltage magnitude at node
VM	node name	AC	Voltage magnitude at node
VP	node name	AC	Voltage phase at node
VR	node name	AC	Real voltage at node
VDB	node name	AC	dbV at node
VG	node name	AC	group delay at node
I	two term. device name	TRAN	Current in device

Function name	Argument	Analysis mode	Meaning
IB	BJT name	TRAN	Base current
IB	MOSFET name	TRAN	Bulk current
IC	BJT name	TRAN	Collector current
ID	MOSFET/JFET name	TRAN	Drain current
IE	BJT name	TRAN	Emitter current
IG	MOSFET/JFET name	TRAN	Gate current
IS	MOSFET/JFET name	TRAN	Source current
IS	BJT name	TRAN	Substrate current
IM	Two term device	AC	Device current
IP	Two term device	AC	Current phase
IR	Two term device	AC	Current real part
II	Two term device	AC	Current imaginary part
IDB	Two term device	AC	Current dB
IG	Two term device	AC	Current group delay

`.PRINT` statements may be placed inside a subcircuit definition in which case the device and node names refer to local devices and nodes. Output will be listed *for every instance of the subcircuit*.

For transient analysis the results are displayed at the interval specified by the time step parameter on the `.TRAN` statement. If this is zero or omitted, it defaults to  $(t_{stop}-t_{start})/50$ . The data is created by interpolation unless the `NORAW` option (see [“`OPTIONS`”](#) on page 216) is specified in which case a time step is forced at the time step interval.

## 6.24.2 Examples

```
.PRINT TRAN V(VOUT)
.PRINT TRAN VOUT
.PRINT TRAN V(VPos, VNeg)
.PRINT TRAN {Vpos-VNeg}
.PRINT AC VDB(VOUT)
```

## 6.25 *.SENS*

```
.SENS V(nodename [,refnodename])| I(sourcename)
```

This statement instructs the simulator to perform a DC sensitivity analysis. In this analysis mode, a DC operating point is first calculated then the linearised sensitivity of the specified circuit voltage or current to every model and device parameter is evaluated. The results are output to a file (`SENS.TXT` by default but can be changed with `SENSFILE` option) and they are also placed in a new data group. The latter allows the data to be viewed in the message window (type `Display`) at the command line and can also be accessed from scripts for further analysis.

## 6.26 *.SETSOA*

```
.SETSOA [ LABEL=label ] [ MODEL=modelname | INST=instname ] [ DEVICE=device ]
[ DERATING=derating ] [ MEAN ] [ ALLOWUNUSED ] [ ALLOWWILD ]
expr1=( min1, max1[, xwindow1] ) [ expr2=( min2, max2[, xwindow2] ) ... ]
```

Defines a Safe Operating Area (SOA) specification. If SOA testing is enabled the simulator will check simulated results against this specification and record any violations. See [.OPTIONS](#) setting SOAMODE for details on how to enable SOA tests.

The results of SOA testing are output to the list file by default and can optionally also be displayed in the command shell message window, or console window if run in non-GUI mode. They are also always available via a script function GetSOAResults(). See [.OPTIONS](#) setting SOAOUTPUT for more details.

<i>label</i>	<p>Optional label that will be included in every violation report. You can use the following symbolic values in this label:</p> <p><code>%INST%</code> - substituted with the instance name that violated the specification. This is only meaningful if MODEL or INST are specified. (See below)</p> <p><code>%MODEL%</code> - substituted with the model name that violated the specification. Only meaningful if MODEL is specified. (See below)</p> <p><code>%EXPR%</code> - substituted with the expression that violated the specification.</p> <p><code>%SUBCKT%</code> - applicable if the .SETSOA command is located within a .SUBCKT definition. Value is substituted with the subcircuit instance reference.</p>
<i>modelname</i>	<p>If specified the expression or expressions supplied in <i>expr1</i> etc. are applied to every instance belonging to <i>modelname</i>. In this case the expression may refer to node voltages and pin currents for each instance processed. See details under <i>expr1, expr2...</i></p>
<i>instname</i>	<p>If specified the expression or expressions supplied in <i>expr1</i> etc. are applied to the specified instance (e.g. Q23, M10, R56). In this case the expression may refer to node voltages and pin currents of the specified instance. See details under <i>expr1, expr2...</i></p>
<i>device</i>	<p>If INST or MODEL is specified using a wildcard specification, only instances of the specified device type will be processed. For example: <code>.SETSOA INST=* DEVICE=resistor...</code></p> <p>will be applied to all resistors in the circuit. See <a href="#">“Creating a Device Configuration File” on page 36</a> for a list of device names.</p>
<i>derating</i>	<p>Derates limit specification by specified factor. Default is 1.0 which means no derating. Value must be greater than 0. An expression containing values defined using .PARAM may be used.</p>

*expr1, expr2...*

Expression to be evaluated and compared against minimum and maximum specs. This expression can access simulation results using access variables. The format and scope of these variables depends on whether MODEL, INST or neither is specified.

If neither is specified, the expression can use the global access variables defined below:

Syntax	Function	Example
<i>nodename</i>	Voltage on node	on VOUT - voltage on node VOUT
n( <i>nodename</i> )	Voltage on node	on n(VOUT) - voltage on node VOUT
<i>instname#param</i>	Instance parameter	M2#vdsat - vdsat value for M2 Q23#c - current in collector of Q23
<i>paramname</i>	Parameter defined using .PARAM	

If there is a clash between a *paramname* and *nodename*, that is if the same name could refer to either a node or a parameter, then the parameter name takes precedence. To access the node in this case, use the n(*nodename*) syntax.

Use the following values if MODEL or INST is specified. In each case (excepting the global access variable) the variable accesses a quantity for the instance being processed. With INST this will be the single instance specified by *instname*. With MODEL all instance belonging to the model specified by *modelname* will be processed.

Syntax	Function	Example
<i>pinname</i>	Current in pin	<i>c</i> - current in collector of transistor
<i>Ipinname</i>	Current in pin	<i>Ic</i> - current in collector of transistor
<i>Ipinname_m</i>	Current in pin scaled according to multiplier (e.g. M parameter). Equivalent to <i>Ipinname</i> /M	<i>Ic_m</i> - current in collector of transistor scaled by multiplier.
<i>Vpinname</i>	Voltage on pin	<i>Vc</i> - voltage on collector of transistor
<i>n(pinname)</i>	Voltage on pin	<i>n(c)</i> - voltage on collector of transistor
<i>Vxy</i> Where x = pin name 1, y= pin name 2. Both x and y must be single letters	Voltage between x and y.	<i>Vbc</i> - voltage from base to collector
<i>pow</i>	Power in device	
<i>pow_m</i>	Power in device scaled according to multiplier. Equivalent to <i>pow</i> /M	
<i>param</i>	Readback parameter	<i>vdsat</i> - 'vdsat' for MOSFET
<i>#global_name</i>	Global node voltage or pin current	<i>#VOUT</i> - voltage on net called VOUT  <i>#q23#c</i> - current in collector of q23
<i>paramname</i>	Parameter defined using .PARAM	

Note that currently the use of V() and I() is not accepted and will result in an error message being displayed.

<i>min, max</i>	Minimum and maximum values respectively. A violation message will be produced if the value of the associated expression is less than <i>min</i> or greater than <i>max</i> . Use '*' if the limit is to be ignored. E.g. (*, 15) will test a maximum value of 15 but the minimum value will not be tested. <i>min</i> and <i>max</i> values may be scaled using the <a href="#">.OPTIONS SOADERATING</a> .
	These values may be entered as expressions containing variables defined using .PARAM.
<i>xwindow</i>	Optional value specifies a minimum window that must be surpassed before limit violations are registered. For example if 10u is specified for <i>xwindow</i> for a transient analysis, then the limit must be exceeded continuously for at least 10uS before the violation is recorded.
	This value may be entered as an expression containing variables defined using .PARAM.
ALLOWUNUSED	If INST or MODEL are specified, an error will result if no instances to be processed are found. If INST is specified the error will occur if <i>instname</i> doesn't exist. If MODEL is specified, the error will occur if there are no instances using <i>modelname</i> even if <i>modelname</i> itself is valid.
	This error will be inhibited if ALLOWUNUSED is specified
ALLOWWILD	If specified, wildcards can be used for <i>modelname</i> and <i>instname</i> . In this case SIMetrix will search for all devices that match the wildcard specification. Use '*' to match any sequence of characters and '?' to match a single character.
MEAN	If specified all tests will be on the mean of the test expression over the whole simulation run.

### 6.26.1 Examples

Test the voltage on the 'p' pin of R1. Will fail if it exceeds 0.5V

```
.setsoa INST=R1 vp=(*,0.5)
```

Test the power dissipation of R2. Fails if it exceeds 0.5mW

```
.setsoa INST=R2 pow=(*,0.5m)
```

Test the current into pin 'p' of R3. Fails if it exceeds 0.5mA

```
.setsoa INST=R3 ip=(*,0.5m)
```

Test the voltage across R4. Fails if it exceeds 0.85V for at least 100uS. Will be reported using label "%INST%, high", which resolves to "R4, high"

```
.setsoa LABEL="%INST%, high" INST=R4 vd=(*,0.85,100u)
```

Test the voltage across R4. Fails if it exceeds 0.7V for at least 500uS

```
.setsoa LABEL="%INST%, low" INST=R4 vd=(*,0.7,500u)
```

Tests voltage between 'c' and 'e' pins for all instances of model N1. Fails if voltage drops below -0.5V or exceeds 25V

```
.setsoa MODEL=N1 vce=(-0.5,25)
```

Tests power all devices of type resistor. Fails if this exceeds 0.25W.

```
.setsoa INST=* ALLOWWILD DEVICE=resistor pow=(*,0.25)
```

Tests the mean power in instance Q1. Fails if it exceeds “2\*bjtderating”. “bjtderating” must be defined using a .PARAM statement.

```
.setsoa LABEL="%INST%", pow(q1)" INST=Q1 MEAN pow=(*,2)
derating=bjtderating
```

Calculates the expression “ $n(c)*(q1\#c-d1\#p)+n(b)*q1\#b+n(e)*(q1\#e+d1\#p)$ ” and fails if its mean exceeds 1.0. Violations will be reported using label “%SUBCKT%, power”. Statement is intended to be placed in a subcircuit definition block and “%SUBCKT%” will resolve to the reference of the subcircuit call.

```
.setsoa LABEL="%SUBCKT%, power" MEAN "n(c)*(q1#cd1#
p)+n(b)*q1#b+n(e)*(q1#e+d1#p)"=(*,1)
```

## 6.27 *.SUBCKT and .ENDS*

```
.SUBCKT subcktname n1 [ n2 ]...
+ [ [params:] param_name1 [=] param_value1
+ [param_name2 [=] param_value2]...]
```

This statement begins a subcircuit definition.

*subcktname*

Subcircuit name. This must begin with a letter but may contain any legal ASCII character except any whitespace (space, tab) or ‘.’. The name must be unique i.e. no other subcircuits may have the same name.

*n1, n2 etc.*

Node names available externally. Must not be zero.

*param\_name, param\_value*

Parameter name and value. This sets default values for parameters used within the subcircuit. These values can be overridden for each subcircuit instance. See [“Using Expressions” on page 17](#) for more info. Note that it is not compulsory to declare default values for subcircuit parameters.

**IMPORTANT:** Either the *params:* specifier or the first ‘=’ may be omitted *but not both*. If both are omitted it becomes impossible for the netlist scanner to tell the difference between parameter names and node names.

```
.ENDS [ subcktname ]
```

Terminates a subcircuit definition. *subcktname* may be added for clarity but will be ignored by SIMetrix.

A subcircuit consists of a .subckt statement followed by a series of device or model descriptions and terminating in a .ends statement. A subcircuit is a circuit that can be called into the main circuit (or indeed another subcircuit) by reference to its name. The .subckt statement is used to

define the subcircuit while a subcircuit call - an 'X' device - is used to create an instance of that subcircuit. Subcircuits have a number of uses:

- To repeat a commonly used section of circuit.
- To hide detail from the main circuit to aid circuit readability.
- To distribute models of integrated devices such as op-amps.

For a detailed discussion see [“Subcircuits” on page 30](#).

Subcircuit definitions usually reside in a text file and are read in as libraries. See *User’s Manual* for further details.

## 6.28 .TEMP

```
.TEMP temperature
```

This statement sets the default simulation temperature. Some devices can override this on a per instance basis. Units are degrees centigrade.

## 6.29 .TF

```
.TF inner_sweep_spec [ V ] pos_out_node [ VN ] neg_out_node
+ [[ INSRC ] in_source ] [ F frequency ] [RUNNAME=runname]
  [SWEEP outer_sweep_spec ]
```

```
.TF inner_sweep_spec I source [ INSRC in_source ]
+ [ F frequency ] [RUNNAME=runname] [SWEEP outer_sweep_spec ]
```

Spice Compatible:

```
.TF V( pos_out_node [, neg_out_node ]) in_source
```

```
.TF I (source) [ INSRC ] in_source
```

This statement instructs the simulator to perform a small signal transfer function analysis.

<i>pos_out_node</i>	Output node.
<i>neg_out_node</i>	Output reference node. Defaults to ground if omitted for standard SPICE syntax.
<i>in_source</i>	Name of input source to which input noise will be referred.
<i>inner_sweep_spec</i>	See <a href="#">“General Sweep Specification” on page 188</a> for syntax. Defines sweep mode.
<i>outer_sweep_spec</i>	If specified, analysis will be repeated according to this specification. See <a href="#">“General Sweep Specification” on page 188</a> for syntax.
<i>frequency</i>	Frequency at which analysis will be performed for non-frequency sweeps. Default 0.
<i>source</i>	Voltage source to specify output current.
<i>runname</i>	If specified, the value for <i>runname</i> will be passed to the simulation data group as a string variable with name <i>UserRunName</i> . This may be used to identify which analysis generated the data which is useful when running netlists with multiple analyses defined



### 6.29.1 Notes

The SIMetrix transfer function analysis remains syntax compatible with the SPICE version but is substantially enhanced. The SPICE version performs the analysis at a single point with frequency = 0. The SIMetrix implementation performs a swept analysis using the same sweep algorithm used for AC, DC and NOISE.

Transfer function analysis is similar to AC analysis in that it performs a swept small signal analysis. However, whereas AC analysis calculates the response at any circuit node from a (usually) single input source, transfer function analysis calculates the individual responses from each source in the circuit to a single specified output node. This allows, for example, the series mode gain, common mode gain and power supply rejection of an amplifier to be measured in one analysis. The same measurements could be performed using AC analysis but several of them would need to be run. Transfer function mode also calculates output impedance or admittance and, if an input source is specified, input impedance.

The names of the output vectors will be of the form

```
Input voltage, output voltage
source_name#Vgain
```

```
Input voltage, output current
source_name#Transconductance
```

```
Input current, output voltage
source_name#Transresistance
```

```
Input current, output current
source_name#Igain
```

Output impedance for voltage out will be called Zout. For a current output, the output admittance will be calculated and will be named Yout.

If an input source is specified the input impedance will be calculated and called Zin.

Note that although the syntax for .TF retains compatibility with SPICE and earlier versions of SIMetrix, the output provided is slightly different. Firstly, the data is complex even if F=0 and secondly the names of the output vectors are different as detailed above.

### 6.29.2 Examples

SPICE compatible. Outputs results at DC.

```
.TF V(Vout) Vin
```

As above but decade sweep from 1k to 100k

```
.TF FREQ DEC 25 1K 100K V(Vout, 0) Vin
```

Note that in the above example the '0' in V(Vout, 0) is compulsory. If is omitted, Vin will be assumed as the reference node.

## 6.30 .TRACE

```
.TRACE vector_name [vector_name ...] graph_id
```

Set up a *trace*. This is graph plot that is updated as the simulation runs.

Where

<i>vector_name</i>	is the name of a net or pin
<i>graph_id</i>	is an integer between 1 and 999 to specify which graphs traces should use - see explanation below

*graph\_id* is an arbitrary number that makes it possible to direct traces to different graphs. Two traces with the same id will be always be put in the same graph. Traces from subsequent simulations with that id will also go to that graph if it still exists otherwise a new one will be created. To force two traces to go to separate graphs, use different id's. Note that it doesn't matter what the id's value actually is - it could be 1 or 100 - as long as traces that must go to the same graph use the same value.

Note that the *AutoAxis* feature available for normal plotting also works for Traces. So if a current and voltage trace are both directed to the same graph, separate axes will be created for them.

### 6.30.1 Examples

```
.trace v1_p 1 q1#c 1
```

In the above example a voltage - v1\_p - and a current - q1#c - will both be traced on the same graph. As they have different units, the AutoAxis feature will force the curves to two different y axes.

```
.trace v1_p 1 q1#c 2
```

In this example the voltage and current traces will be directed to different graph sheets.

### 6.30.2 Notes

The .TRACE statement has now been largely superseded by the .GRAPH statement (see [“.GRAPH” on page 196](#)), which is much more flexible. However, the .TRACE statement is still useful for specifying multiple traces on a single line. .GRAPH can only specify one signal at a time.

## 6.31 .TRAN

```
.TRAN tstop
```

OR

```
.TRAN tstep tstop [ tstart [ tmaxstep ] ] [ UIC ]
+ [SNAPSTEP sstart sstop sstep]
+ [SNAPSHOT slist]
+ [SNAPMODE=DCOP|SAVESTATE|ALL]
+ [FAST=fast_start] [RTNSTEP=rtnstep [RTNSTOP=rtnstop]
+ [RTNSTART=rtnstart] ] [RUNNAME=runname]
+ [SWEEP sweep_spec ]
```

This statement instructs the simulator to perform a transient analysis. In this mode the simulator computes the behaviour of the circuit over the specified time interval. The circuit's currents and voltages are calculated at discrete time points separated by a variable time step. This time step is adjusted automatically by the simulator according to circuit activity. The circuit may contain any number of time varying voltage and current sources (stimuli) to simulate external signals, test generators etc.

<i>tstep</i>	<p>This defines the interval for tabulated results specified by the .PRINT statement. It also defines the output interval for all data if the NORAW option is specified. If there are no .PRINT statements in the netlist and NORAW is not being used, this can be set to zero or omitted altogether as in form 1 above. If set to zero it defaults to <math>(tstop-tstart)/50</math>.</p> <p><i>tstep</i> is also used to define default values for pulse and exponential stimuli.</p> <p>Note that if <i>tstep</i> and NORAW are specified a time point is forced at <i>tstep</i> intervals to calculate the output. This differs from other SPICE programs which generate output at <i>tstep</i> by interpolation.</p> <p><i>tstep</i> does not control the time step used by the simulator. This is controlled automatically according to circuit activity.</p>
<i>tstop</i>	<p>Stop time. Note that if running in GUI mode, a transient analysis can be restarted from the front end. See <i>User's Manual/Analysis Modes/Transient Analysis/restarting a Transient Run</i> for details.</p>
<i>tstart</i>	<p>Start time. This is the time at which the storage of transient analysis outputs commences. It is not the time at which the analysis begins; this is always zero. <i>tstart</i> is zero if it is omitted.</p>
<i>tmaxstep</i>	<p>Maximum time step. The simulator uses the largest time step possible to achieve the required accuracy but will not increase it beyond this value. If not specified it is set to <math>(tstop-tstart)/50</math>.</p>
UIC	<p>If specified a DC operating point is not calculated and initial condition specifications are used instead</p>
<i>fast_start</i>	<p>If specified, the simulation will run at reduced accuracy but higher speed for the time specified by this parameter. The reduced accuracy is implemented by altering a number of tolerances and internal parameters. See notes below for more details.</p>
<i>rtnstep</i>	<p>If this parameter is specified, Real Time Noise analysis will be enabled. Note that this feature is not available with all versions of the program. <i>rtnstep</i> specifies the step size of the noise generators. See <a href="#">“Real Time Noise Analysis” on page 247</a>.</p>
<i>rtnstart</i>	<p>Specifies time at which real time noise generators are switched on.</p>
<i>rtnstop</i>	<p>Specifies time at which real time noise generators are switched off.</p>
<i>sstart</i>	<p>Time at which snapshot saving begins. See below for information on snapshots.</p>
<i>sstop</i>	<p>Time at which snapshot saving stops. See below for information on snapshots</p>
<i>sstep</i>	<p>Interval between snapshot points. See below for information on snapshots</p>
<i>slist</i>	<p>One or more values defining absolute times at which snapshots are saved. See below for information on snapshots</p>
<i>runname</i>	<p>If specified, the value for <i>runname</i> will be passed to the simulation data group as a string variable with name <i>UserRunName</i>. This may be used to identify which analysis generated the data which is useful when running netlists with multiple analyses defined</p>

DCOP, SAVESTATE, Snapshot mode.  
ALL

DCOP: Saves bias point information only.

SAVESTATE: Saves state of circuit for subsequent reload for small signal analysis

ALL: Both of the above

The default is DCOP.

### 6.31.1 Fast Start

If the FAST parameter is specified, the simulation will begin with a number of tolerances and internal parameters altered to speed up the simulation at the expense of accuracy. Just before the end of the fast start period, these tolerances and parameters will be gradually restored to their normal values. Fast start is an aid for simulating circuits such as switching power supplies and oscillators for which the initial start up period is not of interest but takes a long simulation time. Note that although the fast start interval can run sometimes as much as twice as quickly as normal, the fact that accuracy is impaired can mean that the final steady state reached may not be very accurate. This means that after the fast start period, an additional settling time may be required for full accuracy to be reached.

Fast start sets the values of POINTTOL and RELTOL according to the value specified by FAST-POINTTOL and FASTRELTOL respectively.

### 6.31.2 Snapshots

This feature allows the state of a simulation to be saved at user specified times during a transient analysis. The states saved can subsequently be reloaded to perform small signal AC analyses.

This allows the small signal response of a circuit to be examined at any point during a transient analysis. This is especially useful in situations where a circuit is found to be unstable in a transient run but this instability cannot be reproduced at the operating point usually derived for an AC analysis.

The bias point information at the snapshot time may also optionally be saved. This information is output to the list file.

To specify snapshot output, specify either the SNAPSHOT or SNAPSTEP keywords with their associated parameters.

To initialise a small signal analysis with snapshot data, you must specify the SNAPSHOT step mode of a multi-step analysis. See [“Multi Step Analyses” on page 190](#) for details.

## 6.32 Real Time Noise Analysis

This is an extension of transient analysis rather than a separate analysis mode. When activated, real time noise sources are added to all noisy devices with a magnitude and frequency distribution calculated using the same equations used for small signal analysis. This allows noise analysis to be performed on sampled data systems and oscillators.

To use real time noise analysis, the following parameters may be added to the .TRAN analysis line.

RTNstep	Source step size in seconds. This will need to be small enough to cover the frequency range of interest. The noise magnitude starts rolling off at about $1/3 \times \text{stepsize}$ . Default=0 i.e. real time noise analysis disabled.
RTNstart	Optional. Time after analysis start at which the noise sources will be enabled. Default = zero
RTNstop	Optional. Time after analysis start at which the noise sources will be disabled. Default = stop time.

The parameters added to the .TRAN line *must* be named in the same way as .MODEL parameters are named.

### 6.32.1 Example

```
.TRAN 0 1m RTNstep=1u RTNstart=500u
```

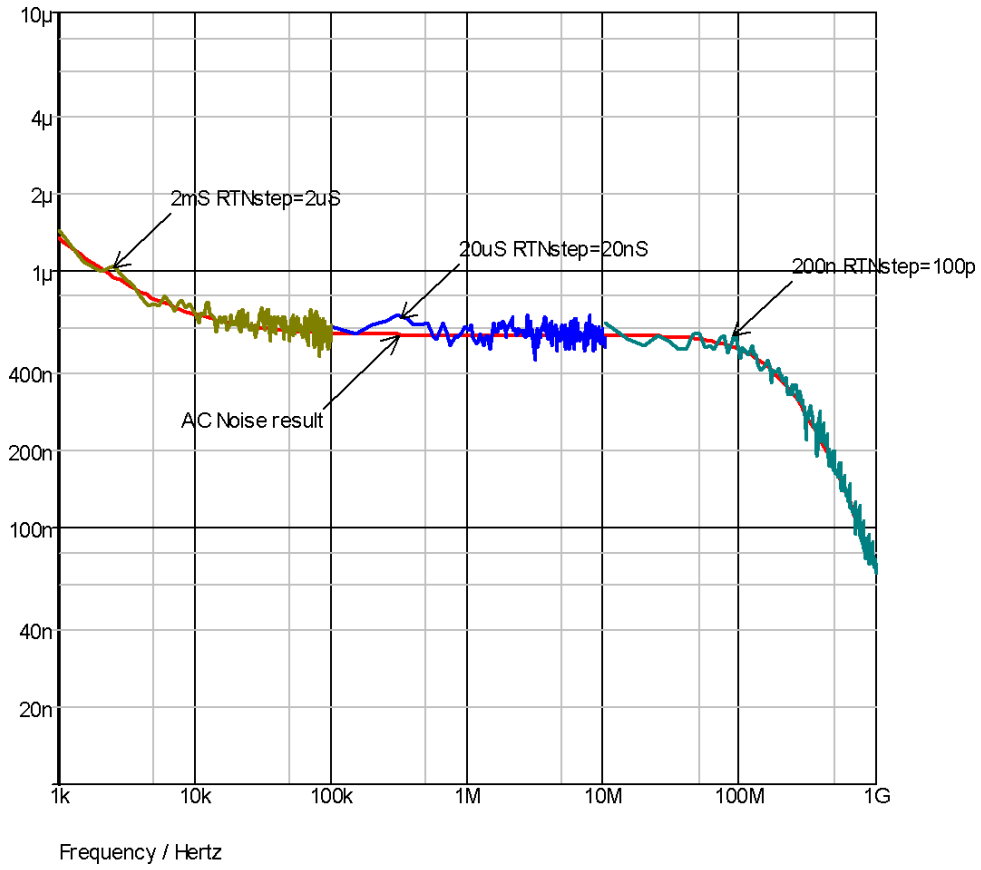
Analysis time 1m, RTN step size 1u, real time sources start at 500u. The step size parameter - i.e. the first parameter on the .TRAN line - *must* be supplied if real time noise parameters are to be included. This is only to comply with the syntax rules not because the step size is needed for any other purpose. In most cases, just set it to zero as in the above example.

### 6.32.2 Test Results

To test real time noise and verify it's accuracy we ran a test on a number of circuits which compare AC noise with real time noise. The procedure was to run real time noise analysis 50 times then plot the averaged Fourier spectrum. This test was repeated for different transient run times and step sizes to build a noise spectrum over several decades. The graph below is the result of one such test. This was carried out on the BSIM3 buffer circuit provided in one of the examples except that a value for AF - the flicker noise parameter - was added to the models. As can be seen in the graph below the real time noise results strongly follow the AC noise results.

Similar tests were performed on circuits containing each of the major noise generating devices including diodes, BJTs, JFETs, resistors (including its flicker noise parameter) and also the NXP MOS9 and MEXTRAM devices. All showed results similar to below with a close similarity between AC noise and real time noise.

These tests were performed using a simple script. This script is called `rtntest.sxscr` and can be found on the installation CDROM at `SCRIPTS/EXAMPLES`. This can also be found at our web site. Please refer to [“Further Documentation” on page 41](#) for details.



## Chapter 7

# Monte Carlo Analysis

### 7.1 Overview

Monte Carlo analysis is a procedure to assess manufacturing yields by repeating simulation runs with varying applied random variations to component parameters. The technique is very powerful and usually gives a more realistic result than worst-case analysis which varies component values to their extremes in a manner which produces the worst possible result.

The implementation of Monte Carlo analysis in SIMetrix has been designed to be quick to set up for simple cases while still providing the required flexibility for more advanced requirements as might be required for integrated circuit design.

SIMetrix offers a level of flexibility for tolerance specification that cannot be found in other products including some high priced UNIX based applications. It is possible, for example, for different model parameters to be dependent on a single random variable. This makes it possible to model the fact that a number of model parameters might be dependent on a single physical characteristic, for example, the base width of a bipolar transistor. Of course, *lot* tolerances are also implemented accounting for the matching of devices in integrated circuits and other multiple components built onto a common substrate. However, in many products, lot tolerances can only be applied to the same type of device. In SIMetrix it is possible to model parametric relationships between different types of device which occur in integrated circuits but which are rarely taken into account.

As well as conventional multiple step Monte Carlo analysis, single step Monte Carlo sweeps may also be performed. These are available for the four swept modes, .AC, .DC, .NOISE and .TF. For example, a Monte Carlo analysis of the DC offset voltage of an amplifier can be performed using a single run of .DC using a special sweep mode. This is dramatically faster than the alternative of repeated .OP runs. This type of analysis can also be used to analyse the gain of an amplifier at a single frequency using .AC or .TF or even the noise, again at a single frequency, using .NOISE.

### 7.2 Specifying a Monte Carlo Run

Monte Carlo runs are invoked in the same way as multi-step analyses (see [“General Sweep Specification” on page 188](#)). The basic syntax is:

```
.analysis_name analysis_parameters SWEEP MONTE num_runs NUMCORES=num_cores
```

Where:

<i>.analysis_name</i>	Dot statement for analysis. Either .TRAN, .AC, .DC, .NOISE, .TF
-----------------------	---



<i>analysis_parameters</i>	Specific parameters for that analysis
<i>num_runs</i>	Number of runs
<i>num_cores</i>	Specify the number of processor cores to use.

### 7.2.1 Examples

Run 10 Monte Carlo runs for 1mS transient analysis

```
.TRAN 1m SWEEP MONTE 10
```

Run 1000 Monte Carlo steps for 1mS transient analysis using 4 processor cores. This will split the 1000 steps into 4 cores with each running 250 steps

```
.TRAN 1m SWEEP MONTE 1000 NUMCORES=4
```

100 Runs of a DC Sweep

```
.DC V1 0 5 0.01 SWEEP MONTE 100
```

AC sweep of voltage source V5 from -300mV to 300mV. Repeat 50 times

```
.AC DEVICE=V5 LIN 100 -300m 300m F=100000 SWEEP MONTE 50
```

## 7.3 Specifying a Single Step Monte Carlo Sweep

Monte Carlo sweep is one of the six modes available to the swept analysis modes, .AC, .DC .NOISE and .TF. The other modes are explained in [“General Sweep Specification” on page 188](#). The general syntax is:

```
.analysis_name MONTE num_points analysis_parameters
```

Where:

<i>.analysis_name</i>	Dot statement for analysis. Either .AC, .DC, .NOISE, .TF
<i>analysis_parameters</i>	Specific parameters for that analysis
<i>num_points</i>	Number of points in sweep

### 7.3.1 Examples

1000 point Monte Carlo sweep.

```
.DC MONTE 1000
```

AC Monte Carlo sweep 100 steps. Frequency = 10K. This is useful if - say - you are interested in the gain of an amplifier at one frequency and it needs to lie within a defined tolerance. Previously you would need to repeat an AC sweep at a single frequency to achieve this which could take a long time especially if the circuit has a difficult to find operating point. The analysis defined by the following line will take very little time even for a large circuit.

```
.AC MONTE 100 F=10K
```

## 7.4 Log File

Unless explicitly disabled with the NOMCLOG option, a log file will always be generated for Monte Carlo analyses. It has the default name of MCLOG.TXT but this can be changed with the MCLOGFILE option. Here is an example of an actual output:

```
Run 1: Seed=1226978751
Run 2: Seed=1521158126
```

Device	Nom.	Run 1		Run 2	
		Value	(Dev.)	Value	(Dev.)
Q10.D1:bv	5.9	5.9185638	(0.314641%)	5.8463766	(-0.90887%)
Q10.Q1:bf	220	283.10907	(28.68594%)	130.81497	(-40.5386%)
Q10.Q1:is	380a	368.7899a	(-2.95004%)	219.7988a	(-42.1582%)
Q11.D1:bv	5.9	5.9425623	(0.721395%)	5.8262401	(-1.25017%)
Q11.Q1:bf	220	285.27225	(29.66921%)	129.91303	(-40.9486%)
Q11.Q1:is	380a	354.1045a	(-6.8146% )	220.1177a	(-42.0743%)
Q12.D1:bv	5.9	5.8957932	(-713ppm )	5.787891	(-1.90015%)
Q12.Q1:bf	220	280.37304	(27.44229%)	130.28208	(-40.7809%)
Q12.Q1:is	380a	359.6985a	(-5.34249%)	225.8706a	(-40.5604%)
Q13.D1:bv	5.9	5.9020281	(343.74ppm)	5.8132485	(-1.47036%)
Q13.Q1:bf	220	280.04731	(27.29423%)	129.20488	(-41.2705%)
Q13.Q1:is	380a	367.7199a	(-3.2316% )	222.1358a	(-41.5432%)
Q14.D1:bv	5.9	5.9178142	(0.301936%)	5.8096709	(-1.531% )
Q14.Q1:bf	220	276.57192	(25.71451%)	129.93424	(-40.939% )
Q14.Q1:is	380a	364.6015a	(-4.05223%)	222.7107a	(-41.3919%)
Q4.D1:bv	5.9	5.9398543	(0.675496%)	5.8354342	(-1.09434%)
Q4.Q1:bf	220	277.08078	(25.94581%)	127.82878	(-41.896% )
Q4.Q1:is	380a	362.7751a	(-4.53287%)	225.9888a	(-40.5293%)
Q7.D1:bv	5.9	5.9281884	(0.47777% )	5.8421649	(-0.98026%)
Q7.Q1:bf	220	276.66227	(25.75558%)	129.29449	(-41.2298%)
Q7.Q1:is	380a	360.4184a	(-5.15304%)	227.0065a	(-40.2614%)
Q8.D1:bv	5.9	5.8811702	(-0.31915%)	5.8260238	(-1.25383%)
Q8.Q1:bf	220	280.33672	(27.42578%)	131.98533	(-40.0067%)
Q8.Q1:is	380a	361.0834a	(-4.97804%)	218.837a	(-42.4113%)
Q9.D1:bv	5.9	5.9001842	(31.215ppm)	5.8517296	(-0.81814%)
Q9.Q1:bf	220	281.41183	(27.91447%)	128.02565	(-41.8065%)
Q9.Q1:is	380a	358.8014a	(-5.57857%)	221.6128a	(-41.6809%)

The 'Device' column provides the name of the device and its model or instance parameter that is being reported. Q10.D1 is a diode ref D1 inside subcircuit Q1, BV is the model parameter.

The 'Nom' column displays the nominal value for that parameter.

Two columns are listed for each run. 'Value' is the actual value of the parameter and '(Dev.)' is the deviation from the nominal.

The 'Seed' values displayed for each run at the top are the values used to seed the random number generator. These can be used to set the SEED option in order to repeat a particular random set. See below for more details.

## 7.5 Seeding the Random Number Generator

The random variations are created using a pseudo random number sequence. The sequence can be seeded such that it always produces the same sequence of numbers for a given seed. In Monte Carlo analysis, the random number generator is seeded with a new value at the start of each run

and this seed value is displayed in the log file (see above). It is also possible to fix the first seed that is used using the SEED option. This makes it possible to repeat a run. To do this, note the seed value of the run of interest then add the line:

```
.OPTIONS SEED=seed_value
```

For example if you wanted to repeat run 2 in the above example you would add this line:

```
.OPTIONS SEED=1521158126
```

The first run of each Monte Carlo analysis will use the same random values as run 2 above. Note this assumes that only changes in values are made to the circuit. Any topology change will upset the sequence.

## 7.6 Specifying Tolerances

### 7.6.1 Overview

Tolerances for Monte Carlo analysis may be specified by one of the following methods:

1. Using a distribution function in an expression.
2. Using the device parameters TOL, MATCH and LOT

Method 1 above is the most general and flexible. TOL, MATCH and LOT parameters are provided primarily for backward compatibility but may also be more convenient in some circumstances.

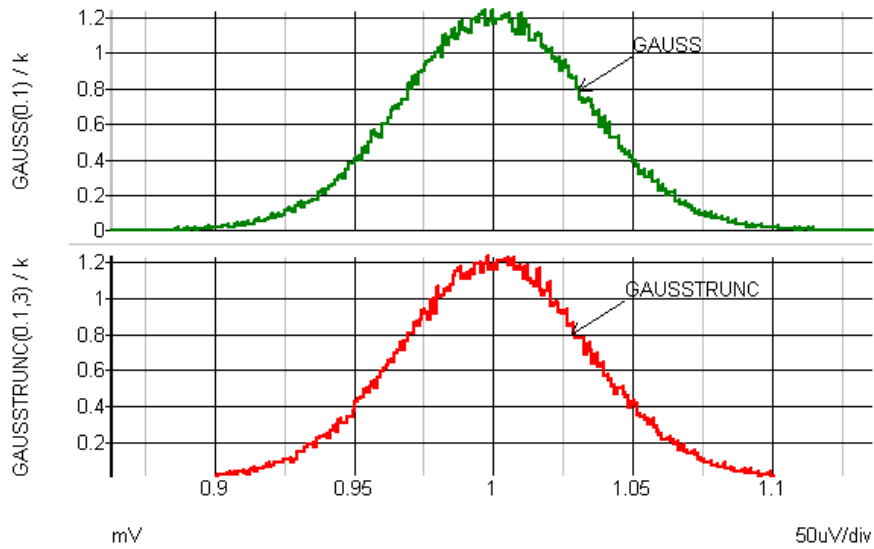
### 7.6.2 Distribution Functions

To specify Monte Carlo tolerance for a model or device parameter, define the parameter using an expression (see [“Using Expressions” on page 17](#)) containing one of the following functions:

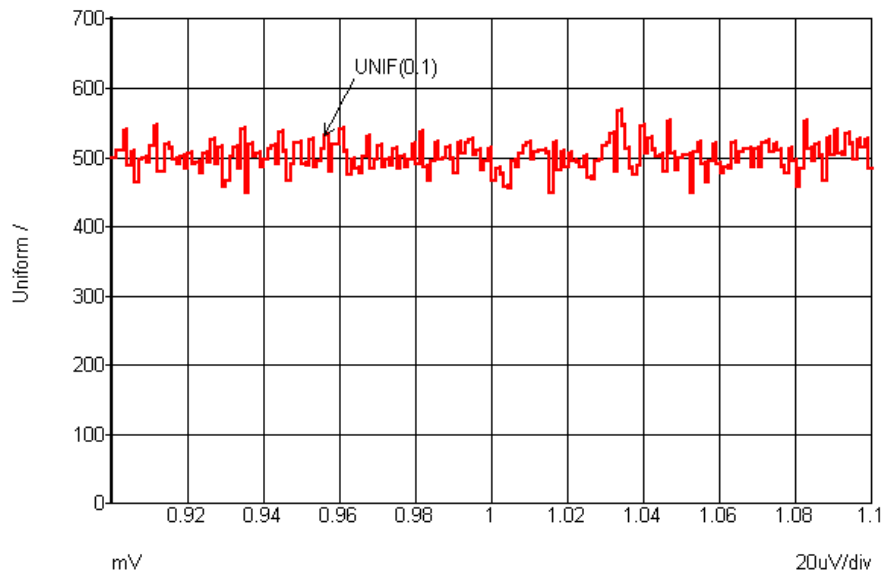
Name	Distribution	Lot?
GAUSS	Gaussian (3-sigma)	No
GAUSSL	Gaussian (3-sigma)	Yes
UNIF	Uniform	No
UNIFL	Uniform	Yes
WC	Worst case	No
WCL	Worst case	Yes
GAUSSTRUNC	Truncated Gaussian	No
GAUSSTRUNCL	Truncated Gaussian	Yes
DISTRIBUTION	User defined distribution	No
DISTRIBUTIONL	User defined distribution	Yes
UD	User defined distribution (alias)	No
UDL	User defined distribution (alias)	Yes

Each of the above functions (except GAUSSTRUNC and GAUSSTRUNCL) takes a single argument that specifies the tolerance. The return value is 1.0 +/- tolerance with the exception of GAUSS and GAUSSL. See [“Gaussian Distributions” on page 256](#) for details. In non-Monte Carlo analyses, all of the above return unity.

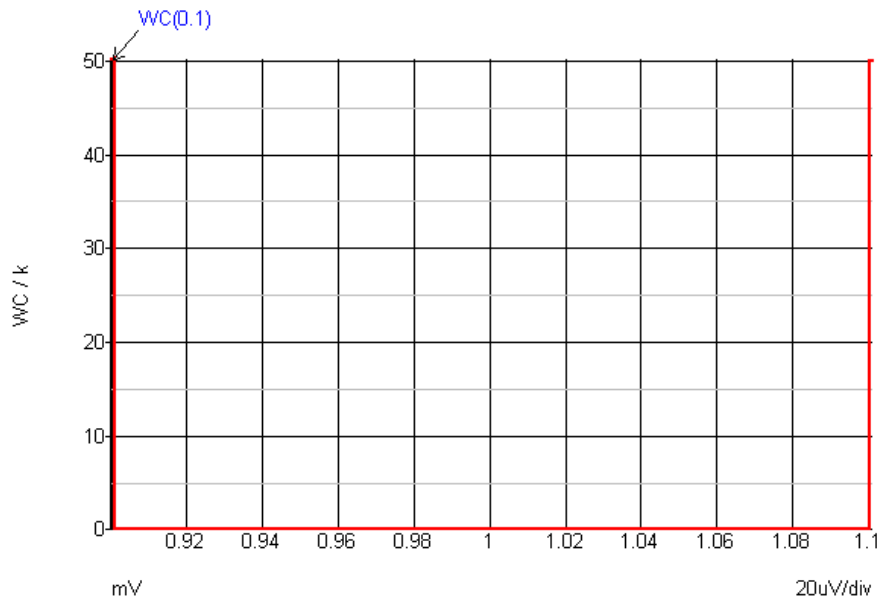
The graphs below show the characteristics of the various distributions. The curves were plotted by performing an actual Monte Carlo run with 100000 steps.



GAUSS and GAUSSSTRUNC



UNIF



WC

### User Defined Distribution

Customised distributions may be defined using the `Distribution` function (or its alias `UD`).

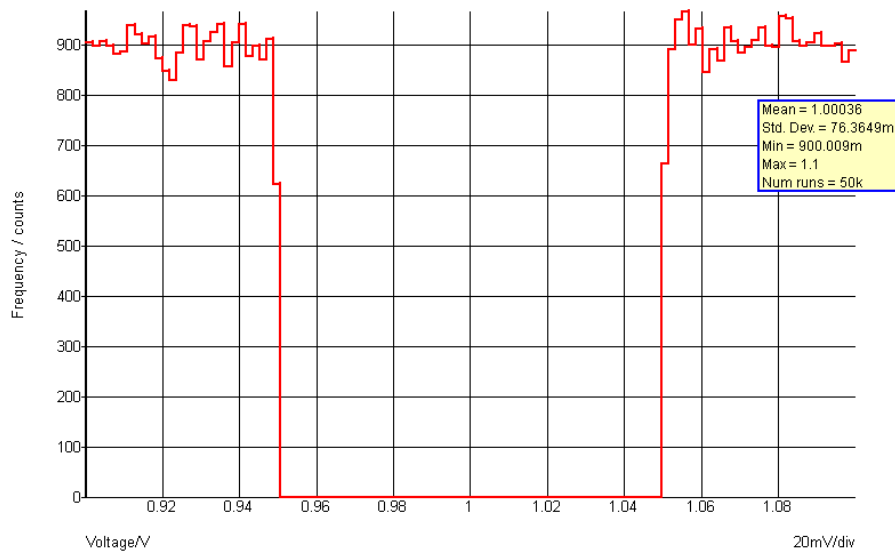
Distribution may take any number of arguments defined as follows:

Arg	Description
1	Base tolerance. In effect scales the extent of the distribution defined in the remaining arguments
Remaining arguments	Lookup table organised in pairs of values. The first value in the pair is the deviation. This should be in the range +1 to -1 and maps to the output range. So +1 corresponds to an output value of +tolerance and -1 corresponds to -tolerance. Each deviation value must be greater than or equal to the previous value. Values outside the range +/- 1 are allowed but will result in the function being able to return values outside the tolerance range. The second value in the pair is the relative probability and must 0 or greater. There is no limit to the number of entries in the table

Custom distributions can be conveniently defined using the `“FUNC”` on page 196 function definition statement. For example, the following defines a binomial distribution:

```
.FUNC binomial(a) = {distribution(a, -1,1, -0.5,1, -0.5,0, 0.5,0, 0.5,1, 1,1 )}
```

The function `‘binomial()’` can subsequently be used in the same way as other distribution functions. This would have a distribution as shown in the following graph:



### Gaussian Distributions

The standard Gaussian distribution functions (GAUSS(), GAUSSL()) return a random variable with a true Gaussian distribution where the tolerance value represents the  $3\sigma$  spread. This can return values that are outside the tolerance specification albeit with low probability. For example GAUSS(0.1) can return values  $>1.1$  and less than 0.9 as defined by the Gaussian distribution. For specifying actual components this is not usually exactly correct as most components are tested at production and devices outside the specified tolerance will be rejected.

This type of component can instead be specified using the GAUSSTRUNC() distribution function. This rejects values outside the specified range expressed as a multiple of  $\sigma$ . Syntax for the GAUSSTRUNC() function is:

```
GAUSSTRUNC(tolerance, sigma_multiplier)
```

Where:

Arg	Description
tolerance	Tolerance. Return value will lie in range 1.0 +/- tolerance
sigma_multiplier	Standard deviation of output expressed as multiplier of $\sigma$

### Examples

Apply 50% tolerance to BF parameter of BJT with gaussian distribution.

```
.MODEL NPN1 NPN IS=1.5e-15 BF={180*GAUSS(0.5)}
```

A production tested 4.7K $\Omega$  2% resistor with a  $3\sigma$  distribution:

```
R1 n1 n2 {4.7K*GAUSSTRUNC(0.1,3)}
```

## Lot Tolerances

The *lot* versions of the functions specify a distribution to be applied to devices whose tolerances track. These functions will return the same random value for all devices that reference the same model.

Note that the same effect as LOT tolerances can be achieved using random variables and subcircuits. For details see [“Creating Random Variables” on page 258](#)

## Lot Tolerance Examples

Specify 50% uniform lot tolerance and 5% gaussian device tolerance for BF parameter

```
.MODEL NPN1 NPN IS=1.5E-15 BF={180*GAUSS(0.05)*UNIFL(0.5)}
```

Here is an abbreviated log file for a run of a circuit using 2 devices referring to the above model:

		Run 1		Run 2	
Device	Nom.	Value	(Dev.)	Value	(Dev.)
Q1:bf	180	93.308486	(-48.162% )	241.3287	(34.0715% )
Q2:bf	180	91.173893	(-49.3478%)	245.09026	(36.16126%)

		Run 3		Run 4	
Device	Nom.	Value	(Dev.)	Value	(Dev.)
Q1:bf	180	185.95824	(3.310133%)	210.46439	(16.92466%)
Q2:bf	180	190.8509	(6.02828% )	207.04202	(15.02335%)

For the four runs BF varies from 91 to 245 but the two devices never deviate from each other by more than about 2.7%.

## Notes

The tracking behaviour may not be as expected if the model definition resides within a subcircuit. When a model is defined in a subcircuit, a copy of that model is created for each device that calls the subcircuit. Here is an example:

```
XQ100 VCC INN Q100_E 0 NPN1
XQ101 VCC INP Q101_E 0 NPN1

.SUBCKT NPN1 1 2 3 SUB
Q1 1 2 3 SUB N1
Q2 SUB 1 2 SUB P1

.MODEL N1 NPN IS=1.5E-15 BF={180*GAUSS(0.05)*UNIFL(0.5)}
.ENDS
```

In the above, XQ100 and XQ101 *will not track*. Two devices referring to N1 *inside* the subcircuit definition would track each other but different instances of the subcircuit will not. To make XQ100 and XQ101 track, the definition of N1 should be placed outside the subcircuit. E.g.

```
XQ100 VCC INN Q100_E 0 NPN1
XQ101 VCC INP Q101_E 0 NPN1

.SUBCKT NPN1 1 2 3 SUB
Q1 1 2 3 SUB N1
Q2 SUB 1 2 SUB P1
```

```
.ENDS
.MODEL N1 NPN IS=1.5E-15 BF={180*GAUSS(0.05)*UNIFL(0.5)}
```

### Creating Random Variables

It is possible to place distribution functions in .PARAM expressions to create a random variable. This provides a means of describing a relationship between different devices or different parameters within the same device.

Random variables may be created at the top level in which case they will be global and have the same value wherever they are used. Random variables may also be created inside subcircuit definitions. In this case they are local to the subcircuit and will have the same value for all devices and parameters *within* the subcircuit but a different value for different instances of the subcircuit.

**Example 1** In this example we make a BJT model using a subcircuit. The random variable is created inside the subcircuit so will have the same value for parameters defined in the subcircuit but will have different values for multiple instances

```
.subckt NPN1 c b e
.PARAM rv1 = UNIF(0.5)
Q1 c b e NPN1
.MODEL NPN1 NPN BF={rv1*180} TF={1e-11*rv1}
.ends
```

For all devices using that model, BF and TF will always have a fixed relationship to each other even though each parameter can vary by +/-50% from one device to the next.

Here is the log of a run carried out on a circuit with two of the above devices:

```
Run 1                      Run 2
Run 1: Seed=1651893287

Run 1
Device  Nom.      Value      (Dev.)
Q1.Q1:bf 180      148.83033746 (-17.3164792%)
Q1.Q1:tf 10p      8.268352081p (-17.3164792%)
Q2.Q1:bf 180      129.69395145 (-27.9478048%)
Q2.Q1:tf 10p      7.205219525p (-27.9478048%)

Run 2: Seed=763313972

Run 2
Device  Nom.      Value      (Dev.)
Q1.Q1:bf 180      265.86053442 (47.7002969% )
Q1.Q1:tf 10p      14.77002969p (47.7002969% )
Q2.Q1:bf 180      186.41647487 (3.564708261%)
Q2.Q1:tf 10p      10.35647083p (3.564708261%)
```

Notice that the BF and TF parameters always deviate by exactly the same amount for each device. However, the two devices do not track each other. If this were needed we would define the random variable outside the subcircuit at the netlist's top level:

```
.PARAM rv1 = UNIF(0.5)
.subckt NPN1 c b e
Q1 c b e NPN1
.MODEL NPN1 NPN BF={rv1*180} TF={1e-11*rv1}
.ends
```



Here is the log for the above:

```
Run 1: Seed=1608521901
```

```
Run 1
Device  Nom.      Value      (Dev.)
Q1.Q1:bf 180      249.54358268 (38.63532371%)
Q1.Q1:tf 10p      13.86353237p (38.63532371%)
Q2.Q1:bf 180      249.54358268 (38.63532371%)
Q2.Q1:tf 10p      13.86353237p (38.63532371%)
```

```
Run 2: Seed=80260241
```

```
Run 2
Device  Nom.      Value      (Dev.)
Q1.Q1:bf 180      116.33087232 (-35.3717376%)
Q1.Q1:tf 10p      6.46282624p (-35.3717376%)
Q2.Q1:bf 180      116.33087232 (-35.3717376%)
Q2.Q1:tf 10p      6.46282624p (-35.3717376%)
```

### 7.6.3 Hspice Distribution Functions

SIMetrix supports the Hspice method of defining Monte Carlo tolerances. This feature needs to be enabled with an option setting; see [“Enabling Hspice Distribution Functions” on page 260](#). The Hspice method uses random variables created using a special .PARAM syntax in one of the following form:

```
.PARAM parameter_name [=] AGAUSS(nominal, abs_variation, sigma, [multiplier]) ...
```

```
.PARAM parameter_name [=] AUNIF(nominal, abs_variation, [multiplier]) ...
```

```
.PARAM parameter_name [=] GAUSS(nominal, rel_variation, sigma, [multiplier]) ...
```

```
.PARAM parameter_name [=] UNIF(nominal, rel_variation, [multiplier]) ...
```

Where:

<i>parameter_name</i>	Name of random variable
<i>nominal</i>	Nominal value
<i>abs_variation</i>	Absolute variation. AGAUSS and AUNIF vary the nominal value +/- this value
<i>rel_variation</i>	Relative variation. GAUSS and UNIF vary the nominal value by +/- <i>rel_variation</i> * <i>nominal</i>
<i>sigma</i>	Scales <i>abs_variation</i> and <i>rel_variation</i> for functions GAUSS and AGAUSS. E.g. if <i>sigma</i> is 3 the standard deviation of the result is divided by 3. So AGAUSS(0,0.01,3) would yield a +/-1% tolerance with a 3 sigma distribution
<i>multiplier</i>	If included this must be set to 1 otherwise an error message will be displayed and the simulation aborted. Included for compatibility with existing model files only.

Random variables created using the above method do not behave in the same way as regular parameters created using the native SIMetrix distribution functions. They actually behave like function calls and return a different value *each time they are used*. Random variables created using

.param and a native distribution function are evaluated just once and always return the same value. Internally, the above are implemented using a .FUNC definition to define a function with no arguments.

For example, the following are both quite legal:

```
.PARAM rv1 = UNIF(10,1)
.PARAM rv2 = 'UNIF(10,1)'
```

The first (rv1) will provide a nominal value 10.0 +/- 1.0 with a new value calculated each time it is used. The second (rv2) is a native SIMetrix distribution function, will produce a value varying from -9.0 to +11.0 and will always have the same value. With the above definitions for rv1 and rv2, consider the following regular .PARAM statements:

```
.PARAM rand1 = rv1
.PARAM rand2 = rv1
.PARAM rand3 = rv2
.PARAM rand4 = rv2
```

rand1 and rand2 will have *different* values. rand3 and rand4 will have the same values.

### Enabling Hspice Distribution Functions

Hspice distribution functions need to be enabled with an option setting as follows:

```
.OPTIONS MCHSPICE
```

**Important:** This option also changes the way Monte Carlo operates in a fundamental way by disabling *model spawning*. This is a process which gives each instance its own separate copy of its model parameters and allows 'dev' (or 'mismatch') tolerances to be implemented. Without *model spawning* dev tolerances cannot be implemented except by giving every instance their own copy of a model.

With the Hspice method this can only be done easily by wrapping up .MODEL statements inside a .SUBCKT definition. Each instance will then effectively get its own .MODEL statement and mismatch parameters can be defined.

#### 7.6.4 TOL, MATCH and LOT Device Parameters

These parameters may be used as a simple method of applying tolerances to simple devices such as resistors. The TOL parameter specifies the tolerance of the device's value. E.g.

```
R1 1 2 1K TOL=0.05
```

The above resistor will have a tolerance of 5% with a gaussian distribution by default. This can be changed to a uniform distribution by setting including the line:

```
.OPTIONS MC_ABSOLUTE_RECT
```

in the netlist.

Multiple devices can be made to track by specifying a LOT parameter. Devices with the same LOT name will track. E.g.

```
R1 1 2 1K TOL=0.05 LOT=RES1
R2 3 4 1k TOL=0.05 LOT=RES1
```

R1 and R2 in the above will always have the same value.

Deviation between tracking devices can be implemented using the MATCH parameter. E.g.

```
R1 1 2 1K TOL=0.05 LOT=RES1 MATCH=0.001
R2 3 4 1k TOL=0.05 LOT=RES1 MATCH=0.001
```

R1 and R2 will have a tolerance of 5% but will always match each other to 0.1%. MATCH tolerances are gaussian by default but can be changed to uniform by specifying

```
.OPTIONS MC_MATCH_RECT
```

The default distributions for tolerances defined this way are the logarithmic versions as described in [“Distribution Functions” on page 253](#). To use a linear distribution, add this statement to netlist (or F11 window in the schematic editor):

```
.OPTIONS mcUseLinearDistribution
```

If using device tolerance parameters, note that any absolute tolerance specified must be the same for all devices within the same lot. Any devices with the same lot name but different absolute tolerance will be treated as belonging to a different lot. For example if a circuit has four resistors all with lot name RN1 but two of them have an absolute tolerance of 1% and the other two have an absolute tolerance of 2%, the 1% devices won't be matched to the 2% devices. The 1% devices will however be matched to each other as will the 2% devices. This does not apply to match tolerances. It's perfectly OK to have devices with different match tolerances within the same lot.

## Chapter 8

# Convergence, Accuracy and Performance

### 8.1 Overview

In transient and DC analyses, an iterative method is used to analyse the circuit. Generally, iterative methods start with an initial guess for the solution to a set of equations and then evaluate the equations with that guess. The result of that evaluation is then used to derive a closer estimate to the final solution. This process is repeated until a solution is found that is within the error tolerance required. SIMetrix and SPICE use Newton-Raphson<sup>1</sup> iteration which usually converges extremely rapidly. However, there are occasions when this process is either unreasonably slow or fails altogether. Under these circumstances the simulation will abort.

SIMetrix offers superior convergence which has been achieved as a result of the following developments to the simulator core:

- Automatic pseudo transient analysis algorithm for operating point solution. See below for details.
- Enhancements to GMIN and source stepping algorithms to use a variable step size. (The standard SPICE3 variants use a fixed step).
- Junction GMIN DCOP Convergence Method
- Proprietary enhancements to transient analysis algorithm.
- New matrix solver
- Improvements to device models.

With these improvements, convergence failure with SIMetrix is extremely rare. However, it is impossible to eliminate this problem altogether and there still remain some circuits which fail.

In this chapter we explain some of the causes of non-convergence and some of the strategies SIMetrix uses to prevent it. Also explained is what to do in the rare event that convergence fails.

---

<sup>1</sup>Sir Isaac Newton 1642-1727 and Joseph Raphson 1648-1715

## 8.2 DC Operating Point

### 8.2.1 Overview

As explained in “[DC Operating Point Algorithms](#)” on page 268, SIMetrix has four different algorithms at its disposal to solve the DC operating point. For this analysis mode to fail, and assuming the default settings are being used, all four algorithms must fail.

The following sections describe the possible reasons for failure of each mode and what can be done about them.

The general procedure is as follows:

1. Check your circuit. Check that all components are the correct way around and have the correct values. Make sure you haven't used 'M' when you meant 'Meg'.
2. Refer to section “[Source and GMIN Stepping](#)” on page 263 and see if GMIN or source stepping can be made to work.
3. Refer to section “[Pseudo Transient Analysis](#)” on page 264 to get pseudo transient analysis converging.
4. Contact technical support. We don't officially offer a convergence fixing service and reserve the right to decline help. However, we are always interested in non-converging circuits and usually we will look at your circuit to see if we can identify the problem.

### 8.2.2 Source and GMIN Stepping

By default, if these modes fail, SIMetrix will carry on and attempt pseudo transient analysis. It will not do so only if instructed not to using the `dcopSequence` option (See “[Controlling DC Method Sequence](#)” on page 270). Pseudo transient analysis usually succeeds but sometimes can take a long time so you may prefer to get one of these methods working instead. Also, if pseudo transient analysis fails it is desirable to first see if GMIN or source stepping can be made to work.

There are a few options you can set to encourage these modes to converge. These are

Name	Default	Set to	What it does
GMINSTEPITERLIMIT	20	100	The number of iterations attempted for each GMIN step
GMINMAXITERS	1000	0 (equivalent to infinity)	Total number of iterations allowed for GMIN stepping
SOURCEMAXITERS	1000	0 (equivalent to infinity)	Total number of iterations allowed for source stepping

It is only worth changing `gminMaxIters` or `sourceMaxIters` if the iteration limit is actually being reached. Often GMIN and source stepping fail to converge before the iteration limit is reached. To find out, select the menu **Simulator | Show Statistics**. This displays, amongst other things, the number of iterations used for GMIN and/or source stepping. If they exceed 1000 then the iteration limit has been reached. This means that GMIN/source stepping may have succeeded if it had been given a chance.

### 8.2.3 Pseudo Transient Analysis

Pseudo transient analysis is the most powerful method that SIMetrix uses and it is rare for it to fail. It is not however infallible and can go wrong for the following reasons:

1. The transient analysis itself failed to converge. (This is rare)
2. The circuit oscillates

#### Convergence failure in pseudo transient analysis

You will get the error message

```
Cannot find DC operating point
No convergence in pseudo transient analysis
```

The reasons why this may happen are the same as for transient analysis and are covered in [“Fixes for Transient Non-convergence” on page 267](#).

#### Circuit oscillation

You will see the message

```
Cannot find DC operating point
Iteration limit exceeded in pseudo transient analysis
```

The circuit can oscillate because:

1. It is designed to i.e. it is or has an oscillator
2. It is supposed to be stable but passes an unstable region during supply ramping
3. It is supposed to be stable but has a fault in its design
4. It is stable but is made unstable by the capacitors added during the pseudo transient analysis

#### If the circuit is an oscillator

If 1. then you must disable the oscillator during the DC solution. You can do this by one of the following methods:

1. Apply an initial condition to a point on the circuit that will break the oscillator’s feedback loop.
2. Use the capacitor/inductor PTAVAL parameter to change its value during pseudo transient analysis. This parameter can be applied to a component or components that form part of the oscillator. In the netlist the parameter is applied at the end of the component line. E.g for a capacitor:

```
C12 N2 N6 1.2n PTAVAL=1
```

In the above a 1.2n capacitor will take the value of 1 farad during pseudo transient analysis.

**The circuit is not supposed to be an oscillator**

If the circuit does not have any intentionally unstable elements then diagnosis of the problem is a little harder. Firstly, you need to rule out 4. above as a possible cause. As explained in [“DC Operating Point Algorithms” on page 268](#), SIMetrix adds its own capacitors to your circuit during pseudo transient analysis in order to overcome potential problems with regenerative action. The problem is that these added capacitors can themselves make a circuit unstable. So the first thing to try is to inhibit the addition of these capacitors. To do this, add the following line to the netlist (See [“Adding Extra Netlist Lines” on page 2](#) to find out how to add to a schematic):

```
.OPTIONS PTACONFIG=1
```

then re-run the simulation.

**The circuit is not supposed to be an oscillator but it is**

If this fails, then life gets even more complicated! If it fails with the message

```
Iteration limit exceeded in pseudo transient analysis
```

then it is very likely that the circuit is oscillating or entering an unstable region. If a different message is displayed go to [“The circuit doesn’t oscillate but still doesn’t converge” on page 265](#). To allow diagnosis of what is happening SIMetrix provides a method of analysing the circuit during the pseudo transient ramp. By default, no data is output during pseudo transient analysis but this can be changed as follows:

1. Set the analysis mode to DC operating point only.
2. Add the simulator option ptaOutputVecs by adding the following line to the netlist:

```
.OPTIONS PTAOUTPUTVECS
```

3. Now run the simulation for a while or until it stops.

You can now probe the circuit in the normal way to see what is oscillating. Once the oscillation has been fixed, you should be able to simulate the circuit successfully.

**The circuit doesn’t oscillate but still doesn’t converge**

As there are no added capacitors, there is a risk that pseudo transient analysis can fail for the same reason that GMIN and source stepping sometimes fail. In this case you will get the message:

```
No convergence in pseudo transient analysis
```

If this happens your only recourse is the final desperation measure. This is to repeat the simulation with all valid values of ptaConfig from 2 to 15. (You can skip 7 as this is the default). ptaConfig is a simulator option that controls some of the parameters used in pseudo transient analysis. Most circuits pass for all settings but a few are more selective.

**Accept Pseudo Transient Unconditionally**

You can specify pseudo transient analysis to be accepted unconditionally at some time after it has started. This is often a good solution to problems caused by circuit oscillation especially if the oscillation is small and unintended. To accept pseudo transient unconditionally, set the option:

```
.OPTIONS PTAACCEPTAT=time
```

Specify a *time* value that is adequate for the circuit state to settle as much as possible.

### 8.2.4 Junction Initialised Iteration

By default, this is the first method to be tried. If it fails, SIMetrix will then attempt source stepping, GMIN stepping and finally pseudo transient analysis. Usually one of these other methods will succeed and it is not worth spending time getting this method to work.

If it does work, however, this is usually the fastest method and this can be put to good use for repetitive runs e.g. Monte Carlo. It can be made to succeed using nodesets (see next section) and with a wisely chosen selection it is possible to speed up repetitive runs. Assuming one of the other methods does complete to a solution, the best way of creating nodesets is by using the SaveRHS command. This is explained in the next section.

### 8.2.5 Using Nodesets

Nodesets have two uses, one to aid convergence and the other to bias the solution in circuits that have more than one stable state.

Initially nodesets work exactly the same way as initial conditions. The nodeset voltage is applied via a 1 Ohm (by default) resistor and the solution is completed to convergence (by any of the methods). The nodeset is then released and the solution repeated. If the nodeset voltage is close to the actual solution the convergence of the second solution should be rapid.

With SIMetrix, it is rarely necessary to use nodeset's to find the DC solution of a circuit. They can, however, be useful for speeding up the operating point analysis for circuit that have already been solved. You may wish to do this for a Monte-Carlo analysis, for example.

SIMetrix provides a means of creating nodeset's using the SaveRHS command. To make use of this, proceed as follows:

1. Run a DC operating point analysis
2. Save the solution to a file using the SaveRhs command as follows:

```
SaveRhs /nodeset RHS.TXT
```

This will save to the file RHS.TXT a .nodeset statement specifying the solution at each node.

3. Paste the contents of RHS.TXT to the netlist. Alternatively, include the file using the .INC statement. (See [“Adding Extra Netlist Lines” on page 2](#) to find out how to add to a schematic).

If you now repeat the DC analysis, you should now find that the solution is very rapid. Depending on the nature of your circuit, you may also find that the solution is found easily even if you modify the circuit. This is not, however, guaranteed.

## 8.3 Transient Analysis

### 8.3.1 What Causes Non-convergence?

There are a number of reasons for convergence failure in transient analysis but most have their root in one of the following:

1. The circuit does not have a real and finite solution
2. The circuit contains discontinuities
3. There is insufficient precision available to meet the required tolerance



1. is a circuit problem. A trivial example of 1. is a PN junction biased by a large voltage. Without any series resistance, the voltage does not need to be very high for the current in the device to exceed the range of the machine. However, this can also be a result of more subtle problems. A linear circuit which is unstable can suffer unbounded growth which will ultimately overflow. This will show as a convergence failure.

An example of 2. is a bistable circuit where the device capacitances are not modelled. The action of switching state would theoretically occur in zero time, a situation the simulator cannot be guaranteed to handle.

2. above is the cause of many convergence problems. Some of these are caused by poor model design. However, this can also be the result of regenerative feedback if there is no time limiting elements. For example a bistable circuit with no capacitance will switch state in zero time. Such discontinuous action will often lead to convergence failure.

3. is common but difficult to diagnose. In some cases it is possible for the effect of a change in the least significant digits in the calculations to get magnified to such an extent that they exceed the required tolerance.

### 8.3.2 Fixes for Transient Non-convergence

1. Type this at the command line:

**where**

This will list nodes and devices that are causing the convergence problem. If any nodes are on the top level of your schematic, these will be highlighted. This should give a clue to the cause of the problem.

2. As with DC operating point, check your circuit. In particular, check that you are not doing anything which might cause numerical difficulties such as forward biasing a zero resistance PN junction with a large zero source impedance voltage source.
3. Do anything that will prevent small time steps being needed. Gross non-linearities, regenerative loops and high gain loops all require small time-steps if not well damped. It may be that you have left out damping components to simplify the circuit and speed the simulation.
4. Avoid *over-idealising*. A common misconception is that simplifying a circuit by removing reactive components such as capacitors will speed up a simulation and make it easier to converge. Capacitors have a number of stabilising effects on simulation and are usually beneficial.
5. Avoid using unrealistically large capacitors or inductors and unrealistically small resistors if at all possible. You should especially avoid such components if non-grounded.
6. If you have some large capacitors in your circuit, try adding a small amount of ESR using the built-in capacitor ESR parameter rather than a separate resistor.
7. If all else fails you can try relaxing some of the tolerances. If your circuit does not have any small (sub- $\mu\text{A}$ ) currents then set ABSTOL to 1e-9 or 1e-6. You can also increase VNTOL (default 1e-6) to say 1e-3 if your circuit only has large voltages. Increasing RELTOL is the very last thing you should try. In our experience, increasing RELTOL beyond its default value (0.001) is rarely a reliable solution and can make matters worse.
8. Contact technical support. We don't officially offer a convergence fixing service and reserve the right to decline help. However, we are always interested in non-converging circuits and usually we will look at your circuit to see if we can identify the problem.

## 8.4 DC Sweep

DC sweep is basically a repeated DC operating point and so the issues relating to that mode also apply to DC sweep. However, if you are sweeping a voltage or current source, then an altogether better way of dealing with DC sweep problems is to simulate the DC sweep using transient analysis with a slow ramp.

Using transient analysis to perform DC sweep also resolves problems that can occur with circuits that have regions where there is more than one stable state e.g. bistables or schmitt triggers. Consider sweeping the input voltage of a schmitt trigger circuit. When the input voltage is between the lower and upper thresholds, the circuit has two stable states and the DC algorithm could find either of them. As each step in a DC analysis is initialised with the previous step, it will usually find the correct solution *but this is not guaranteed*. This means that the output could change state even though the input has not passed either threshold. This problem doesn't occur in transient analysis as in this mode the circuit is running as it would in real life.

## 8.5 DC Operating Point Algorithms

SIMetrix uses five alternative strategies to resolve the DC operating point. These are:

1. Junction initialised iteration. This is our name for the standard algorithm sometimes simply known as 'DC Iteration'.
2. Source stepping.
3. Diag GMIN stepping.
4. Junction GMIN stepping.
5. Pseudo transient analysis.

These are described in the following sections.

### 8.5.1 Junction Initialised Iteration

This is the standard algorithm and is sometimes known simply as 'DC iteration'. Each semiconductor junction is initialised with a small voltage and iteration then proceeds until convergence (or otherwise). This method often succeeds and is usually the quickest. However, the starting point is only a bit better than an educated guess and can be so far removed from the real solution that it never has a chance of succeeding. ('Junction initialised iteration' is a name we have coined and you may see it referred to as JI2 elsewhere in this manual and also in messages output by SIMetrix)

### 8.5.2 Source Stepping

Source stepping. This method - as with all the remaining methods to be described - belong to a class of convergence strategies known as continuation methods. These all work by repeating the iterative process while gradually varying some circuit parameter. The circuit parameter is chosen so that at its start value the solution is known or trivial and at its final value the solution is the operating point that is required. In source stepping, all the circuit's power sources are gradually ramped up from zero to their final value. While at zero, the circuit's solution is trivial; all the voltages and currents are zero. At the first step, the supplies might be ramped up to 10% of their maximum and the solution iterates to convergence. Then the supplies are increased and the process is repeated. At each step the solution is initialised with the previous solution which, if the steps are small, will be close to the new solution that is required and convergence will therefore be relative easy to achieve.

This method is quite effective and is included in all SPICE based simulators including those derived from SPICE2. However the SPICE versions use a fixed step size, whereas in SIMetrix (since version 2.0), the step size is variable so if a step fails, the step size is reduced and it tries again.

However, even with an arbitrarily small step size, this method can fail if the circuit contains some kind of regenerative action. As the supplies are ramped it is possible for the circuit to abruptly switch from one state to another as in a schmitt trigger. Although circuits such as schmitt triggers do give difficulty, even circuits that do not have such elements can also give trouble.

### 8.5.3 Diagonal GMIN Stepping

In this method, a large conductance term is added to every diagonal entry of the solution matrix and gradually reduced. This is similar to placing a low value resistor from every node of the circuit to ground but is by no means equivalent. The high conductance term (=low resistance) in the matrix effectively swamps non-linearities and as a result the solution is easy to find. The term is gradually reduced until it is zero.

This method is also effective and sometimes works for circuits for which source stepping fails. It is included with all SPICE3 derived simulators but, as with source stepping, the SPICE variants use a fixed step while SIMetrix uses a variable step.

GMIN stepping suffers from the same problems as source stepping but not always with the same circuits so it always worth trying both approaches.

The received wisdom has always been that GMIN stepping is more effective than source stepping. This has not however been borne out by our own research which has shown the source stepping converges more often and more quickly. For this reason, SIMetrix attempts source stepping before GMIN stepping. This is the reverse of SPICE3 and its derivatives.

### 8.5.4 Junction GMIN Stepping

The junction GMIN stepping method incrementally steps the conductance across semiconductor junctions. This in effect sweeps the GMIN option parameter.

This method is effective for CMOS IC designs as long as GMIN is implemented as a conductance between drain and source. This is not the default configuration for LEVEL 1 to 3 MOSFETs in which GMIN is implemented as two conductances between the drain and bulk and source and bulk. For other MOSFET models such as BSIM3, the default GMIN is now between source and drain. For designs containing these devices, Junction GMIN Stepping is the first method attempted after JI2. For circuits that do not contain such devices, this method is not attempted at all.

### 8.5.5 Pseudo Transient Analysis

This method finds the solution using transient analysis. In SIMetrix, a transient analysis is conducted while ramping up all power sources, in effect simulating the action of switching on the power supplies. This is not the same as source stepping as the latter is a pure DC method with all reactive components set to zero. Because reactive components - i.e. capacitors and inductors - are included in transient analysis, effects such as abrupt changes are damped and occur gradually over a finite time. This eliminates the problem - described above - that the DC continuation methods suffer from.

The above assumes, however, that the circuit is well modelled with all reactive elements correctly specified. With integrated circuit design this is usually the case, but for discrete circuits frequently is not. Opamp macro models, for example, consist of many idealised elements that are not always damped by reactive elements. Without such damping, pseudo transient analysis can fail for the

same reason as source and GMIN stepping. So, SIMetrix automatically adds additional capacitance to the circuit to prevent this situation from arising.

The end result is a convergence strategy that *nearly always succeeds*. However, it is generally the slowest method so in SIMetrix it is, by default, attempted last.

Although pseudo transient analysis is very powerful it is not completely infallible. Its *Achilles Heel* is oscillation. Because a transient analysis is being performed it is possible for the circuit to oscillate. If this happens, pseudo transient analysis can end up going on forever without ever finding a stable solution. In our experience, however, this is actually rare. A number of steps are taken to damp oscillators so that even circuits that are designed to oscillate still succeed with pseudo transient analysis.

SIMetrix provides a number of facilities to inhibit circuit oscillation during pseudo transient analysis. These are described in “[Pseudo Transient Analysis](#)” on page 264.

### 8.5.6 Controlling DC Method Sequence

You may have a circuit that only succeeds with - say - pseudo transient analysis and so attempting the other methods just wastes time. In this situation, you can force the simulator to attempt this method exclusively. To do this you need to set the two simulator options noOpiter and dcoSequence. noOpiter inhibits the first method (junction initialised iteration) while dcoSequence controls which and what order the remaining methods are attempted. The value of dcoSequence consists of any combination of SOURCE, GMIN, JUNGMIN and PTA separated by the pipe symbol: '|'. SOURCE, GMIN, JUNGMIN and PTA refer respectively to ‘source stepping’, ‘DIAG GMIN stepping’, ‘Junction GMIN stepping’ and ‘pseudo transient analysis’. The order in which these words appear in the value of dcoSequence, determines the order in which the corresponding methods will be attempted. So for example:

```
.OPTIONS NOOPITER DCOPSEQUENCE=GMIN|PTA
```

will force GMIN stepping to be attempted first followed by pseudo-transient analysis. Junction initialised iteration, junction GMIN stepping and source stepping won’t be attempted at all. Note that PTA must always be the last entry.

## 8.6 Singular Matrix Errors

A singular matrix error occurs when the circuit does not have a unique and finite solution. For example, a circuit containing a floating capacitor does not have a unique DC solution as the capacitor can be at any voltage. Also circuits with shorted inductors, voltage sources or a combination of both will fail with this error.

If you get this error, you must first check your circuit. The simulator will tell you where the problem is either as a node name or a device name.

If you think your circuit is OK then it is possible that the error is occurring because during the course of iterating to a solution, some node voltages or device currents reached very high values and the limited accuracy of the machine made it seem that the matrix was singular. This can happen with junction initialised iteration. If this is the case, try setting the option:

```
.OPTIONS NOOPITER
```

This will inhibit this mode and the simulator will start with source stepping. This method, and the others that follow, don’t generally suffer from this problem.

Note that the simulation will abort if a singular matrix is detected in junction initialised iteration. It will not automatically attempt the other methods. This is because, by far the most common reason for singular matrices is circuit error.

## 8.7 Transient Analysis - ‘Time step too small’ Error

The message:

```
Timestep too small
```

is not actually due to non-convergence. It means that, because of the nature of your circuit, to achieve the required accuracy, a time step smaller than the minimum permissible was needed. This can happen if you perform a very long transient analysis on a circuit with relatively short time constants. If you get this message, you can try reducing the minimum time step with the MinTimeStep simulator option. The default value for MinTimeStep is  $1e-9 \times \text{max time step}$  and the max time step defaults to  $(T_{\text{stop}} - T_{\text{start}}) / 50$  where  $T_{\text{stop}}$  and  $T_{\text{start}}$  are respectively the stop and start times of the transient analysis. This option can be set in the user interface. See *User’s Manual/Analysis Modes/Transient Analysis/Setting up a Transient Analysis/Time Step*.

## 8.8 Accuracy and Integration Methods

### 8.8.1 A Simple Approach

The accuracy of the simulation can be a complicated subject. So we will start with simple advice. If you wish to increase the accuracy of a simulation, reduce the value of RELTOL. This defaults to 0.001 so to reduce it to say  $1e-5$  add the following line to the netlist:

```
.OPTIONS RELTOL=1e-5
```

(The setting of RELTOL is supported by the front end. See *User’s Manual/Analysis Modes/Simulator Options/Setting Simulator Options/Tolerances* for details.)

The simulation will run slower. It might be a lot slower it might be only slightly slower. In very unfortunate circumstances it might not simulate at all and fail with a convergence error.

Conversely, you can speed up the simulation by increasing RELTOL, but we don’t recommend it. Increasing RELTOL beyond its default value often degrades accuracy to an unacceptable level.

To increase speed with a reasonably controlled loss of precision, increase POINTTOL to 0.1 or even 1.0 but no higher.

### 8.8.2 Iteration Accuracy

For DC and transient modes, the simulator essentially makes an approximation to the true answer. For DC analysis an iterative method is used to solve the non-linear equations which can only find the exact answer if the circuit is linear. The accuracy of the result for non-linear circuits is determined by the number of iterations; accuracy is improved by performing more iterations but obviously this takes longer. In order to control the number of iterations that are performed an estimate is made of the error by comparing two successive iterations. When this error falls below a predetermined tolerance, the iteration is deemed to have converged and the simulator moves on the next step or completes the run. Most SPICE simulators use something similar to the following equations to calculate the tolerance:

For voltages:  $TOL = RELTOL * \text{instantaneous\_value} + VNTOL$

For currents:  $TOL = RELTOL * \text{instantaneous\_value} + ABSTOL$

"instantaneous\_value" is the larger of the current and previous iterations. VNTOL has a default value of  $1\mu V$  so for voltages above 1mV, RELTOL dominates. ABSTOL has a default of 1pA so for currents above 1nA, RELTOL dominates.

The above method of calculating tolerance works fine for many circuits using the default values of VNTOL and ABSTOL. However, SPICE was originally designed for integrated circuit design where voltages and currents are always small, so the default values of ABSTOL and VNTOL may not be appropriate for - say - a 100V 20A power supply. Suppose, that such a PSU has a current that rises to 20A at some point in the simulation, but falls away to zero. When at 20A it has a tolerance of 20mA but when it falls to zero the tolerance drops to ABSTOL which is 1pA. In most situations the 1pA tolerance would be absurdly tight and would slow down the simulation. Most other SPICE products recommend increasing ABSTOL and VNTOL for PSU circuits and indeed this is perfectly sound advice. However, In SIMetrix the tolerance equation has been modified to make this unnecessary in most cases. Here is the modified equation:

For voltages:  $TOL = RELTOL * MAX( peak\_value * POINTTOL, instantaneous\_value ) + VNTOL$

For currents:  $TOL = RELTOL * MAX( peak\_value * POINTTOL, instantaneous\_value ) + ABSTOL$

peak\_value is the magnitude of the largest voltage or current encountered so far for the signal under test. POINTTOL is a new tolerance parameter and has a default value of 0.001. So for the example we gave above, peak\_value would be 20 and when instantaneous\_value falls to zero the tolerance would be:

$$0.001 * MAX(20 * 0.001, 0) + 1p = \text{approx. } 20\mu A$$

20μA is a much more reasonable tolerance for a signal that reaches 20A.

The above method has the advantage that it loosens the tolerance only for signals that actually reach large values. Parts of a circuit that only see small voltages or currents - such as the error amplifier of a servo-controlled power supply - would still be simulated with appropriate precision.

POINTTOL can be increased to improve simulation speed. It is a more controlled method than increasing RELTOL. POINTTOL can be raised to 0.1 or even 1.0 but definitely no higher than 1.0.

### 8.8.3 Time Step Control

The tolerance options mentioned above also affect the time step control algorithm used in transient analysis. In SIMetrix, there are three mechanisms that control the time step, one of which has to be explicitly enabled. These are:

1. Iteration time step control
2. LTE time step control
3. Voltage delta limit

Item 3 above is inactive unless explicitly enabled using the MAXVDELTADEL option setting. See below for details.

#### Iteration Time Step Control

Iteration control reduces the time step by a factor of 8 if convergence to the specified accuracy cannot be achieved after 10 iterations. (10 by default but can be changed with ITL4 option). If convergence is successful, the time step is doubled. As this mechanism is controlled by the success or otherwise of the iteration it is also affected by the same tolerance options described in the above section about iteration accuracy.

### LTE Time Step Control

The theory behind this method is beyond the scope of this manual but essentially it controls the accuracy of the numerical integration method used to model reactive devices such as inductors and capacitors. These devices are governed by a differential equation. It is not possible in a non-linear circuit to solve these differential equations exactly so a numerical method is used and this - like the iterative methods used for non-linear devices - is approximate. In the case of numerical integration, the accuracy is determined by the time step. The smaller the time step the greater the accuracy but also the longer the simulation time.

The accuracy to which capacitors are simulated is controlled by RELTOL, POINTTOL and two other options namely TRTOL and CHGTOL. The latter is a charge tolerance and has a similar effect to VNTOL and ABSTOL but instead represents the charge in the capacitor. It's default value is 1e-14 which, like ABSTOL and VNTOL is appropriate for integrated circuits but may be too low for PSU circuits with large capacitors. However, the peak detection mechanism controlled by POINTTOL described in the above section also works for the LTE time step control algorithm and it is therefore rarely necessary to alter CHGTOL.

TRTOL is a dimensionless value and has a default value of 7. It affects the overall accuracy of the numerical integration without affecting the precision of the iteration. So reducing TRTOL will increase the accuracy with which capacitors and inductors are simulated without affecting the accuracy of the iterative method used to simulate non-linear elements. However, in order for the simulation of reactive devices to be accurate, the non-linear iteration must also be accurate. So, reducing TRTOL much below unity will result in a longer simulation time but no improvement in precision. Increasing TRTOL to a large value, however, may be appropriate in some circumstances where the accuracy to which reactive devices are simulated is not that important. This may be the case in a circuit where there is an interest in the steady state but not in how it was reached.

Inductors are controlled by the same tolerances except CHGTOL is replaced by FLUXTOL. This defaults to 1e-11.

The default LTE time step algorithm used in SIMetrix is slightly different to that used by standard SPICE. The standard SPICE variant is also affected by ABSTOL and VNTOL. The SIMetrix algorithm controls the time step more accurately and as a result offers better speed-accuracy performance.

### Voltage Delta Limit

This places a limit on the amount of change allowed in a single timestep for each node. This limit is governed by the option setting MAXVDELTAREL and MAXVDELTAABS and is included to overcome a problem that can cause false clocking of flip-flops. The limit can be calculated from:

$$\text{MAXVDELTAABS} + \text{MAXVDELTAREL} * (\text{node\_voltage})$$

where node\_voltage is the larger of the node voltage at current time step and the node voltage at the previous time step. The above is calculated for all voltage nodes. If the change in voltage exceeds this limit, the time step is cut back.

The above mechanism is not enabled if MAXVDELTAREL is zero or less and MAXVDELTAABS is zero by default.

Setting MAXVDELTAREL to a value of about 0.4 will usually fix problems of false clocking in flip-flops. However, this will slow down the simulation slightly and it is not recommended that this setting is used in circuits that do not contain flip-flops.

### 8.8.4 Accuracy of AC analyses

The small-signal analysis modes .AC, .TF and .NOISE do not use approximate methods and their accuracy is limited only by the precision of the processor's floating point unit. Of course the DC operating point that always precedes these analysis modes is subject to the limitations described above. Also, the device models used for non-linear devices are also in themselves approximations. So these modes should not be seen as exact but they are not affected by any of the tolerance option settings.

### 8.8.5 Summary of Tolerance Options

#### RELTOL

Default = 0.001. This affects all DC and transient simulation modes and specifies the relative accuracy. Reduce this value to improve precision at the expense of simulation speed. We do not recommend increasing this value except perhaps to run a quick test. In any case, you should never use a value larger than 0.01.

#### POINTTOL

Proprietary to SIMetrix. Default = 0.001. Can increase to a maximum of 1.0 to improve speed with loss of precision. Reduce to 0 for maximum accuracy but note this may just slow down the simulation without really improving precision where it is needed.

#### ABSTOL

Default = 1pA. This is an absolute tolerance for currents and therefore has units of Amps. This basically affects the tolerance for very low values of current. Sometimes worth increasing to resolve convergence problems or improve speed for power circuits.

#### VNTOL

Default = 1V. Same as ABSTOL but for voltages.

#### TRTOL

Default = 7. This is a relative value and affects how accurately charge storage elements are simulated. Reduce it to increase accuracy of reactive elements but there is no benefit reducing below about 1.0. In circuits where there is more interest in the steady state rather than how to get there, simulation speed can be improved by increasing this value.

#### CHGTOL

Default = 1e-14. Minimum tolerance of capacitor charge. Some convergence and speed improvement may be gained by increasing this for circuits with large capacitors. Generally recommended to leave it alone.

#### FLXTOL

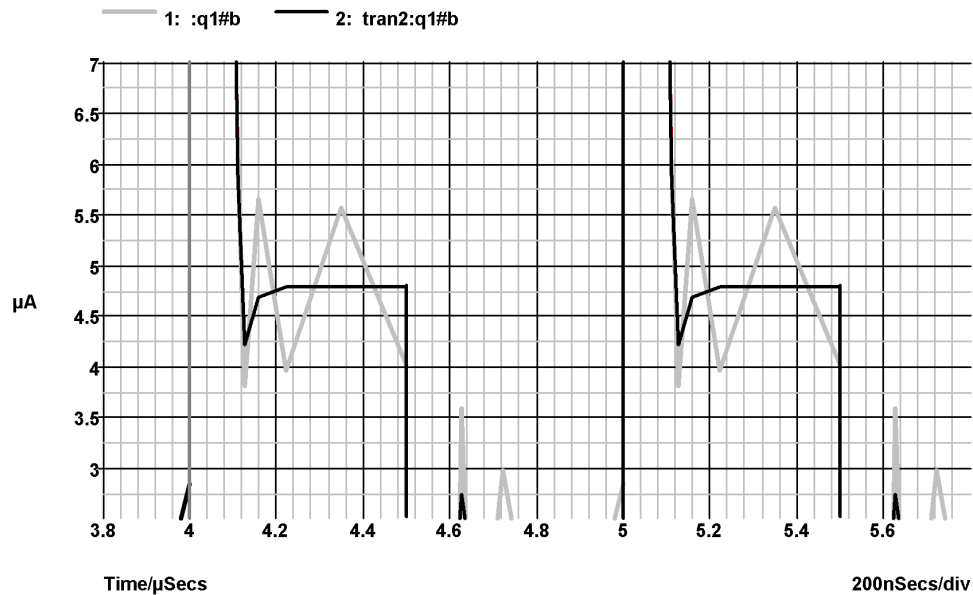
Default = 1e-11. Same as CHGTOL except applied to inductors.



### 8.8.6 Integration Methods - METHOD option

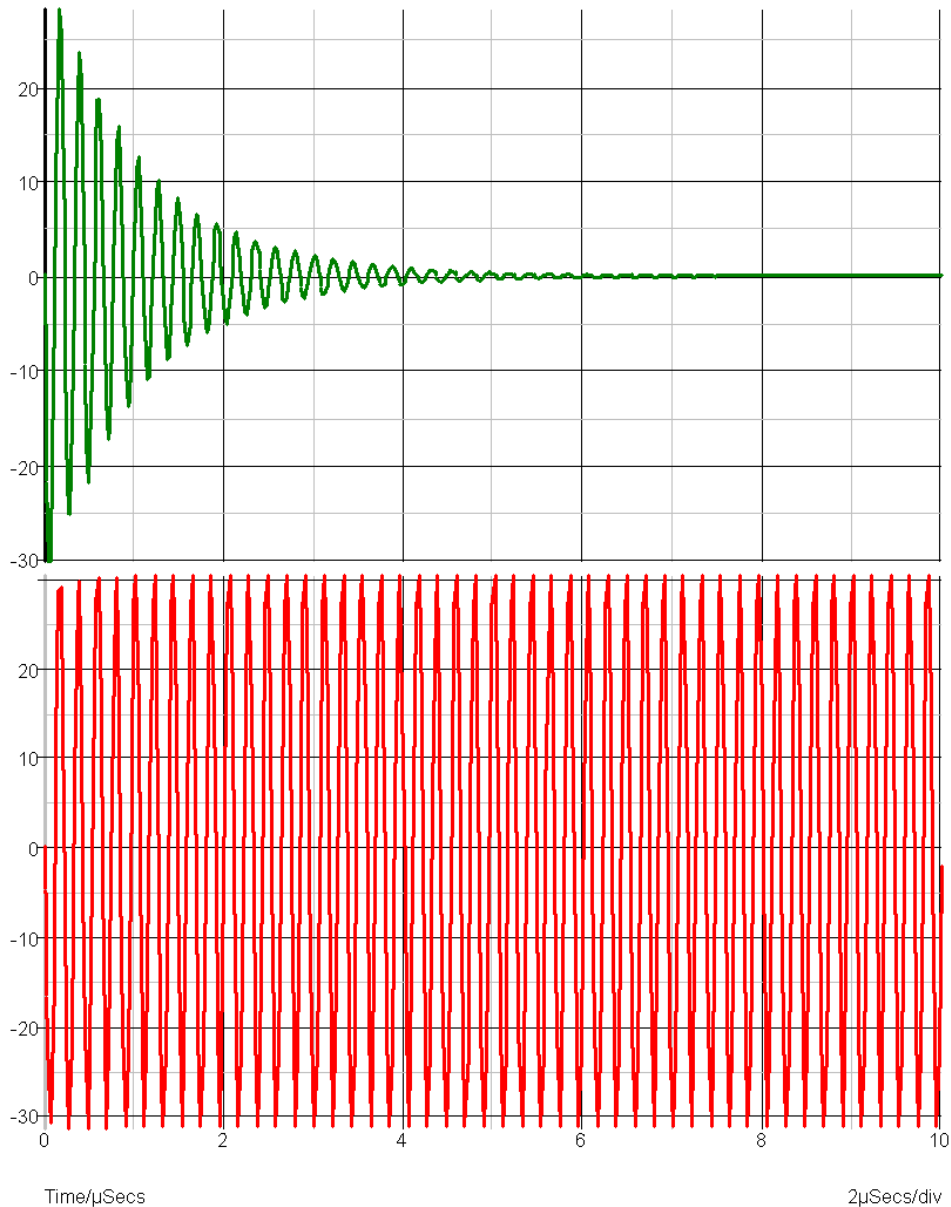
SIMetrix, along with most other SPICE products use three different numerical integration methods to model reactive elements such as capacitors and inductors. These are Backward Euler, Trapezoidal Rule and Gear. Backward Euler is used unconditionally at various times during the course of a simulation but at all other times the method used is controlled by the METHOD option (as long as ORDER is set to 2 or higher - see below).

The METHOD option can be set to TRAP (trapezoidal - the default) or GEAR. Gear integration can solve a common problem whereby the solution seems to oscillate slightly. An example is shown below.



The grey curve was simulated with the default trapezoidal integration method whereas the black used Gear integration. Note that gear integration introduces a slight overshoot. This is a common characteristic. To find out whether such overshoots are a consequence of the integration or are in fact a real circuit characteristic, you should simulate the circuit with much smaller values of RELTOL (see above). It is also suggested that you switch back to trapezoid integration when using tight tolerances; the oscillating effect shown above will vanish if the tolerance is tight enough.

Note, you should not use Gear integration if you are simulating strongly resonant circuits such as oscillators. Gear integration introduces a numerical damping effect which will cause resonant circuits to decay more rapidly than they should. For example:



The above curves are the result of simulating a simple LC circuit that is completely undamped. The top trace was the result of Gear integration and the bottom, trapezoidal. The bottom curve is correct and agrees with theory. The top curve is inaccurate. If the analysis was done with Gear integration but with a smaller value of RELTOL, the damping effect would be less, so for all methods the result is ultimately accurate if the tolerance is made small enough. But trapezoidal gives accurate results without tight values of RELTOL.

### ORDER option

This defaults to 2 and in general we recommend that it stays that way. Setting it to 1 will force Backward Euler to be used throughout which will degrade precision without any speed improvement. It can be increased up to a value of 6 if METHOD=GEAR but we have not found any circuits where this offers any improvement in either speed or precision.

## 8.9 Using Multiple Core Systems

### 8.9.1 Single Step Runs

SIMetrix will make use of multiple core processors to speed up simulations. It does this by dividing the work for calculating device equations amongst multiple threads each running on its own core. For example, a circuit with 100 transistors will need the equations governing the transistors to be calculated for each iteration. With a 4 core system, each core can be assigned the equations for 25 transistors to be calculated in parallel which will allow the iteration to complete in less time.

However, only the device equation calculation is subject to multiple core execution. There are many other tasks that are performed during a simulation run that remain *single-threaded*, that is executed in sequence on a single core. For this reason multiple cores will not give a speed up equal to the number of cores or even anything close.

### 8.9.2 Using Multiple Cores for Single Step Runs

SIMetrix will automatically choose how many cores to use for the simulation. For simple circuits it will use a single core and beyond a certain level of complexity it will use all the cores available on a single chip. So if you have a 4-core machine where all 4 cores are implemented on a single processor chip, SIMetrix will use all 4 cores as long as the circuit complexity is sufficient to justify it.

If you have a machine with, for example, 8 cores implemented using 2 4-core processor ICs, SIMetrix will use just one of the ICs so therefore 4 cores.

You can override the number of cores using the `mpnumthreads` .OPTIONS setting. E.g.:

```
.OPTIONS MPNUMTHREADS=2
```

will force 2 cores to be used as long as the computer system does actually have 2 cores. SIMetrix will not use more threads than there are physical cores available.

Be aware that hyperthreaded logical processors are not counted as a physical processor. So if you have 4 physical cores and 8 logical cores implemented using hyperthreading, SIMetrix will use a maximum of 4 cores.

### 8.9.3 Multi-core Multi-step Simulation

Multiple core execution does give a very substantial speed improvement when applied to multi-step analyses. This is covered in the User's Manual, Chapter 7, Using Multiple Cores for Multi-step Analyses.

## 8.10 Matrix Solver

To simulate a circuit, SIMetrix formulates a set of linear equations from the non-linear equations that govern the devices in the circuit. This is part of an iterative algorithm that is repeated successively to converge on the solution to the non-linear system. The linear system of equations is solved using a matrix solver.

SIMetrix has two matrix solvers and you can choose between them. The two solvers are:

1. Sparse 1.3 developed by Kenneth Kundert and which is the solver supplied with SPICE 3

2. KLU developed by a research group at the University of Florida under Prof. Tim Davis. This was developed for circuit simulation and was moulded to perform well for the type of matrix that circuit simulators tend to generate. The solver makes use of more modern techniques than the original SPICE3 solver which was developed in the 1980s.

SIMetrix uses KLU by default and for most applications this is the better choice. For circuits with more than about 500 nodes it is almost always faster for the following reasons:

1. It has uses superior ordering algorithms. The matrix that arises from circuit simulation problems is sparse which means that nearly all terms are zero. Exploiting sparsity to greatest effect depends on the row and column ordering. KLU makes use of modern research to produce superior ordering to Sparse 1.3
2. The factorisation algorithm is superior
3. It can be reordered efficiently and rapidly. The optimum matrix ordering that is ideal for DC and long time steps is often different to that needed for small time steps. Sparse 1.3 can not be reordered very efficiently and tends to use the same ordering throughout the simulation. KLU can be reordered much more frequently providing optimal ordering at all times

Although KLU is usually the best choice, Sparse 1.3 can give better results for small circuits. To change the matrix solver use this option:

```
.options spsolver=solver
```

Where solver is:

KSPARSE for Sparse 1.3

or

KLU for KLU

Currently .SENS analyses always use Sparse 1.3 regardless of the spsolver setting.

## Chapter 9

# Digital Simulation

### 9.1 Overview

As well as an analog simulator, SIMetrix incorporates an event driven digital simulator tightly coupled to the analog portion. This system can rapidly and accurately simulate mixed signal circuits containing both analog and digital components. Of course, an analog only simulator can simulate a mixed signal circuit using digital models constructed from analog components, but this approach is slow. The advantage of this mixed-mode approach is that it is dramatically faster, typically in the order of 100 times for pure digital circuits.

The SIMetrix mixed mode simulator is based on the XSPICE system developed by the Georgia Technical Research Institute. Although based on XSPICE, SIMetrix features many enhancements over the original system. See [“Enhancements over XSPICE” on page 301](#) for details of these improvements.

If you only use digital models supplied in the device library, then you don’t need to know much about the digital simulator in order to use it. Just select the devices you need from the parts browser and simulate in the normal way. This chapter describes some of the inner workings of the simulator including how it interfaces to the analog system. More importantly, perhaps, this chapter also describes how you can design your own digital models.

### 9.2 Logic States

The digital simulator is described as ‘12-state’ which means that a digital signal can be in 1 of 12 states. These 12 states are combined from 3 levels and 4 strengths as follows:

Logic levels	Strengths
HIGH	STRONG
LOW	RESISTIVE
UNKNOWN	HI-IMPEDANCE
UNDETERMINED	

Logic levels HIGH and LOW are self-explanatory. UNKNOWN means the signal could be either HIGH or LOW but which is not known at this stage. The start up state of a flip-flop is an example of an UNKNOWN state. Strength refers to the driving force behind the signal. STRONG is the highest with HI-IMPEDANCE the lowest. It is used to resolve conflicts when two outputs are

connected together. For example consider a LOW-RESISTIVE signal (as possessed by a pull-down resistor) connected to a HIGH-STRONG signal. There is a conflict between the two logic levels but as they are different strengths, the stronger wins and therefore the resulting level is HIGH.

### 9.2.1 State resolution table

The following table defines how a state is decided when two outputs are connected:

0S	1S	XS	0R	1R	XR	0Z	1Z	XZ	0U	1U	XU	
0S	0S	XS	XS	0S	0S	0S	0S	0S	0S	0S	XS	XS
1S	XS	1S	XS	1S	1S	1S	1S	1S	1S	XS	1S	XS
XS	XS	XS	XS	XS	XS	XS	XS	XS	XS	XS	XS	XS
0R	0S	1S	XS	0R	XR	XR	0R	0R	0R	0U	XU	XU
1R	0S	1S	XS	XR	1R	XR	1R	1R	1R	XU	1U	XU
XR	0S	1S	XS	XR	XR	XR	XR	XR	XR	1U	XU	XU
0Z	0S	1S	XS	0R	1R	XR	0Z	XZ	XZ	0U	XU	XU
1Z	0S	1S	XS	0R	1R	XR	XZ	1Z	XZ	XU	1U	XU
XZ	0S	1S	XS	0R	1R	XR	XZ	XZ	XZ	XU	XU	XU
0U	0S	XS	XS	0U	XU	XU	0U	XU	XU	0U	XU	XU
1U	XS	1S	XS	XU	1U	XU	XU	1U	XU	XU	1U	XU
XU	XS	XS	XS	XU	XU	XU	XU	XU	XU	XU	XU	XU

0S = LOW-STRONG

1S = HIGH-STRONG

XS = UNKNOWN-STRONG

0R = LOW-RESISTIVE

1R = HIGH-RESISTIVE

XR = UNKNOWN-RESISTIVE

0Z = LOW-HI-Z

1Z = HIGH-HI-Z

XZ = UNKNOWN-HI-Z

0U = LOW-UNDETERMINED

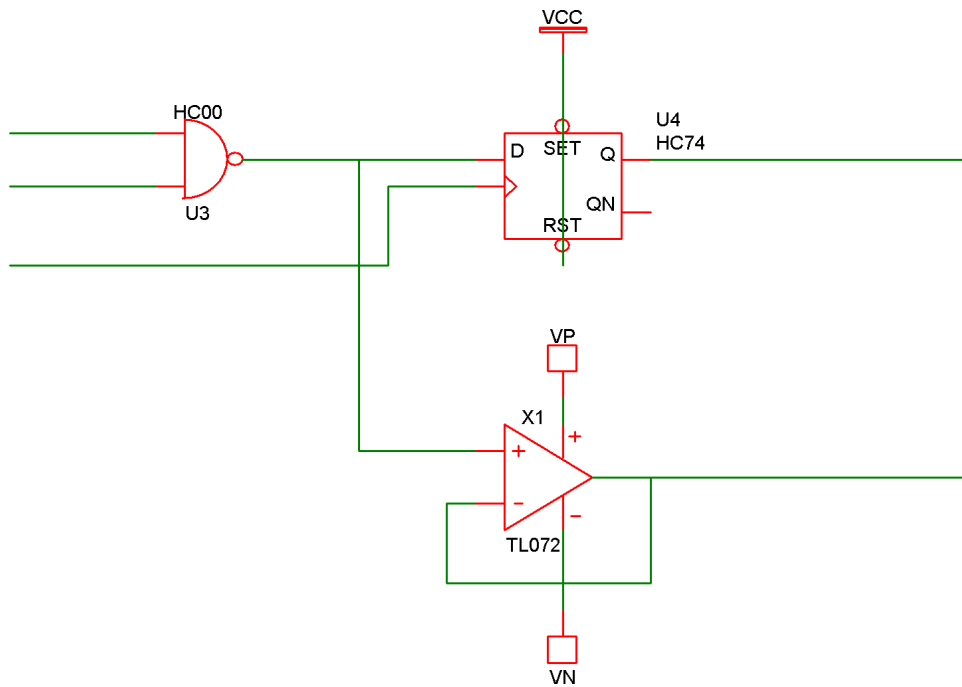
1U = HIGH-UNDETERMINED

XU=UNKNOWN-UNDETERMINED

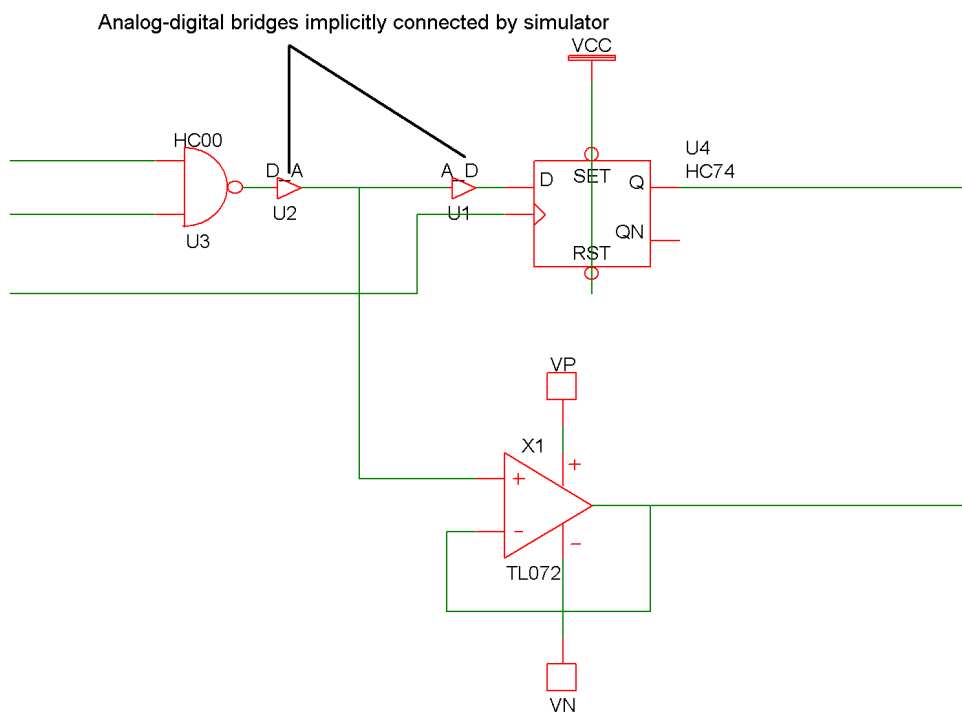
## 9.3 Analog to Digital Interfaces

At the simulator level, there are two types of node namely analog and digital and they cannot be connected together. At the netlist level it *is* possible to connect analog components to digital outputs and inputs. When SIMetrix sees an analog component connected to a digital signal, it automatically interconnects them using an *interface bridge*. It will use an analog-digital bridge to connect an analog signal to a digital input and a digital-analog bridge to connect to a digital output. If you connect an analog component to a signal which connects to both digital inputs and

outputs both types of bridge will be used and the digital inputs and outputs will be separated from each other as illustrated in the following diagrams.



Circuit entered in schematic editor



Circuit that is actually simulated

One problem with the above approach is that the A-D and D-A bridges introduce an additional delay to the signal path which would therefore alter the performance of the digital system even if the analog node does not present any significant load. This is overcome by assigning a negative

load to the input of the digital bridge which in effect reduces the delay of the driving gate. In the above example U2 has a negative input load which reduces the delay of U3.

### 9.3.1 How A-D Bridges are Selected

When SIMetrix implicitly places an AD bridge in a circuit, it must choose an appropriate model for the bridge. All AD bridges are based on DAC\_BRDIGE and ADC\_BRIDGE models described in [“Analog-Digital Interface Bridge” on page 174](#), and [“Digital-Analog Interface Bridge” on page 181](#). The model is chosen according to the FAMILY parameter assigned to the digital device to which the bridge is connected. The FAMILY parameter along with the associated OUT\_FAMILY and IN\_FAMILY parameters are explained more fully in [“Logic families” on page 282](#). Basically the FAMILY parameter specifies the logic family to which the device belongs e.g. ‘HC’ for high speed CMOS.

The name of the model used to interconnect digital to analog is always of the form:

```
family_name_dac
```

and to interconnect analog to digital

```
family_name_adc
```

For example if the family name is HC the D-A bridge is called HC\_DAC. There is a selection of A-D and D-A bridges in the model library supplied with SIMetrix. (In BRIDGES.LB).

## 9.4 Logic Families

The digital simulator only knows about the 12 logic states described in [“Logic States” on page 279](#). It doesn’t know anything about threshold voltages or output impedances and consequently cannot directly handle the effects of interconnecting devices from different logic families. It does however feature a mechanism of determining the level of compatibility between families and will raise an error if incompatible devices are interconnected. For example, ECL and high speed CMOS operate at completely different thresholds and cannot be connected except via a special interface gate. SIMetrix knows this so that if you attempt to connect such devices, an error message will be displayed and the simulation will not run. Conversely, it is perfectly OK to drive an LSTTL input from an HC output and SIMetrix will operate normally if you do so. If you drive an HC input from an LSTTL output SIMetrix will issue a warning as, although this may work in practice, it cannot be guaranteed to do so under all circumstances.

Another problem arises when connecting inputs from different logic families together. SIMetrix deals with this by treating groups of inputs as if they were all from the same logic family provided they are compatible. This selected logic family is then used to resolve any output-input conflict as described above. It is also used to select an analog-digital interface bridge as described in [“Analog to Digital Interfaces” on page 280](#).

Groups of outputs from different families are dealt with in the same way as inputs described above.

SIMetrix knows how to resolve these situations by referring to a set of three tables called the ‘Logic Compatibility Tables’. A standard set of tables is built in to the simulator but they can also be redefined. See [“Logic Compatibility Tables” on page 283](#).

### 9.4.1 Logic Family Model Parameters.

There are three model parameters used to specify the logic family to which a device belongs. These are:



Parameter name	Description
IN_FAMILY	Family for inputs
OUT_FAMILY	Family for outputs
FAMILY	Family for both inputs and outputs if IN_FAMILY/OUT_FAMILY not specified

The parameters are text strings. Any name may be used that is defined in the logic compatibility tables but you must *not* use the underscore character in a family name. The families supported by the internal tables are listed in [“Supported Logic Families” on page 285](#).

The underscore character is used to define a sub-family that has the same characteristics as the main family as far as logic compatibility is concerned but which will call a different interface bridge when connected to an analog node. This is used to define schmitt trigger devices such as the 74HC14. In an all-digital circuit this behaves exactly like a normal inverter with a slightly longer delay. When the input is connected to an analog system an interface bridge with the appropriate hysteresis is called up instead of the normal interface.

### 9.4.2 Logic Compatibility Tables

As explained in the above section, there are three of these. Each table has a row and column entry for each of the logic families supported. These are:

- Resolve In-Out table. Decides what to do when an output is connected to an input from a different family. Possible responses are OK, ERR (error - not permissible) and WARN (OK but give warning to user)
- Resolve In-In table. Decides how to treat the situation when two inputs from dissimilar families are connected. As described above SIMetrix must treat a group of inputs connected together as all belonging to the same logic family for the purpose of deciding an analog interface bridge (see [“Analog to Digital Interfaces” on page 280](#)) and to resolve in-out family conflicts. Possible responses are ROW, COLUMN and ERR. ROW means that the family defining the ROW entry has priority and COLUMN means that the family defining the COLUMN entry has priority. ERR means that it is an error to interconnect these two inputs. You can also enter OK which signifies that the two families are equivalent and it doesn't matter which is chosen. Currently this response is exactly equivalent to ROW.
- Resolve Out-Out table. Works the same way as the Resolve In-In table but used to define output priorities.

The tables can be redefined by specifying a file containing the new definition. If running in GUI mode a new file can be specified at any time using the ReadLogicCompatibility command (*Script Reference Manual/Function Reference/ReadLogicCompatibility*). It can also be specified as the configuration setting CompatTable. The format of this file is described in the following section.

### 9.4.3 Logic Compatibility File Format

For an example of a compatibility table, see the file COMPAT.TXT which you will find in the SCRIPT directory. This file is actually identical to the built-in definitions except for the UNIV family which cannot be redefined.

The file format consists of the following sections:

1. Header

2. In-Out resolution table
3. In-In resolution table
4. Out-Out resolution table

### Header

The names of all the logic families listed in one line. The names must not use the underscore ('\_') character.

### In-Out resolution table:

A table with the number of rows and columns equal to the number of logic families listed in the header. The columns represent outputs and the rows inputs. The entry in the table specifies the compatibility between the output and the input when connected to each other. The entry may be one of three values:

Value	Meaning
OK	Fully compatible
WARN	Not compatible but would usually function. Warn user but allow simulation to continue.
ERR	Not compatible and would never function. Abort simulation.

### In-In resolution table

A table with the number of rows and columns equal to the number of logic families listed in the header. Both column and rows represent inputs. The table defines how inputs from different families are treated when they are connected. The entry may be one of four values:

Value	Meaning
ROW	Row take precedence
COL	Column takes precedence
OK	Doesn't matter. (Currently identical to ROW)
ERR	Incompatible, inputs cannot be connected.

### Out-out resolution table

A table with the number of rows and columns equal to the number of logic families listed in the header. Both column and rows represent outputs. The table defines how outputs from different families are treated when they are connected. The entry may be one of four values:

Value	Meaning
ROW	Row take precedence
COL	Column takes precedence
OK	Doesn't matter. (Currently identical to ROW)

Value	Meaning
ERR	Incompatible, outputs cannot be connected.

#### 9.4.4 Supported Logic Families

The following logic families are supported by the internal Logic Compatibility Tables.

Family name	Description
TTL	TTL - 74 series
HC	High speed CMOS - 74HC series
HCT	TTL compatible High speed CMOS - 74HCT series
FAST	FAST TTL - 74F series
LS	Low power schottky TTL - 74LS series
ALS	Advanced low power schottky TTL - 74ALS series
4000-5	4000 series CMOS - 5V operation
4000-10	4000 series CMOS - 10V operation
4000-15	4000 series CMOS - 15V operation
ECL10K	ECL 10K series
ECL10KE	ECL Eclipse series
AC	Advanced CMOS - 74AC series
ACT	TTL compatible Advanced CMOS - 74ACT series
FORCE5	Used for 5V VCC rails.
UNIV	Universal family - see below

#### 9.4.5 Universal Logic Family

The internal tables support the concept of a ‘Universal logic family’. This is called UNIV and can connect to any logic family without error. This is the default if no FAMILY parameter is supplied.

#### 9.4.6 Internal Tables

The internal tables are documented in the on-line help system. Refer to topic “Internal Tables” which is listed as a keyword in the index tab.

## 9.5 Load Delay

### 9.5.1 Overview

The digital simulator includes mechanisms to model the delay introduced when an output is loaded. Two sources of delay are provided for, namely ‘input delay’ and ‘wire delay’. Input delay is determined by the capacitive input while wire delay is an additional delay caused by the capacitance of the interconnection.

Both input delay and wire delay are affected by the driving outputs ‘resistance’.

### 9.5.2 Output Resistance

Most devices that have digital outputs have three parameters to define output resistance. Note that the resistance we are referring to here is not an actual analog resistance but a conceptual value that when multiplied by load capacitance provides a delay value.

The three output resistance parameters are: `out_res`, `out_res_pos`, `out_res_neg`. `out_res_pos` and `out_res_neg` define the output resistance for positive and negative transitions respectively. `out_res` provides a default value for `out_res_pos` and `out_res_neg`.

### 9.5.3 Input Delay

Most digital inputs include an ‘input\_load’ capacitance parameter. The total input delay is obtained by multiplying the sum of all connected input capacitances by the driving output’s output resistance as described above.

### 9.5.4 Wire Delay

Wire delay is derived from the number of connected inputs following a non-linear relationship defined in a look-up table.

#### Defining Look-up Table

The wire delay look-up table must be defined in a file containing pairs of values with one pair per line. The first value in the pair is the number of connections and the second is the capacitance. For example:

```
0 0
1 0
2 1e-12
5 10e-12
10 30e-12
```

Linear interpolation is used to derive missing values.

To specify the wire table used for a simulation, add the line:

```
.OPTIONS WireTable=filename
```

where *filename* is the path of the wire table file.

## 9.6 Digital Model Libraries

### 9.6.1 Using Third Party Libraries

The SIMetrix digital simulator is based on XSPICE and all the XSPICE digital devices have been implemented. Virtually all of these have been enhanced in a number of ways but all remain backward compatible with the original XSPICE. Consequently any 100% XSPICE compatible digital model will work with SIMetrix.

## 9.7 Arbitrary Logic Block - User Defined Models

### 9.7.1 Overview

The arbitrary logic block is an internal component that can be defined to perform any logic function. Using a simple descriptive language it is possible to define combinational logic elements, synchronous and asynchronous registers as well as look-up table (ROMs) and arrays (RAMs).

Each ALB device is defined as a normal .MODEL statement which refers to a separate file containing the logic description. This section is mostly concerned with the descriptive language used in the definition file.

### 9.7.2 An Example

We start with a simple example. The following is a description of a simple 8 bit synchronous counter. (This definition would be put into a file referred to in a .MODEL statement. This is described later). A circuit using this model is supplied as an example. See EXAMPLES/ALB\_Examples/count.sch

```
PORT (DELAY = 10n) CountOut out[0:7] ;
EDGE (DELAY=5n, WIDTH=8, CLOCK=in[0]) Count ;
Count = Count + 1 ;
CountOut = count ;
```

We will go through this line by line.

The first line:

```
PORT (DELAY = 10n) CountOut out[0:7] ;
```

is a PORT statement and in this case defines the characteristics of an output.

```
(DELAY = 10n)
```

says that the output delay is 10nS that is the actual output pins will change state 10nS after the output is assigned.

```
CountOut
```

names the output CountOut.

```
out[0:7]
```

defines the port as an output and specifies the actual pins used on the device. This specifies the first 8 pins on the output port. There are two sets of pins on an ALB one assigned for inputs and referred to as "in[a:b]" and the other assigned for outputs and referred to as "out[a:b]". The line ends in a semi-colon which terminates the statement. All statements must end in a semi-colon.

The next line:

```
EDGE (DELAY=5n, WIDTH=8, CLOCK=in[0]) Count ;
```

defines an edge triggered register.

```
CLOCK=in[0]
```

specifies the pin used for the clock (it must always be an input pin). This is always positive edge triggered.

```
DELAY=5n
```

This is the clock to output delay. (See illustration below)

```
WIDTH=8
```

This specifies the width of the register i.e. 8 bits

The next line:

```
Count = Count + 1 ;
```

defines the operation to be performed at each clock edge. In this case the value in the register is simply incremented by one. When it reaches 255 it will reset to 0.

The final line

```
CountOut = count ;
```

defines what appears at the output. This says that the output equals the count register.

The following diagram illustrates the internal structure of the counter.



### Reset Count at 200

We will now make a small modification to the counter so that the counter only counts up to 199 before resetting back to zero. Change the line:

```
Count = Count + 1 ;
```

to:

```
Count = Count==199 ? 0 : Count + 1 ;
```

This says 'If the count equals 199 set to zero otherwise increment by one'. As before, this will happen on each clock edge.

### Add an Asynchronous Reset

The logic definition language supports the addition of asynchronous controls to synchronous registers. Here we will add an asynchronous reset. The complete definition becomes:

```
PORT (DELAY = 10n) CountOut out[0:7] ;
PORT                Reset    in[1] ;

EDGE (DELAY=5n, WIDTH=8, CLOCK=in[0]) Count ;

Count := !Reset ? 0 ;
```

```
Count = Count==199 ? 0 : Count + 1 ;

CountOut = count ;
```

To add the reset signal we have to add two lines to the definition. The first:

```
PORT          Reset      in[1] ;
```

defines the signal pin to be used for the reset and the second:

```
Count := !Reset ? 0 ;
```

defines the action to be taken. This is an asynchronous action statement. The '!' means NOT so the line says 'If Reset is NOT TRUE (i.e. low) set the count to zero otherwise do nothing'. Asynchronous action statements are always of the form:

```
register_name := condition ? action ;
```

The ':' signifies that the statement is asynchronous and that the action should happen immediately.

### 9.7.3 Example 2 - A Simple Multiplier

```
PORT (DELAY=10n) MultOut out[0:7] ;
PORT in1 in[0:3] ;
PORT in2 in[4:7] ;

MultOut = in1*in2 ;
```

The above defines a simple combinational circuit, that of a 4X4 digital multiplier. The inputs in1 and in2 are treated as 4 bit unsigned values so if both are zero the output will be zero and if both are 1111 (i.e. 15) the result will be 11100001 (i.e. 225). See the circuit EXAMPLES/ALB\_Examples/Mult.sch.

### 9.7.4 Example 3 - A ROM Lookup Table

The following definition is that of a lookup table to define a sine wave:

```
PORT (DELAY=10n) ROMout out[0:7] ;
PORT          input in[0:7] ;

READONLY (WIDTH=8) ROM[256] =

128, 131, 134, 137, 140, 143, 146, 149, 152, 156, 159, 162,
165, 168, 171, 174, 176, 179, 182, 185, 188, 191, 193, 196,
199, 201, 204, 206, 209, 211, 213, 216, 218, 220, 222, 224,
226, 228, 230, 232, 234, 236, 237, 239, 240, 242, 243, 245,
246, 247, 248, 249, 250, 251, 252, 252, 253, 254, 254, 255,
255, 255, 255, 255, 255, 255, 255, 255, 255, 255, 254, 254,
253, 252, 252, 251, 250, 249, 248, 247, 246, 245, 243, 242,
240, 239, 237, 236, 234, 232, 230, 228, 226, 224, 222, 220,
218, 216, 213, 211, 209, 206, 204, 201, 199, 196, 193, 191,
188, 185, 182, 179, 176, 174, 171, 168, 165, 162, 159, 156,
152, 149, 146, 143, 140, 137, 134, 131, 128, 124, 121, 118,
115, 112, 109, 106, 103, 99, 96, 93, 90, 87, 84, 81, 79, 76,
73, 70, 67, 64, 62, 59, 56, 54, 51, 49, 46, 44, 42, 39, 37,
35, 33, 31, 29, 27, 25, 23, 21, 19, 18, 16, 15, 13, 12, 10,
9, 8, 7, 6, 5, 4, 3, 3, 2, 1, 1, 0, 0, 0, 0, 0, 0, 0, 0,
0, 0, 1, 1, 2, 3, 3, 4, 5, 6, 7, 8, 9, 10, 12, 13, 15, 16,
```

```
18, 19, 21, 23, 25, 27, 29, 31, 33, 35, 37, 39, 42, 44, 46,
49, 51, 54, 56, 59, 62, 64, 67, 70, 73, 76, 79, 81, 84, 87,
90, 93, 96, 99, 103, 106, 109, 112, 115, 118, 121, 124 ;
```

```
ROMout = ROM[input] ;
```

See the example circuit EXAMPLES/ALB\_Examples/SineLookUp.sch

### 9.7.5 Example 4 - D Type Flip Flop

The following is the definition for the 74X74 Dtype flip flop supplied with the standard SIMetrix model library. This model is somewhat more complicated as it models a number of timing artefacts such as setup time and minimum clock width. Each line below has been annotated to describe its function. Full details are explained in the following sections.

```
// Input port definitions
PORT D in[0] ; // D input
PORT CK in[1] ; // Clock
PORT SR in[2:3] ; // Set/reset inputs. r bit 3 s bit 2

PORT out out[0:1] ; // Outputs Q and !Q

// Edge triggered register.
// HOLD is hold time i.e. time after clock edge that data
// must remain stable. Setup time is implemented by
// delaying the D input

// MINCLOCK is minimum clock width.
// USER[n] references values supplied in the .MODEL statement
// The final '=2' initialise the register with the value 2
// i.e. Q=0 and Q!=1
EDGE (WIDTH=2, DELAY=USER[4], HOLD=USER[2], MINCLOCK=USER[3],
CLOCK=in[1]) DTYPE=2;

// COMB defines a combinational register. This is effectively
// a delay element. These delay the D input (to implement
// setup time) and the set/reset inputs to implement minimum
// set and reset times
COMB (DELAY=USER[0], WIDTH=1) D_DEL ;
COMB (DELAY=USER[1], WIDTH=2) SR_DEL ;

// These assign the combinational registers
SR_DEL = SR ;
D_DEL = D ;

// asynchronous action
DTYPE := SR_DEL==1||SR_DEL==2 ? (SR_DEL==2 ? 1 : 2) ;

// synchronous action
DTYPE = D_DEL ? 1 : 2 ;

// Both outputs are forced high if S and R are both active
// Output will be restored to previous value when one of
// S and R becomes inactive
out = SR_DEL==0 ? 3 : DTYPE ;
```



### 9.7.6 Device Definition - Netlist Entry and .MODEL Parameters

#### Netlist entry

```
Axxxx [ in_0 in_1 .. in_n ] [ out_0 out_1 .. out_n ] model_name
+ : parameters
```

#### Connection details

Name	Description	Flow	Type
in	Input	in	d
out	Output	out	d

#### Instance parameters

Name	Description	Type
trace_file	Trace file	string
user	User device parameters	real vector

#### Model format

```
.MODEL model_name d_logic_block parameters
```

#### Model parameters

Name	Description	Type	Default	Limits	Vector bounds
file	Definition name	file string	none	none	n/a
def	Definition	string	none	none	n/a
out_delay	Default output delay	real	1n	$1e^{-12} - \infty$	n/a
reg_delay	Default internal register delay	real	1n	$0 - \infty$	n/a
setup_time	Default triggered setup time	level real	0	$0 - \infty$	n/a
hold_time	Default triggered hold time	edge real	0	$0 - \infty$	n/a
min_clock	Default minimum clock width	real	0	$0 - \infty$	n/a

Name	Description	Type	Default	Limits	Vector bounds
trace_file	Trace log file	string		none	n/a
user	User defined parameters	real vector	none	none	none
user_scale	Scale of user values	real	1	0 – $\infty$	n/a
input_load	Input load value (F)	real	1p	none	n/a
family	Logic family	string	UNIV	none	n/a
in_family	Input logic family	string	UNIV	none	n/a
out_family	Output logic family	string	UNIV	none	n/a
out_res	Digital output resistance	real	100	0 – $\infty$	n/a
min_sink	Minimum sink current	real	-0.001	none	n/a
max_source	Maximum source current	real	0.001	none	n/a
sink_current	Input sink current	real	0	none	n/a
source_current	Input source current	real	0	none	n/a

### Notes

Usually the logic block definition would be placed in a file referred in the FILE parameter. Alternatively the definition may be placed directly in the .MODEL statement as the value of the DEF parameter. In this case the definition must be enclosed in quotation marks (").

The USER\_SCALE parameter scales all values found in the USER parameter.

### 9.7.7 Language Definition - Overview

The following sections describe the full details of the arbitrary logic block language.

All logic definitions are divided into two sections. The first contains the ports and register definitions and the second section consists of the assignment statements. (The first section can be empty in very simple cases).

### 9.7.8 Language Definition - Constants and Names

Constants follow the usual rules. Any decimal number with optional sign and exponent or engineering suffix is permitted. In addition, numbers in hexadecimal are also allowed. The format is the same as for the 'C' programming language i.e. prefixed with '0X'. E.g.:

0X10 = 10 hex = 16.

Identifiers used for register, port and variable names must begin with an alphabetic character or underscore and consist of alphanumeric characters and underscores.

### 9.7.9 Language Definition - Ports

Port statements define the inputs and outputs to the logic device. They are of the form

```
PORT ( DELAY=output_delay) port_name OUT [ pin1| pin1:pin2 ]
```

OR

```
PORT port_name IN|OUT [ pin1| pin1:pin2 ]
```

Ports define a label to a single pin or sequence of pins so that they can be treated as a single entity in the remainder of the logic definition. In the case of outputs they can optionally also define an output delay. (If this is not specified a default output delay defined in the devices .MODEL statement is used).

<i>port_name</i>	Any name to reference the port. Must start with a letter or underscore and consist only of letters numbers and underscores. Names are not case sensitive.
<i>pin1, pin2</i>	Identifies pin or range of pins that port accesses. See next section for more details.
<i>output_delay</i>	Output delay in seconds. When an output port is assigned a value, the actual output is updated after this delay has elapsed (+ any loading delay). You may use engineering units in the normal way. E.g. 10n is 10e-9.

#### Relationship between ports, netlist entry and symbol definition

The netlist entry for an arbitrary logic block is of the form:

```
Axxx [ input_node_list ] [ output_node_list ] model_name
```

The pin numbers in the port statements above, i.e. *pin1* and *pin2* are the positions within the *input\_node\_list* for input ports and *output\_node\_list* for output ports.

So if the netlist entry is:

```
A12 [ 1 2 3 4 ] [ A B C D ] ARB1
```

the port definition:

```
PORT output OUT[0:3] ;
```

assigns the label `output` to the netlist pins A B C and D. If, for example, the value 7 is evaluated and assigned to `output`, pins A B and C would be set to a logic '1' and pin D would be set to a logic '0'. Pins 1 2 3 & 4 would be used for input ports in a similar way.

The netlist entry relates directly to a symbol definition for an arbitrary logic block. When defining a symbol to be used with an ALB you should observe the following rules

- The first input pin's name and the first output pin's name should both be prefixed with a '['.
- The last input pin's name and the last output pin's name should both be suffixed with a ']'.
- Use **Property/Pin | Edit Pin Order...** to define the pin order with input pins first then output pins.
- You should assign a MODEL property with the value 'A'.

### 9.7.10 Language Definition - Registers and Variables

Registers are the main working elements of the arbitrary logic block. There are four main types. These are:

- Edge triggered. The value of these change on the rising edge of an assigned clock.
- Level triggered. The value of these change when an assigned enable is at a logic ‘1’ level.
- Combinational. The value of these change after a specified delay.
- Read-only. These are given a fixed value which cannot be changed. These would usually be arranged in indexable arrays to implement a read only memory.

Edge and level triggered registers may be arranged in indexable arrays. Level or edge triggered arrays form a read-write memory or RAM.

In addition to registers there are also local variables. These can be assigned a value that can later be used in a register assignment.

All registers must be declared. Local variables are declared by simply assigning a value to them.

The syntax for register declarations follow:

#### Edge Triggered Register Declaration

```
EDGE ( CLOCK=input_pin_spec
      [, DELAY=reg_delay]
      [, WIDTH=reg_width]
      [, MINCLOCK=reg_minclock]
      [, HOLD=reg_hold_time]
      [, ASYNCDELAY=reg_asyncdelay]
      [, BITWISE=0|1 ] ) name [[array_size]]
      [= initial_condition *[, initial_condition] ] ;
```

<i>input_pin_spec</i>	This specifies which input pin is the clock and must be of the form: IN[n] where n is a pin number. See <a href="#">“Relationship between ports, netlist entry and symbol definition” on page 293</a> for details on how pin numbers relate to netlist entries and symbol definitions.
<i>reg_delay</i>	Register delay in seconds. This is the delay between the clock rising edge and the register value changing. You can use engineering units in the normal way. Default: REG_DELAY parameter in .MODEL statement defines default value. This in turn has a default value of 1nS.
<i>reg_width</i>	Register width in bits. This has a maximum of 32. Default: 32
<i>reg_minclock</i>	Minimum clock width. This <i>must</i> be less than or equal to reg_delay. The register value will not update if the clock width is less than this value. Default: MIN_CLOCK parameter in .MODEL statement defines default value. This in turn has a default value of 0.

<i>reg_hold_time</i>	Register hold time. This is the time that the input data (i.e. assignment value) must remain stable after the clock edge, for the new value to be accepted. If the BITWISE parameter is set to '1' (which it is by default) the hold time is applied on a bit by bit basis. That is any individual bit in the register that remains stable during the hold period will attain the new value even if other bits violate the hold time. If BITWISE is '0' then if a single bit violates the hold time, the whole register will remain unchanged even if some bits remain stable during the hold period. Setting BITWISE to '0' saves system memory which can be important for large arrays (i.e. RAMs). Default: HOLD_TIME parameter in .MODEL statement defines default value. This in turn has a default of 0.
<i>reg_asyncdelay</i>	Time the register takes to acquire a value set by an asynchronous assignment. This <i>must</i> be less than or equal to <i>reg_delay</i> . Default: <i>reg_delay</i>
BITWISE value	See <i>reg_hold_time</i> Default: '1' for single registers, '0' for arrays.
<i>name</i>	Register name.
<i>array_size</i>	If specified, the register is arranged as an addressable array of size <i>array_size</i> . Default: 1
<i>initial_condition</i>	Value assigned to register when simulation starts. Default: 0

Notes: To implement register setup time, assign a value to *reg\_hold\_time* equal to the sum of the register setup and hold times then delay the input data by a period equal to the setup time.

### Level Triggered Register Declaration

```

LEVEL (CLOCK=input_pin_spec
[, DELAY=reg_delay]
[, WIDTH=reg_width]
[, SETUP=reg_setup_time]
[, ASYNCDELAY=reg_asyncdelay]
[, BITWISE=0|1 ] name [[array_size]]
[ = initial_condition *[, initial_condition]] ;

```

<i>input_pin_spec</i>	This specifies which input pin is the enable and must be of the form: IN[n] where n is a pin number. See <a href="#">“Relationship between ports, netlist entry and symbol definition” on page 293</a> for details on how pin numbers relate to netlist entries and symbol definitions.
<i>reg_delay</i>	Register delay in seconds. If the enable is already high, this is the time taken for the register to acquire new data. Otherwise it is the delay between enable rising edge and the register value changing. You can use engineering units in the normal way. Default: REG_DELAY parameter in .MODEL statement defines default value. This in turn has a default value of 1nS.
<i>reg_width</i>	Register width in bits. This has a maximum of 32. Default: 32

<i>reg_setup_time</i>	Register hold time. This is the time that the input data (i.e. assignment value) must remain stable prior to an enable falling edge, for the new value to be accepted. If the BITWISE parameter is set to '1' (which it is by default) the setup time is applied on a bit by bit basis. That is any individual bit in the register that remains stable during the setup period will attain the new value even if other bits violate the setup time. If BITWISE is '0' then if a single bit violates the setup time, the whole register will remain unchanged even if some bits remain stable during the setup period. Setting BITWISE to '0' saves system memory which can be important for large arrays (i.e. RAMs). Default: SETUP_TIME parameter in .MODEL statement defines default value. This in turn has a default of 0.
<i>reg_asyncdelay</i>	Time the register takes to acquire a value set by an asynchronous assignment. This <i>must</i> be less than or equal to <i>reg_delay</i> . Default: <i>reg_delay</i>
BITWISE value	See <i>reg_setup_time</i> Default: '1' for single registers, '0' for arrays.
<i>name</i>	Register name.
<i>array_size</i>	If specified, the register is arranged as an addressable array of size <i>array_size</i> . Default: 1
<i>initial_condition</i>	Value assigned to register when simulation starts. Default: 0

### Combinational Register Declaration

```
COMB ( [, DELAY=reg_delay]
      [, WIDTH=reg_width]
      [, BITWISE=0|1 ] ) name [ = initial_condition ] ;
```

<i>reg_delay</i>	Register delay in seconds. You can use engineering units in the normal way. If BITWISE is '1' (the default) this delay is applied on a bit by bit basis. If BITWISE is '0' then the delay is applied to the whole register. That is the output will not change until all inputs have remained stable for the delay time. Setting BITWISE to '0' is useful when using combinational registers to implement asynchronous state machines as it eliminates race conditions. Default: REG_DELAY parameter in .MODEL statement defines default value. This in turn has a default value of 1nS.
<i>reg_width</i>	Register width in bits. This has a maximum of 32. Default: 32
<i>name</i>	Register name.
<i>initial_condition</i>	Value assigned to register when simulation starts. Default: 0

### Read-only Register Declaration

```
READONLY ([, WIDTH=reg_width] name[[array_size]]
          [ = initial_condition *[, initial_condition]] ;
```

<i>reg_width</i>	Register width in bits. This has a maximum of 32. Default: 32
------------------	---

<i>array_size</i>	If specified, the register is arranged as an addressable array of size <i>array_size</i> . Default: 1
<i>name</i>	Register name.
<i>initial_condition</i>	Value assigned to register when simulation starts. Default: 0

Read-only registers are usually arranged as an addressable array. When reading a read-only register, the value returned is the value defined by the initial conditions. As the name implies it is not possible to assign read-only registers.

### 9.7.11 Language Definition - Assignments

Registers and output ports can be assigned using the assignment operator '='. Assignment values can be constants, input ports, other registers, local variables or expressions of any or all of these. Assignments are of the form:

```
register | output_port | OUT[pin1:pin2] | OUT[pin1] | local_var = expr ;
```

OR

```
clocked_register[index] = expr ;
```

<i>register</i>	Combinational, edge triggered or level triggered register name.
<i>output_port</i>	Output port name
<i>pin1, pin2</i>	Output pin numbers. OUT[ <i>pin1:pin2</i> ] and OUT[ <i>pin1</i> ] allow outputs to be assigned with having to declare them in a PORT statement.
<i>local_var</i>	Any name not already used for a port or register. This defines the value for a local variable that can be used in subsequent expressions. A local variable may not be used in an expression that precedes its definition.
<i>expr</i>	Local variables, input ports, registers and constant values combined using arithmetic, Boolean, bitwise Boolean, shift, conditional and relational operators. See <a href="#">“Expression Operators” on page 297</a> for detailed documentation on all operators.
<i>clocked_register</i>	Edge or level triggered register.
<i>index</i>	Array index. This must be smaller than the array size. Arrays are based at 0. That is the first element is zero and the last is (array length-1).

### Expression operators

The following table lists all operators available. These are listed in order of precedence. Precedence determines the order of evaluation. For example in the expression:

```
var1<var2 && var3<var4
```

The sub-expressions var1<var2 and var3<var4 are evaluated first and the result of that those evaluations combined using && to yield the final result. This is because < has higher precedence than &&. The precedence can be altered using parentheses in the usual way.

Class	Operators	Description
Index	[]	E.g. var1[4]. Index operator to access array element.
Unary	+ -	Operator to single value e.g. -5
Arithmetic multiplicative	* / %	Arithmetic multiply/divide/modulus treating all values as unsigned integers. % returns remainder after division
Arithmetic additive	+ -	Arithmetic operation treating all values as unsigned integers
Shift	« »	Shift-left and shift right. E.g. reg1 « 2 will shift reg1 left by two bits
Relational	< > <= >=	If condition met result is 1 (=TRUE) otherwise result is zero (=FALSE)
Equality	== <> !=	== means EQUAL <> and != both mean NOT EQUAL Return 1 when condition met and 0 when condition is not met
Bitwise AND	&	Performs a Boolean AND bit by bit
Bitwise XOR	^	Performs a Boolean exclusive OR bit by bit
Bitwise OR		Performs a Boolean OR bit by bit
Logical AND	&&	Returns 1 if both values are non-zero (TRUE) otherwise returns zero (FALSE)
Logical OR		Returns 1 if either value is non-zero (TRUE) otherwise return zero (FALSE)
Conditional expression	cond ? res1 : res2	Returns res1 if cond is non-zero (TRUE) otherwise returns res2 Example A<B ? 16 : 0 returns 16 if A is less than B otherwise returns 0

Note that the operators and their precedence are a subset of those used in the ‘C’ programming language with the exception of <>.

### Controlling Output Enables

An output can be set into a high impedance state using a modification to an output port variable. Use the suffix .EN after the output port or port identifier to signify that the result of the expression should control the output enable. E.g. the following is extracted from the 74XX244 definition:

```
PORT (DELAY=USER[0]) Output out[0:3] ;
Output.En = Out_En_Del ? 0 : 0xf ;
```

### Examples

```
Y = !Enable ? A_Del != B_Del : 1 ;
```



If Enable is 0 then Y will be the result of A\_Del != B\_Del otherwise the result will be 1.

```
Shift = !Par_En_Del ? Par_Data_Del :(Shift<<1) | Ser_Data_Del;
```

This describes the action of a parallel loadable shift register.

```
out[0]= !in[1]&!in[2] | in[1]&!in[2]&in[0] |
!in[1]&in[2]&in[0]
```

An example of referencing inputs and outputs directly without needing PORT statements.

### 9.7.12 Language Definition - User and Device Values

Sometimes it is convenient to use the logic description to define the functionality of a block but have the timing and other specifications specified separately. This is achieved by USER and DEVICE values. USER values are specified in the .MODEL statement while DEVICE values are specified on the device at the netlist (or schematic device) level. The values are referenced in the logic definition in the form:

```
USER[index]
```

and

```
DEVICE[index]
```

These can replace any constant value in an expression, register qualifier or port qualifier. (Register and port qualifiers are the values in parentheses after the register/port keyword. E.g. DELAY, HOLD, SETUP etc.).

To set USER values in a .MODEL statement, assign the parameter USER. This is a *vector* parameter, that is it can have any number of values and these must be enclosed in square brackets '[' and ']'. For example:

```
.MODEL Counter8 d_logic_block file=counter_8.ldf
+ user=[10n, 5n]
```

The logic definition to which this model refers - counter\_8.ldf - can use USER[0] and USER[1] to refer to the values 10n and 5n respectively.

To set DEVICE values in a netlist, the netlist entry for the device must be appended with:

```
: USER=[ values ]
```

For example:

```
A$U3 [clock] [Q0 Q1 Q2 Q3 Q4 Q5 Q6 Q7] Counter8 :
+ USER=[10n, 5n]
```

The logic definition for this device can use DEVICE[0] and DEVICE[1] to access the USER values in the netlist i.e. 10n and 5n respectively. Always remember to include the colon. This acts as a separator between the device name and any parameters.

### 9.7.13 Diagnostics: Trace File

In order to debug models, a tracing facility is provided. If the .MODEL TRACE\_FILE parameter or instance parameter of the same name is specified, a file will be created which lists the values of all internal registers at each time point.

The file will usually have a number of lines of the form: Roll back to <time>

For example the following is an extract from an actual trace file

```
5.00022e-05  2696    9   2696    0
5.09397e-05  2696    9   2696    0
5.09407e-05  2692   10  2692    0
```

Roll back to 5.08599e-05

```
5.09397e-05  2696    9   2696    0
5.09407e-05  2692   10  2692    0
5.09657e-05  2692   10  2692    0
```

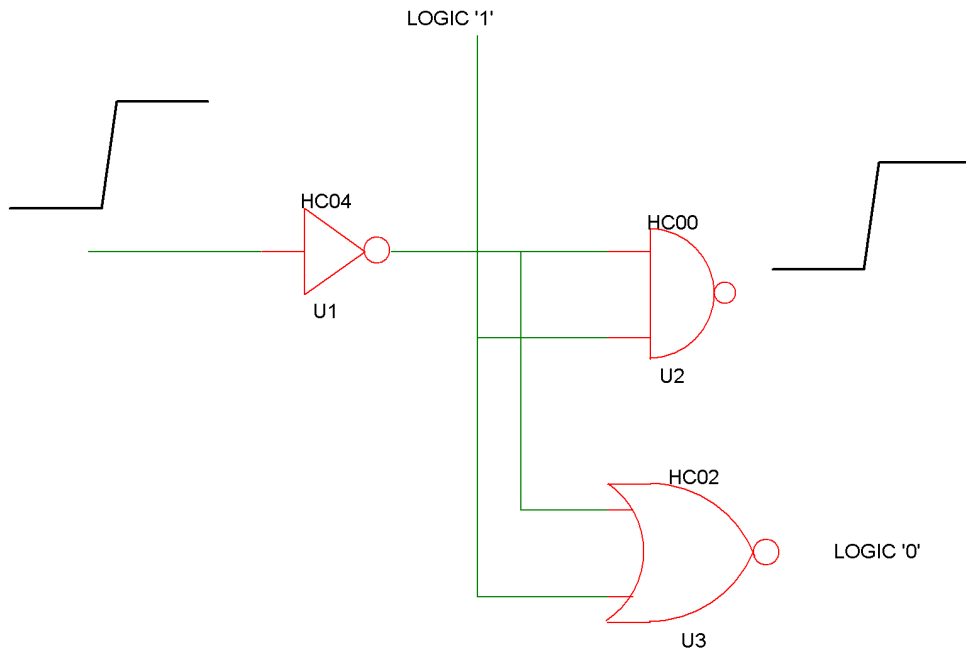
Roll-back occurs when an analog time step is rejected but the digital simulation has already advanced past the new analog time. In this case the digital simulator has to back-track events. This mechanism is central to the operation of the mixed-mode system and is explained in more detail in [“Mixed-mode Simulator - How it Works” on page 300](#).

## 9.8 Mixed-mode Simulator - How it Works

### 9.8.1 Event Driven Digital Simulator

The digital simulator is said to be *Event Driven*. An event is essentially a change of state e.g. a gate output changing from logic ‘0’ to logic ‘1’. When an event occurs on an output, all devices with inputs connected to that output are notified of the event and can respond appropriately by generating new events.

For example, consider the following circuit fragment.



U1 receives an event, a rising edge at its input at time = T. U1 has a propagation delay of 5.5nS, so on receipt of the event at its input, U1 posts an event at its output with a time T+5.5nS. At that time this event is received by U2 and U3. U3 does not respond to this event because one of its inputs is permanently at logic ‘1’ so its output will always be low. U2, however, does respond and creates a low-high event at a time delayed by its propagation delay of 6.5nS i.e. T+5.5nS+6.5nS.

Any device with an input connected to the output of U2 will process this new event and so the process continues.

In addition to the propagation delays described above, there are also additional delays caused by loading effects. Each input has an effective input capacitance and each output a resistance. For each event, an additional delay is added equal to the sum of all capacitances on the node multiplied by the driving output's resistance.

### 9.8.2 Interfacing to the Analog Simulator

Connections between the analog and digital system are made via special interfaces bridges. (As described in “[Analog to Digital Interfaces](#)” on page 280 these bridges are implicitly included by the simulator and it isn't necessary for the user to wire them in.) The digital to analog interface has an output that looks like - to a first approximation - an analog representation of a digital gate. This output changes voltage at a specified rise and fall time when the digital input changes state. More importantly, the analog system is notified when an event occurs at the input to a D-A interface bridge and a timestep is forced at that time. This is known as a *breakpoint* and is the analog equivalent of an event. The analog system is only notified of events that occur at the input of D-A bridges. It knows nothing of events that are internal to the digital system.

Analog to digital interface bridges are much like a comparator. When the analog input passes a threshold, the output state changes appropriately and a digital event is generated.

#### Time Step Control

With two simulators running largely independently, something is needed to synchronise the timesteps. Basically the analog system is in control. It tells the digital system to process events up to a certain time, that time being the analog system's next anticipated time point. A problem arises, however in that the next analog timestep is not guaranteed to be accepted. The analog system frequently rejects timesteps either because of slow convergence or because a shorter timestep is needed to maintain the required accuracy. If the analog system has to cut back the timestep to a point prior to the most recent digital event, then the digital system has to back-track. This process is known as roll-back and the need for the digital simulator to be able to perform it substantially increases its complexity. In order to roll-back the digital simulator has to store its past history back to the most recent accepted analog timepoint

## 9.9 Enhancements over XSPICE

- Gate delays in XSPICE are *stored* i.e. like a transmission line not like a real gate. SIMetrix gate delays are *inertial* so if a pulse shorter than the propagation delay is received, it is swallowed not transmitted.
- Automatic interface creation. In XSPICE you have to explicitly join digital and analog nodes via interface bridges. In SIMetrix this is done automatically.
- Fan out implemented. The underlying mechanism for load dependent delay was there but none of the models supported it. Static loading effects (as in bipolar logic) was not supported at all. In SIMetrix it is.
- Input load reflected in analog to digital interfaces. The AD interfaces in XSPICE have infinite input impedance regardless of what the digital output is driving. SIMetrix AD interfaces reflect the digital capacitive and static load at their inputs.
- Output strength reflected in digital to analog interfaces. The DA interfaces in XSPICE have zero output impedance regardless of what is driving them. SIMetrix DA interfaces reflect

the strength of the digital output driving the input. A hi-z logic state will look like a hi-z logic state when transferred to the analog domain. This is not the case with XSPICE.

- AD interface threshold detection. All AD interfaces switch at a particular input threshold. In the XSPICE system the output switched at the first analog timepoint that exceeded the threshold. This could be a long way passed the threshold if the analog time steps are large. In SIMetrix a mechanism has been implemented that cuts back the time step so that the threshold is hit within a specified time tolerance.
- Arbitrary logic block device. This allows the definition of any logic device using a simple descriptive language. The language accommodates combinational logic, synchronous and asynchronous registers as well as look up tables (i.e. ROMS) and arrays (i.e. RAMs).
- Arbitrary analog to digital converter. Up to 32 bits with specified input range and offset, conversion time and maximum conversion rate. Output may be in two's complement or offset binary.
- Arbitrary digital to analogue converter. Up to 32 bit with specified input range and offset and output slew time. Input may be in two's complement or offset binary.
- Voltage controlled oscillator (analog in digital out). There was one of these in the original XSPICE code but it suffered a number of problems and was scrapped. The SIMetrix version is all new.

